

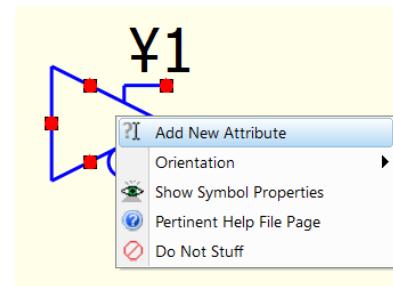
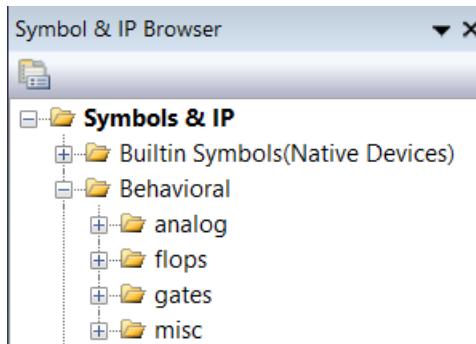
Qspice - Device Reference Guide by KSKelvin

KSKelvin Kelvin Leung

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Device, Instance and Model Parameters

- Device
 - Device symbol in this guide can be found in Qspice : View > Symbol & IP Browser (shortcut F2)
- Detail description of Qspice device is in Help, Qspice > Simulator > Device Reference
- Instance and Model Parameters
 - A device normally consists of instance and model parameters
 - Instance parameters are described with text attribute. To add text attribute, right click device and select "Add New Attribute"
- Model parameters are described with .model statement
e.g. .model SW SW Ron=1 Roff=1Meg Vt=0 Vh=0



B. Behavioral Source

B. Behavioral Source : Instance Parameters

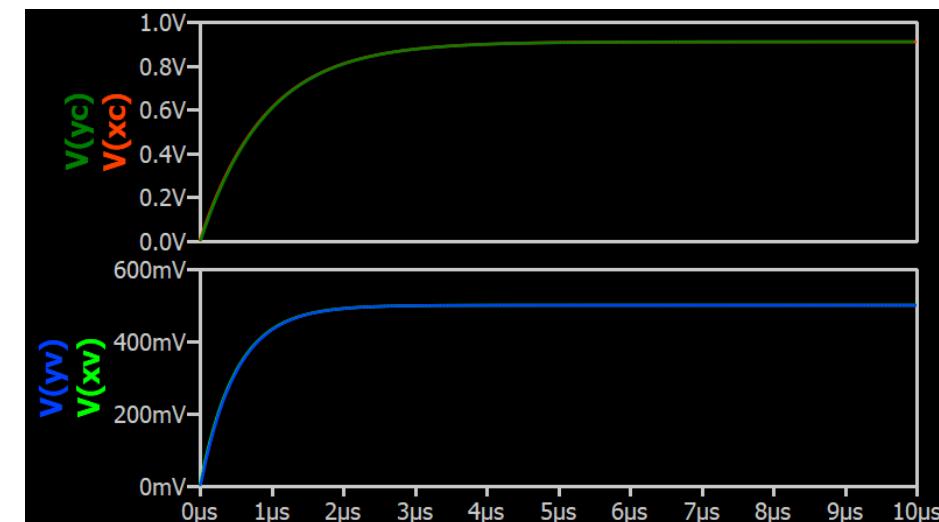
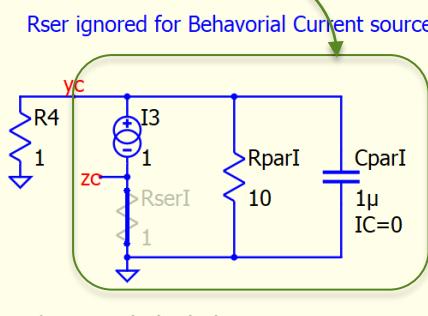
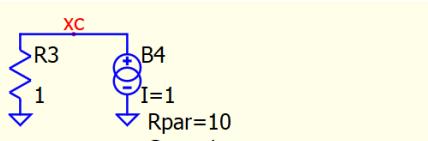
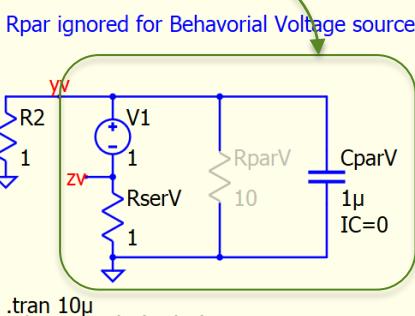
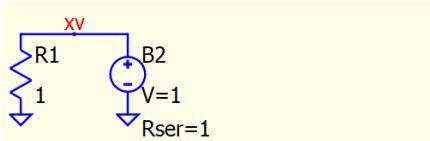
Behavioral Source Instance Parameters

Name	Description	Units	Default
CPAR	Parallel capacitance	F	0.0
I ¹	Expression for current	A	(not set)
IC	Initial value	A or V	0.0
LAPLACE	<u>Frequency dependence</u>		(none)
NORTON	Use a Norton equivalent for a behavioral resistance		(not set)
R ¹	Expression for resistance	Ω	(not set)
RPAR	Parallel resistance <small>Ignore in V</small>	Ω	Infinite
RSER	Series resistance <small>Ignore in I and R (Norton)</small>	Ω	0.0
SYNTHESIZE	Use the synthesized Laplacian circuit even for .AC		(not set)
THEVENIN	Use the Thévenin equivalent for a behavioral resistance		(not set)
V ¹	Expression for voltage	V	(not set)

B. Instance Params : Rser, Rpar and Cpar

Qspice : B Source - Rpar Rser Cpar in V and I.qsch

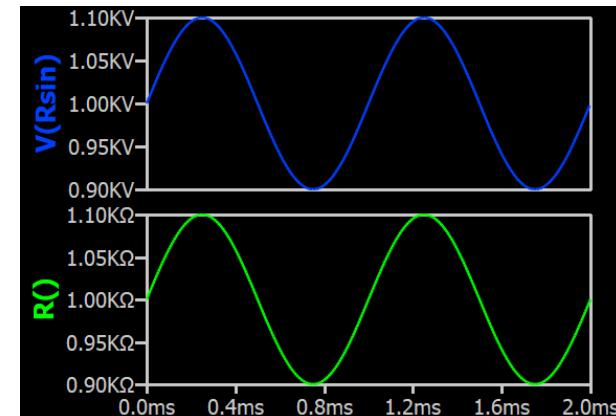
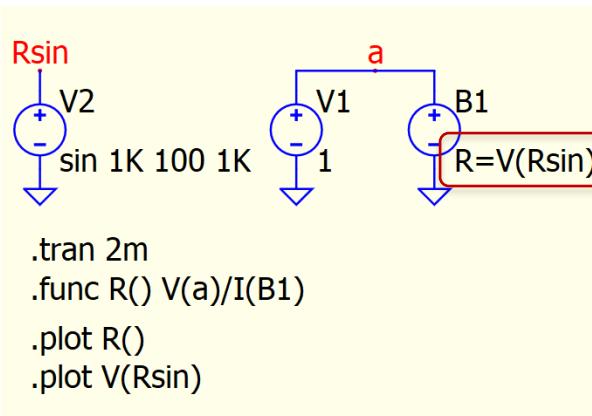
- Rser, Rpar and Cpar in Behavioral Voltage and Current Source
 - Behavioral Voltage ($V=<\text{expression}>$) : Only Rser and Cpar are active
 - Behavioral Current ($I=<\text{expression}>$) : Only Rpar and Cpar are active
 - I don't recommend to use Rser and Rpar in Behavioral Resistance as it will be very confusing depends on Norton or Thevenin equivalent
 - In this example, IC initial value is used to allow 0V or 0A for transient simulation. As behavioral source not have effect in .ac (except for Laplace), .tran is used to reveal these parameters characteristic



B. Instance Params : Behavioral Resistor

Qspice : B Source - Behavioral R.qsch

- Behavioral Resistor
 - Syntax : Bnnn n001 n002
 $R = <\text{expression}>$
 - Expression of resistance

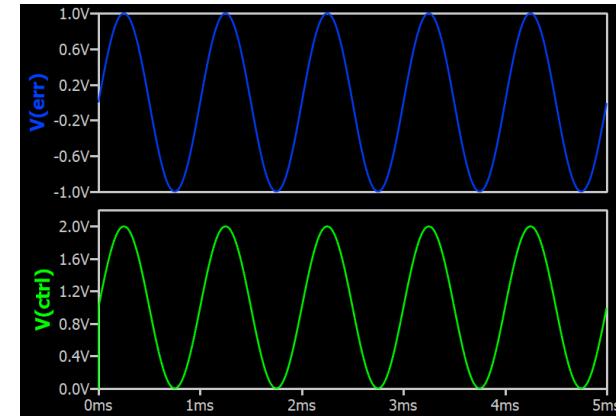
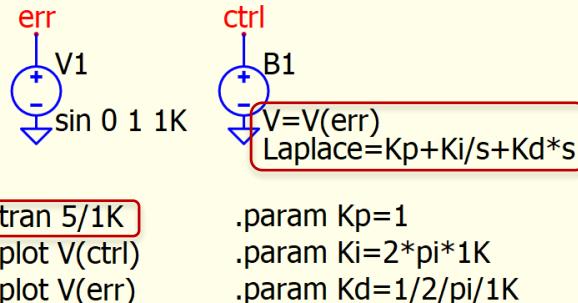


B. Instance Params : Laplace

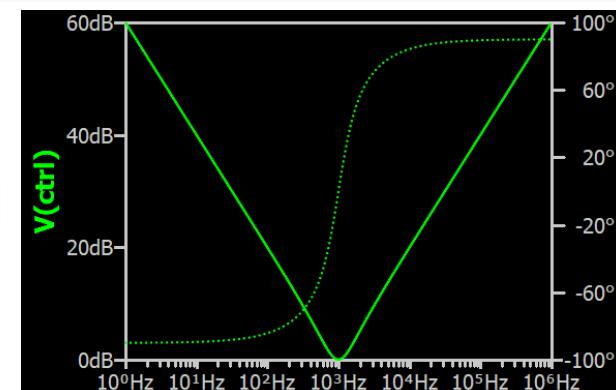
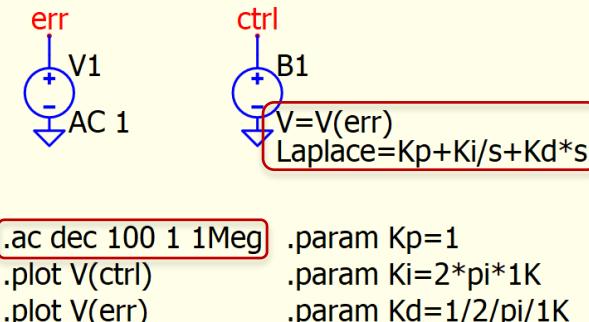
Qspice : B Source - Laplace (.tran).qsch | B Source - Laplace (.ac).qsch

- Laplace (.tran)
 - Laplace equation in B-source, by adding a new attribute Laplace=formula
 - In this simulation
 - $v_{ctrl} = \left(K_p + \frac{K_i}{s} + K_d s \right) v_{err}$
 - Laplace B-source support both transient (.tran) and ac (.ac) analysis

B-source with Laplace in .tran analysis



B-source with Laplace in .ac analysis

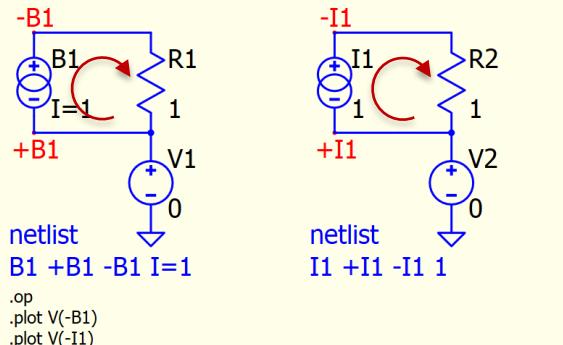


B. Current Direction and Netlist format

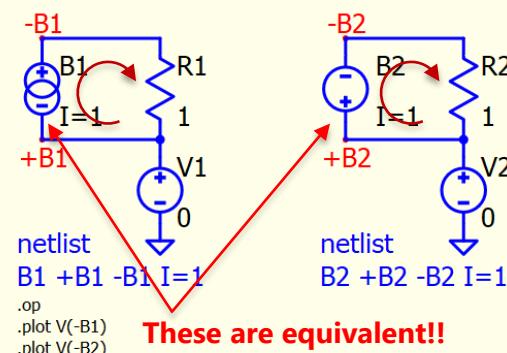
Qspice : B Source - I - direction.qsch | B Source - I - direction2.qsch

- Current Direction

- In Spice, positive current always flows from first node (+) to second node (-) in a device
- However, for B-source and I-source, their symbol labels are visually connected in a way that the "+" label is linked to the second node (-ve) in the source netlist, and the "-" label is connected to the first node (+ve) in the source in netlist

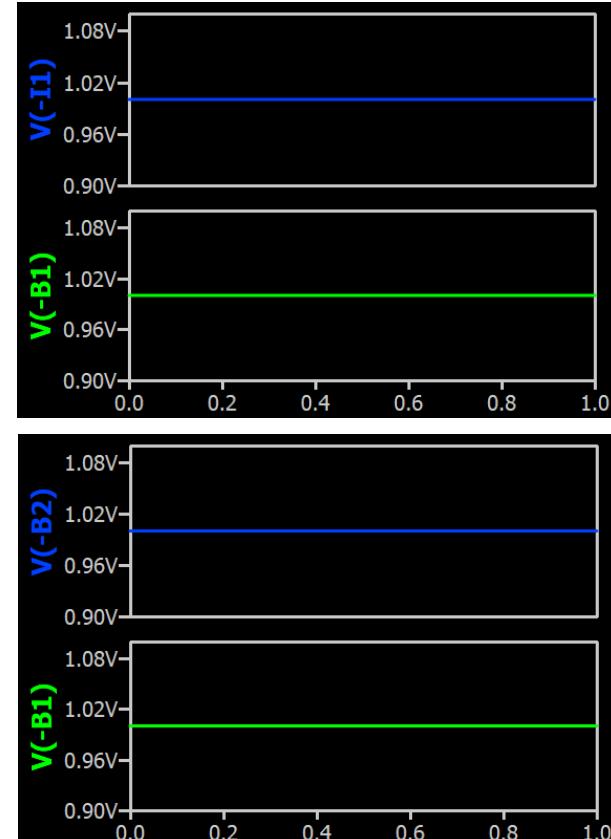


** in spice positive current always flow from + node to - node in netlist
+/- in I-source or B-source symbol is for visual purpose only



These are equivalent!!

** in spice positive current always flow from + node to - node in netlist
+/- in I-source or B-source symbol is for visual purpose only



B. Function and Operators

HELP > Simulator > Device Reference > B. Behavioral Sources

Functions

Name	Description
abs(x)	Absolute value of x
acos(x)	arc cosine of x
arccos(x)	Synonym for acos()
acosh(x)	arc hyperbolic cosine of x
asin(x)	arc sine of x
arcsin(x)	Synonym for asin()
asinh(x)	Arc hyperbolic sine
atan(x)	Arc tangent of x
arctan(x)	Synonym for atan()
atan2(y,x)	Four quadrant arc tangent of y/x
atanh(x)	Arc hyperbolic tangent
buf(x)	1 if x > .5, else 0
ceil(x)	Integer equal or greater than x
cos(x)	Cosine of x
cosh(x)	Hyperbolic cosine of x
ddt(x)	Time derivative x
delay(x,y)	x delayed by y
delay(x,y,z)	x delayed by y, but store no more than z history
dlim(x,y,z)	x bounded by y which it asymptotically starts to approach at y+z as a first inverse order Laurent series
exp(x)	e to the x
floor(x)	Integer equal to or less than x
hypot(x,y)	$\sqrt{x^2 + y^2}$
idt(x,y,z)	Time integral of x with initial condition of y reset when z > .5 $\int x \, dtimes + y$

if(x,y,z)	If x > .5, then y else z
int(x)	Convert x to integer
inv(x)	0. if x > .5, else 1.
limit(x,y,z)	Intermediate value of x, y, and z
In(x)	Natural logarithm of x
log(x)	Alternate syntax for ln()
log10(x)	Base 10 logarithm
max(x,y)	The greater of x or y
min(x,y)	The smaller of x or y
pow(x,y)	x^y
pwr(x,y)	$ x ^y$
pwrs(x,y)	$abs(x)^y$ $sgn(x)*abs(x)^y$
random(x)	Random number from 0. to 1. depending on the integer value of x. Interpolation between random numbers is linear for non-integer x.
sin(x)	Sin x
sinh(x)	Hyperbolic sine of x
sqrt(x)	\sqrt{x}
table(x,a,b,c,d,...)	Interpolate x from the look-up table given as a set of pairs of constant values.
tan(x)	Tangent of x.
tanh(x)	Hyperbolic tangent of x
ulim(x,y,z)	x bounded by y which it asymptotically starts to approach at y-z as a first inverse order Laurent series

Operators grouped in reverse order of precedence of evaluation

Operand	Description
&	Boolean AND
	Boolean OR
>	True if expression on the left is greater than the expression on the right.
<	True if expression on the left is less than the expression on the right.
>=	True if expression on the left is greater than or equal the expression on the right.
<=	True if expression on the left is less than or equal the expression on the right.
+	Addition
-	Subtraction
*	Multiplication
/	Division
**	** / ^ Raise left hand side to power of right hand side. Same as '^'.
!	Boolean not the following expression.

Available Function in B source not listed

- Trunc(x) ; floor(x) ; int(x) : rounded down integer
- Rint(x) ; round(x) : rounded to nearest integer
- Ceil(x) : rounded up integer
- Ustep(x) : $x > 0 ? 1 : 0$
- Uramp(x) : $x > 0 ? x : 0$

Available Variable or Constant not listed in HELP

- Time : Simulation Time
- Temp : Temperature
- PI : 3.14159265358979323846
- E : 2.7182818284590452354
- K : 1.380649e-23 J/K
- Q : 1.602176487e-19 Coulomb

B. Function and Operators – `delay(x,y)` or `delay(x,y,z)`

Qspice : B Source - delay fix.qsch

- `delay(x,y)` or `delay(x,y,z)`
 - `Delay(x,y,z)` can reduce the amount of waveform memory that must be stored

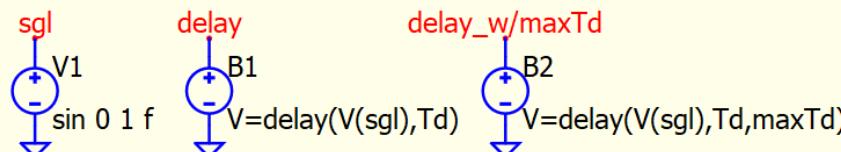
$\text{delay}(x,y)$	x delayed by y
$\text{delay}(x,y,z)^1$	x delayed by y , but store no more than z history

- y can be parameter and z must be fixed constant
 - y must less than z or error will return

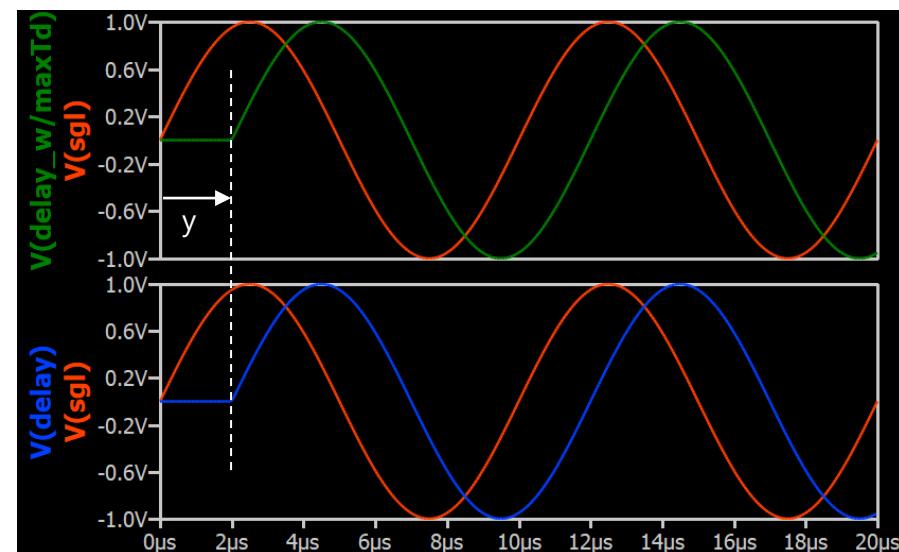
Syntax : delay(x,y) - x delayed by y

Syntax : delay(x,y,z) - x delayed by y, but store no more than z history

```
.param f = 100K  
.param Td = 2μ  
.param maxTd = 5μ
```



```
.tran 2/f  
.plot V(sgl) V(delay)  
.plot V(sgl) V(delay)
```



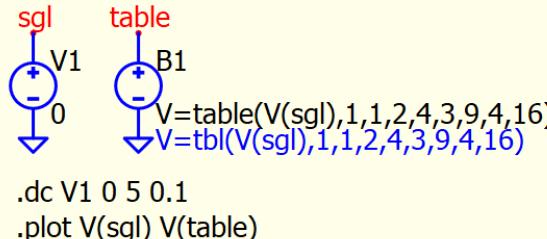
B. Function and Operators – table(x,a,b,c,d,...)

Qspice : B Source - table.qsch | B Source - table(.func).qsch | B Source - table(attribute).qsch

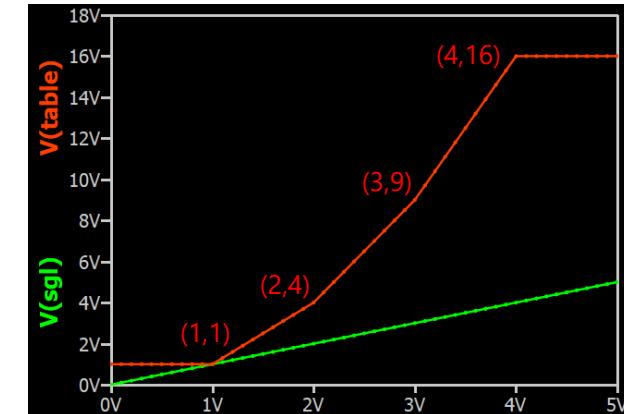
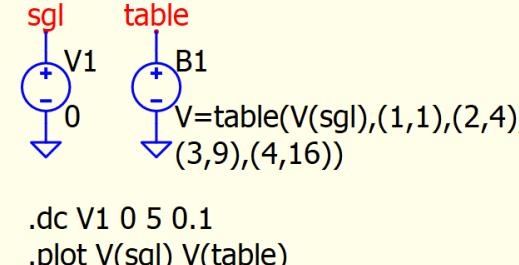
- Table(x,a,b,c,d,...)
 - Interpolate x from the look-up table given as a set of pairs of constant values
 - TBL is an alternative name for Table, and it is also supported in Qspice

- Setup a table
 - As table may contain a lot of data points, for visual purpose in schematic, user can consider
 - Each pair of (x,y) data uses a bracket
 - Break table with 2nd or more attribute
 - Use .func to define a table

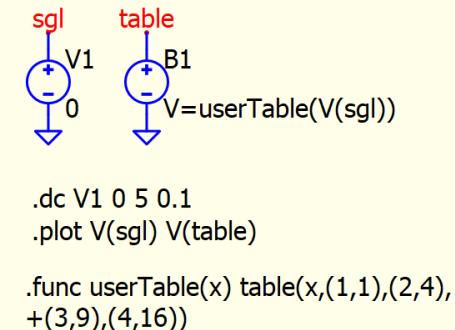
Basic table setup in B-source



Define a table with 2nd or more attribute



Define a table with .func and with + line break

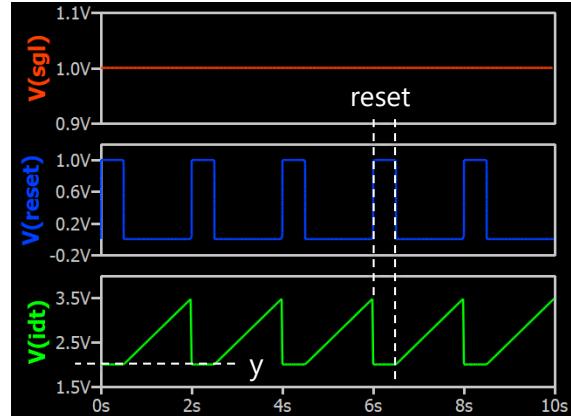
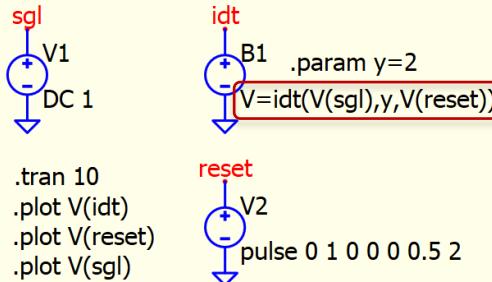


B. Function and Operators – Integral idt(x,y,z)

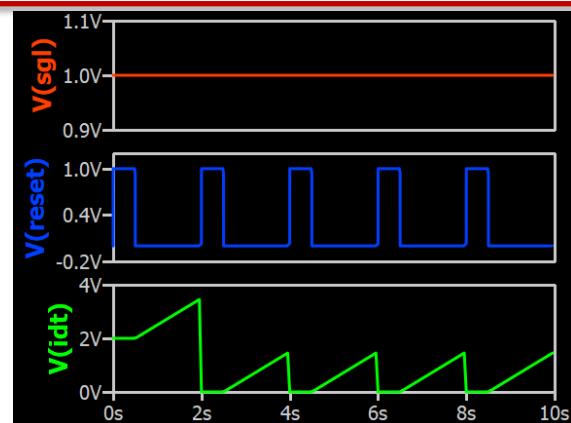
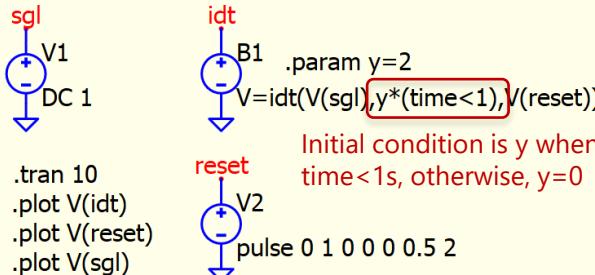
Qspice : B Source - idt.qsch | B Source - idt (y-conditional).qsch

- $\text{idt}(x,y,z)$
 - Time Integral of x
 - $= \int x dt + y$
 - y is initial condition, which is the DC value during integral function is reset
 - z is to reset integral
 - Special technique for initial condition
 - If initial condition needs to be changed over time, conditional function can be used
 - User can also use voltage source to control initial voltage y over time

Syntax : $\text{idt}(x,y,z)$
Time integral of x with initial condition of y
reset when $z > .5$



Syntax : $\text{idt}(x,y,z)$
Time integral of x with initial condition of y
reset when $z > .5$

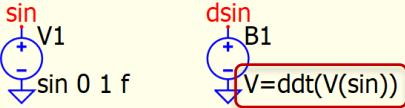


B. Function and Operators – Time Derivative ddt(x) and limit(x,y,z)

Qspice : B Source - ddt.qsch | B Source - limit.qsch

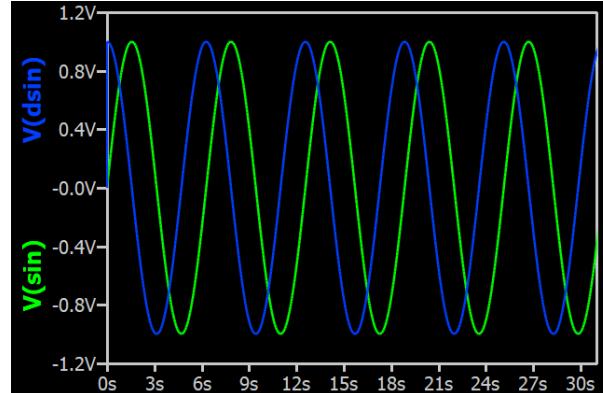
- $\text{ddt}(x)$
 - Time derivative
 - $= \frac{dx}{dt}$

Syntax : $\text{ddt}(x)$
Time derivative x

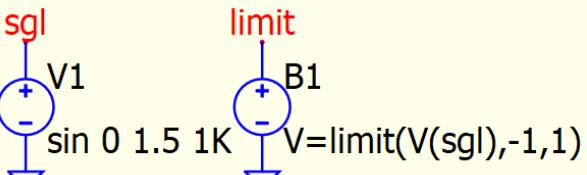


Formula
 $d(\sin(\omega t))/dt = \omega \cos(\omega t)$

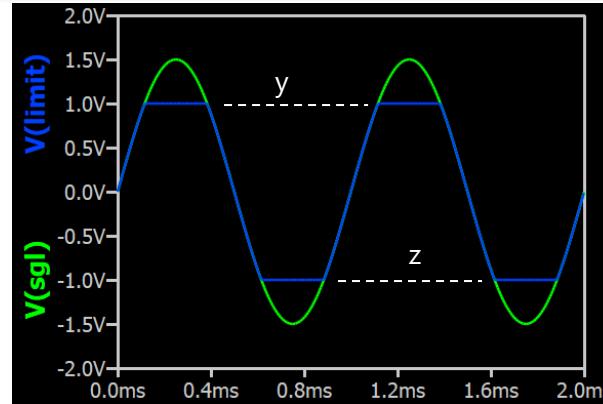
```
.param f=1/2/pi
.param omega=2*pi*f
.tran 5/f
.plot V(sin) V(ddsin)
```



- $\text{limit}(x,y,z)$
 - Intermediate value of x, y, and z



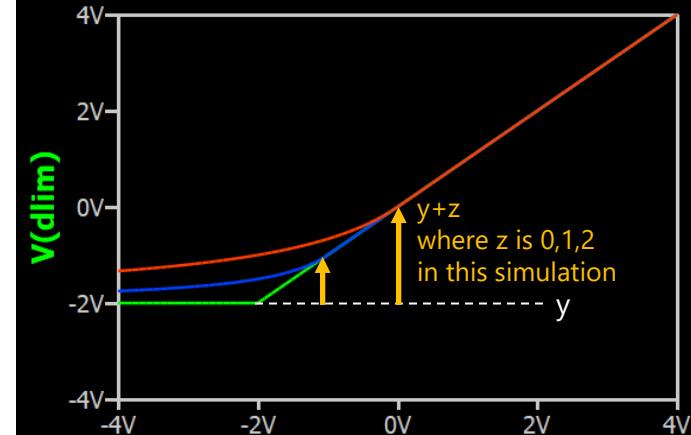
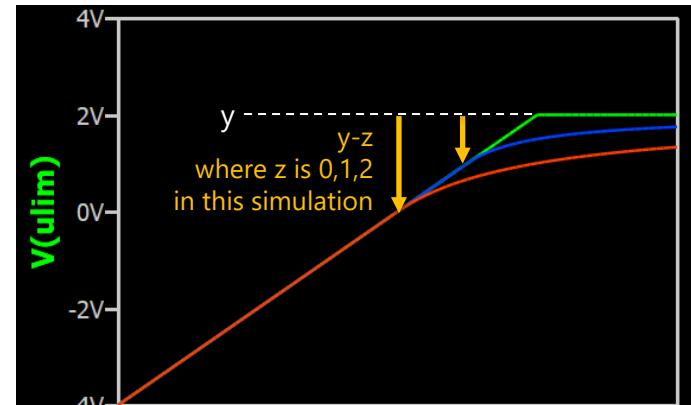
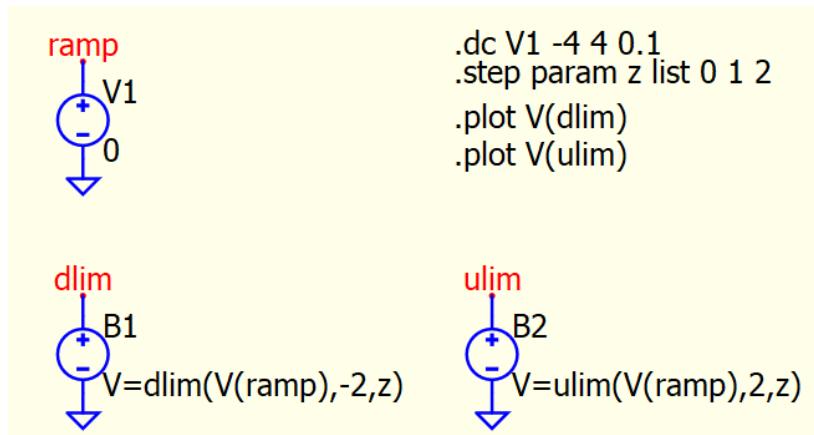
```
.tran 2m
.plot V(sgl) V(limit)
```



B. Function and Operators – dlim(x,y,z) and ulim(x,y,z)

Qspice : B Source - dlim ulim.qsch

- dlim(x,y,z) and ulim(x,y,z)
 - dlim(x,y,z) : x bounded by y which it asymptotically starts to approach at $y+z$ as a first inverse order Laurent series
 - ulim(x,y,z) : x bounded by y which it asymptotically starts to approach at $y-z$ as a first inverse order Laurent series
 - These functions are used for soft limit



B. Function and Operators – random(x) [Basic Concept]

Qspice : B Source - random (seed).qsch

- **Random(x)**

- Random(x) : Random number from 0 to 1 depending on the integer value of x
- This is pseudo random function which takes a seed and output a number "appears random"

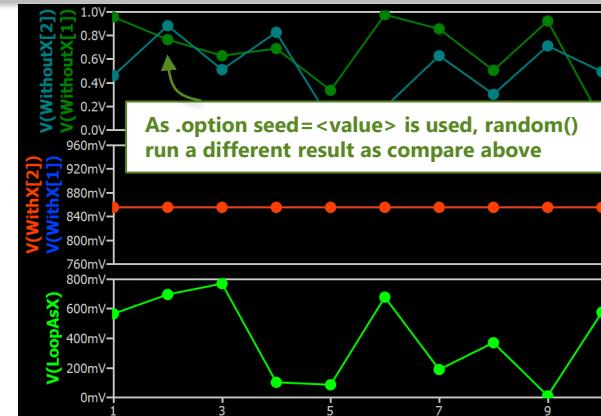
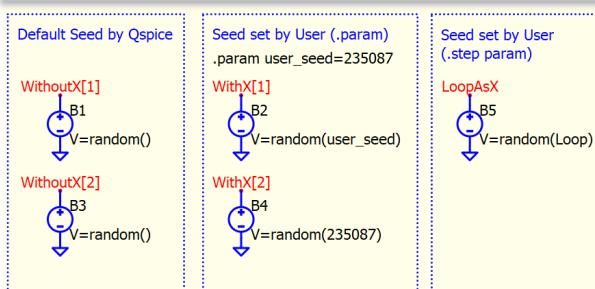
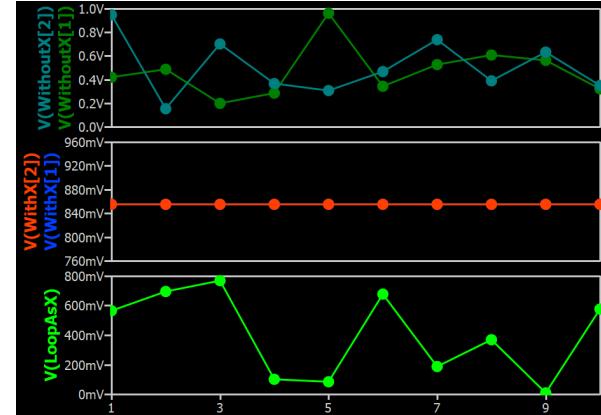
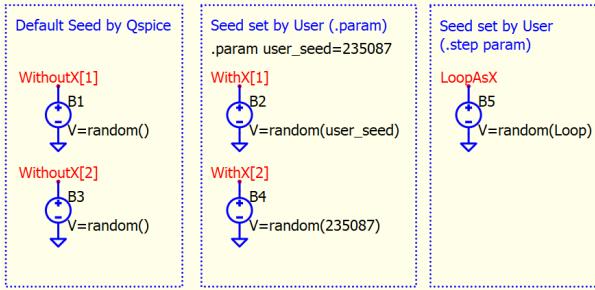
- **Random()**

- Seed is determined by Qspice
- If .option seed=<value> is used, user can assign an initial seed
- If .option seedclock is used, seed is from 10MHz clock and process ID, which appear random in every run

- **Random(x)**

- Seed is set by user
- Assign a fixed value (e.g. .param), or varying value (from .step param)

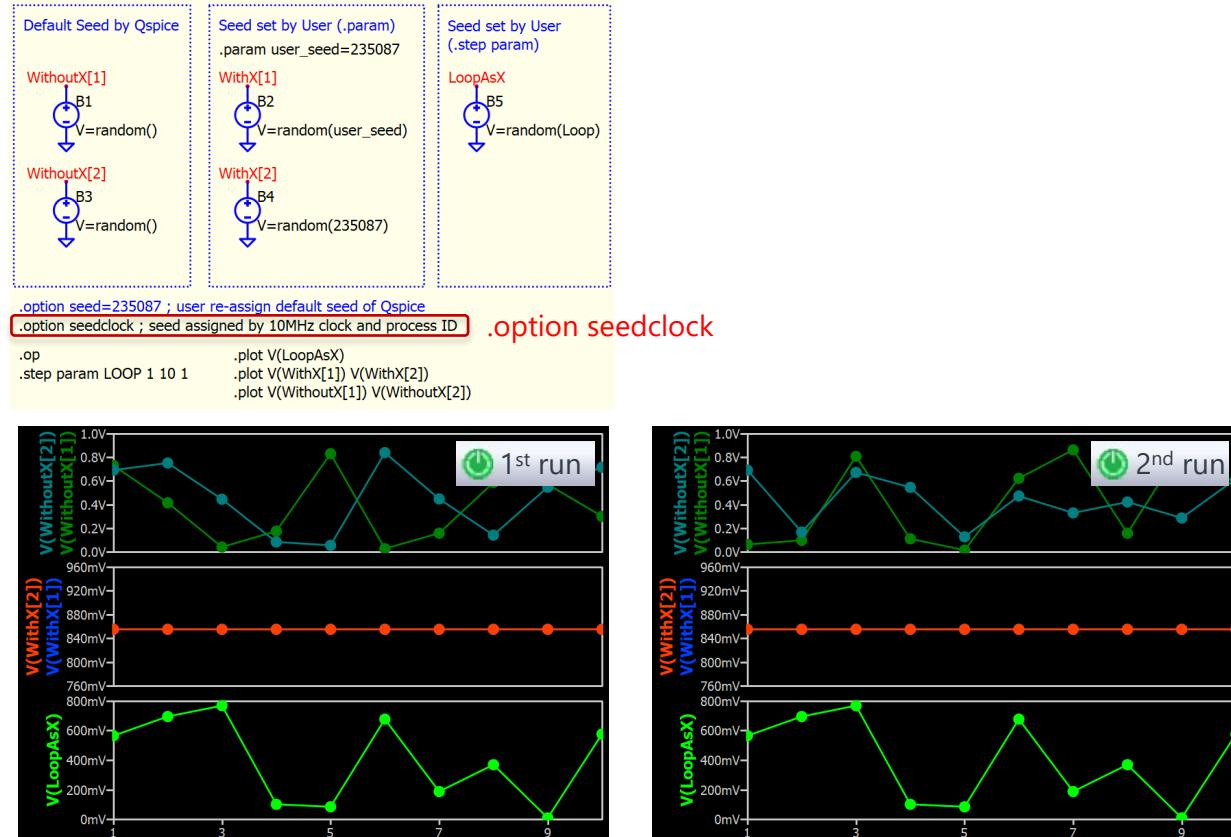
- These two examples run same results every time in Qspice as initial seed not be changed in each run



B. Function and Operators – random(x) [.option seedclock]

Qspice : B Source - random (seed).qsch

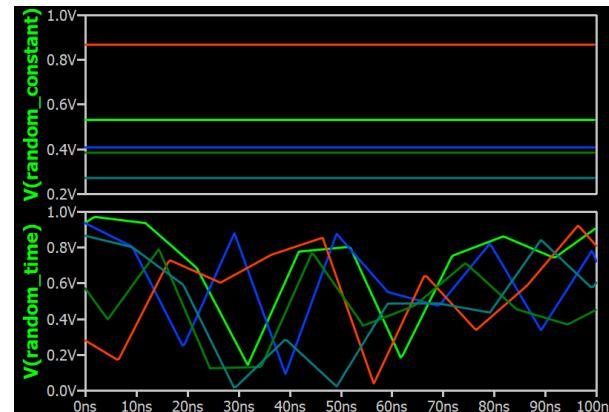
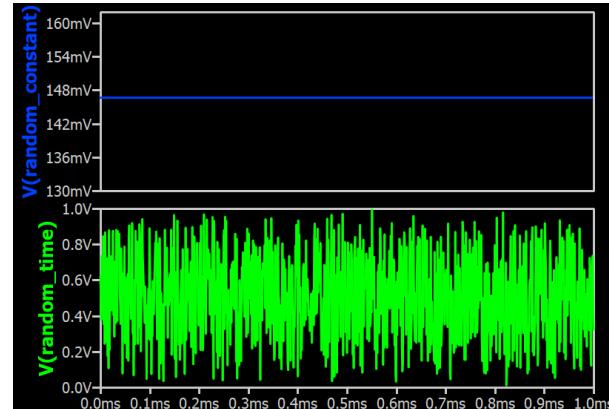
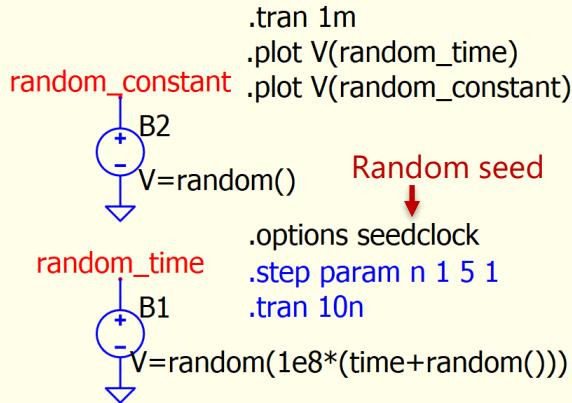
- Random(x)
 - .option seedclock
 - Initialize the random number generator with a 10Mhz clock and the process ID number
 - If seedclock is used, initial seed are different in every run
 - random() give different random pattern in every run
 - But random(x) with user defined seed and not be impacted



B. Function and Operators – random(x) [Random in .tran timestep]

Qspice : B Source – random (.tran).qsch

- Random(x)
 - Random number from 0 to 1 depending on the integer value of x
 - The one without arguments must be processed in the preprocessor (from Mike Engelhardt)
 - To create a random sequence in transient, x must change in each time step : i.e. $\text{random}(1\text{e}8 * \text{time})$, multiple time with $1\text{e}8$ is for x to be a large integer for random generation
 - For random run in each step, function can be
 - $\text{random}(1\text{e}8 * (\text{time} + \text{random}()))$



With **random(1e8*(time+random()))**, it allows random voltage also at 0s

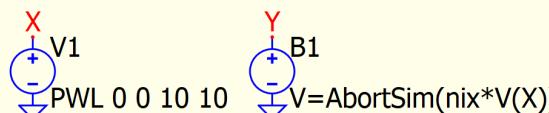
B. Function and Operators – AbortSim(x), variable/constant

Qspice : B Source - AbortSim.qsch ; B Source - Buildin Variable Constant.qsch

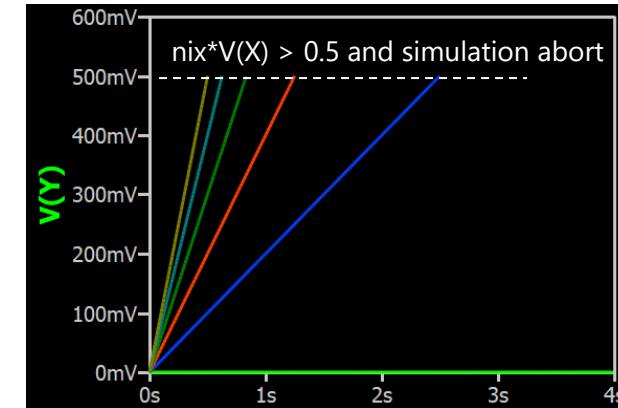
- AboutSim(x)

- To stop the current simulation from a behavioral source
- If $x > 0.5$: *abort simulation*
- else : *return x*
- The function works for .dc and .tran
- Refer to Ø-Device, MaxExtStepSize() for same feature but in .dll

syntax : AbortSim(double arg)
if arg > 0.5 : stops simulation and goes to next step (if any)
else : returns the argument

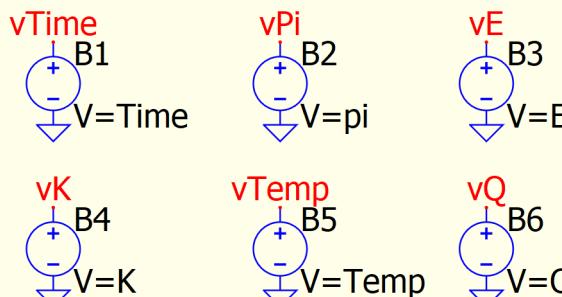


.tran 4
.step param nix 0 1 0.2



- Build-in Variable / Constant

- Time : Simulation Time
- Temp : Temperature
- PI : 3.14159265358979323846
- E : 2.7182818284590452354
- K : 1.380649e-23 J/K
- Q : 1.602176487e-19 Coulomb

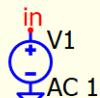


B. Behavioral Source Laplace – Filter Functions

B. Laplace – Filter Functions (Gaussian Filter)

Qspice : B Source - Laplace - Gaussian Filter.qsch

```
.param FREQ=1K  
.param BW=200  
.ac lin 1000 1 5K  
.step param N list 1 2 4 8
```



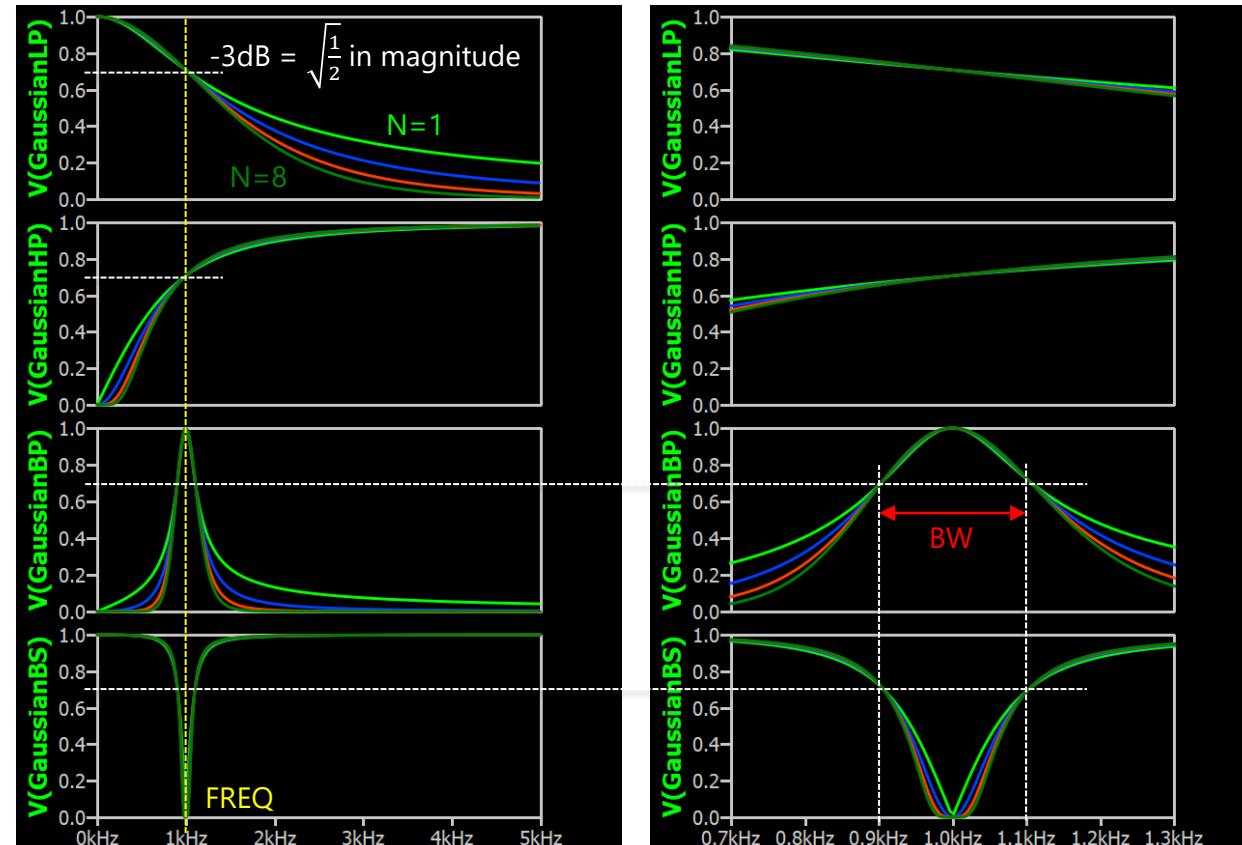
GaussianLP

GaussianHP

GaussianBP

GaussianBS

.plot V(GaussianBS)
.plot V(GaussianBP)
.plot V(GaussianHP)
.plot V(GaussianLP)



B. Laplace – Filter Functions (Bessel Filter)

Qspice : B Source - Laplace - Bessel Filter.qsch

```
.param FREQ=1K
.param BW=200
.ac lin 1000 1 5K
.step param N list 1 2 4 8
```

in
V1

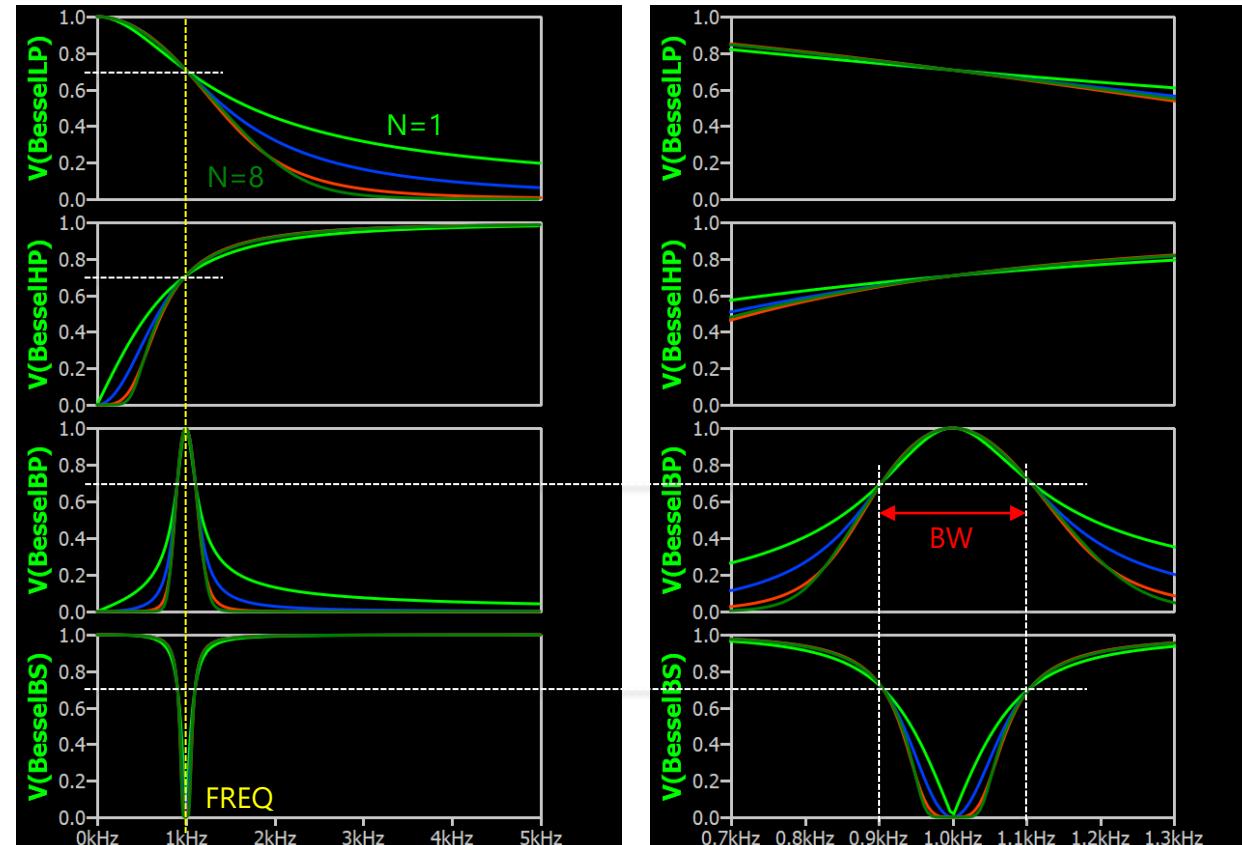
BesselLP
B1
V=V(in)
Laplace=BesselLP(N,Freq)

BesselHP
B3
V=V(in)
Laplace=BesselHP(N,Freq)

BesselBP
B2
V=V(in)
Laplace=BesselBP(N,Freq,BW)

BesselBS
B4
V=V(in)
Laplace=BesselBS(N,Freq,BW)

```
.plot V(BesselBS)
.plot V(BesselBP)
.plot V(BesselHP)
.plot V(BesselLP)
```



B. Laplace – Filter Functions (Butterworth Filter)

Qspice : B Source - Laplace - Butterworth Filter.qsch

```
.param FREQ=1K  
.param BW=200  
.ac lin 1000 1 5K  
.step param N list 1 2 4 8
```



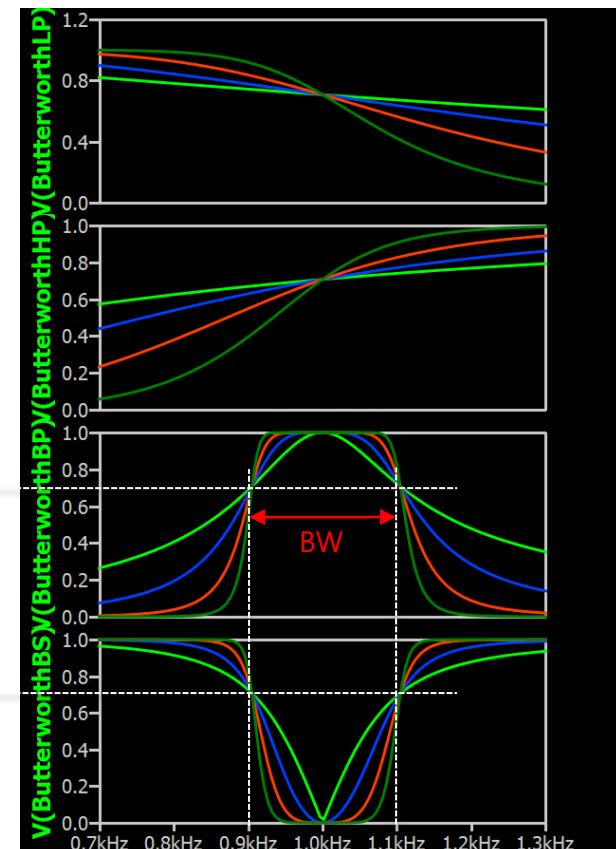
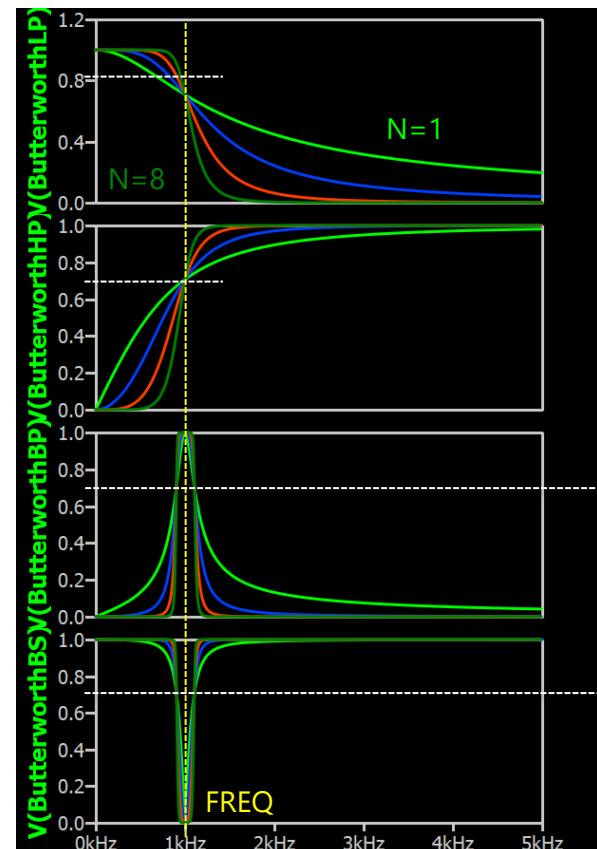
ButterworthLP
B1
V=V(in)
Laplace=ButterworthLP(N,Freq)

ButterworthHP
B3
V=V(in)
Laplace=ButterworthHP(N,Freq)

ButterworthBP
B2
V=V(in)
Laplace=ButterworthBP(N,Freq,BW)

ButterworthBS
B4
V=V(in)
Laplace=ButterworthBS(N,Freq,BW)

```
.plot V(ButterworthBS)  
.plot V(ButterworthBP)  
.plot V(ButterworthHP)  
.plot V(ButterworthLP)
```



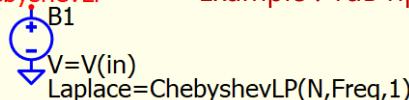
B. Laplace – Filter Functions (Chebyshev Filter)

Qspice : B Source - Laplace - Chebyshev Filter.qsch

```
.param FREQ=1K  
.param BW=200  
.ac lin 1000 1 5K  
.step param N list 1 2 4 8
```

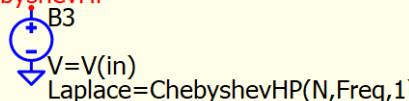


ChebyshevLP

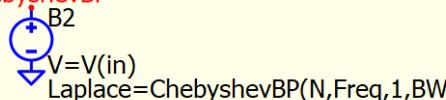


Example : 1dB ripple

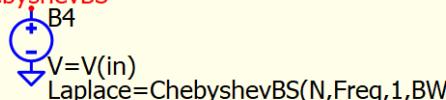
ChebyshevHP



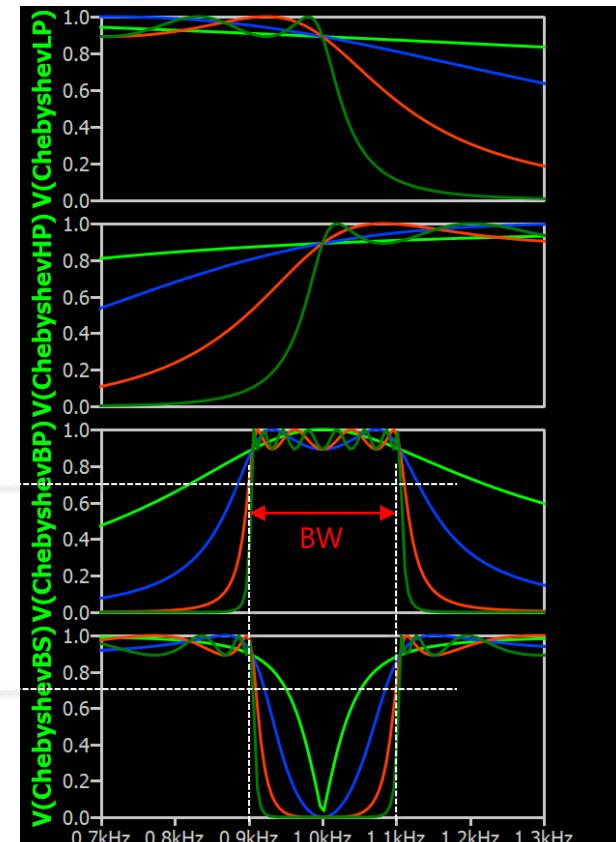
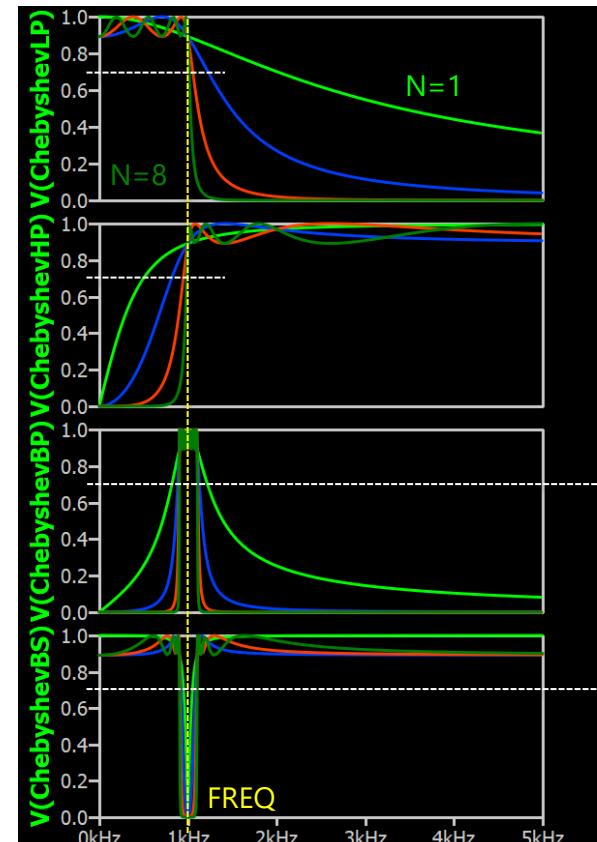
ChebyshevBP



ChebyshevBS



```
.plot V(ChebyshevBS)  
.plot V(ChebyshevBP)  
.plot V(ChebyshevHP)  
.plot V(ChebyshevLP)
```



B. Laplace – Filter Functions (Chebyshev2 Filter)

Qspice : B Source - Laplace - Chebyshev2 Filter.qsch

```
.param FREQ=1K  
.param BW=200  
.ac lin 1000 1 5K  
.step param N list 1 2 4 8
```



Chebyshev2LP Example : 20dB rejection

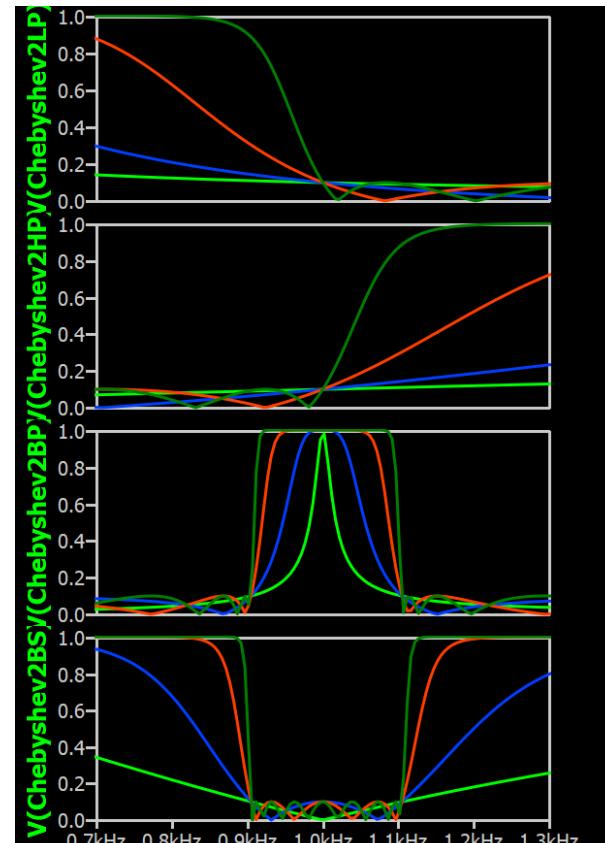
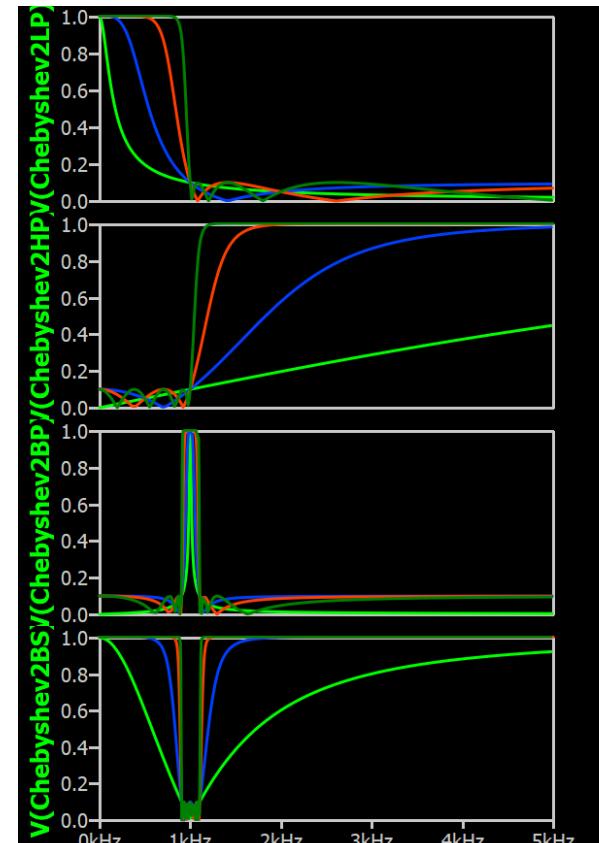
Chebyshev2LP
B1
V=V(in)
Laplace=Chebyshev2LP(N,Freq,20)

Chebyshev2HP
B3
V=V(in)
Laplace=Chebyshev2HP(N,Freq,20)

Chebyshev2BP
B2
V=V(in)
Laplace=Chebyshev2BP(N,Freq,20,BW)

Chebyshev2BS
B4
V=V(in)
Laplace=Chebyshev2BS(N,Freq,20,BW)

```
.plot V(Chebyshev2BS)  
.plot V(Chebyshev2BP)  
.plot V(Chebyshev2HP)  
.plot V(Chebyshev2LP)
```

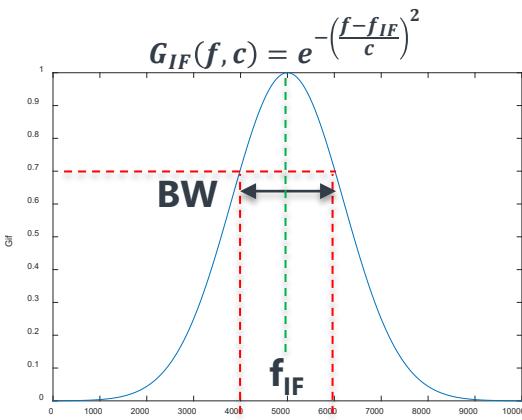


B. Laplace – Filter Functions (HELP : Laplace s-Domain Support)

Qspice : B Source - Laplace - GaussianBP.qsch | Gaussian_Filter_Formula.m

- Example of Laplace Gaussian Band Pass Filter

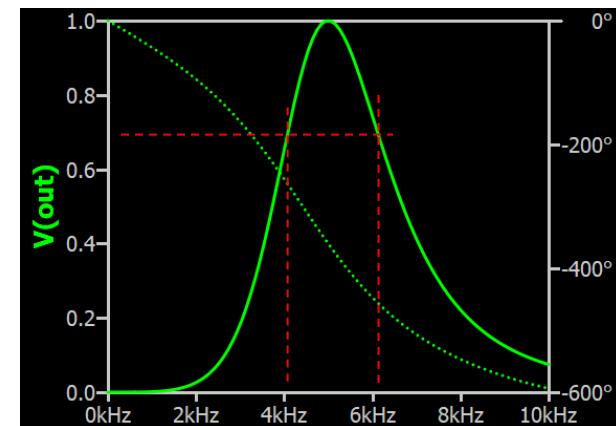
- General form of Gaussian filter frequency response : $G_{IF}(f, c) = e^{-\left(\frac{f-f_{IF}}{c}\right)^2}$
 - f_{IF} is center frequency
- Bandwidth (BW) is defined as $f_{BW} = f_{IF} \pm \frac{BW}{2}$ where $G_{IF}(f_{BW}, c) = \frac{1}{\sqrt{2}} \approx 0.7071$
 - Bandwidth refers to the width of spectral band at half of its maximum power or $\frac{1}{\sqrt{2}}$ of its maximum voltage
- Therefore, $c = \frac{BW}{2\sqrt{-\ln(\frac{1}{\sqrt{2}})}} \text{ or } BW = 2\sqrt{-\ln(\frac{1}{\sqrt{2}})} \times c$
- Qspice : GaussianBP(N, Freq, BW), where N is filter order, Freq is f_{IF} and BW is Bandwidth



```
.param fif=5000
.param c=1699
.param BW=2*sqrt(-log(1/sqrt(2)))*c
.option listparam
in V1
out B1
V=V(in)
Laplace = GaussianBP(4,fif,BW)
an example of 4th-order
```

.ac lin 100 1 10000
.plot V(out)

.meas Vmax max mag(V(out))
.meas fcenter FIND frequency WHEN mag(V(out))=Vmax
.meas fL FIND frequency WHEN mag(V(out))=Vmax/sqrt(2) rise=1
.meas fH FIND frequency WHEN mag(V(out))=Vmax/sqrt(2) fall=last
.meas BandWidth fH-fL



B. Laplace – Filter Functions (HELP : Laplace s-Domain Support)

Qspice : B Source - Laplace - GaussianBP.qsch | Gaussian_Filter_Formula.m

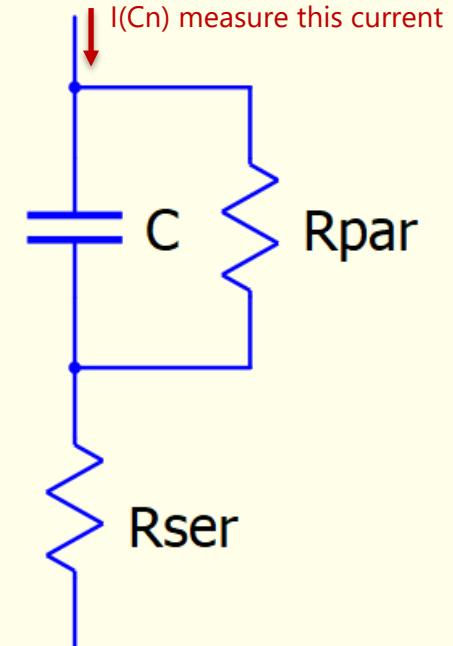
- Appendix : Derive c from f_{IF} and BW
 - Substitute $G_{IF}(f_{BW}, c) = \frac{1}{\sqrt{2}}$ and $f_{BW} = f_{IF} \pm \frac{BW}{2}$ into general formula $G_{IF}(f, c) = e^{-\left(\frac{f-f_{IF}}{c}\right)^2}$
 - $\frac{1}{\sqrt{2}} = e^{-\left(\frac{f_{IF} \pm \frac{BW}{2} - f_{IF}}{c}\right)^2} = e^{-\left(\frac{\pm \frac{BW}{2}}{c}\right)^2} = e^{-\left(\frac{BW}{2c}\right)^2}$
 - $\ln\left(\frac{1}{\sqrt{2}}\right) = -\left(\frac{BW}{2c}\right)^2 \rightarrow \sqrt{-\ln\left(\frac{1}{\sqrt{2}}\right)} = \frac{BW}{2c}$
 - $BW = 2\sqrt{-\ln\left(\frac{1}{\sqrt{2}}\right)} \times c \text{ OR } c = \frac{BW}{2\sqrt{-\ln\left(\frac{1}{\sqrt{2}}\right)}}$

C. Capacitor

C. Capacitor Instance Parameters in Qspice HELP

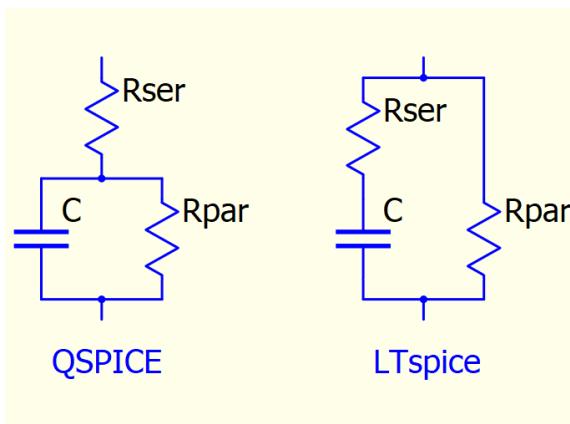
Capacitor Instance Parameters			
Name	Description	Units	Default
CAPACITANCE	Capacitance(not usually labeled)	F	0.0
CSAT	Capacitance asymptotically approached in saturation	F	10% of CAPACITANCE
IC	Initial voltage on capacitor	V	0.0
L ¹	Length	m	0.0
M	Number of identical parallel devices		1.0
RPAR	Equivalent parallel resistance	Ω	Infinite
RSER	Equivalent series resistance	Ω	0.0
SATFRAC	Fractional drop in capacitance at VSAT		0.7
TC	Polynomial temperature coefficient list		0.0
TC1	1st order temperature coefficient	$^{\circ}\text{C}^{-1}$	0.0
TC2	2nd order temperature coefficient	$^{\circ}\text{C}^{-2}$	0.0
TEMP	Instance temperature	$^{\circ}\text{C}$	Circuit temperature
TNOM	Temperature capacitance was measured(aka TREF)	$^{\circ}\text{C}$	Circuit TNOM
VSAT	Voltage that drops capacitance to SATFRAC×CAPACITANCE	V	Infinite
W ¹	Width	m	0.0

Rpar and Rser in C model



C. Capacitor – Rser and Rpar in Qspice and LTspice

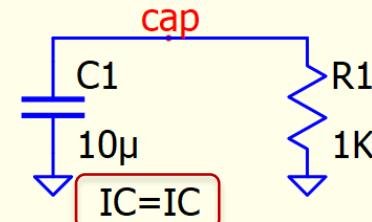
- Qspice vs LTspice
 - Beware that Qspice and LTspice treat capacitor Rser and Rpar differently
 - Capacitor conversion from LTspice to Qspice in .subckt or netlist
 - Ltspice
`Cn N001 N002 <capacitance> Rser=x Rpar=y`
 - Qspice
`Cn N001 N002 <capacitance> Rser=x`
`RparCn N001 N002 y`



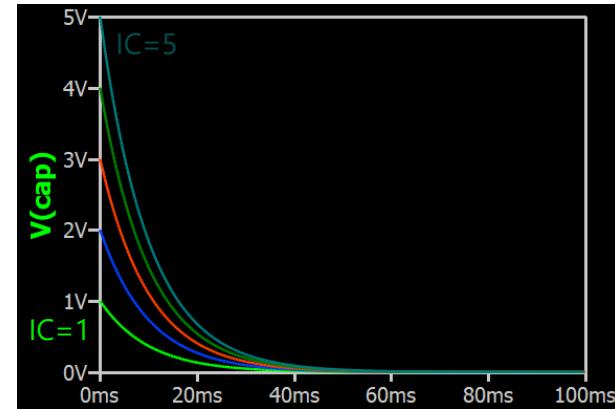
C. Instance Params : IC Initial Condition and TC Temp Coefficient

Qspice : Capacitor - IC.qsch

- IC
 - IC : Initial Condition
 - Default IC=0V
 - Use in transient analysis for initial voltage of capacitor at time=0s



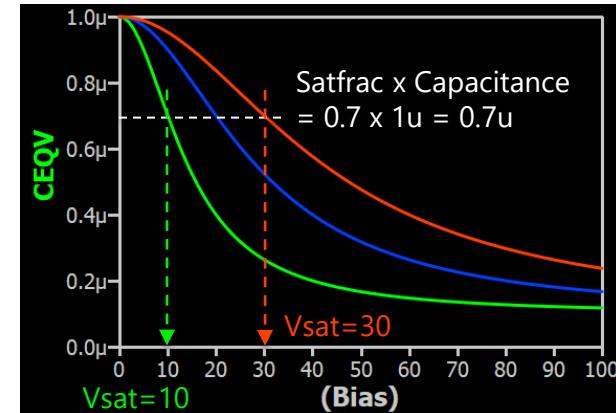
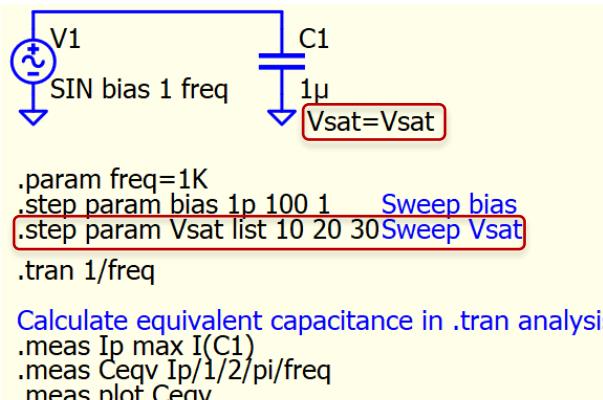
```
.step param IC 1 5 1  
.tran 100m  
.plot V(cap)
```



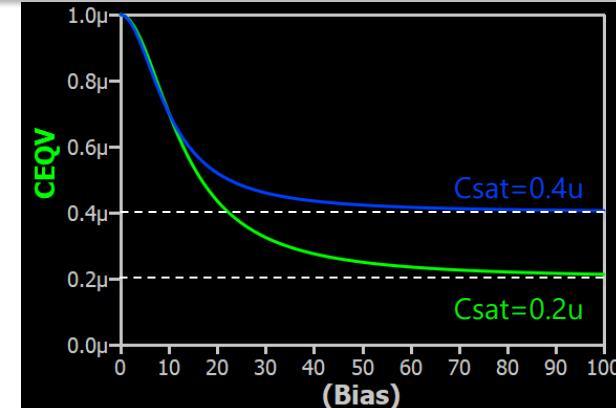
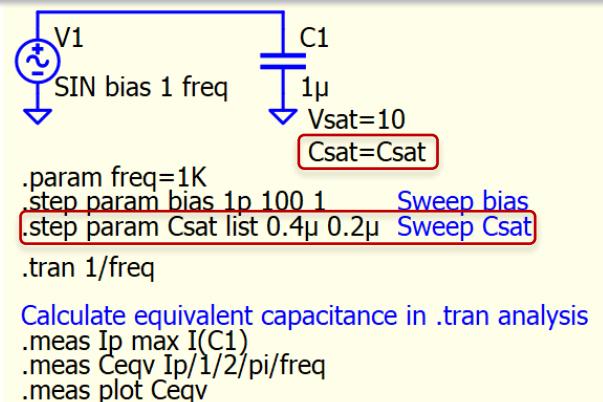
C. Instance Params : Vsat, Csat, Satfrac : For Nonlinear Capacitance

Qspice : C Capacitor - Vsat (.tran).qsch ; C Capacitor - Csat (.tran).qsch

- Vsat and Satfrac
 - Vsat : Voltage that drops capacitance to **Satfrac x Capacitance**
 - Satfrac : Fractional drop in capacitance at Vsat
 - **Default Vsat=Infinite (V)**
 - **Default Satfrac=0.7**



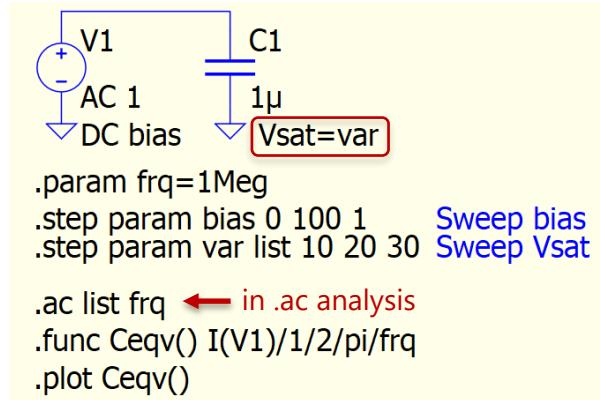
- Csat
 - Csat : Capacitance asymptotically approached in saturation
 - ** Vsat must be set to see its effect
 - **Default Csat=10% of C**



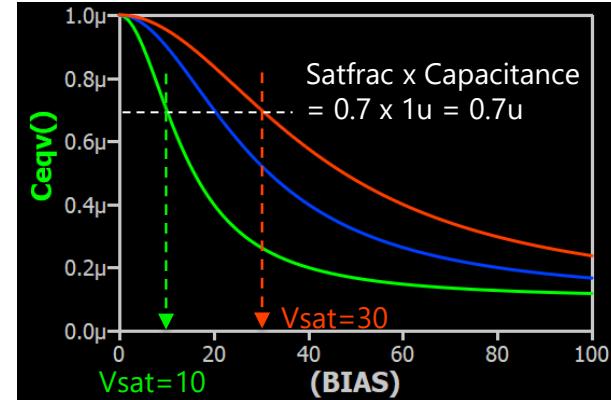
C. Instance Params : Replicate previous graph with .ac analysis

Qspice : C Capacitor - Vsat (.ac).qsch

- Vsat and Satfrac
 - Vsat : Voltage that drops capacitance to **Satfrac x Capacitance**
 - Satfrac : Fractional drop in capacitance at Vsat
 - **Default Vsat=Infinite (V)**
 - **Default Satfrac=0.7**



- Capacitance equation
 - $X_C = \frac{1}{\omega C} = \frac{V_c}{I_c}$
 - $C = \frac{|I_{cl}|}{|V_c| \omega} = \frac{|I_{cl}|}{2\pi f |V_c|}$
 - This formula is used to calculate equivalent capacitance (small signal model) at different capacitor bias voltage



C. Instance Params : Thermal Parameter

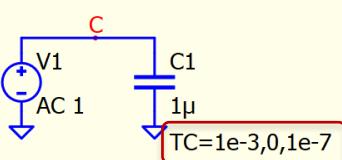
- Thermal Equation of Capacitor
 - $C = C_{nom} \times (1 + \sum TC_n (T - T_{nom})^n)$
 - Where T is operating temperature TEMP, which uses as `.temp`, `.dc temp` or `.step param temp`
 - Thermal Instance Parameter and equation relationship
 - TC : Polynomial of Thermal Coefficient where $TC = <TC1>, <TC2>, <TC3>, <TC4>, \dots$
 - $TC_n = TC_n$
 - $TC1, TC2$: 1st and 2nd order Thermal Coefficient
 - $TC1 = TC_1$ and $TC2 = TC_2$
- TEMP : Instance Temperature (Simulation Temperature of this capacitor)
- TNOM : Temperature Capacitance was measured
 - C_{nom} : Capacitance C @ TNOM

C. Instance Params : TC, TC1 and TC2

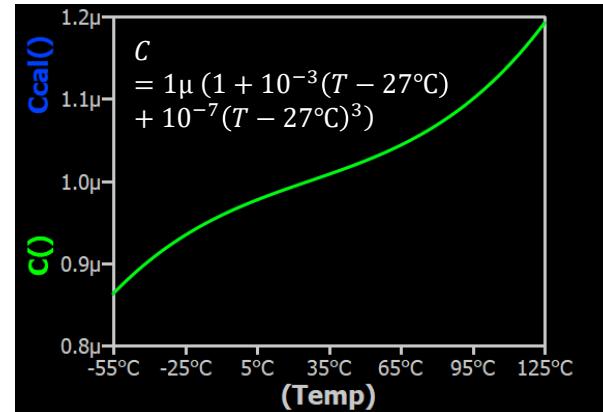
Qspice : C Capacitor - TC.qsch | C Capacitor - TC1 TC2.qsch

- TC

- TC : Temperature Coefficient list
- Default TC=0**
- TC can be defined as
TC=<value1>,<value2>,...
- Formula
- $C = C_{nom}(1 + \sum TC_n(T - T_{nom})^n)$
- In this example, Default T_{nom} is used, which is 27°C.

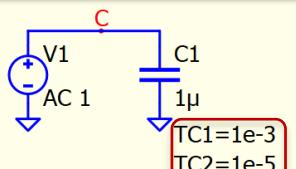


```
.step param TEMP -55 125 1
.param frq=1Meg
.ac list frq
.func imZ() V(C)/I(C1)
.func C() -1/2/pi/frq/imZ()
.plot C() Ccal()
.func Ccal() 1μ*(1+1e-3*(TEMP-27)+1e-7*(TEMP-27)^3)
```

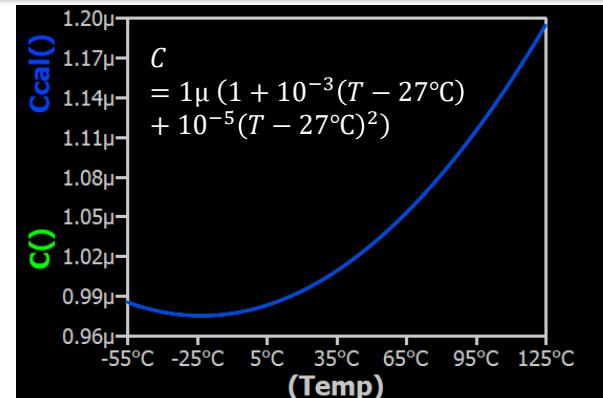


- TC1 and TC2

- TC1 : 1st order temp coeff
- TC2 : 2nd order temp coeff
- $C = C_{nom}(1 + TC_1(T - T_{nom}) + TC_2(T - T_{nom})^2)$



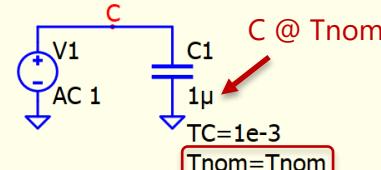
```
.step param TEMP -55 125 1
.param frq=1Meg
.ac list frq
.func imZ() V(C)/I(C1)
.func C() -1/2/pi/frq/imZ()
.plot C() Ccal()
.func Ccal() 1μ*(1+1e-3*(TEMP-27)+1e-5*(TEMP-27)^2)
```



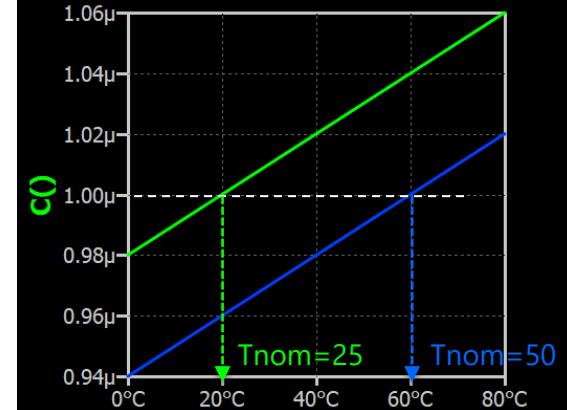
C. Instance Params : Tnom and TEMP

Qspice : C Capacitor - Tnom.qsch | C Capacitor - Temp.qsch

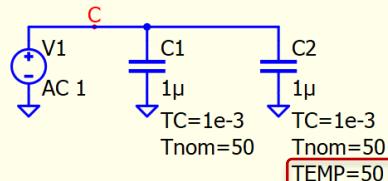
- Tnom
 - Nominal temperature
 - **Default Tnom=27°C**
 - Capacitance Cnom in thermal equation is measured at Tnom (i.e. at Tnom, calculated capacitance equal model capacitance)



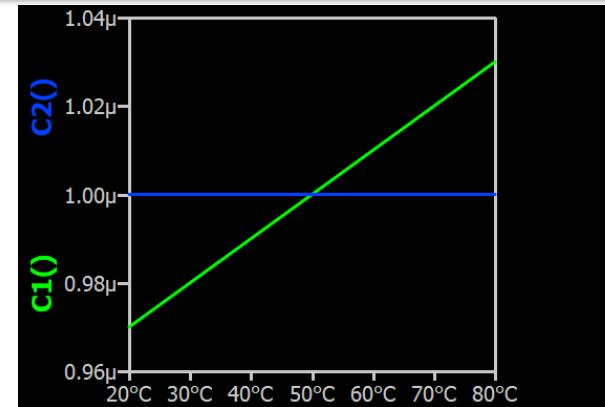
```
.step param TEMP 0 80 1  
.step param Tnom list 20 60  
.param frq=1Meg  
.ac list frq  
.func imZ() V(C)/I(C1)  
.func C() -1/2/pi/frq/imZ()  
.plot C()
```



- TEMP
 - Instance temperature
 - **Default TEMP=Circuit Temp**
 - With TEMP, capacitor is fixed at this temperature in regardless change of circuit temperature



```
.step param TEMP 20 80 1  
.param frq=1Meg  
.ac list frq  
.func imZ1() V(C)/I(C1)  
.func imZ2() V(C)/I(C2)  
.func C1() -1/2/pi/frq/imZ1()  
.func C2() -1/2/pi/frq/imZ2()  
.plot C1() C2()
```



C. Capacitor – Behavioral Capacitance (C)

Qspice : C Capacitor - Behavioral C.qsch

- C
 - Behavioral Capacitance
 - **Format : $C=<\text{equation}>$**
 - Qspice supports behavioral capacitance for a given equation which can include any circuit node voltage or device current

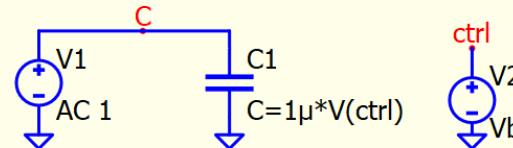
Arbitrary Capacitance-Based Capacitance Device

QSPICE also supports a behavioral capacitance where an equation for charge is not available. To use it, give an equation for the capacitance is given. The equation can include any circuit node voltages or device currents of devices modeled as Thévenin equivalents(V-, L-, E-, or H-devices). An original numerical method is used to track the charge on the capacitance not before seen in SPICE programs.

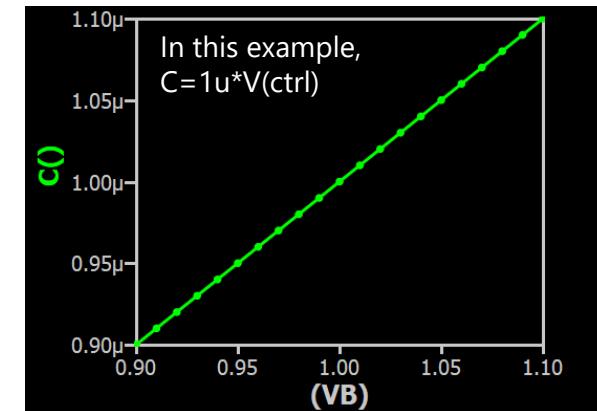
Syntax: Cnnn N1 N2 C=<expression> [additional instance parameters]

Name	Description	Units	Default
C	Equation of charge	Coulomb	
IC	Initial voltage on capacitor	V	0.0
M	Number of identical parallel devices		1.0
RPAR	Equivalent parallel resistance	Ω	Infinite
NOISELESS	Ignore the noise contribution from RPAR		not set
TEMP	Instance temperature	$^{\circ}\text{C}$	Circuit temperature

Behavioral Capacitor Model with $C=<\text{eqn}>$



```
.step param Vb 0.9 1.1 0.01
.param frq=1Meg
.ac list frq
.func C() -1/2/pi/frq/(im(V(C)/I(C1)))
.plot C()
```



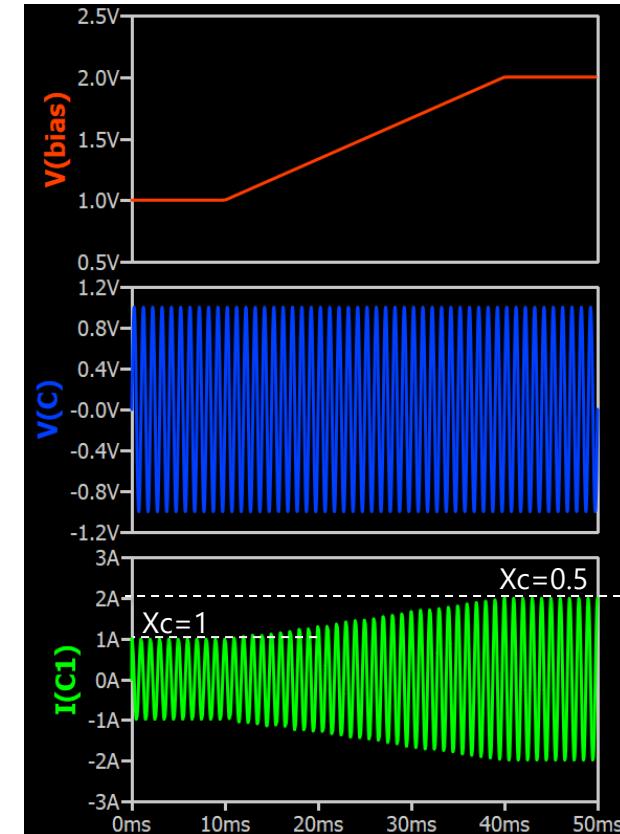
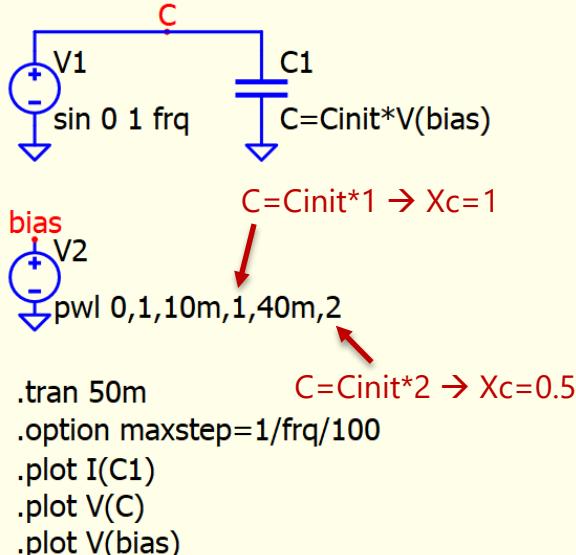
C. Capacitor – Behavioral Capacitance (C)

Qspice : C Capacitor - Behavioral C (.tran).qsch

- C
 - Behavioral Capacitance
 - This schematic demonstrate using behavioral capacitance model in transient (.tran) analysis
 - This example assume capacitance is linear to its bias voltage

Behavioral Capacitor model with $C = <\text{eqn}>$

```
.param frq=1K  
.param Xc=1  
.param Cinit=1/2/pi/frq/Xc
```



C. Capacitor – Why Qspice not include parasitic inductance (ESL or Lser)

- Answer by Mike Engelhardt in Qspice forum
 - <https://forum.qorvo.com/t/parasitic-inductance-of-passive-components-lser/15608/3>
 - <https://forum.qorvo.com/t/esl-in-capacitor-model/16944/2>

 Engelhardt Oct '23

I did not implement Lser for capacitors because it usually caused more harm than good.

A series inductance is not a great way to model the internal inductance of a capacitor. For foil capacitors, you really need a ladder of series R & L driving a distributed capacitance, though I've been able to match the complex impedance within a few degrees over several decades of frequency with just two lumps.

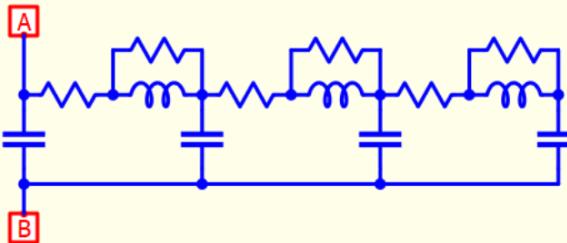
For ceramic capacitors, modeling their internal inductance is not really meaningful without modeling the parasitics of the PCB.

Anyway, when I watch people using Lser, it only increases simulation times without actually improving the integrity of the simulation.

Your mileage will vary,
-Mike



For any type of film capacitor, it is more of a distributed $R_{ser}/R_{par}/L_{ser}/C_{par}$ network. Poorly described with a single lumped series L. For a ceramic capacitor, a series inductance can be a more viable representation, but usually adds no accuracy to the simulation since connecting inductance often dominates. It was a mistake to support Lser as a part of a capacitor in LTspice. It did much more harm than good. Anyway, below would be a viable equivalent schematic of a film capacitor in lumped constants between nodes A and B:



The diagram shows a horizontal bus at the bottom with two vertical nodes, A and B, connected to it. Between these nodes are four parallel branches. Each branch consists of a resistor (wavy line) in series with a capacitor (parallel lines). In the middle of each branch is a small inductor symbol (a zigzag line). This represents a distributed R-C-L network for a film capacitor, as opposed to a single lumped series inductor.

Notice there is nowhere a series inductance.

D. Diode

Model Parameters

Diode Model Parameters in Qspice HELP

Diode Instance Parameters

Name	Description	Units	Default
AREA	Relative area		1.0
M	Number of identical parallel devices		1.0
TEMP	Instance temperature	°C	Circuit temperature

Diode Model Parameters

Name	Description	Units	Default
AF	Flicker noise exponent	1.	1.0
BV	Reverse breakdown voltage	V	Infinite
CJO	Zero-bias junction capacitance	F	0.0
EG	Activation energy	eV	1.11
FC	Forward-bias depletion capacitance coefficient		0.5
GMAX	Maximum conductivity(straight-line extension)	Ω	10000.
GP	Parallel conductivity added in lieu of global Gmin	Ω	0.
IBV	Current at breakdown voltage	A	1e-10
IBVL	Low-level reverse breakdown knee current	A	0.0
IKF	High-injection knee current	A	1e308
IS	Saturation current	A	1e-14
ISR	Recombination current parameter	A	0.0
KF	Flicker noise coefficient		0.0
M	Grading coefficient		0.5

N	Emission coefficient		1.0
NBV	Reverse breakdown emission coefficient		1.0
NBVL	Low-level reverse breakdown emission coefficient		1.0
NR	ISR emission coefficient		2.0
RS	Series resistance	Ω	0.0
TBV1	1st order BV temperature coefficient	°C ⁻¹	0.0
TBV2	2nd order BV temperature coefficient	°C ⁻²	0.0
TIKF	IKF temp coefficient	°C ⁻¹	0.0
TNOM	Parameter measurement temperature(aka TREF)	°C	27
TGP1	1st order GP temperature coefficient ¹	°C ⁻¹	0.0
TGP2	2nd order GP temperature coefficient ¹	°C ⁻²	0.0
TRS1	1st order RS temperature coefficient ¹	°C ⁻¹	0.0
TRS2	2nd order RS temperature coefficient ¹	°C ⁻²	0.0
TT	Transit-time ²	sec	0.0
VJ	Junction potential	V	1.0
VP	dQ/dt damping parameter for diffusion charge		0.01
XTI	Saturation current temperature exponent		3.0

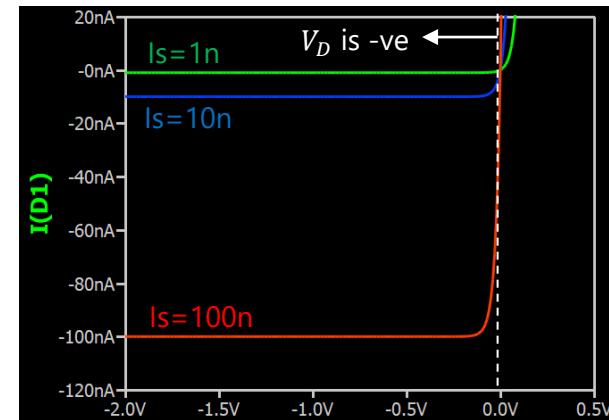
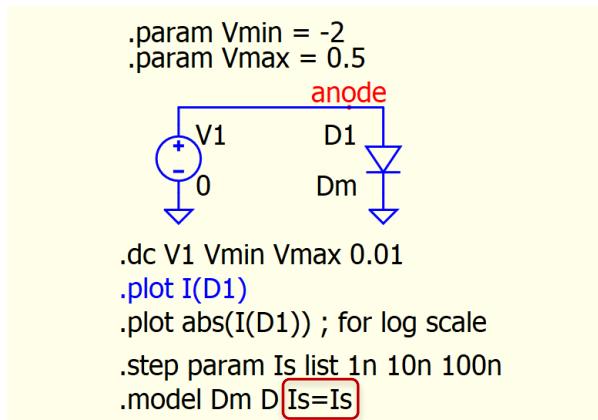
.model parameters only for information display but no electrical behavior

- MFG : manufacturer name
- Vrev : Peak reverse voltage
- Iave : Average current rating

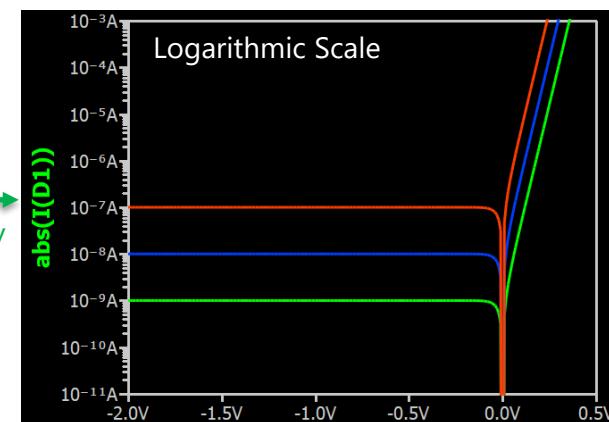
D. Diode (I-V Characteristic) : IS

Qspice : Dmodel - IS.qsch

- IS
 - Is : Saturation current
 - Saturation current in reverse region
 - **Default IS = 1e-14A**
 - $I_D = I_s (e^{\frac{qV_D}{nkT}} - 1)$
 - $\frac{kT}{q}$ is called thermal voltage
 - q : electronic charge
 - 1.602176487e-19 Coulomb
 - k : Boltzmann constant
 - 1.380649e-23 J/K
 - T : Temperature in Kelvin
 - $T = T_{celsius} + 273.15^\circ C$
 - V_D : Diode voltage
 - n : emission coefficient



$|I_d|$ →
Magnitude only



D. Diode (I-V Characteristic) : N and Rs

Qspice : Dmodel - N.qsch / Dmodel - Rs.qsch

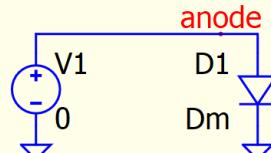
- N
 - n : emission coefficient

Default N=1

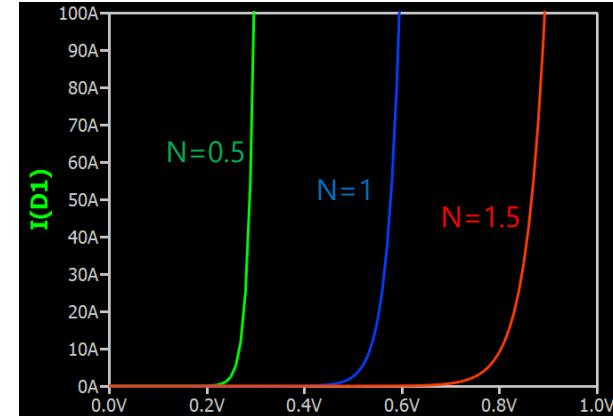
$$I_D = I_s \left(e^{\frac{qV_D}{nkT}} - 1 \right)$$

- N affects threshold voltage in forward bias

```
.param Vmin = 0  
.param Vmax = 1  
.step param n list 0.5 1 1.5
```



```
.dc V1 Vmin Vmax 0.01  
.plot I(D1)  
.model Dm D Is=10n N=n
```



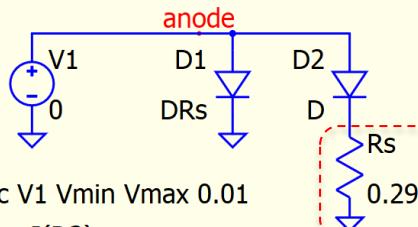
- RS
 - Rs : Series resistance

Default RS=0Ω

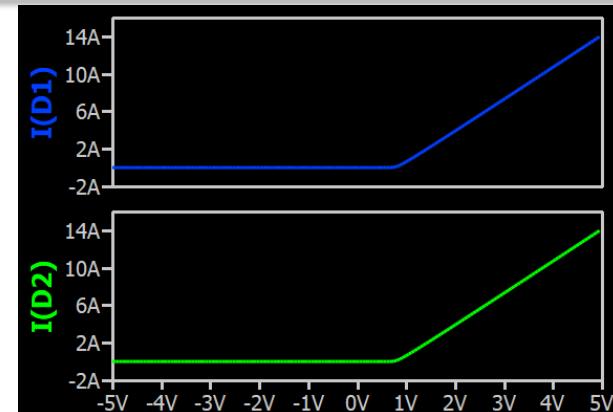
- This is equivalent to resistor added in series to diode

** V_D in $I_D = I_s \left(e^{\frac{qV_D}{nkT}} - 1 \right)$ formula only represent diode model voltage drop. If RS is added, diode model anode to cathode voltage is $V_D + I_D R_s$

```
.param Vmin = -5  
.param Vmax = 5
```



```
.dc V1 Vmin Vmax 0.01  
.plot I(D2)  
.plot I(D1)  
.model DRs D Rs=0.29
```

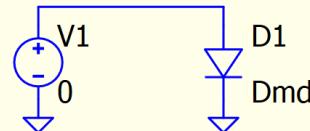


D. Diode (I-V Characteristic - Thermal) : EG

Qspice : Dmodel - EG.qsch

- Eg
 - Activation energy
 - **Default Eg=1.1eV**
 - Eg is temperature dependence factor which modifies effective value of IS (saturation current) and VJ (junction potential)
- Eg has no effect at Tnom
- Example
 - Eg=1.1 or Eg=3.4 with identical I-V characteristic at Tnom=27°C
 - I-V characteristic which different temperature dependence with different Eg

EG: Activation energy / Energy Gap

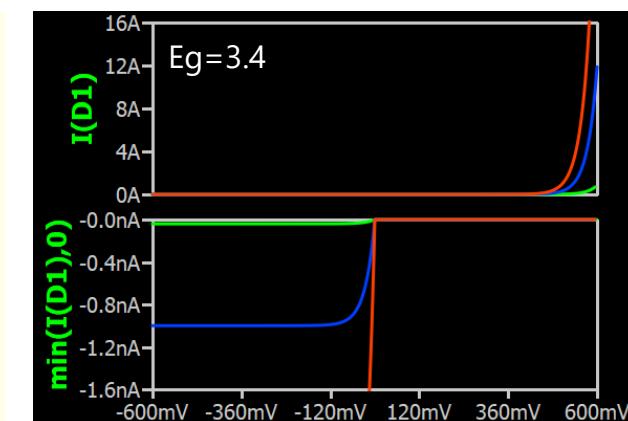
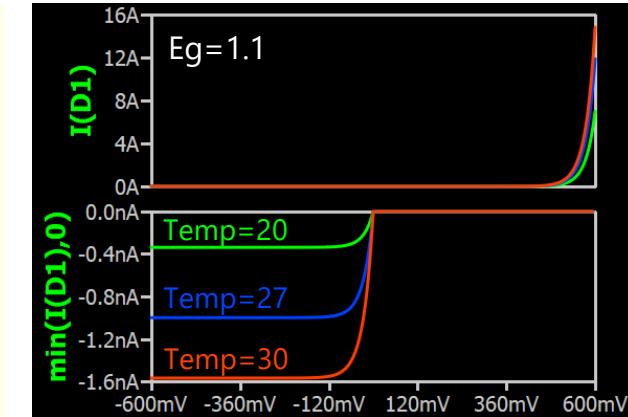


```
.dc V1 -.6 .6 0.001 temp list 20 27 30  
.model Dmdl D Is=1n N=1 Eg=1.1  
.model Dmdl D Is=1n N=1 Eg=3.4  
.plot min(I(D1),0)  
.plot I(D1)
```

EG: Activation energy / Energy Gap



```
.dc V1 -.6 .6 0.001 temp list 20 27 30  
.model Dmdl D Is=1n N=1 Eg=1.1  
.model Dmdl D Is=1n N=1 Eg=3.4  
.plot min(I(D1),0)  
.plot I(D1)
```



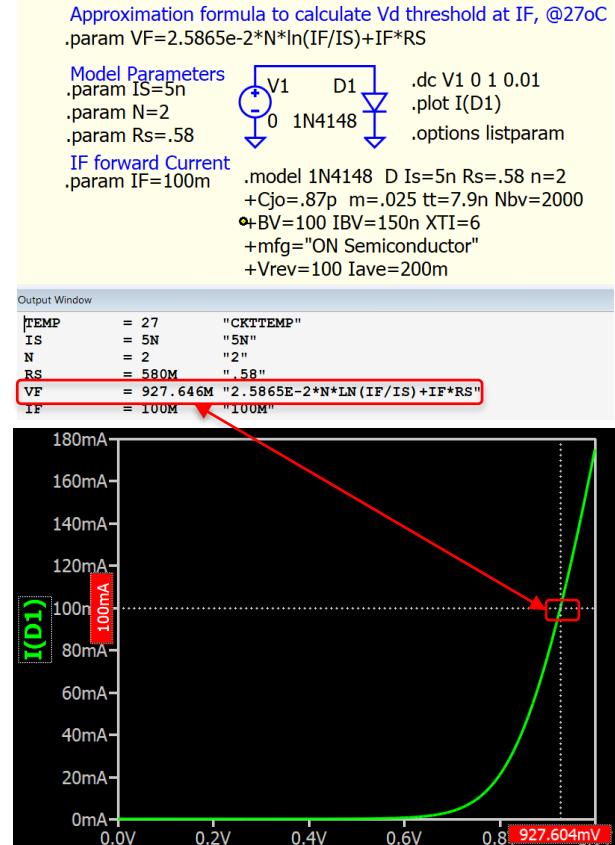
D. Diode (I-V Characteristic - Thermal) : EG

- EG : Activation energy / Energy Gap / Bandgap
 - Germanium : 0.67eV
 - Silicon : 1.11eV
 - GaN : 3.4eV
 - Ultra-fast Recovery :
 - Silicon-Schottky : 0.69eV
 - SiC-Schottky : 3.2eV

Forward Voltage (VF) or Threshold @ Specified Forward Current (IF)

** Condition : Recombination current is not used : ISR=0

- Background
 - In datasheet, it generally specify forward threshold by defining as forward voltage drop (VF) at a specified forward current level (IF)
- Diode model include RS
 - $V_{D,ext} = V_D + I_D R_S$ and $I_d = I_s (e^{\frac{qV_D}{nkT}} - 1)$
 - where $V_{D,ext}$ is diode voltage drop including series resistance
 - Re-arrange I_d formula : $V_D = n \frac{kT}{q} \ln \left(\frac{I_d}{I_s} + 1 \right)$
 - Therefore,
 - $V_{D,ext} = n \frac{kT}{q} \ln \left(\frac{I_d}{I_s} + 1 \right) + I_D R_S$
 - Substitute $V_{D,ext}$ by VF and I_D by IF and Qspice .model parameters
 - $V_F = N \frac{kT}{q} \ln \left(\frac{IF}{IS} + 1 \right) + IF \times RS$
 - where Qspice default temperature T is 27°C = 300.15K
 - $k=1.380649e-23 \text{ J/K}$ and $q=1.602176487e-19 \text{ C}$ $\rightarrow \frac{kT}{q} = 2.5865e-2$
 - Equation can be simplified with $IF \gg IS$ where $\left(\frac{IF}{IS} + 1 \right) \rightarrow \frac{IF}{IS}$
- Simplified Results in Qspice
 - $VF = 2.5865e-2 * N * \ln(IF/IS) + IF * RS$
 - IS, N and RS are in diode .model
 - IF is specified forward current for diode threshold (e.g. IF=100mA)



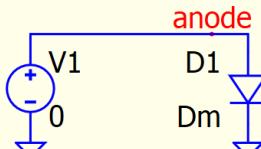
D. Diode (I-V Characteristic : Breakdown) : BV, IBV and NBV

Qspice : Dmodel - BV IBV.qsch / Dmodel - NBV.qsch

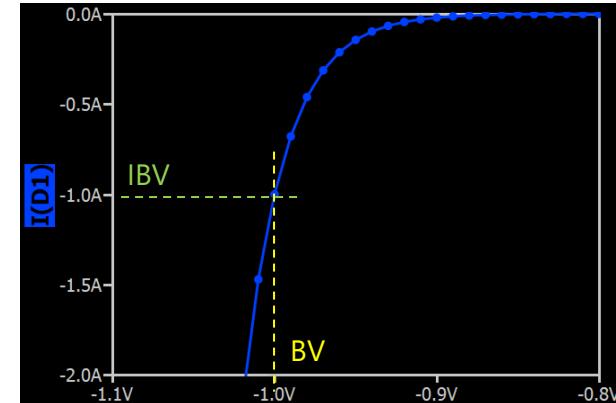
- BV and IBV

- BV : Breakdown Voltage
- IBV : Current at breakdown voltage
- Default BV=Infinite**
- Default IBV=1e-10**
- Breakdown region eqn
 - $I_D = -IBV e^{-\frac{q(BV+V_D)}{kT}}$

```
.param Vmin = -1.2  
.param Vmax = 0
```



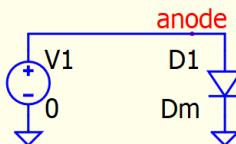
```
.dc V1 Vmin Vmax 0.01  
.plot I(D1)  
.model Dm D BV=1 IBV=1
```



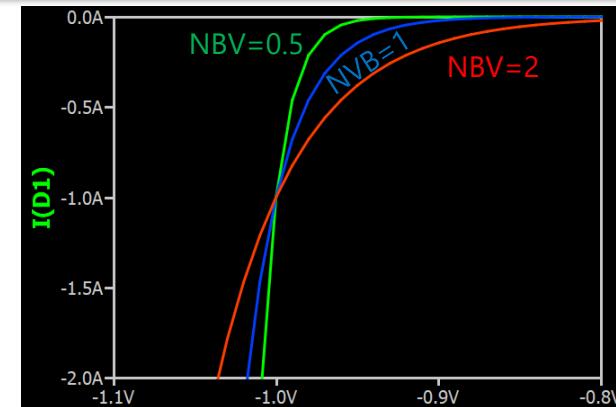
- NBV

- NBV : Reverse breakdown emission coefficient
- Default NBV=1**
- Change the sharpness of breakdown reverse current

```
.param Vmin = -1.2  
.param Vmax = 0
```



```
.dc V1 Vmin Vmax 0.01  
.plot I(D1)  
.model Dm D BV=1 IBV=1 NBV=nbv  
.step param nbv list 0.5 1 2
```



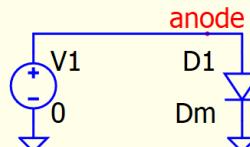
D. Diode (I-V Characteristic : Breakdown) : IBVL and NBVL

Qspice : Dmodel - IBVL.qsch / Dmodel - NBVL.qsch

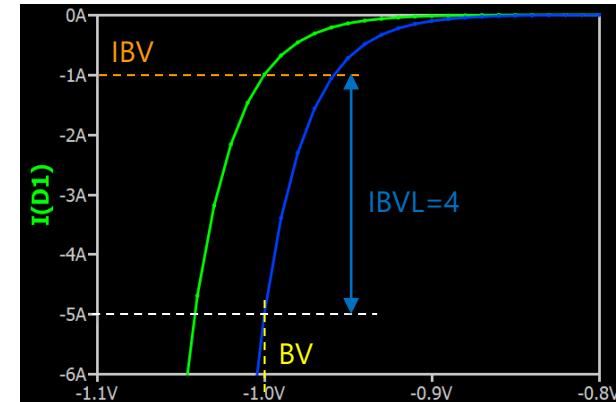
- **IBVL**

- IBVL : low-level reverse breakdown knee current
- **Default IBVL=1**

```
.param Vmin = -1.2  
.param Vmax = -0.6
```



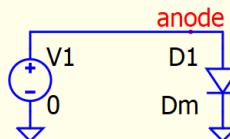
```
.dc V1 Vmin Vmax 0.01  
.plot I(D1)  
.step param ibvl list 0 4  
.model Dm D BV=1 IBV=1 IBVL=ibvl
```



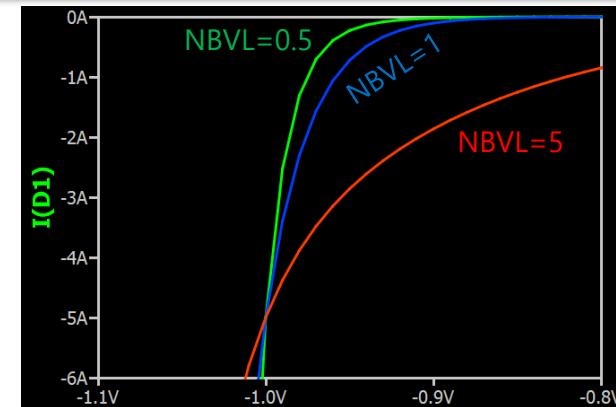
- **NBVL**

- NBVL : Low-level reverse breakdown emission coefficient
- **Default NBVL=1**
- Change the sharpness of breakdown reverse current when IBVL is used

```
.param Vmin = -1.2  
.param Vmax = -0.6
```



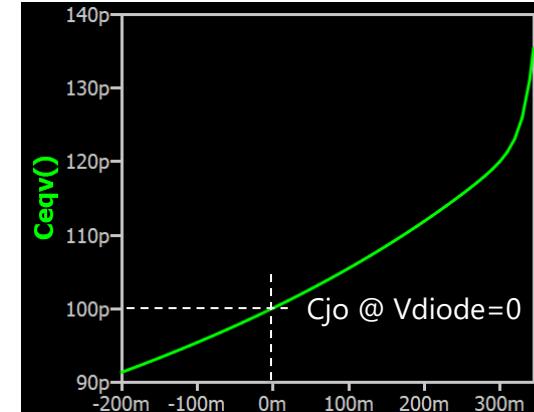
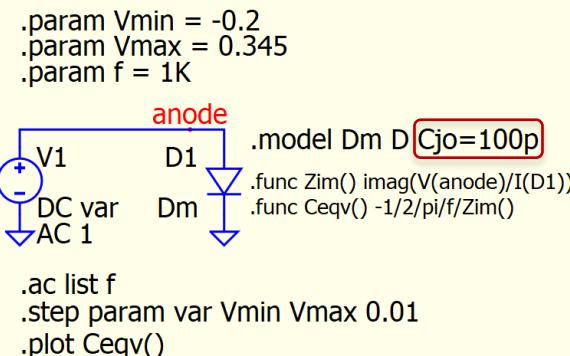
```
.dc V1 Vmin Vmax 0.01  
.plot I(D1)  
.step param nbvl list 0.5 1 5  
.model Dm D BV=1 IBV=1 IBVL=4  
+NBVL=nbvl
```



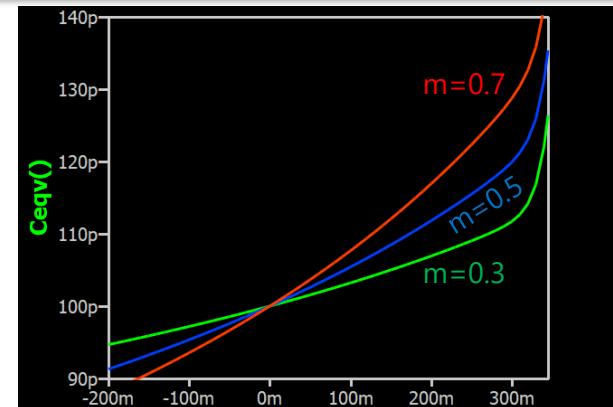
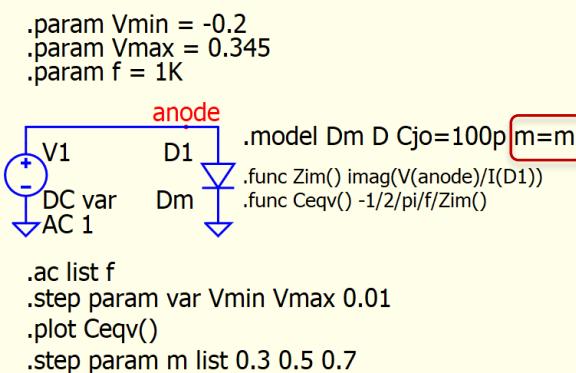
D. Diode (Capacitance) : CJO and M

Qspice : Dmodel - CJO.qsch / Dmodel - M.qsch

- CJO
 - Cjo : Zero-bias junction capacitance
 - **Default CJO=0F**
 - $C_j = \frac{C_{jo}}{\left(1 - \frac{V_D}{\Phi_0}\right)^m}$
 - Φ_0 : Junction potential (VJ)
 - m : Grading coefficient
 - M = 0.33 : linearly garded
 - M = 0.5 : abrupt junction



- M
 - m : grading coefficient
 - **Default M=0.5**
 - $C_j = \frac{C_{jo}}{\left(1 - \frac{V_D}{\Phi_0}\right)^m}$
 - m : Grading coefficient
 - M = 0.33 : linearly garded
 - M = 0.5 : abrupt junction

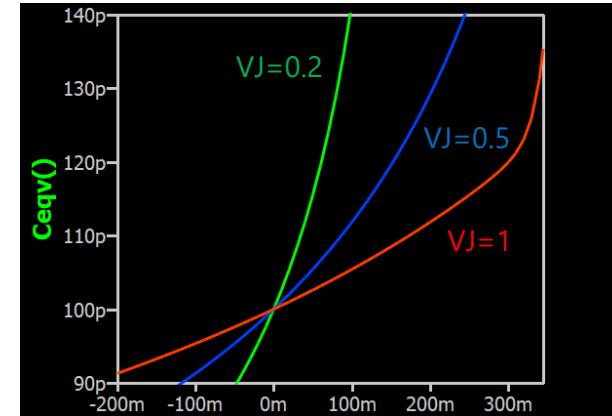


D. Diode (Capacitance) : VJ and FC

Qspice : Dmodel - VJ.qsch / Dmodel - FC.qsch

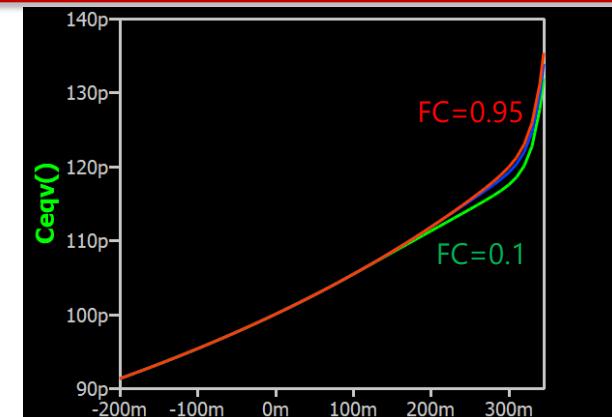
- VJ
 - V_j : Junction potential
 - **Default VJ=1V**
 - $C_j = \frac{C_{jo}}{\left(1 - \frac{V_D}{\Phi_0}\right)^m}$
 - Φ_0 : Junction potential (V_j)
 - may range from 0.2 to 1V

```
.param Vmin = -0.2
.param Vmax = 0.345
.param f = 1K
.anode
V1           .model Dm D Cjo=100p [VJ=vj]
DC var       .func Zim() imag(V(anode)/I(D1))
AC 1          .func Ceqv() -1/2/pi/f/Zim()
D1           Dm
.DC
.ac list f
.step param var Vmin Vmax 0.01
.plot Ceqv()
.step param vj list 0.2 0.5 1
```



- FC
 - F_c : Forward-bias depletion capacitance coefficient
 - **Default FC=0.5**
 - A factor between 0 and 0.95 (limit by 0.95 in Qspice), which determines how the junction capacitance is calculated when the junction is forward-biased

```
.param Vmin = -0.2
.param Vmax = 0.345
.param f = 1K
.anode
V1           .model Dm D Cjo=100p [FC=fc]
DC var       .func Zim() imag(V(anode)/I(D1))
AC 1          .func Ceqv() -1/2/pi/f/Zim()
D1           Dm
.DC
.ac list f
.step param var Vmin Vmax 0.01
.plot Ceqv()
.step param fc list 0.1 0.2 0.95
```

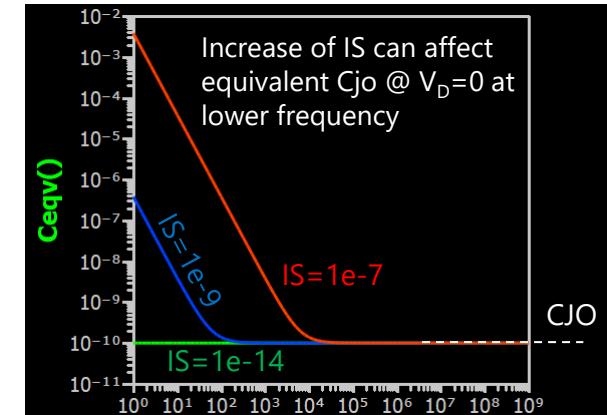


D. Diode (Capacitance) : Parameters can affect Cj in frequency

Qspice : Dmodel - Cj Effect – IS.qsch

- Params can affect Cj in frequency
 - IS : Saturation current

```
.param Vmin = -0.2
.param Vmax = 0.345
.param f = 1K
.anode
V1
DC 0
AC 1
D1
Dm
.func Zim() imag(V(anode)/I(D1))
.func Ceqv() -1/2/pi/f/Zim()
.ac list f
.step dec param f 1 1G 10
.plot Ceqv()
.model Dm D Cjo=100p Is=Is
.step param Is list 1e-14 1e-9 1e-7
```



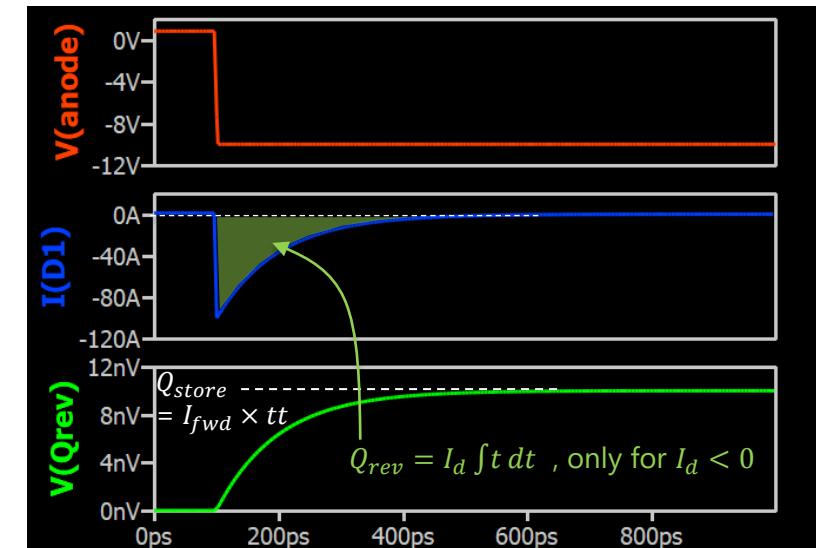
D. Diode (Reverse Recovery) : TT

Qspice : Dmodel - TT.qsch

- TT : Transit-time
 - TT is not the time it takes a diode to turn off. It's a measure of **the amount of charge that needs to be pulled out to turn the diode off**. Specifically, **the stored charge is TT times the forward current**. For the product to be Coulomb, the dimensions of TT must be time
 - $Q_{store} = I_{fwd} \times tt$, where tt is transit-time in Qspice
 - **Default TT=0s** [equivalent to disable reverse recovery from TT]
 - ** If TT is used, Rs must be non-zero (it can affect forward I-V characteristic if Rs=0 with a finite TT)

```
.param v fwd=0.834  
.param v rev=-10  
.param td=0.1n  
.param p=1p  
  
anode  
V1 D1 Dm  
pwl 0 v fwd td v fwd td+p v rev
```

```
.tran 10*td  
.option maxstep=p/50  
.plot V(Qrev)  
.plot I(D1)  
.plot V(anode)  
  
.param tt=10n  
.model Dm D Rs=1e-12 Tt=tt  
Mike's comment : If TT isn't zero,  
Rs can not be zero, because of the  
way QSPICE handles dQ/dT soft recovery.  
  
Integral negative diode current :  $Q = I \cdot t$   
Qrev  
B1  
V=idt(uramp(I(V1)),0)  
.meas Ifwd max -I(V1)  
.meas Qstore Ifwd*tt
```

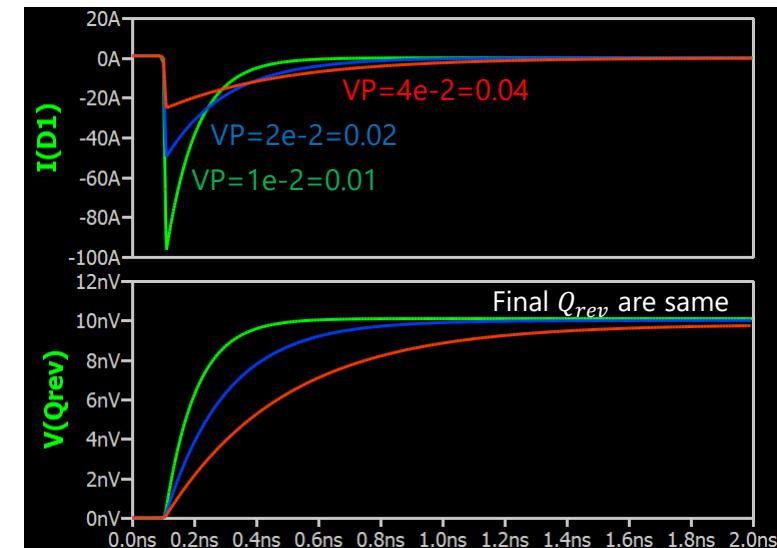


D. Diode (Reverse Recovery) : VP

Qspice : Dmodel - VP.qsch

- VP : dQ/dt damping parameter for diffusion charge
 - Default VP=0.01
 - It affect current amplitude at reverse recovery
 - Increase VP can reduce current amplitude but increase reverse recovery time

```
.param vfwd=0.834  
.param vrev=-10  
.param td=0.1n  
.param p=1p  
  
anode  
V1 D1 Dm  
  
.tran 20*td  
.option maxstep=p/50  
.plot V(Qrev)  
.plot I(D1)  
  
.step param vp list 1e-2 2e-2 4e-2  
.param tt=10n  
.model Dm D Rs=1e-12 Tt=tt Vp=vp  
  
pwl 0 vfwd td vfwd td+p vrev  
  
Integral negative diode current : Q=I*t  
Qrev  
B1  
V=idt(uramp(I(V1)),0)
```



D. Diode (Reverse Current) : CJ

Qspice : Dmodel - CJO (RR).qsch

- CJ : Junction capacitance

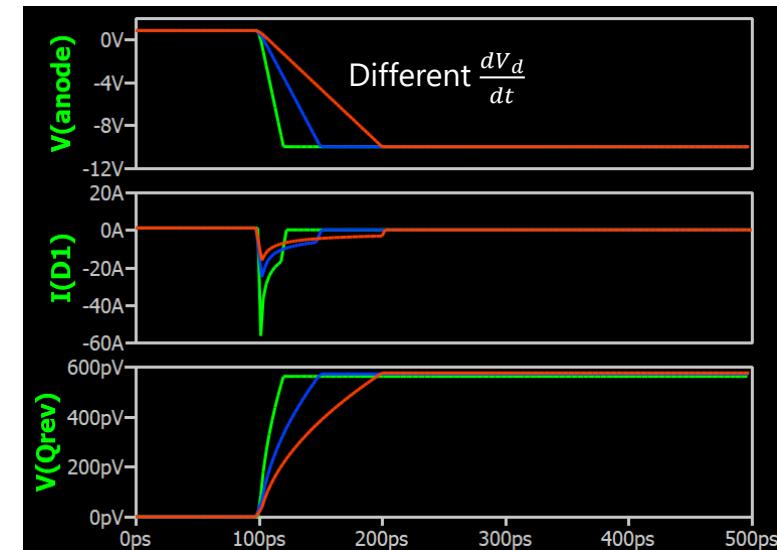
- Junction capacitance leads to reverse current but **NOT** a reverse recovery
 - For example, SiC has negligible reverse recovery and its model may not have TT but with CJO
- Reverse charge depends on junction capacitance and reverse voltage
- $\frac{dV_d}{dt}$ or $\frac{dI_d}{dt}$ are factors that can affect peak reverse current in reverse recovery

```
.param vfwd=0.834  
.param vrev=-10  
.param td=0.1n  
.param p=duratio  
  
anode  
V1 D1 Dm  
  
.tran 5*td  
.option maxstep=p/50  
.plot V(Qrev)  
.plot I(D1)  
.plot V(anode)  
  
.step param duration list 20p 50p 100p  
.model Dm D CJO=100p
```

pwl 0 vfwd td vfwd td+p vrev

Integral negative diode current : $Q = I \cdot t$

Q_{rev}
B1
 $V = idt(uramp(I(V1)), 0)$



D. Diode (Reverse Current) : CJ

Qspice : Dmodel - CJ in Reverse Voltage.qsch / Dmodel - CJ in Reverse Current.qsch

- C_j Explanation

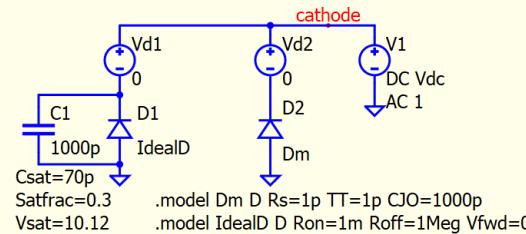
- Junction capacitance is in parallel to diode and its capacitance is a function of diode reverse voltage

- Simulation #1

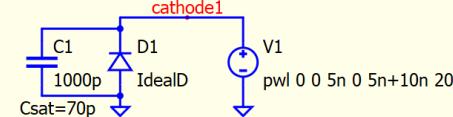
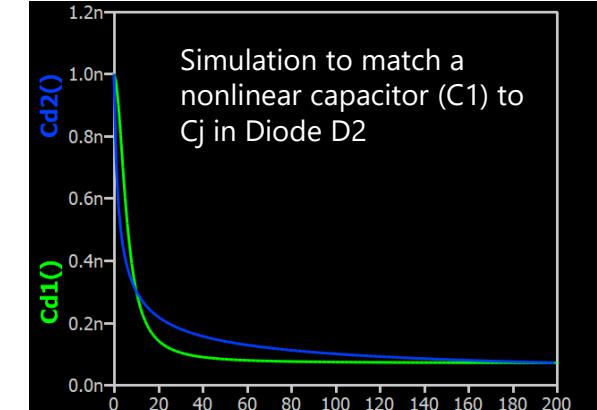
- C_j is nonlinear to diode reverse voltage, to model C_j, it requires use non-linear capacitor with C_{sat}, Satfrac and V_{sat}

- Simulation #2

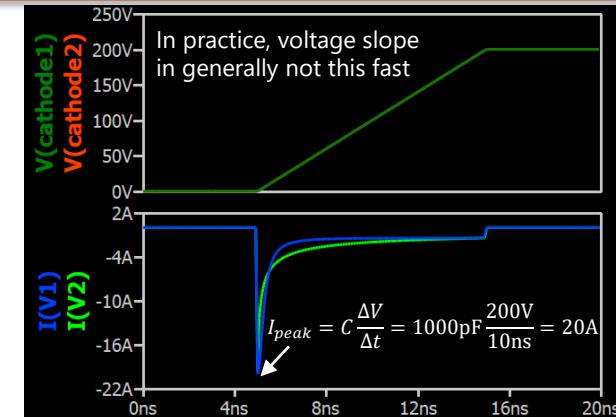
- Apply reverse voltage can simulate capacitor charging current, which act like reverse recovery but actually is not
- Reverse recovery rely on forward current as reverse recovery is to remove this charge to turn off the diode
- However, C_j is simply a mechanism that current charging a nonlinear capacitor



```
.ac list f      .param f=1Meg      .plot Cd1() Cd2()
.step param Vdc 0 200 1
.func imZD1() imag(V(drain)/I(Vd1))
.func imZD2() imag(V(drain)/I(Vd2))
.func Cd1() -1/2/pi/f/imZD1()
.func Cd2() -1/2/pi/f/imZD2()
```



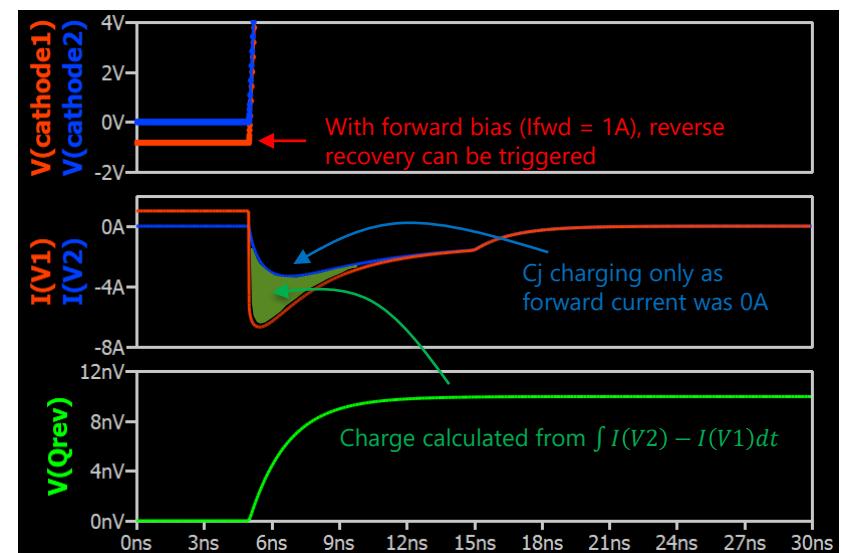
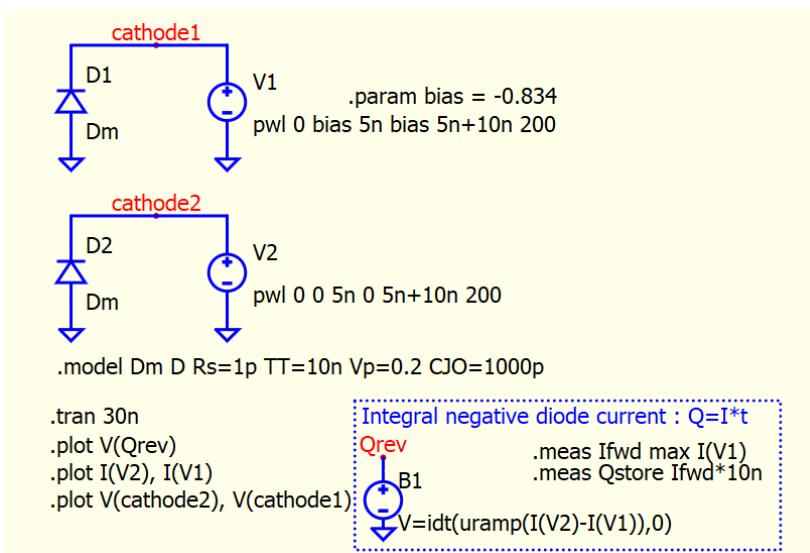
```
.tran 20n
.plot I(V2), I(V1)
.plot V(cathode2), V(cathode1)
.model Dm D Rs=1p TT=1p CJO=1000p
.model IdealD D Ron=1m Roff=1Meg Vfwd=0
```



Explanation of Reverse Recovery and Junction Capacitance Charging

Qspice : Dmodel - Reverse Recovery and Capacitor Charging.qsch

- Explanation of Reverse Recovery and Junction Capacitance Charging Current
 - Reverse Recovery is only preset if forward current is applied
 - If forward current is 0A, reverse current is by charging junction capacitance (C_j), and this is a nonlinear capacitance (capacitance decrease with cathode voltage) and therefore, reverse current reduce over time even ramp of cathode voltage is constant, where $I_d = C_j \frac{dV_d}{dt}$, where C_j is a function of V_d
 - If forward current is preset, reverse recovery is applied (TT and Vp). A extra portion of reverse current is generated and this extra charge equal $I_{fwd} \times TT$



PSPICE Static Model Params (Recombination) : IKF, ISR and NR

** Modeling of Recombination Current

- Semiconductor Device Modeling with SPICE (Section 1.9.1)

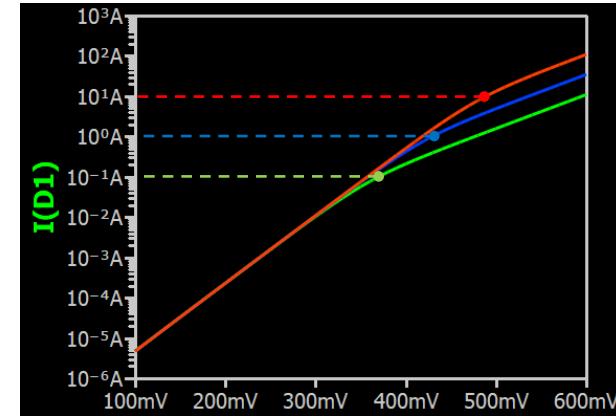
- $I_D = (K_{hli}I_F + K_{gen}I_R) - I_{Breakdown}$
 - $I_F = I_S \left(e^{\frac{qV_D}{nkT}} - 1 \right)$
 - I_S is IS : Saturation current (default = 1e-14A)
 - n is N : Emission coefficient (default = 1)
 - $K_{hli} = \sqrt{\frac{I_{KF}}{I_{KF} + I_F}}$ for $I_{KF} > 0$: If $I_{KF} \rightarrow \infty$, $K_{hli} = 1$
 - I_{KF} is IKF : High injection knee current (default = 1e308)
 - $I_R = I_{SR} \left(e^{\frac{qV_D}{n_R kT}} - 1 \right)$
 - I_{SR} is ISR : Recombination current parameter (default = 0A)
 - n_R is NR : ISR emission coefficient (default = 2)
 - $K_{gen} = \sqrt{\left[\left(1 - \frac{V_D}{\Phi_0} \right)^2 + 0.005 \right]^m}$
 - m is M : Grading coefficient (default = 0.5)
 - Φ_0 is VJ : Junction potential (default = 1V)
 - $I_{Breakdown} = IBV e^{-\frac{q(BV+V_D)}{kT}}$
 - IBV is IBV : Current at breakdown voltage (default = 1e-10A)
 - BV is BV : Reverse breakdown voltage (default = Infinite V)
 - This is equation to describe breakdown region. Reverse leakage is described in $(K_{hli}I_F + K_{gen}I_R)$

D. Diode (Recombination) : IKF

Dmodel - IKF.qsch

- IKF
 - IKF : High injection knee current
 - **Default IKF=1e308**
 - $I_D = (K_{hli}I_F + K_{gen}I_R)$
 - $I_D = K_{hli}I_F$
 - $K_{hli} = \sqrt{\frac{I_{KF}}{I_{KF} + I_F}}$ for $I_{KF} > 0$
 - The modification effect may only be easily observed with ID in log scale

```
.param Vmin = 0.1
.param Vmax = 0.6
.anode
V1 0 D1 Dm
.DC V1 {Vmin} {Vmax} 0.01
.PLOT I(D1)
.step param ikf list 0.1 1 10
.model Dm D Is=100n N=1 IKF={ikf}
```



D. Diode (Recombination) : ISR

Qspice : Dmodel - ISR.qsch

- ISR
 - Isr : Recombination current parameter
 - **Default ISR=0A**
 - $I_D = (K_{hli}I_F + K_{gen}I_R)$
 - In following examples, I_F is forced to be negligible as compare to $K_{gen}I_R$ in calculating I_D

$$\bullet I_D = K_{gen} I_{SR} \left(e^{\frac{qV_D}{n_R kT}} - 1 \right)$$

$$\bullet K_{gen} = \sqrt{\left[\left(1 - \frac{V_D}{\Phi_0} \right)^2 + 0.005 \right]^m}$$

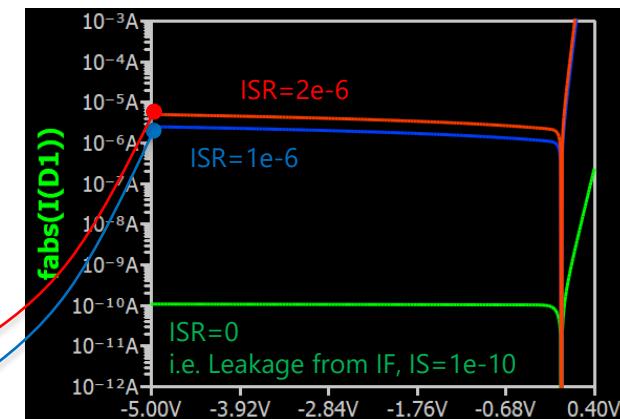
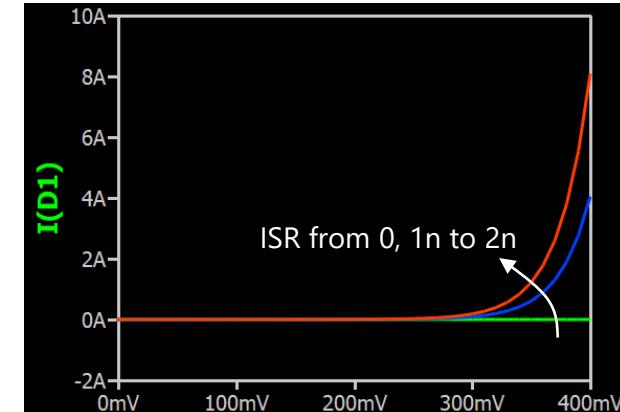
• n_R is NR : default = 2V

• m is M : default = 0.5

• Φ_0 is VJ : default = 1V

```
.param Vmin = -5
.param Vmax = 0.4
.anode
V1 0 D1
Dm
.dc V1 Vmin Vmax 0.01
.plot I(D1)
.step param isr list 0 1e-6 2e-6
.model Dm D Is=1e-10 N=2 ISR=isr NR=1
Is and N are set to equivalent with negligible If as
compare to Ir to demonstrate Ir effect
```

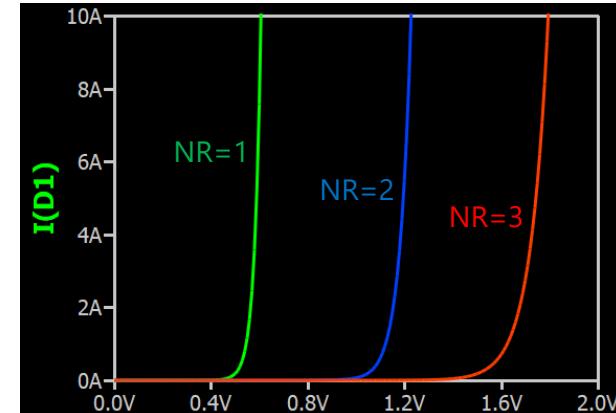
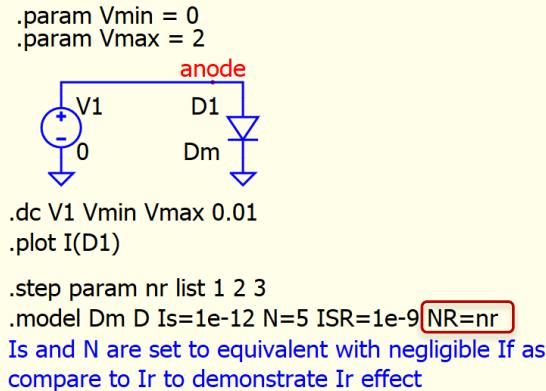
- Remark
 - As IS is set to 1e-12, in reverse and ISR=0, leakage current can still be observed through equation I_F
 - @ $V_D = -5V$
 - Therefore
 - ID for ISR=2e-6, $VD=-5$ is $4.8990\mu A$
 - ID for ISR=1e-6, $VD=-5$ is $2.4495\mu A$



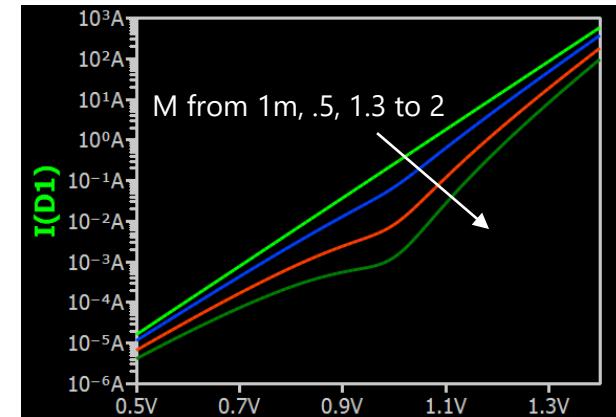
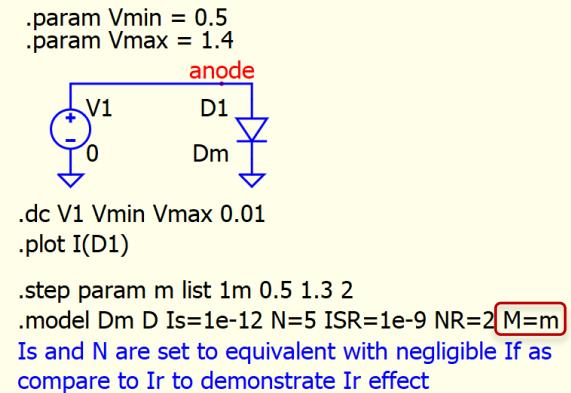
D. Diode (Recombination) : NR and M

Qspice : Dmodel - NR.qsch / Dmodel - M (Recombination).qsch

- NR
 - Nr : ISR emission coefficient
 - Default NR=2**
 - $I_D = K_{gen} I_{SR} \left(e^{\frac{qV_D}{n_R kT}} - 1 \right)$



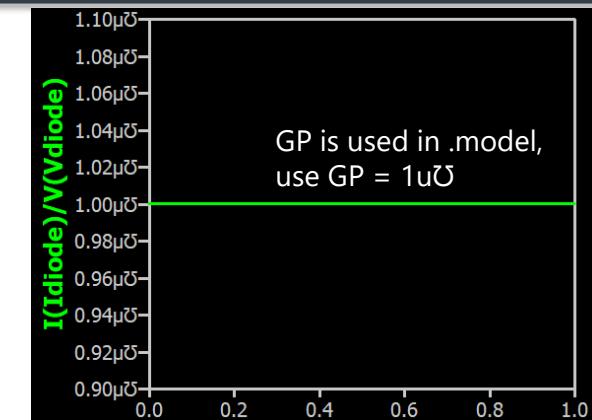
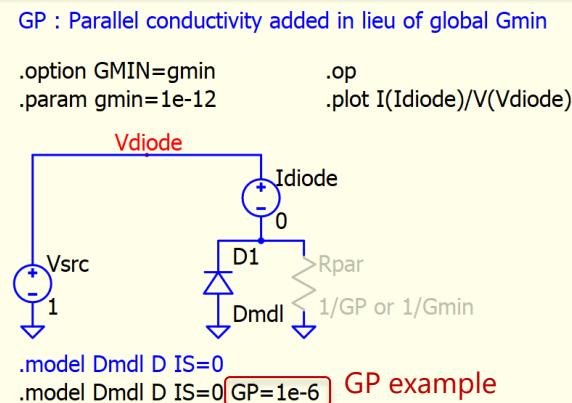
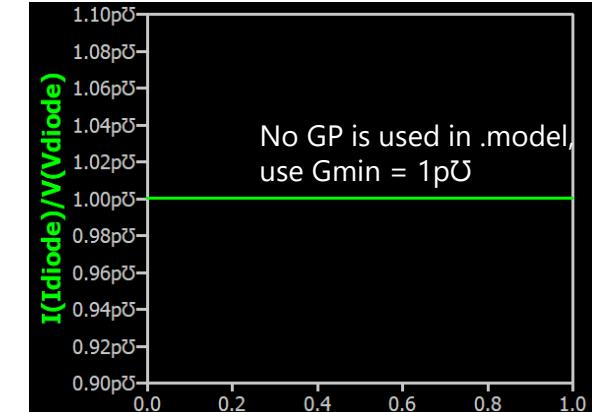
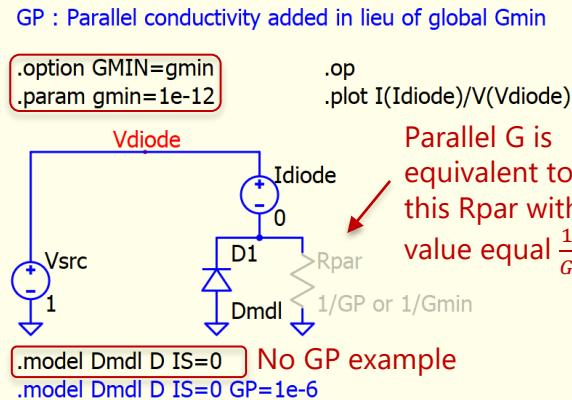
- M
 - M : Grading coefficient
 - Default M=0.5**
 - $K_{gen} = \sqrt{\left(1 - \frac{V_D}{\Phi_0}\right)^2 + 0.005}^m$
 - The modification effect may only be easily observed with ID in log scale



D. Diode (Parallel Conductance) : GP, TGP1 and TGP2

Qspice : Dmodel - GP.qsch

- GP
 - Parallel conductivity added in lieu of global Gmin
 - **Default GP=0**
 - If GP is not used, Gmin is used
 - Otherwise, GP is used
 - Gmin is minimum conductance (G) in parallel to PN junction (Default gmin in .option is 1e-12)
 - This parallel conductance is tested in this section by placing a diode in reverse with IS=0, thereby eliminating any contribution from the reverse current of the diode. This allows us to solely observe the effect of the parallel conductance.



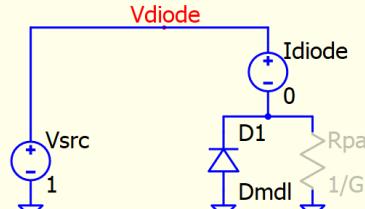
D. Diode (Parallel Conductance) : GP, TGP1 and TGP2

Qspice : Dmodel - GP - TGP1 TGP2.qsch

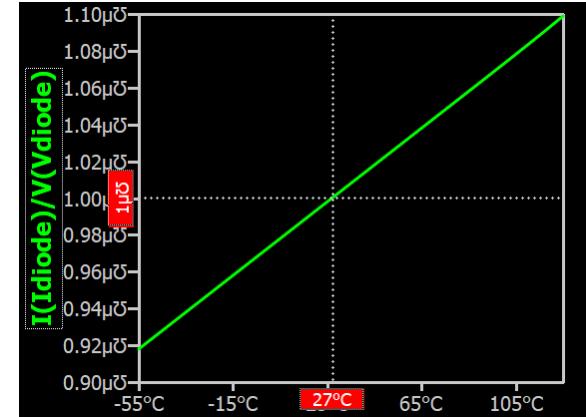
- TGP1, TGP2
 - TGP1 : 1st order GP temperature coefficient
 - TGP2 : 2nd order GP temperature coefficient
 - **Default TGP1=0**
 - **Default TGP2=0**
 - Equation
 - $G(T) = GP \times (1 + TGP1 \times \Delta T + TGP2 \times \Delta T^2)$
 - where $\Delta T = T - T_{nom}$
 - In default T_{nom} is 27°C

GP : Parallel conductivity added in lieu of global Gmin

```
.option GMIN=gmin          .dc temp -55 125 1
.param gmin=1e-12           .plot I(Idiode)/V(Vdiode)
```

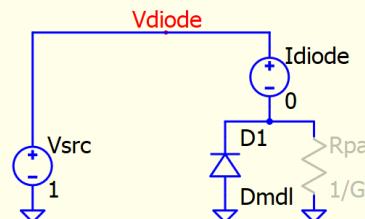


```
.model Dmdl D GP=1e-6 TGP1=1e-3 TGP2=0
```

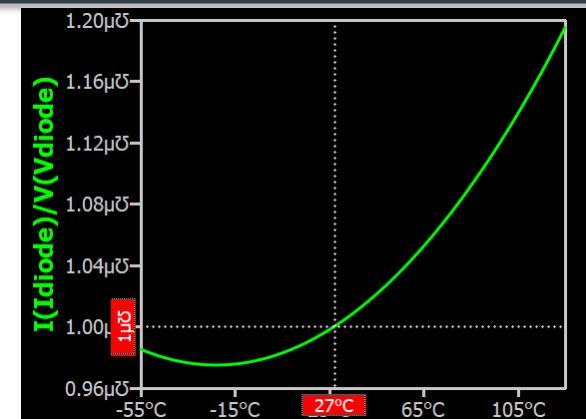


GP : Parallel conductivity added in lieu of global Gmin

```
.option GMIN=gmin          .dc temp -55 125 1
.param gmin=1e-12           .plot I(Idiode)/V(Vdiode)
```



```
.model Dmdl D GP=1e-6 TGP1=1e-3 TGP2=1e-5
```

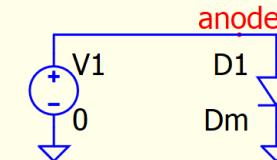


Textbook Diode Modeling

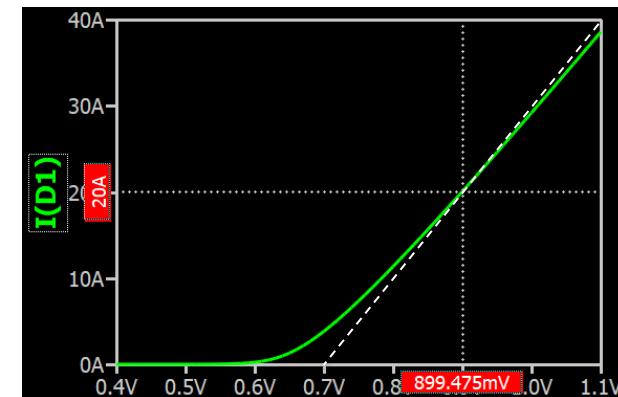
Qspice : Dmodel (Textbook).qsch

- Textbook Diode Modeling
 - $IS=1e-12$ to minimize leakage current when diode is OFF
 - $RS=\frac{\Delta V_D}{\Delta I_D}$ in the region that diode is ON
 - $N=\frac{VF-IF\times RS}{0.025865\times \ln\left(\frac{IF}{IS}\right)}$: IF is current at VF
- Assume textbook requirement is
 - Threshold = 0.7V and $\frac{\Delta I_D}{\Delta V_D} = 100A/V$
 - By $VF = \frac{IF}{\frac{\Delta I_D}{\Delta V_D}} + \text{Threshold}$
 - We use a higher IF to determine the curve,
 - @ IF=20A $\rightarrow VF = \frac{20A}{100A/V} + 0.7V = 0.9V$
 - Therefore
 - $IS=1e-12$
 - $RS=1/100=0.01$
 - $N=\frac{0.9-20\times 0.01}{0.025865\times \ln\left(\frac{20}{1e-12}\right)}=0.883$

```
.param Vmin = 0.4  
.param Vmax = 1.2
```



```
.dc V1 Vmin Vmax 0.01  
.plot I(D1)  
.model Dm D Is=1e-12 N=0.883 RS=0.01
```



D. Diode

Behavioral Diode Model Parameters

Behavioral Diode Model Parameters in Qspice HELP

QSPICE includes a simplified, behavioral, diode. To use those device equations, specify a non-zero RON.

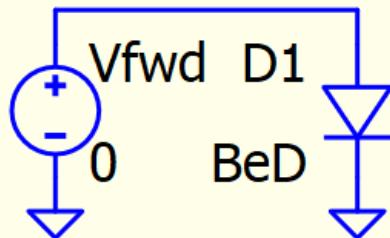
Behavioral Diode Model Parameters

Name	Description	Units	Default
RON	Forward on resistance	Ω	0.0^3
ROFF	Off resistance	Ω	$1./GMIN$
RZEN	Breakdown resistance(aka RREV)	Ω	RON
VFWD	Forward voltage drop	V	0.0
VREV	Reverse voltage drop	V	0.0
EPSILON	Width of quadratic region splining off and on regions	V	0.0
REVEPSILON	Width of quadratic region splining breakdown and on regions	V	0.0
CJO	Shunt capacitance	F	0.0

^{3]} The value of zero means don't use these equations, but the conventional SPICE semiconductor diode equations.

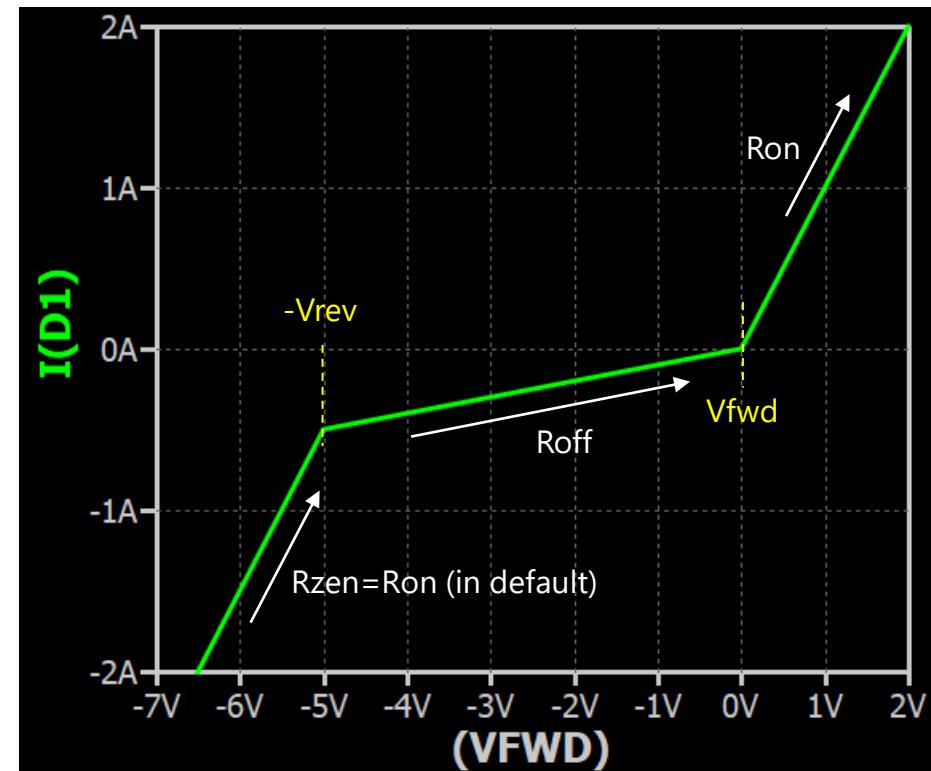
Behavioral Diode Model Params : Ron, Roff, Vfwd, Vrev

Qspice : Behavioral D Model - Ron Roff Vfwd Vrev.qsch



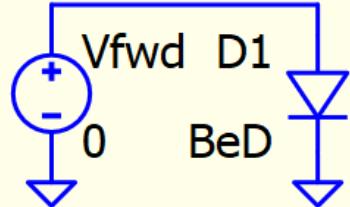
```
.model BeD D Ron=1 Roff=10  
+ Vfwd=0 Vrev=5  
+ Epsilon=0 Revepsilon=0  
.dc Vfwd -7 2 0.1  
.plot I(D1)
```

** Important Note : Refer to Qspice help, Ron must include and set to non-zero to activate behavioral diode model



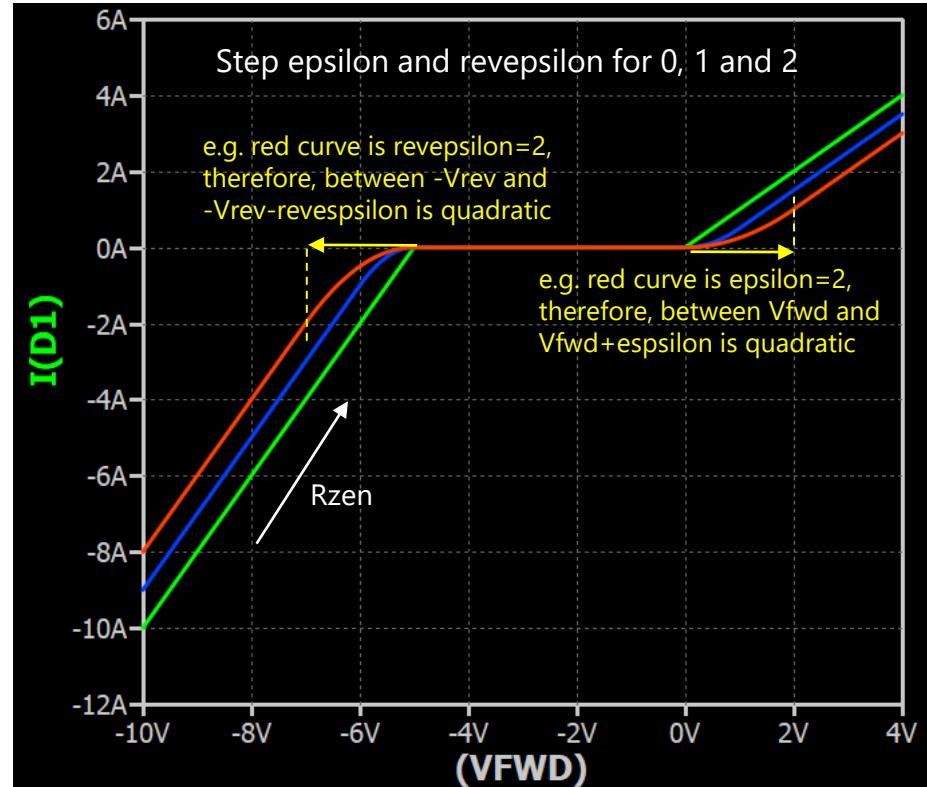
Behavioral Diode Model Params : Rzen, Epsilon, Revepsilon

Qspice : Behavioral D Model - Epsilon Revepsilon Rzen.qsch



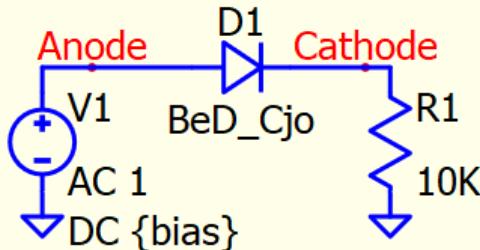
```
.model BeD D Ron=1 Roff=10Meg  
+ Vfwd=0 Vrev=5  
+ Epsilon={val} Revepsilon={val}  
+ Rzen=0.5  
  
.step param val 0 2 1  
.dc Vfwd -10 4 0.1  
.plot I(D1)
```

* Roff change to 10Meg in this study



Behavioral Diode Model Params : Cjo

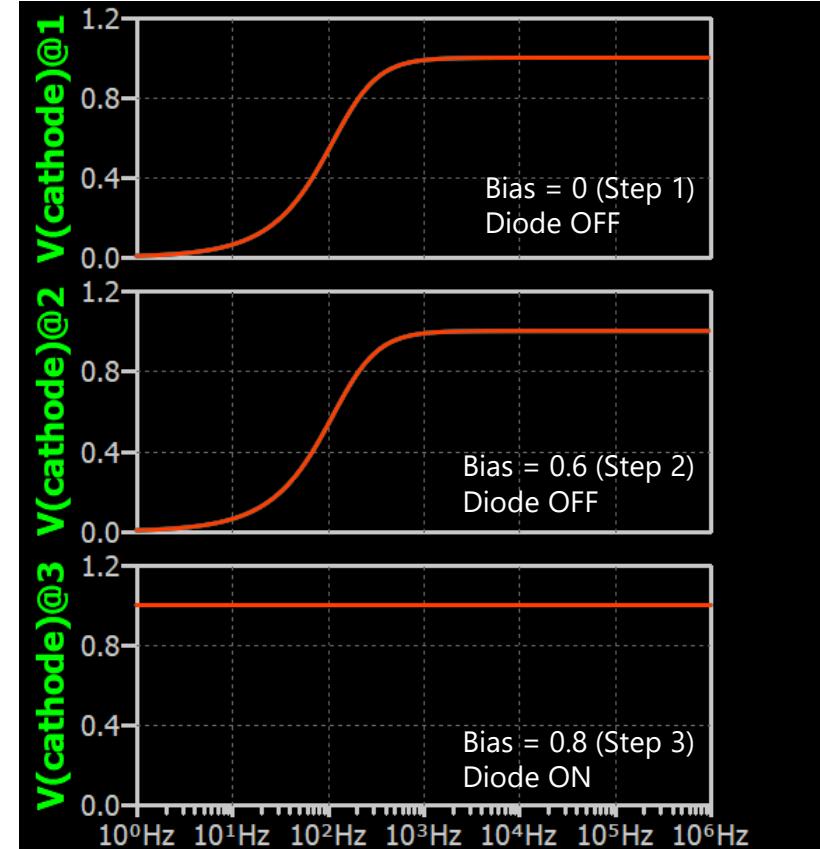
Qspice : Behavioral D Model - Cjo.qsch



```
.param bias = 0  
.model BeD_Cjo D Ron=1m Roff=1Meg  
+ Vfwd=0.7 Cjo=100n
```

Cjo is equivalent to a capacitor parallel the behavioral diode

```
.ac dec 100 1 1Meg  
.step param bias list 0 0.6 0.8  
  
.plot V(cathode)@3  
.plot V(cathode)@2  
.plot V(cathode)@1
```



D. Diode

Ideal Diode .model

Ideal Diode Model

Qspice : Special - IdealD (.dc).qsch / Special - IdealID (.tran).qsch

- Ideal Diode Characteristic
 - No breakdown current
 - No reverse leakage
 - No capacitance effect
 - No reverse recovery
- Ideal Model with Diode .model
 - .model Idlm D N=0.01 RS=10 μ ; Vf@1A=0
 - .model Idlm D N=0.36 RS=10 μ ; Vf@1A=0.3
 - .model Idlm D N=0.85 RS=10 μ ; Vf@1A=0.7
 - ** RS is added to prevent gmin stepping without series resistance
- Ideal Model with Behavioral Diode .model
 - .model IdealD D Vfwd=0 Ron=1m Roff=100Meg ; Vf,th=0
 - .model IdealD D Vfwd=0.3 Ron=1m Roff=100Meg ; Vf,th=0.3
 - .model IdealD D Vfwd=0.7 Ron=1m Roff=100Meg ; Vf,th=0.7

E. F. G. H. Dependent Sources

E. F. G. H. Dependent Sources

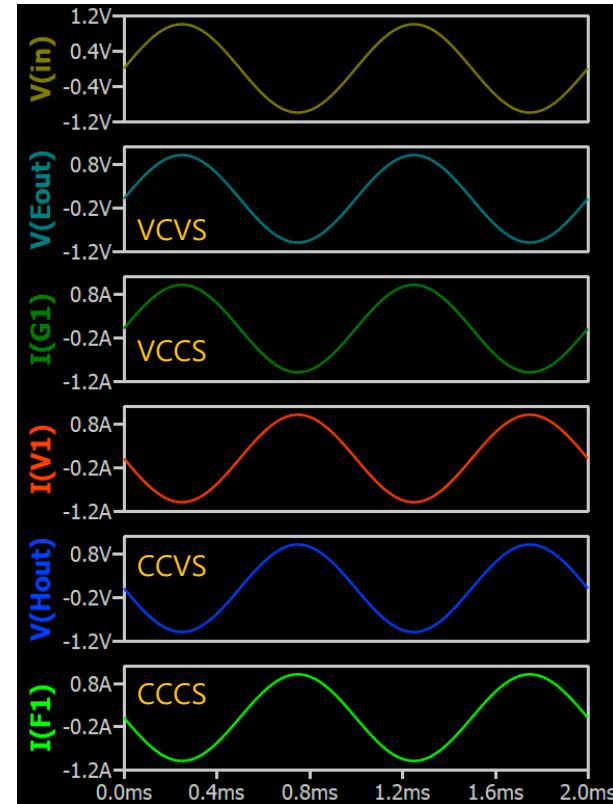
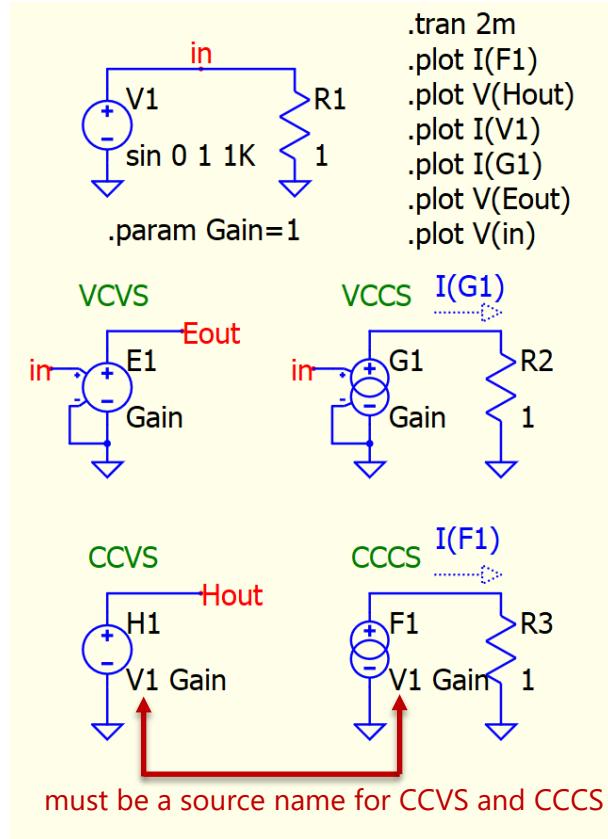
Qspice : Dependent Source - Basic.qsch

- Dependent Sources

- [E] VCVS : Voltage Dependent Voltage Source
- [G] VCCS : Voltage Dependent Current Source
- [H] CCVS : Current Dependent Voltage Source
- [F] CCCS : Current Dependent Current Source

- ** Current Dependent Src

- For current dependent source, the current sense has to come from voltage source instead of current source
- A 0V voltage source can be used for current sensing
- (Explanation from Mike Engelhardt) Sensing the current in a current is complicated because it might have VSAT or VSAT2, meaning it's not a current source

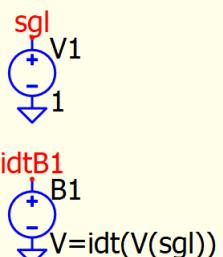


E-Source Alternative Syntax – Equivalent to Behavioral Voltage Src

Qspice : E-source - alternative syntax.qsch

- E-source

- Syntax: Exxx n+ n- value={<expression>}
 - Must use curly braces
- This is an alternative syntax of the behavioral voltage source (B-source)
- This syntax only available in using text, no Qspice symbol support this format, for Qspice to backward compatible to legacy spice syntax



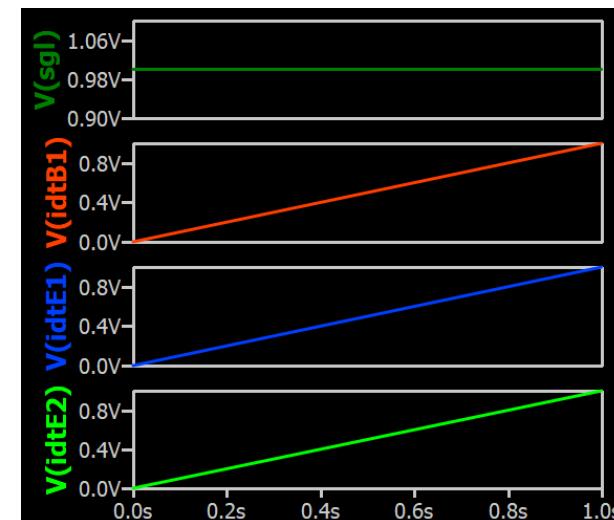
```
.tran 1  
.plot V(idtE2)  
.plot V(idtE1)  
.plot V(idtB1)  
.plot V(sgl)  
.plot V(idtB1)
```

Syntax: Exxx n+ n- value={<expression>}
alternative syntax of the behavioral source with E-source
formula must have curly bracket {}

E1 idtE1 0 Value {idt(V(sgl))} ← Can accept without "="

E2 idtE2 0 Value={idt(V(sgl))}

```
V1 sgl 0 1  
B1 idtB1 0 V=idt(V(sgl))  
E1 idtE1 0 Value {idt(V(sgl))}  
E2 idtE2 0 Value={idt(V(sgl))}  
.plot V(idtE2)  
.plot V(idtE1)  
.plot V(idtB1)  
.plot V(sgl)  
.tran 1  
.end
```

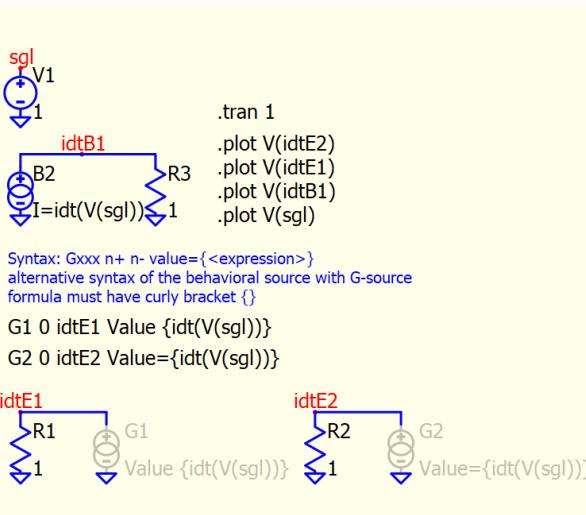


G-Source Alternative Syntax – Equivalent to Behavioral Current Src

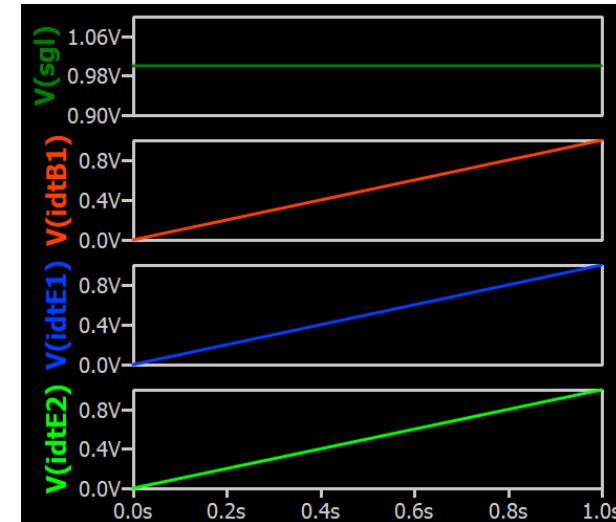
Qspice : G-source - alternative syntax.qsch

- G-source

- Syntax: $G_{xxx} n+ n- \text{ value}=\{\text{<expression>}\}$
 - Must use curly braces
- This is an alternative syntax of the behavioral current source (B-source)
- This syntax only available in using text, no Qspice symbol support this format, for Qspice to backward compatible to legacy spice syntax



```
V1 sgl 0 1
R1 idtE1 0 1
R2 idtE2 0 1
R3 idtB1 0 1
B2 0 idtB1 I=idt(V(sgl))
G1 0 idtE1 Value {idt(V(sgl))}
G2 0 idtE2 Value={idt(V(sgl))}
.plot V(idtE2)
.plot V(idtE1)
.plot V(idtB1)
.plot V(sgl)
.tran 1
.end
```



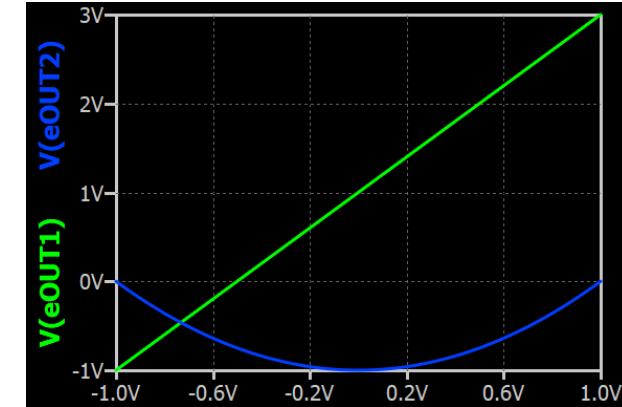
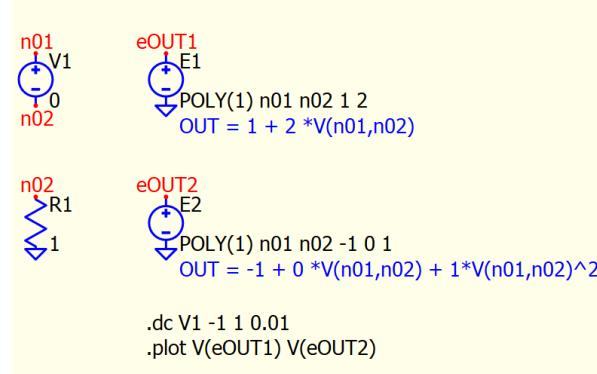
Polynomial Functions POLY

Qspice : E-source - POLY one dimension.qsch

- Polynomial Functions

- POLY(NDIM)

- Polynomial equations in n-dimension
 - Detail can be found in Hspice user guide, for n-dimensional definition
 - Poly supports E-, F-, G-, H- element statement



- One-dimensional eqn

- **POLY(1) n01 n02 1 2**
 - **POLY(1)** is one-dimension
 - **n01 n02** is voltage difference between $V(n01, n02)$
 - 1 2 are polynomial coefficient : $1 + 2 * V(n01, n02)$

- E-source netlist syntax

- **POLY()** requires legacy e-source syntax
 - **E1 eOUT1 0 POLY(1) n01 n02 1 2**

I. Current Source

I. Current Source : Instance Parameters

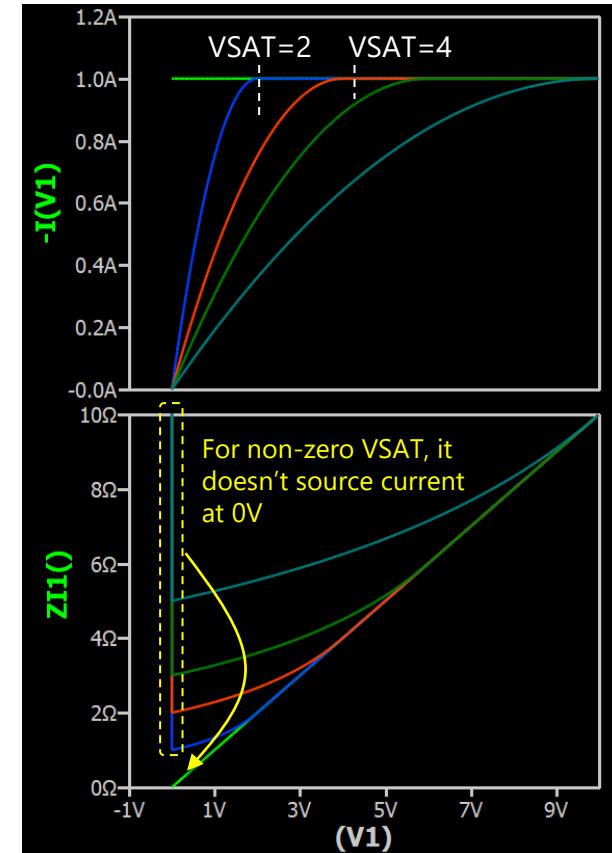
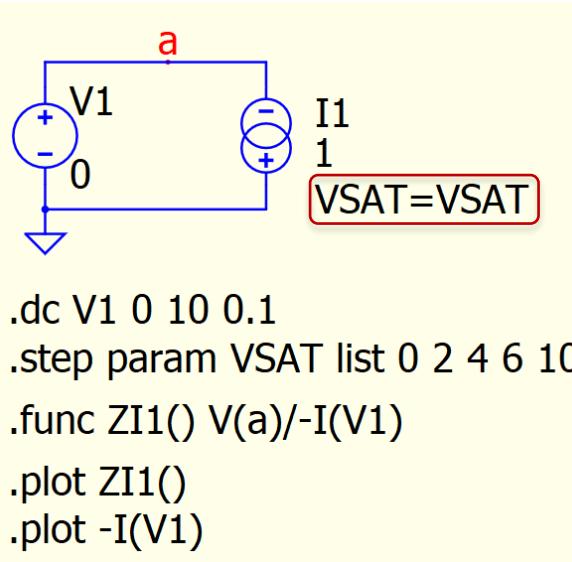
Current Source Instance Parameters

Name	Description	Units	Default
AC	AC magnitude, optionally followed by phase angle	A, °	0.
ACMAG	AC magnitude	A	0.
ACPHASE	AC phase	°	0.
DC	DC value of source	A	0.
EXP	Exponential source description		
LOG	Interpolate between PWL and CHIRP points		(not set)
PULSE	Pulse description		
PWL	Piecewise linear description		
SFFM	Single frequency FM description		
SINE	Sinusoidal source description(aka SIN)		
TIMECTRL	Time step control, one of NONE, LIMITS ¹ , BREAKS ² , or BOTH	String	LIMITS
VSAT ³	Don't source power(example)	V	0.
VSAT2	Don't source power and don't conduct in reverse	V	0.
XTRAP	Extrapolate beyond PWL and CHIRP points		(not set)

I. Instance Params : VSAT

Qspice : I Source - VSAT.qsch

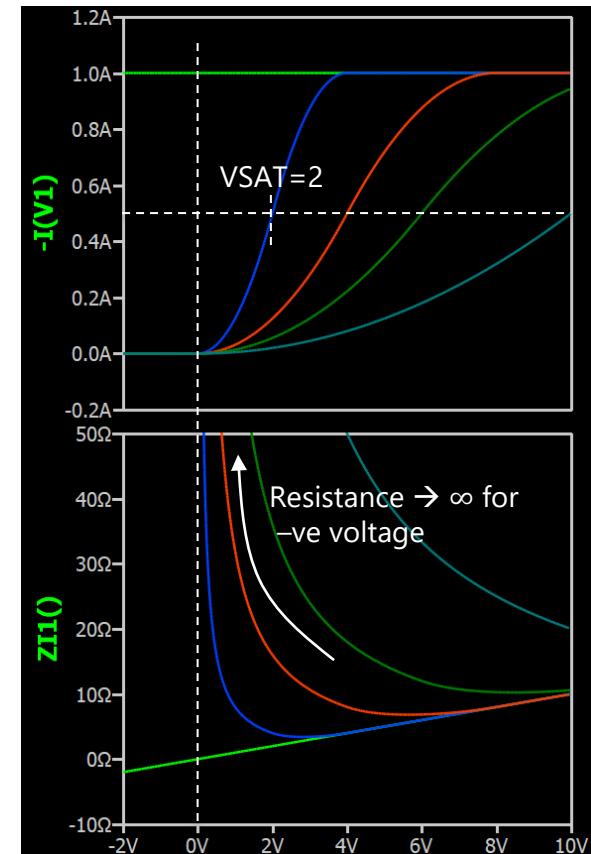
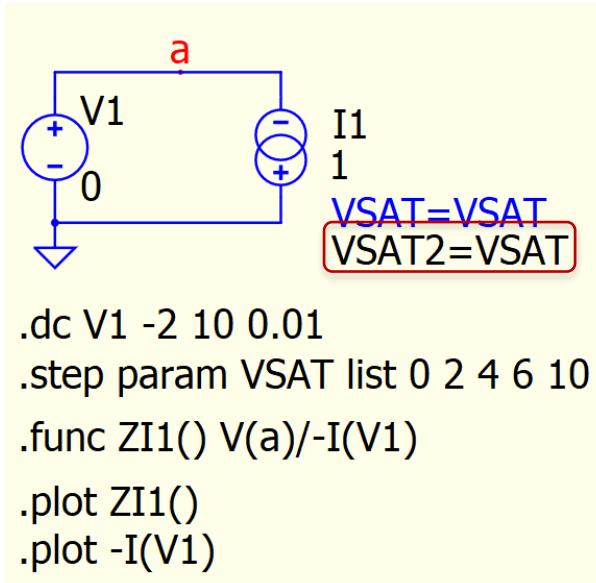
- VSAT
 - VSAT : Does **NOT** source power
 - **Default VSAT=0V**
 - Characteristic
 - Only source current when $V(-ve,+ve) > VSAT$
 - Current source doesn't source current at $V(-ve,+ve)=0$
 - Equivalent to Open
 - Not to apply negative voltage between $V(-ve,+ve)$ as it will have current flow out from -ve
 - Usage
 - Useful for modeling an active load or a bias current in a macromodel



I. Instance Params : VSAT2

Qspice : I Source - VSAT2.qsch

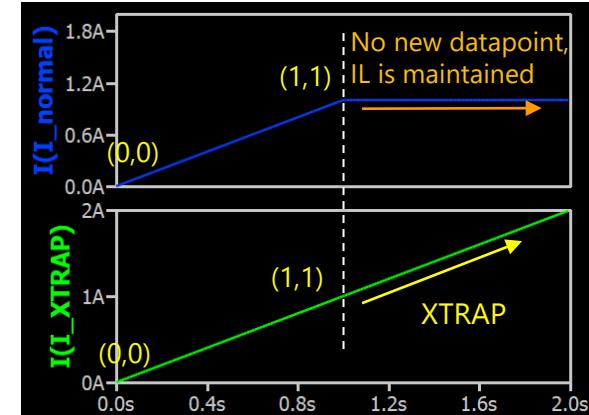
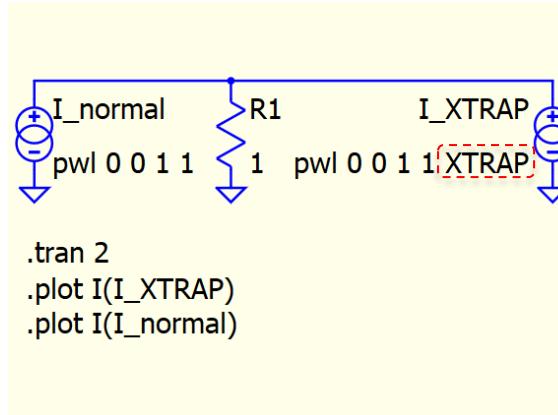
- VSAT2
 - VSAT2 : Does **NOT** source power and **NOT** conduct in reverse
 - **Default VSAT2=0V**
 - If VSAT2 is used, VSAT will be overridden



I. Instance Params : XTRAP

Qspice : I Source - XTRAP.qsch

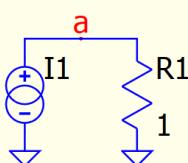
- XTRAP
 - Xtrap : Extrapolate beyond PWL and CHIRP points
 - **Default XTRAP is not set**
 - Without XTRAP, the current stays constant with the value specified with the last time point



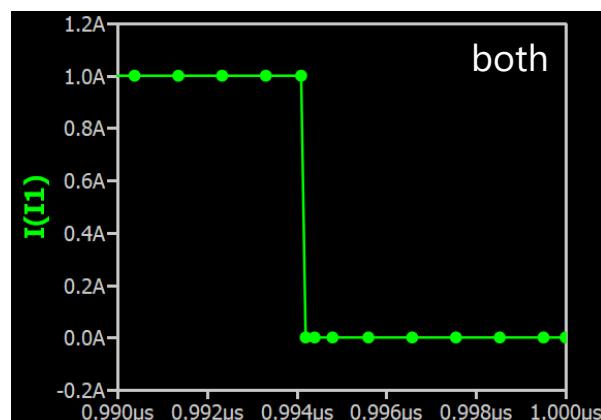
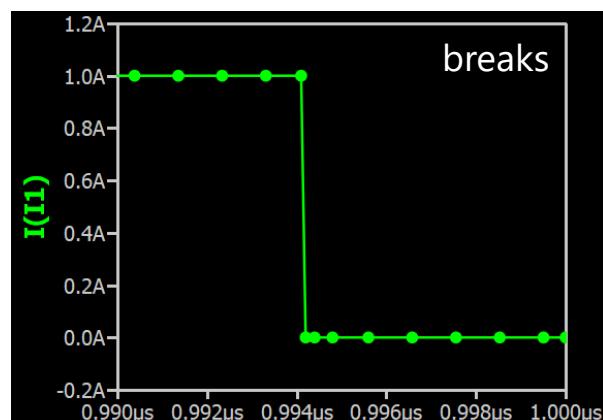
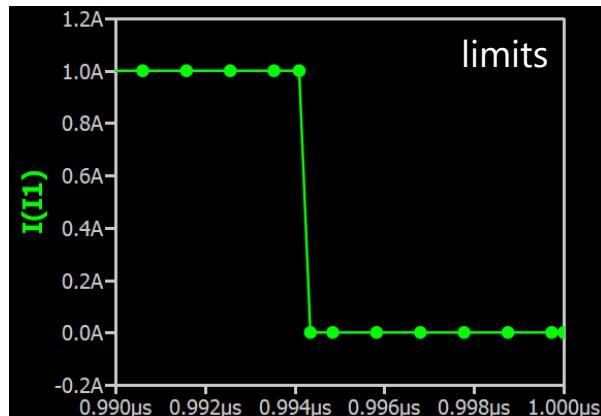
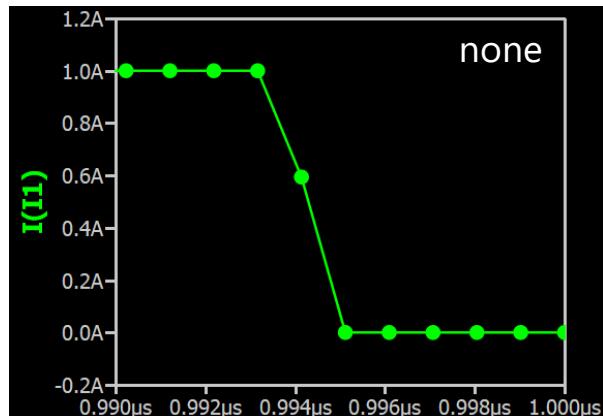
I. Instance Params : Timectrl

Qspice : I Source - TIMECTRL.qsch

- TIMECTRL
 - Timectrl : Time step control
 - None
 - Limits
 - Breaks
 - Both
 - **Default Timectrl=Limits**



```
pulse 0 1 4n 0 0 10n 20n  
Timectrl=none  
Timectrl=limits  
Timectrl=breaks  
Timectrl=both  
.tran 1000n  
.plot I(I1) I(I2)
```



J. JFET Transistor

J. JFET Model Parameters

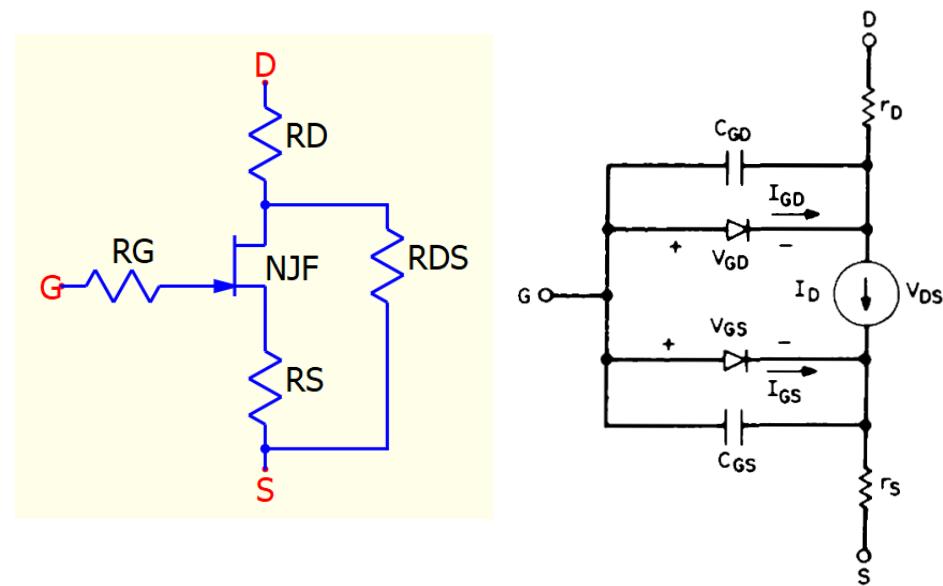
JFET Model Parameters

Name	Description	Units	Default
AF	Flicker noise exponent		1.0
ALPHA	Impact ionization coefficient	V ⁻¹	0.0
B	Doping tail parameter		0.0
BETA	Transconductance parameter	A/V ²	0.0001
BETATCE	Exponential transconductance parameter temperature coefficient	%/°C	0.0
CGD	Zero-bias G-D junction capacitance	F	0.0
CGDO	G-D overlap(i.e. constant) capacitance	F	0.0
CGS	Zero-bias G-S junction capacitance	F	0.0
CGSO	G-S overlap(i.e. constant) capacitance	F	0.0
ETA	Philips, et al.-style subthreshold conduction parameter		0.0
ETATC1	ETA first order tempco	°C ⁻¹	0.0
ETATC2	ETA second order tempco	°C ⁻²	0.0
FC	Forward bias junction fit parameter		0.5
GDSNOI	Shot noise coefficient for nlev = 3	A	2.0
GMAX	Maximum junction conductivity(straight line extension)	Ω	10K
IS	Junction saturation current	A	1e-14
ISR	Recombination current parameter	A	0.0
KF	Flicker Noise Coefficient		0.0
LAMBDA	Channel length modulation parameter	V ⁻¹	1.0
M	Grading coefficient(aka MJ)		0.5
N	Emission coefficient		1.0

NLEV	Noise level(equation selector)		0.0
NR	ISR emission coefficient		2.0
PB	Gate junction potential	V	1.0
RD	Drain resistance	Ω	0.0
RDTC1	RD first order tempco	°C ⁻¹	0.0
RDTC2	RD second order tempco	°C ⁻²	0.0
RDS	Additional Drain-Source leakage resistance	Ω	infinite
RDSTC1	RDS first order tempco	°C ⁻¹	0.0
RDSTC2	RDS second order tempco	°C ⁻²	0.0
RG	Gate resistance	Ω	0.0
RGTC1	RG first order tempco	°C ⁻¹	0.0
RGTC2	RG second order tempco	°C ⁻²	0.0
RONX	Channel conductivity multiplier in linear region ¹		1.0
RS	Source resistance	Ω	0.0
RSTC1	RS first order tempco	°C ⁻¹	0.0
RSTC2	RS second order tempco	°C ⁻²	0.0
TNOM	Parameter measurement temperature(aka TREF)	V	0.0
VK	Impact ionization knee current	V	0.0
VT0	Threshold Voltage(aka VTO or VT)	V	-2.0
VTOTC	Threshold Voltage temperature coefficient	°C ⁻¹	1.0
XTI	Saturation current temperature exponent		3.0

J. JFET Basic Equation

- JFET equation in Semiconductor Device Modeling with SPICE Section 3.1.3)
 - For channel pinched off : $V_{GS} - V_{T0} \leq 0$
 - $I_D = 0$
 - For saturated region : $0 \leq V_{GS} - V_{T0} \leq V_{DS}$
 - $I_D = \beta (V_{GS} - V_{T0})^2 (1 + \lambda V_{DS})$
 - For linear region : $0 < V_{DS} < V_{GS} - V_{T0}$
 - $I_D = \beta [2 (V_{GS} - V_{T0}) - V_{DS}] (1 + \lambda V_{DS})$

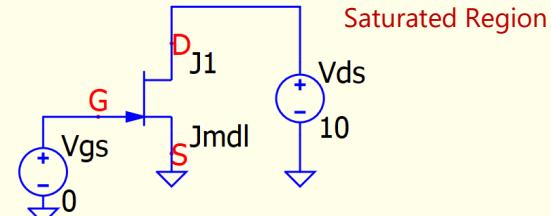


J. JFET Instance Params (I_D) : BETA and VTO

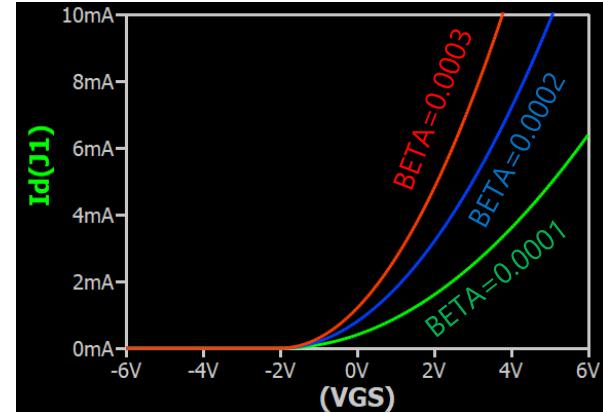
Qspice : JFET - Beta.qsch / JFET - VTO.qsch

BETA

- Beta : Transconductance parameter
- **Default BETA=0.0001A/V²**
- $I_D = \beta (V_{GS} - V_{T0})^2 (1 + \lambda V_{DS})$

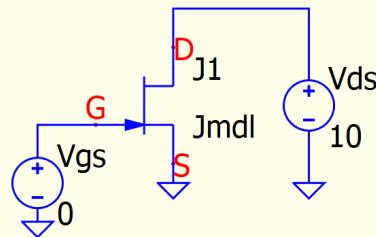


```
.dc Vgs -5 5 0.01  
.plot Id(J1)  
.step param beta list 0.0001 0.0002 0.0003  
.model Jmdl NJF BETA={beta}
```

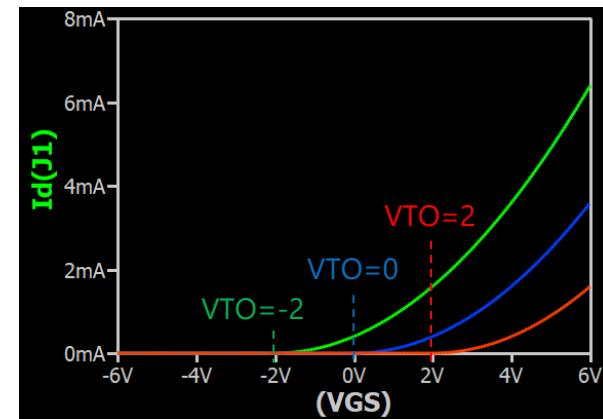


VTO (aka VT0 or VT)

- VTO : Threshold Voltage
- **Default VTO=-2V**
- $I_D = \beta (V_{GS} - V_{T0})^2 (1 + \lambda V_{DS})$



```
.dc Vgs -6 6 0.01  
.plot Id(J1)  
.step param vto list -2 0 2  
.model Jmdl NJF VTO={vto}
```

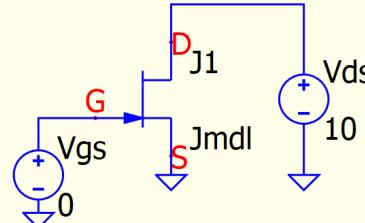


J. JFET Instance Params (I_D) : Lambda and Betatce

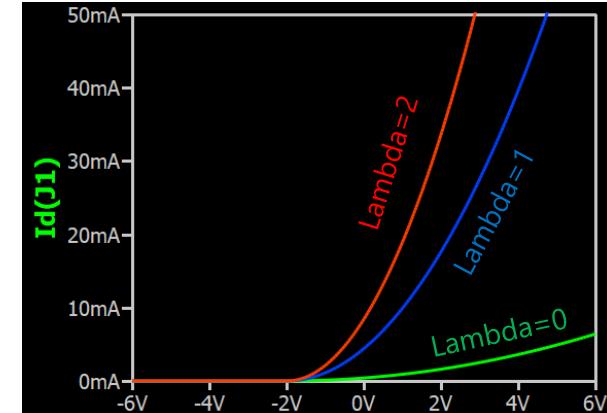
Qspice : JFET - LAMBDA.qsch / JFET - BETATCE.qsch

LAMBDA

- Lambda : Channel length modulation parameter
- **Default LAMBDA=0V⁻¹**
- $I_D = \beta (V_{GS} - V_{T0})^2 (1 + \lambda V_{DS})$

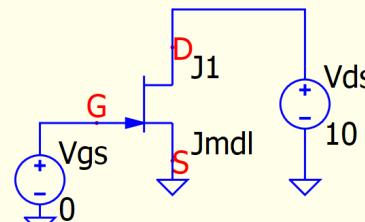


```
.dc Vgs -6 6 0.01  
.plot Id(J1)  
.step param lambda list 0 1 2  
.model Jmdl NJF LAMBDA={lambda}
```

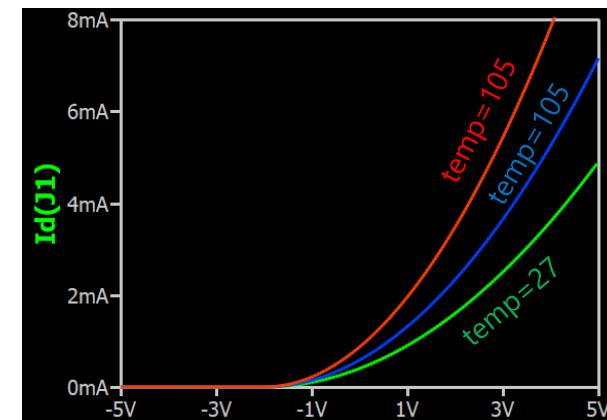


BETATCE

- Betatce : Exponential transconductance parameter temperature coefficient
- **Default BETATCE=0 (%/°C)**



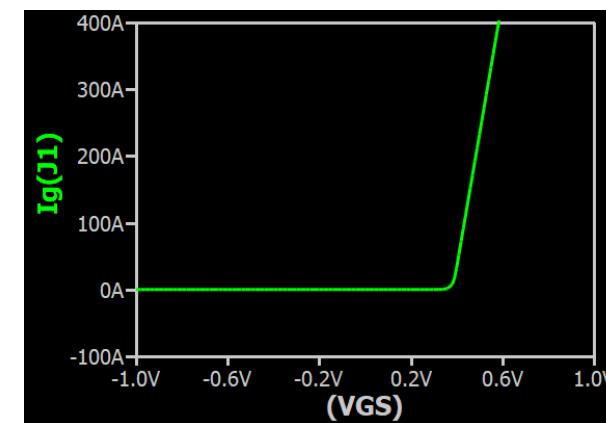
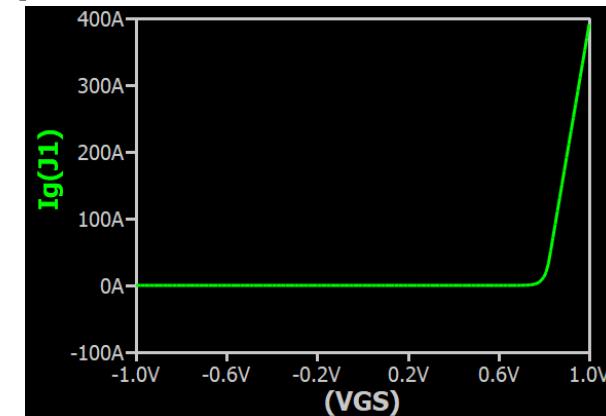
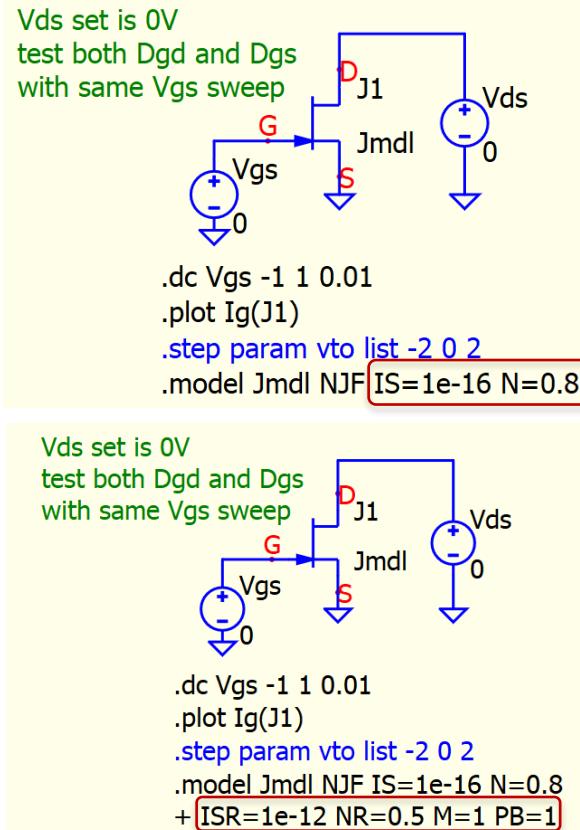
```
.dc Vgs -5 5 0.01 .temp 27 65 105  
.plot Id(J1)  
.param betatce=1  
.model Jmdl NJF BETATCE={betatce}
```



J. JFET Instance Params (Diode GD and GS) : IS, N, ISR, NR, M and PB

Qspice : JFET - IS N.qsch / JFET - ISR NR M PB.qsch

- Two diodes in JFET
 - DGD and DGS
 - These two diodes are identical model, with recombination current included
 - $I_{GS} = (I_F + K_{gen}I_R) + I_I$
 - $I_F = I_S \left(e^{\frac{qV_D}{nKT}} - 1 \right)$
 - $I_R = I_{SR} \left(e^{\frac{qV_D}{n_RKT}} - 1 \right)$
 - $K_{gen} = \sqrt{\left[\left(1 - \frac{V_D}{\Phi_0} \right)^2 + 0.005 \right]^m}$
 - I_S : IS Junction saturation current (Default IS=1e-14A)
 - n : N emission coefficient (Default N=1)
 - I_{SR} : ISR Recombination current parameter (Default ISR=0A)
 - n_R : ISR emission coefficient (Default NR=1)
 - m : M Grading coefficient (Default M=0.5)
 - Φ_0 : PB Gate junction potential (Default PB=1V)
- Diode modeling refer to D. Diode section



J. JFET Instance Params (Diode GS) : Alpha and VK

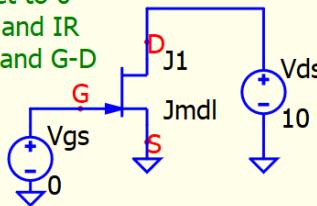
Qspice : JFET - ALPHA VK.qsch

- Gate Source Diode in Pspice model

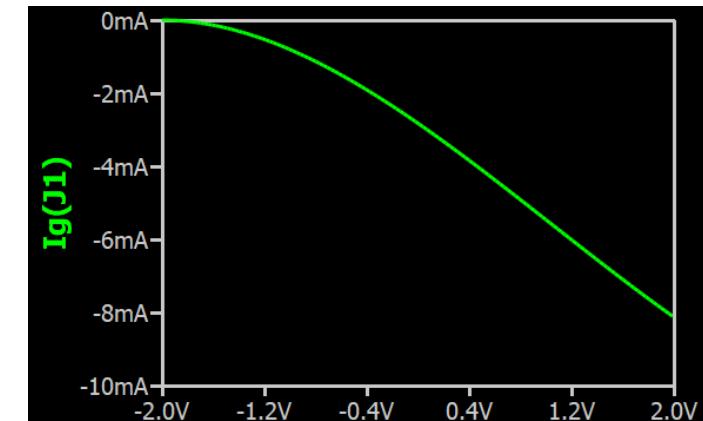
$$I_{GS} = (I_F + K_{gen} I_R) + I_I$$

- $I_I = \alpha I_D [V_{DS} - (V_{GS} - V_{TO})] e^{\frac{V_k}{V_{DS} - (V_{GS} - V_{TO})}}$ for $0 < G_{GS} - V_{TO} < V_{DS}$
- $I_I = 0$ otherwise
- α is ALPHA Impact ionization coefficient (Default ALPHA=0V⁻¹)
- V_k is VK Impact ionization knee current (Default VK=0V)

IS and ISR set to 0
to disable IF and IR
in diode G-S and G-D



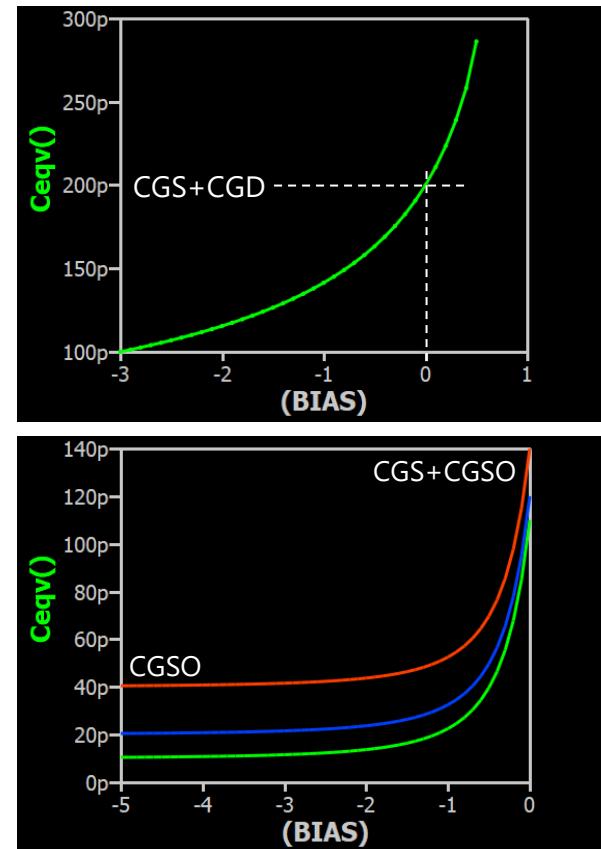
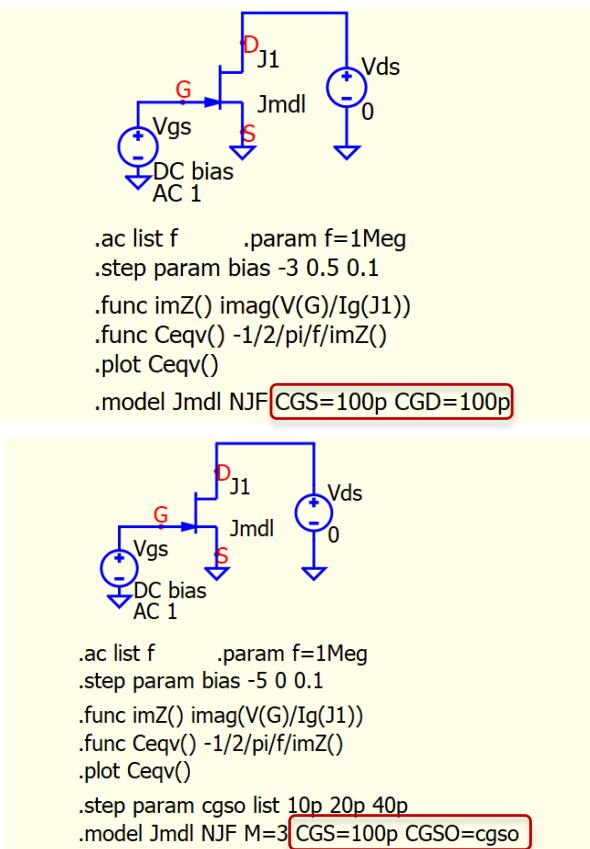
```
.dc Vgs -2 2 0.01
.plot Ig(J1)
.step param vto list -2 0 2
.model Jmdl NJF IS=0 ISR=0
+ALPHA=1 VK=1
```



J. JFET Instance Params (Capacitance) : CGS, CGD, CGSO, CDSO

Qspice : JFET - CGS CGD.qsch / JFET - CGSO CGDO.qsch

- CGS, CGD
 - CGS : Zero-bias G-D junction capacitance
 - CGD : Zero-bias G-S junction capacitance
 - **Default CGS=0F**
 - **Default CGD=0F**
 - This example simulate with both CGS and CGD
- CGSO, CDSO
 - CGSO : G-S overlap capacitance
 - CDSO : D-S overlap capacitance
 - **Default CGSO=0F**
 - **Default CDSO=0F**
 - This example only simulate CGS with CGSO. GDSO has same effect but to affect CDSO
 - ** M, PB, FC has effect in junction capacitance, refer to D. diode



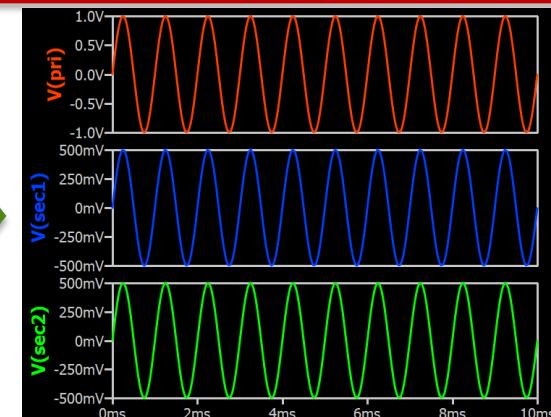
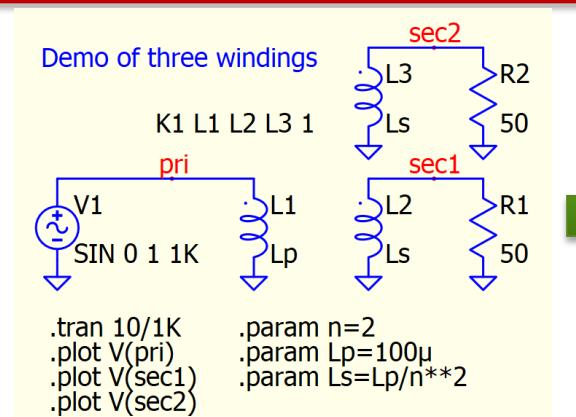
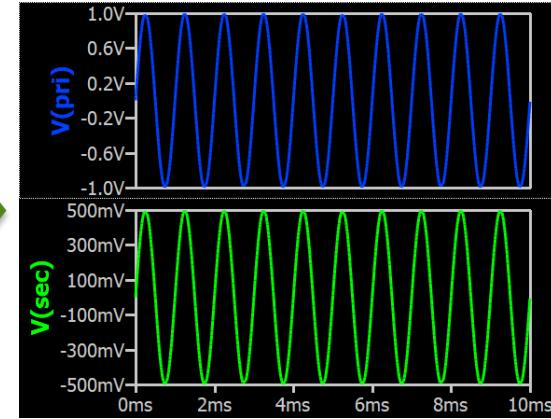
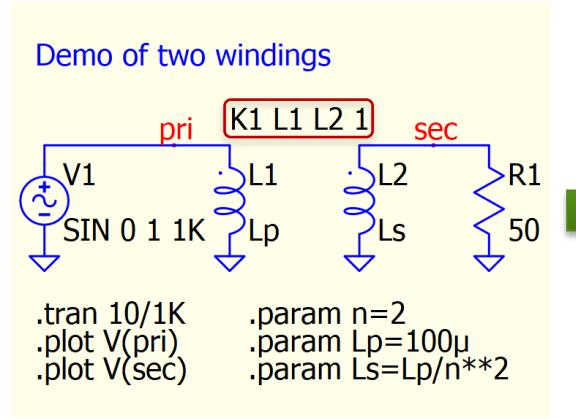
K. Mutual Inductance

K. Mutual Inductance

Qspice : K Mutual - Two Winding.qsch / K Mutual - Three Winding.qsch

- K Mutual Inductance
 - K : coupling coefficient of coupled inductors
 - Ideal coupling : 1
 - Range : -1 to 1
 - Two or more coupled inductors are required
 - Press L two times to get symbol with a dot notation (not necessary, but recommend for current direction)

- Inductors as Transformer
 - $\frac{L_p}{N_p^2} = \frac{L_s}{N_s^2}$ and $n = \frac{N_p}{N_s}$
 - N is number of turns
 - $L_p = n^2 L_s$ or $L_s = \frac{1}{n^2} L_p$
 - In practice, L_p is measured from primary with secondary open



L. Inductor

Inductor L Instance Parameters in Qspice HELP

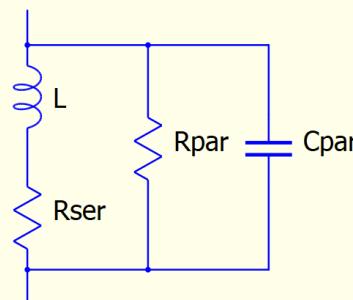
Inductor Instance Parameters			
Name	Description	Units	Default
AU	Wire or stripline is made of gold		
AL	Wire or stripline is made of aluminum		see below
AG	Wire or stripline is made of silver		
BEND	Fractional inductance correction for wire bend or proximity effects		1.
CPAR	Parallel capacitance	F	0.
CU	Wire or stripline is made of copper		see below
DIAMETER	Diameter of wire or air coil	m	
FREQUENCY	Frequency at Q. Also used to compute Rser due to skin effect		
HEIGHT	Height of PCB stripline above ground plane	m	
IC	Initial current if uic is specified on .tran statement	A	none
INDUCTANCE	Inductance of inductor	H	0.0
ISAT	Current causing inductance to drop to SATFRAC×INDUCTANCE	A	Infinite
LENGTH	Length of wire, stripline, or air coil	m	
LSAT	Inductance asymptotically approached in saturation	H	10% of INDUCTANCE
M	Number of parallel inductors		1.0
NI	Wire is made of nickel		
Q	Quality factor at FREQUENCY		
RPAR ¹	Equivalent parallel resistance	Ω	INDUCTANCE÷(15.91×GMIN)
RSER	Equivalent series resistance	Ω	0.0
SATFRAC	Fractional drop in inductance at ISAT		0.7
TC ²	Temperature coefficient polynomial		(none)
TC1 ²	1st order temperature coefficient		0.0
TC2 ²	2nd order temperature coefficient		0.0
THICK	Thickness of stripline on top of a PCB	m	0.0
TNOM	Temperature inductance was measured(aka TREF)	°C	Circuit TNOM
TURNS	Number of turns of an air coil		
VERBOSE	Print wire L, Rser, Rpar results on the console		(not set)
WIDTH	Width of stripline on top of a PCB	m	

Arbitrary Inductance Device

QSPICE also supports an arbitrary inductance device. To use it, give an equation for the flux due to the inductor. The equation can include any circuit node voltages or device currents of devices modeled as Thévenin equivalents(V-, L-, E-, or H- devices). In the interest of completeness, the device supports transinductance.

Syntax: Cnnn N1 N2 Q=<expression> [additional instance parameters]

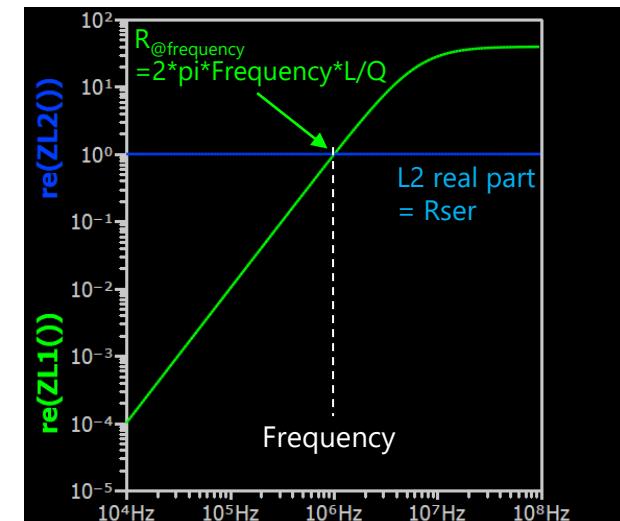
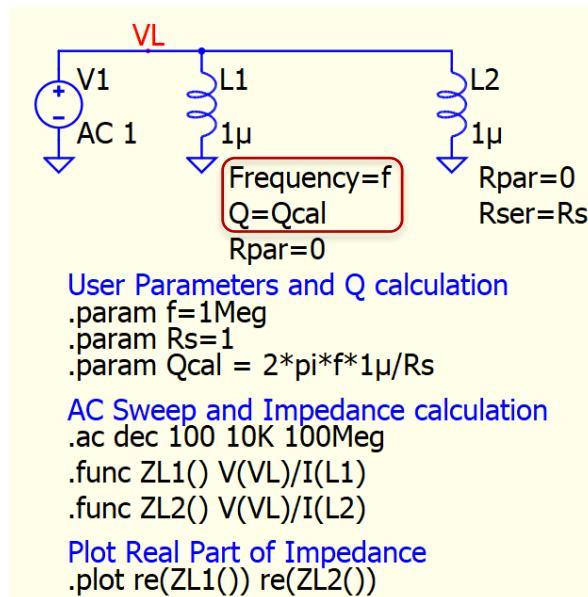
Name	Description	Units	Default
FLUX	Equation of flux(aka F)	Weber	
IC	Initial flux due to the inductor	Weber	
M	Number of identical parallel devices		1.0
RPAR	Equivalent parallel resistance	Ω	Infinite
RSER	Equivalent series resistance	Ω	0.0
NOISELESS	Ignore the noise contribution from RPAR and RSER		not set
TEMP	Instance temperature	°C	Circuit temperature



L. Instance Params : Rser, Frequency and Q

Qspice : L - Rser Frequency Q.qsch

- Rser
 - Equivalent series resistance
 - Default Rser=0
 - Rser is a constant over entire frequency
- Frequency and Q
 - Frequency : Frequency at Q, also used to compute Rser due to skin effect
 - Q : Quality factor at FREQUENCY
 - Formula
 - $Q = \frac{x_L}{R} = \frac{2\pi f L}{R_{@f}}$
 - Therefore, series resistance can change over frequency to simulate skin effect if Frequency and Q are used

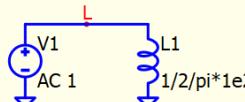


L. Instance Params : Rpar – Equivalent Parallel Resistance

Qspice : L - Rpar Prove.qsch | L - Rpar (.option LFT).qsch

- Rpar
 - Equivalent parallel resistance
 - Default
Rpar=Inductance/(15.91*Gmin)
 - 15.91 is only an approximate, exact formula is $\frac{2\pi}{L}$
 - Gmin is minimum conductance in .option, default gmin=1e-12
 - To calculate Rpar, .ac analysis is used, with Lp-Rp model (Rpar=Rp)
 - Impedance : $Z = \frac{V}{I}$
 - Admittance : $Y = \frac{Z}{j\omega} = G + jB$
 - $Rp = \frac{1}{G}$, where G is conductance
- .option LFT for Rpar
 - If circuit option LFT is sent, then the resistance is chosen to be equal to the reactance at frequency LFT
 - Rpar formula changed to **Rpar = $2\pi LFT / Inductance$**

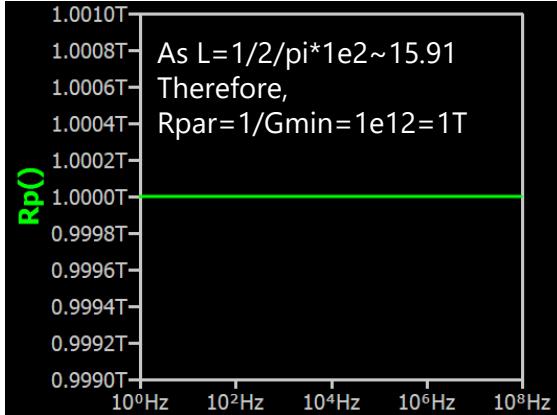
Default Rpar=Inductance/(15.91*Gmin) in HELP
**15.91 is approximation from $1/2/\pi \cdot 10^2$



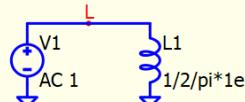
.ac dec 100 1 100Meg
Default gmin in Qspice is 1e-12
.option gmin=1e-12

Formula to calculate Rp from Lp-Rp model
.func Z() V(L)/I(L1)
.func Y() 1/Z()
.func Rp() 1/re(Y())
.plot Rp()

** Inductor always with a default Rpar!



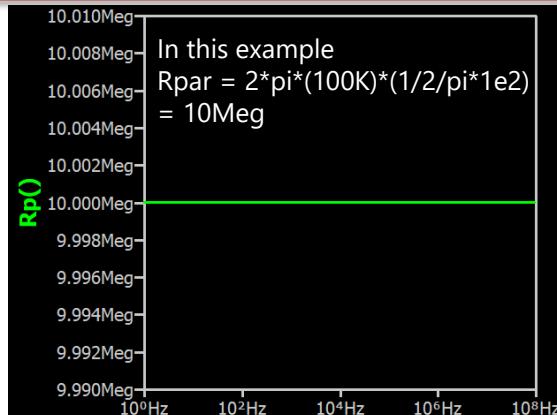
Default Rpar=Inductance/(15.91*Gmin) in HELP
**15.91 is approximation from $1/2/\pi \cdot 10^2$



.option LFT=100K
.ac dec 100 1 100Meg
Default gmin in Qspice is 1e-12
.option gmin=1e-12

Formula to calculate Rp from Lp-Rp model
.func Z() V(L)/I(L1)
.func Y() 1/Z()
.func Rp() 1/re(Y())
.plot Rp()

** If .option LFT is used, Rpar formula is changed



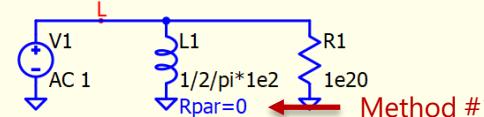
L. Instance Params : Rpar – Equivalent Parallel Resistance

Qspice : L - Rpar=0 Gmin=1e-308 LFT=1e308.qsch

- Force Rpar to Infinite

- If simulation requires to set Rpar to infinite, three method can be considered
- #1 : Set Rpar=0
 - This method is mentioned by Mike Engelhardt in Qspice forum and not documented in HELP
- #2 : Set gmin=1e-308
 - As $1/gmin$ is infinite, Rpar becomes infinite
 - This is useful if multiple inductors in schematic, but be caution it may introduce other problem if non-linear device in schematic when gmin is required
- #3 : Set .option LFT=1e308
 - As LFT is infinite, Rpar becomes infinite
 - I suggest to use this method
- In this demonstration, a R1 is added in parallel for visual aids, as Rpar=infinite will return NaN in Rp() and nothing is shown in waveform viewer.

Default Rpar=Inductance/(15.91*Gmin) in HELP
**15.91 is approximation from $1/2/\pi^2 \cdot 10^2$



.ac dec 100 1 100Meg

Default gmin in Qspice is 1e-12

.option gmin=1e-308

.option LFT=1e308

Method #1

Method #2 : $Rpar = Inductance / (1591 * Gmin)$

Method #3 : $Rpar = 2 * \pi * LFT * Inductance$

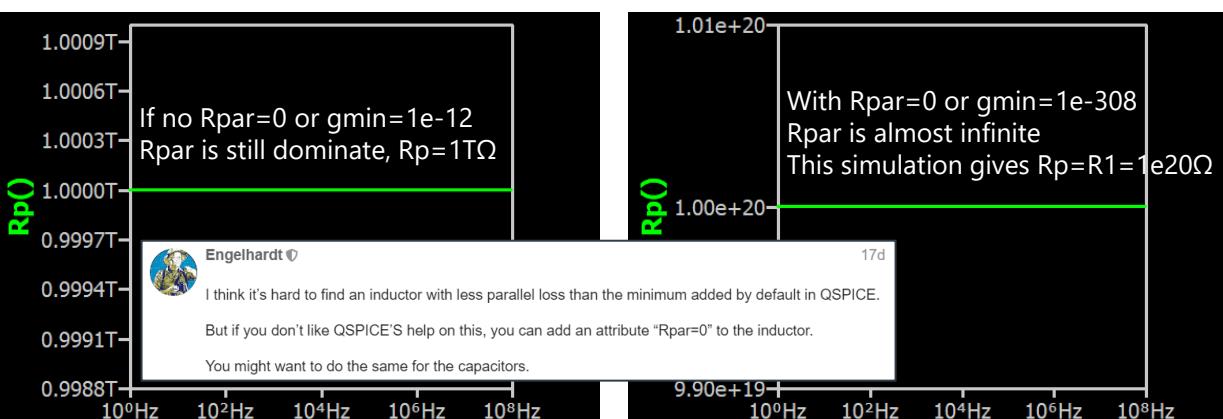
Formula to calculate Rp from Lp-Rp model:

.func Z() V(L)/-I(V1)

.func Y() 1/Z()

.func Rp() 1/re(Y())

.plot Rp()



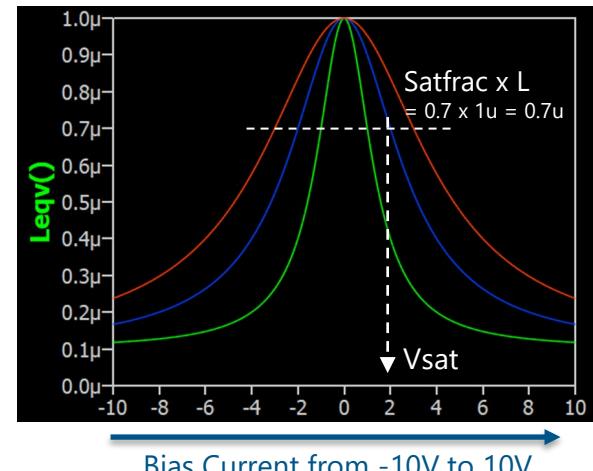
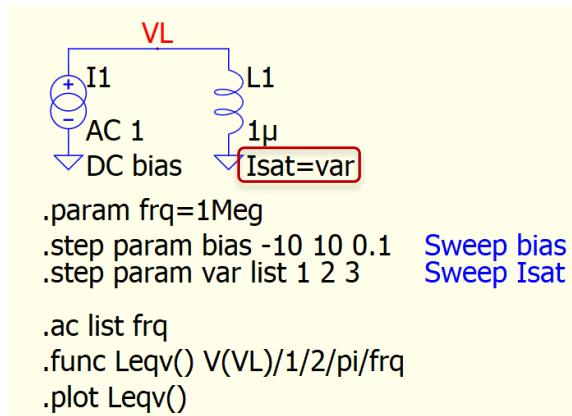
L. Instance Params : Rpar – Equivalent Parallel Resistance

- Quick Summary of Rpar
- Rpar formula priority
 - 1st priority : If **Rpar=<value>**, Rpar is set to equal <value>
 - 2nd priority : If **.option LFT** is set and **without Rpar**, $Rpar = 2\pi LFT * \text{Inductance}$
 - 3rd priority : If **no .option LFT** and **without Rpar**, $Rpar = \text{Inductance} / (15.91 * gmin)$
- Force Rpar to Infinite
 - #1 : Set Instance parameter Rpar=0 individually
 - #2 : Set **.option LFT=1e308**
 - #3 : Set **.option gmin=1e-308** (not recommend)

L. Instance Params : Isat, Lsat, Satfrac - For Nonlinear Inductance

Qspice : L Inductor - Isat (.ac).qsch

- Isat and Satfrac
 - Isat : Current that drops inductance to **Satfrac x Inductance**
 - Satfrac : Fractional drop in inductance at Isat
 - **Default ISAT=Infinite (A)**
 - **Default SATFRAC=0.7**
 - Nonlinear effect is valid in +ve and -ve current direction



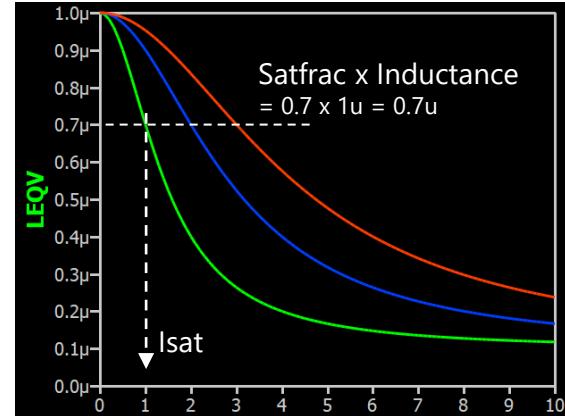
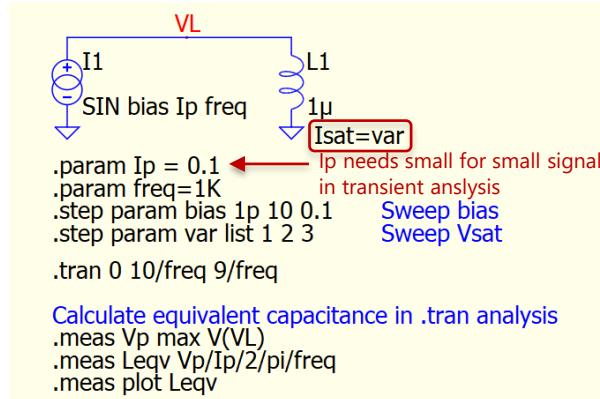
• Inductance equation

- $X_L = \omega L = \frac{V_L}{I_L}$
- $L = \frac{|V_L|}{|I_L|} \frac{1}{\omega} = \frac{|V_L|}{2\pi f |I_L|}$
- This formula is used to calculate equivalent inductance (small signal model) at different inductor bias current

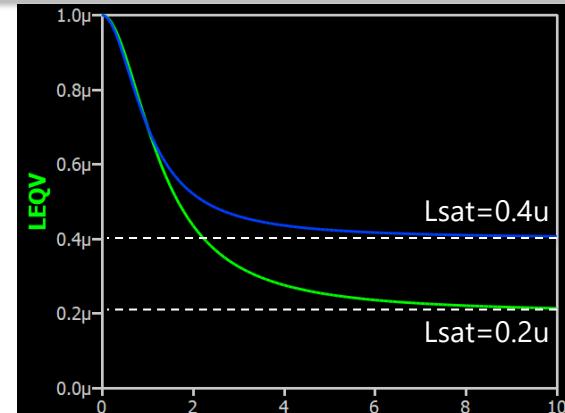
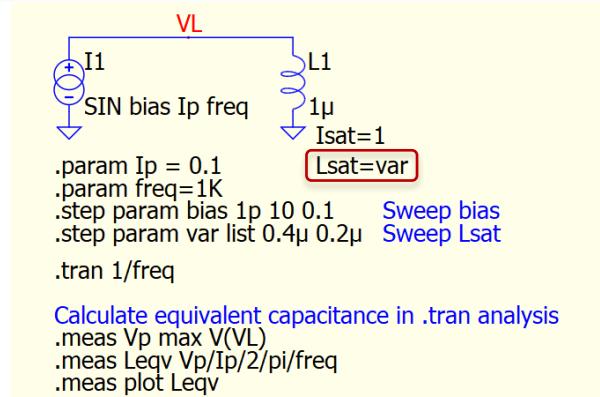
L. Instance Params : Isat, Lsat, Satfrac - For Nonlinear Inductance

Qspice : L Inductor - Isat (.tran).qsch / L Inductor - Lsat (.tran).qsch

- Isat and Satfrac
 - **Isat** : Current that drops inductance to **Satfrac x Inductance**
 - **Satfrac** : Fractional drop in inductance at Isat
 - **Default ISAT=Infinite (A)**
 - **Default SATFRAC=0.7**



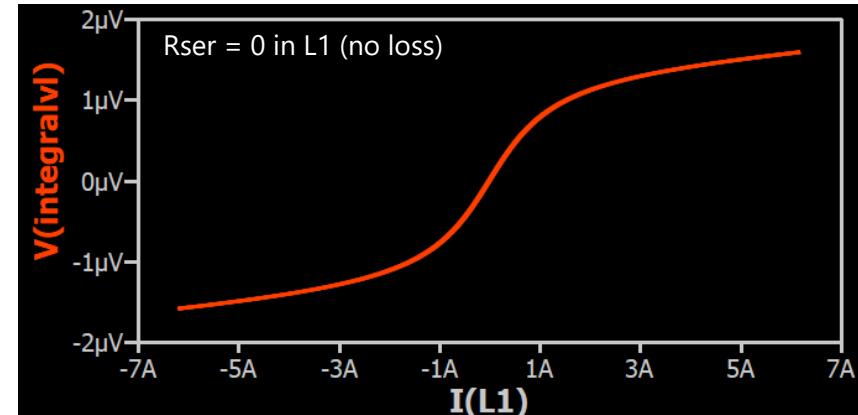
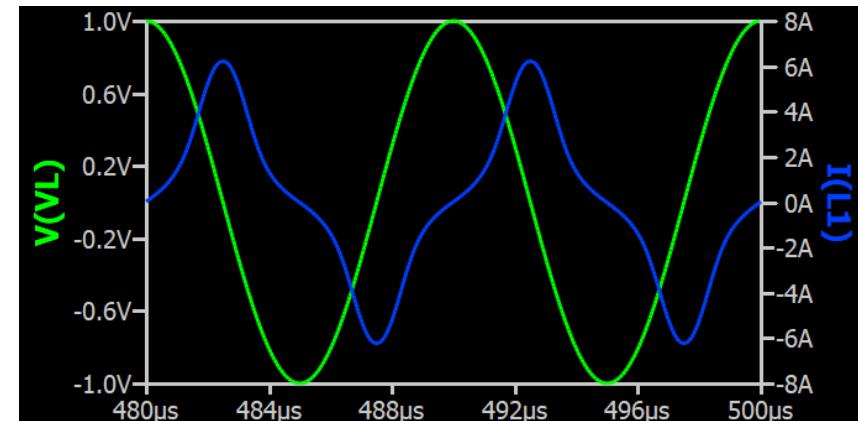
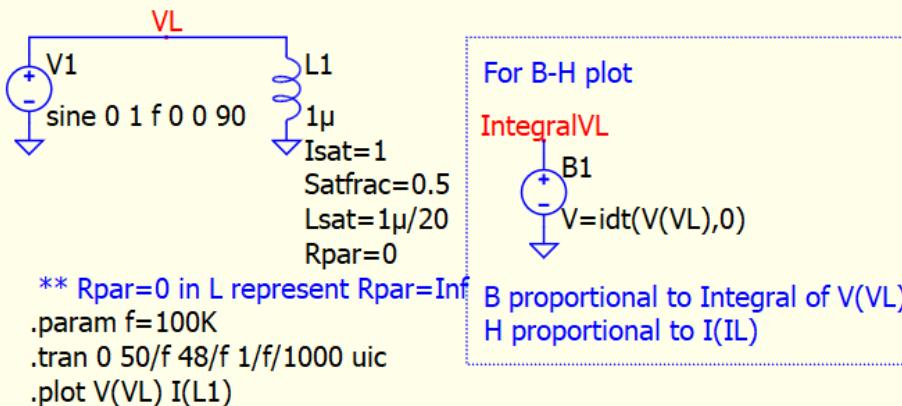
- Lsat
 - **Lsat** : Inductance asymptotically approached in saturation
 - ** Lsat must be set to see its effect
 - **Default LSAT=10% of L**



Demonstration of Nonlinear Inductor (model B-H saturation)

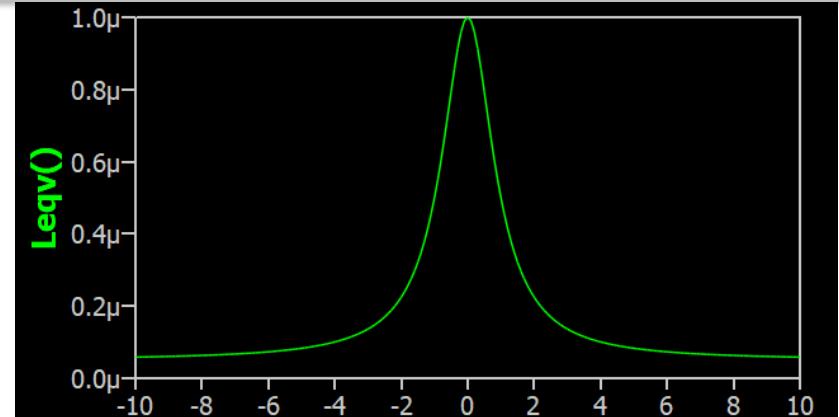
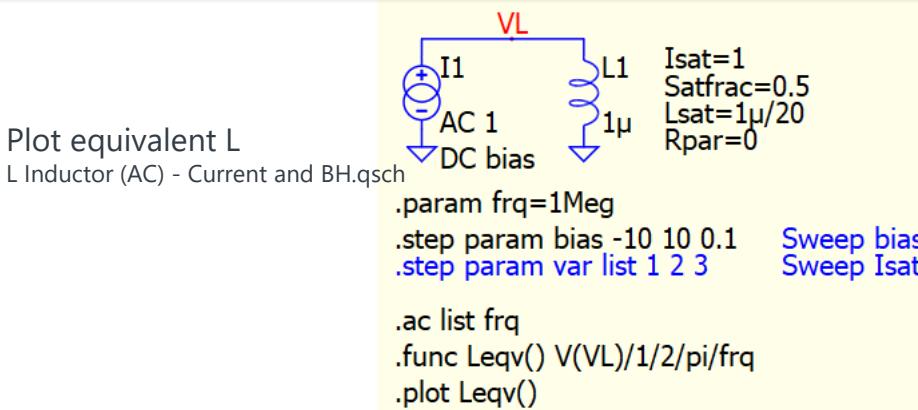
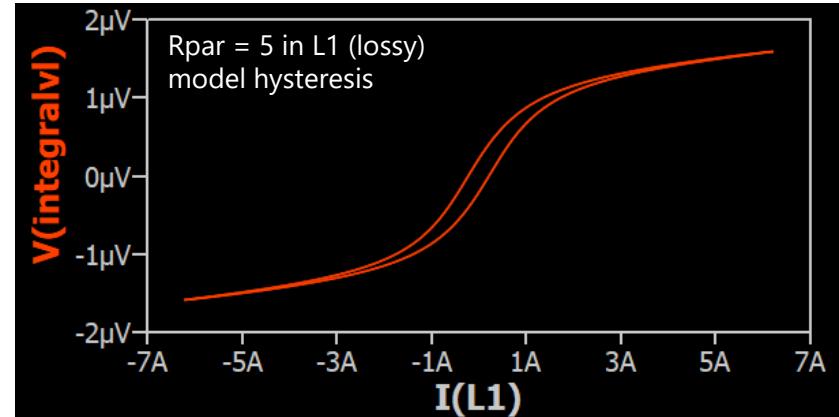
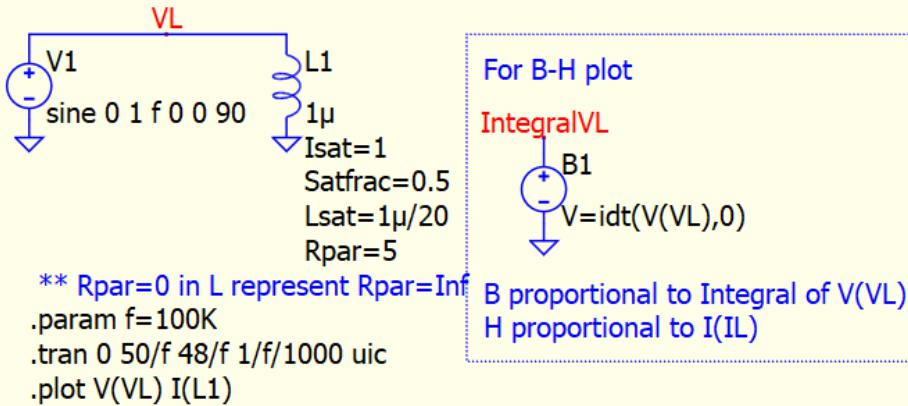
Qspice : L Inductor Nonlinear (Tran) - Current and BH.qsch

- Nonlinear Inductor in Qspice
 - This simulation demonstrate transient of non-linear inductor with a sinusoidal voltage source, which can expect a non-linear current
- Reference : B and H for inductor
 - Magnetic field intensity $H = \frac{B}{\mu} = \frac{N}{l_e} i_L$ (unit : A/m)
 - Magnetic field strength $B = \frac{\phi_B}{A_e} = \frac{1}{N A_e} \int v_L dt$ (unit : Tesla)
 - B also called magnetic flux density



Demonstration of Nonlinear Inductor (model B-H hysteresis : lossy)

Qspice : L Inductor Nonlinear (Tran) - Current and BH.qsch



Comment about Saturation and Hysteresis of B-H curve

Isat, Lsat and Satfrac are key parameters in Qspice for non-linear inductance modeling. General interest is just a saturating include. This represents inductor saturating when current reach certain level (i.e. inductance drop according to current, which can model by Isat, Lsat and Satfrac). This characteristic is saturation in B-H curve.

For hysteresis of B-H curve, it can generally model with a parallel resistor Rpar to represent loss.

May be some people prefer to model non-linear inductor with other way, but I found Qspice definition generally good enough as L vs bias current can be easily measure practically.

L. Arbitrary Inductance : Inductor modeling with FLUX

- Arbitrary Inductance Device

- To use arbitrary inductance device, give an equation for the flux due to the inductor

Arbitrary Inductance Device

QSPICE also supports an arbitrary inductance device. To use it, give an equation for the flux due to the inductor. The equation can include any circuit node voltages or device currents of devices modeled as Thévenin equivalents(V-, L-, E-, or H- devices). In the interest of completeness, the device supports transinductance.

Syntax: Cnnn N1 N2 Q=<expression> [additional instance parameters]

Name	Description	Units	Default
FLUX	Equation of flux(aka F)	Weber	
IC	Initial flux due to the inductor	Weber	
M	Number of identical parallel devices		1.0
RPAR	Equivalent parallel resistance	Ω	Infinite
RSER	Equivalent series resistance	Ω	0.0
NOISELESS	Ignore the noise contribution from RPAR and RSER		not set
TEMP	Instance temperature	$^{\circ}\text{C}$	Circuit temperature

- Basic Formula between Inductance and Flux

- [equation 1] : Inductor Voltage v_L and Flux ϕ relationship : $v_L = \frac{d\phi}{dt}$
- [equation 2] : Inductor Voltage v_L and Inductor Current i_L relationship : $v_L = L \frac{di_L}{dt}$
- By $\frac{d\phi}{dt} = L \frac{di_L}{dt} \rightarrow \text{Inductance } L = \frac{d\phi}{di_L}$

L. Arbitrary Inductance : Inductor modeling with FLUX

Qspice : Flux formula.qsch

- Qspice inductor modeling with Flux ϕ
 - For linear inductor, if $\frac{d\phi}{di_L}$ is constant $\rightarrow \phi = L i_L$
 - Therefore, $L = \frac{\phi}{i_L}$
 - In Qspice : $\text{flux} = L * I(\text{Lnnn})$
 - where Lnnn is the name attribute of inductor symbol (e.g. L1, L2)
 - For nonlinear inductor, ϕ can be expressed by
$$\phi = a \tanh(b i_L)$$
 - Therefore, $L = \frac{d\phi}{di_L} = \frac{d a \tanh(b i_L)}{di_L} = a b (1 - \tanh^2(b i_L))$
 - In Qspice : $\text{flux} = a * \tanh(b * I(\text{Lnnn}))$
 - $L_{0A} @ 0A = a * b$: L_{0A} is inductance at 0A
 - b determines the spread
 - If $b i_L$ is large, $(1 - \tanh^2(b i_L)) = 0$, therefore, this formula will give 0H inductance when i_L is large
 - Nonlinear and linear flux formula can be combined to handle 0H inductance when i_L is large
 - In Qspice : $\text{flux} = a * \tanh(b * I(\text{Lnnn})) + L_{\min} * I(\text{Lnnn})$
 - $L_{\min} @ i_L = \infty$: L_{\min} : L_{\min} is inductance at current $\rightarrow \infty$
 - $L_{0A} @ i_L = 0$: $a * b - L_{\min}$
 - b determines the spread

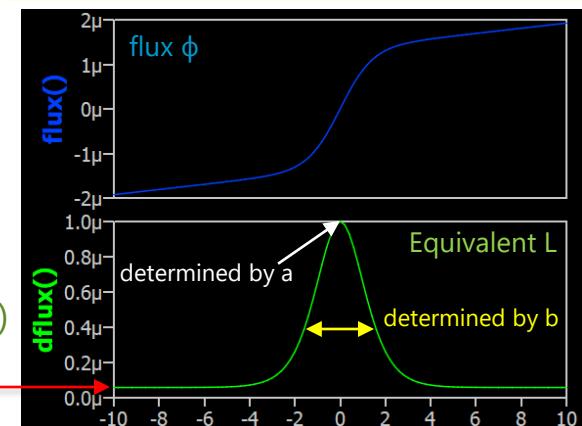
$$L = \frac{d\phi}{di_L} = \text{dflux}()$$

determined by L_{\min}

Assume flux formula is $a * \tanh(b * IL) + L_{\min} * IL$
.param b = 0.7
.param L0A = 1u
.param a = (L0A-Lmin)/b
.param Lmin=58n
.func flux() a*tanh(b*IL)+Lmin*IL

Calculate Inductance by dflux/dIL
.func dflux() D(flux())

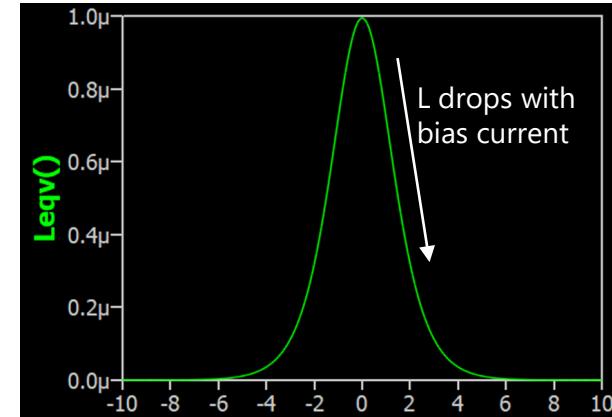
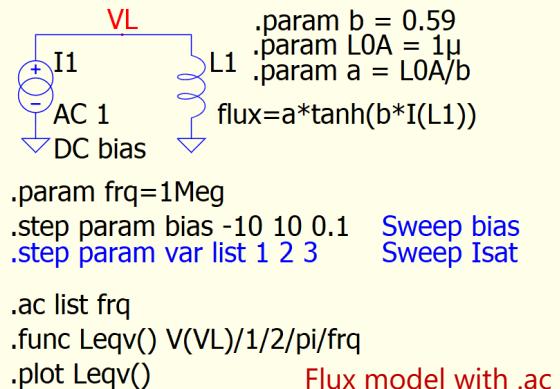
Sweep IL from -10A to 10A
.step param IL -10 10 0.2
.op
.plot dflux()
.plot flux()



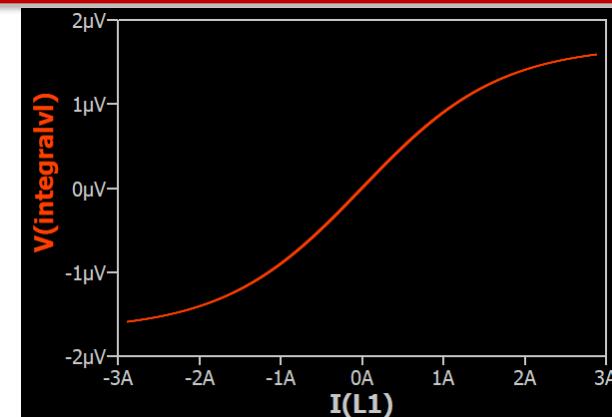
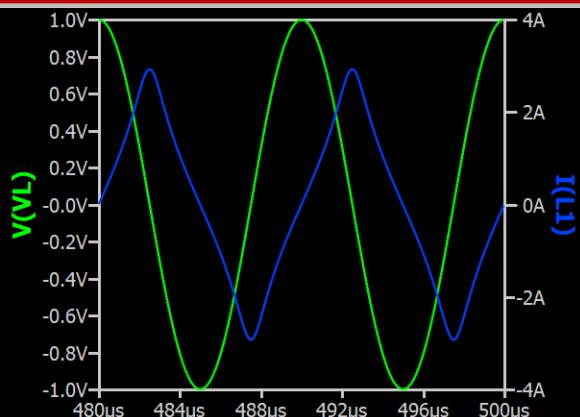
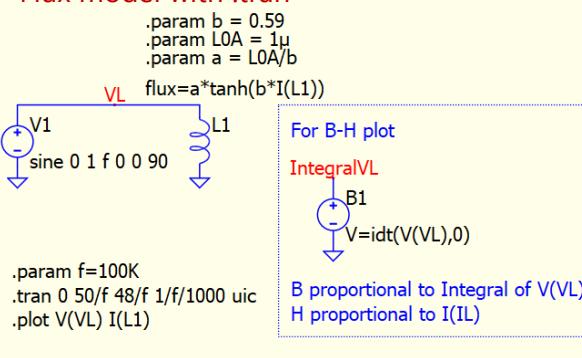
L. Arbitrary Inductance : Inductor modeling with FLUX

Qspice : L Inductor (AC) - Flux eqn 1.qsch ; L Inductor Nonlinear (Tran) - Flux eqn 1.qsch

- Flux model
 - .ac is used to calculate inductance and bias current relationship
 - .tran is used to demonstrate non-linear inductor current and proportional B-H curve
 - Flux equation uses format
 - $\text{Flux} = a * \tanh(b * I(L1))$



Flux model with .tran



L. Arbitrary Inductance : Inductor modeling with FLUX – Nonlinear with Lmin

Qspice : L Inductor (AC) - Flux eqn 2.qsch ; L Inductor Nonlinear (Tran) - Flux eqn 2.qsch

- Flux Model

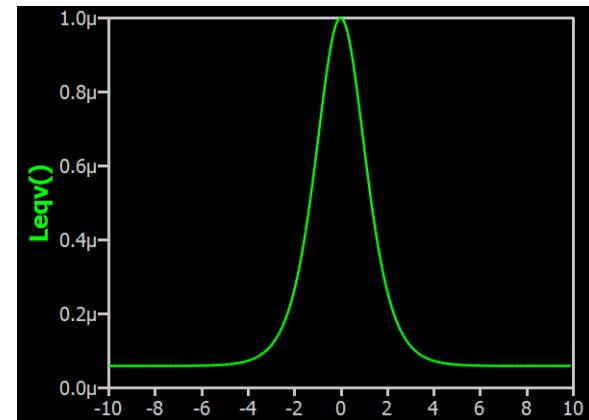
- This is nonlinear flux model include Lmin at large inductor current
- Flux equation uses format
 - Flux = $a \tanh(b \cdot I(L)) + L_{min} \cdot I(L)$

```

VL
I1
AC 1
DC bias
.param b = 0.7
.param LOA = 1μ
.param a = (LOA-Lmin)/b
.param Lmin=58n
flux=a*tanh(b*I(L1))+Lmin*I(L1)

.param frq=1Meg
.step param bias -10 10 0.1 Sweep bias
.step param var list 1 2 3 Sweep Isat

.ac list frq
.func Leqv() V(VL)/1/2/pi/frq
.plot Leqv()
  
```



```

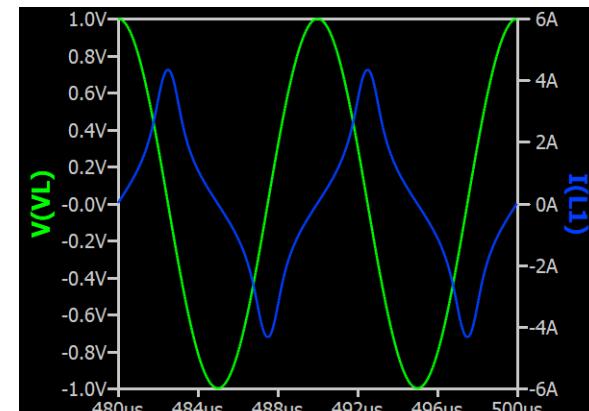
VL
V1
sine 0 1 f 0 0 90
.param f=100K
.tran 0 50/f 48/f 1/f/1000 uic
.plot V(VL) I(L1)

.param b = 0.7
.param LOA = 1μ
.param a = (LOA-Lmin)/b
.param Lmin=58n
flux=a*tanh(b*I(L1))+Lmin*I(L1)
  
```

For B-H plot

IntegralVL
B1
V=idt(V(VL),0)

B proportional to Integral of V(VL)
H proportional to I(IL)

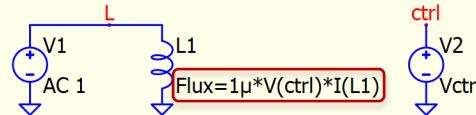


L. Behavioral Inductance with Flux (Arbitrary Inductance)

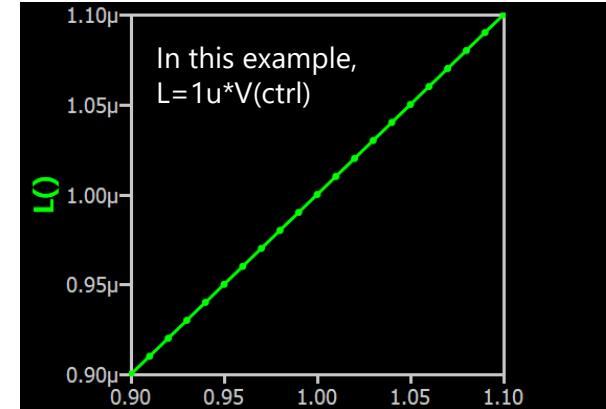
Qspice : L - Behavioral L with Flux.qsch

- Behavioral L with Flux
 - For linear inductor
 - $\phi = L \times I_L$
 - In Qspice
 - Flux = <eqn> * I(Ln)
 - <eqn> is inductance equation supports voltage node or device current
 - Ln is name attribute of inductor

Linear Inductor flux formula : Flux = L * IL
Therefore, behavioral inductance model can be derived using Arbitrary Inductance Device



```
.step param Vctrl 0.9 1.1 0.01
.param frq=1Meg
.ac list frq
.func imZ() V(L)/I(L1)
.func L() imZ()/2/pi/frq
.plot L()
```



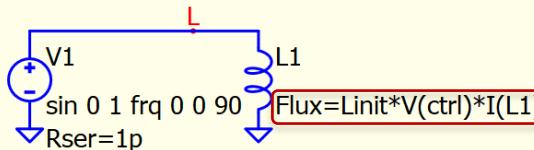
L. Behavioral Inductance with Flux (Arbitrary Inductance)

Qspice : L - Behavioral L with Flux (.tran).qsch

- Flux
 - Behavioral Inductance with flux
 - This schematic demonstrate using behavioral inductance (with flux) model in transient (.tran) analysis

Linear Inductor flux formula : $\text{Flux} = L * \text{IL}$
Therefore, behavioral inductance model can be derived using Arbitrary Inductance Device

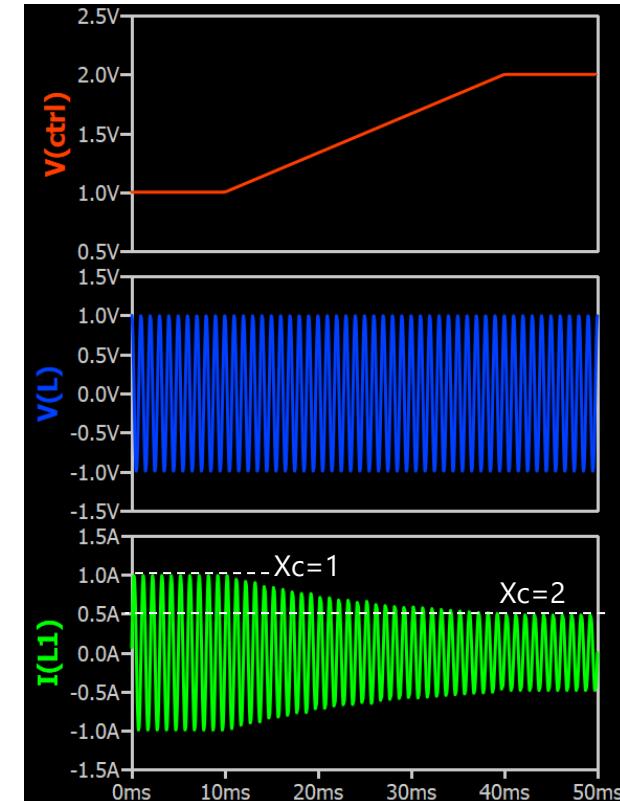
```
.param frq=1K  
.param XL=1  
.param Linit=XL/2/pi/frq
```



$L=Linit*1 \rightarrow XL=1$

$L=Linit*2 \rightarrow XL=2$

```
.tran 50m uic  
.option maxstep=1/frq/100  
.plot I(L1)  
.plot V(L)  
.plot V(ctrl)
```



M. MOSFET

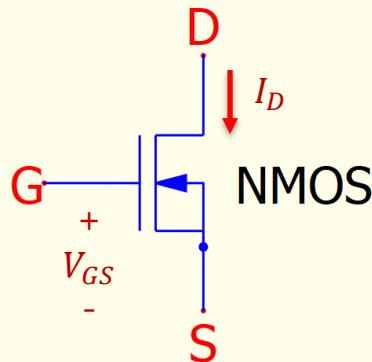
Model Levels for

NMOS | PMOS

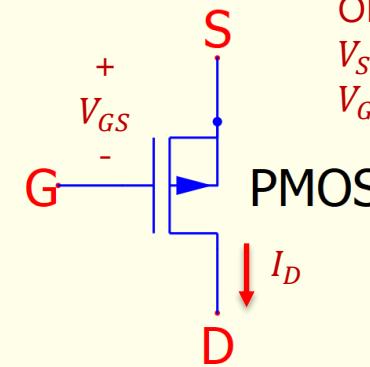
M. MOSFET

- MOSFET Syntax
 - Mnnn D G S B <model> [instance parameters]
 - D : Drain
 - G : Gate
 - S : Source
 - B : Substrate or Body
 - .model <model> <NMOS|PMOS|VDMOS> [model parameters]

M. MOSFET NMOS and PMOS



Ohmic / Saturation
 $V_D > V_S$
 V_{GS} is +ve ($V_G > V_S$)



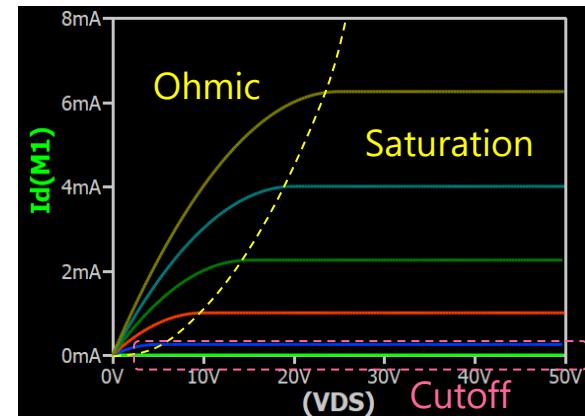
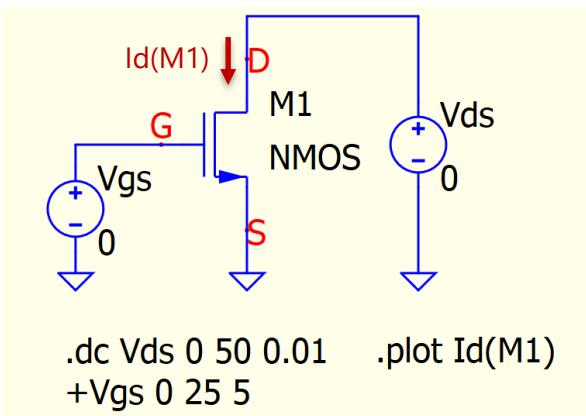
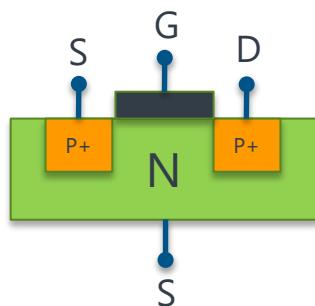
Ohmic / Saturation
 $V_S > V_D$
 V_{GS} is -ve ($V_G < V_S$)

Voltage Relations	NMOS
$V_{GS} > V_{th}$ $V_{DS} < V_{GS} - V_{th}$	Ohmic (Triode/Linear)
$V_{GS} > V_{th}$ $V_{DS} \leq V_{GS} - V_{th}$	Saturation (Active)
$V_{GS} < V_{th}$	Cutoff

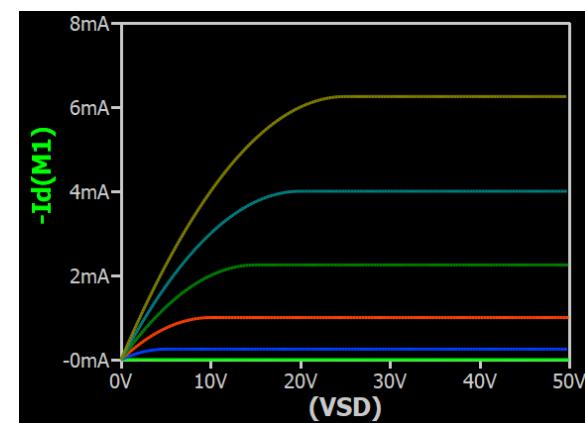
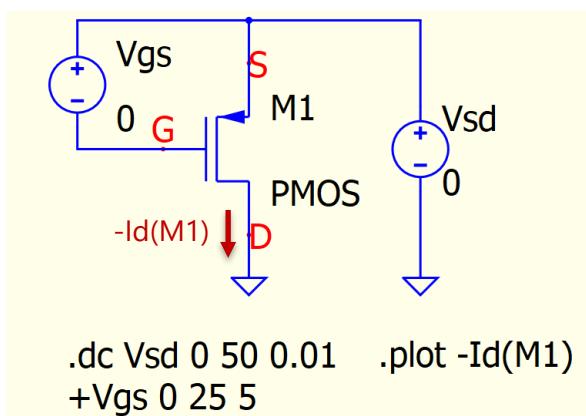
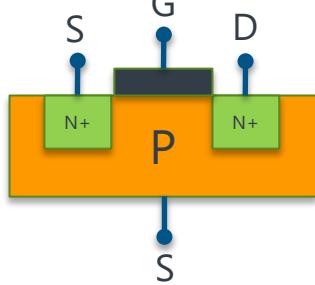
M. MOSFET NMOS and PMOS Ohmic, Saturation and Cutoff

Qspice : NMOS PMOS (Basic) - Region NMOS.qsch | NMOS PMOS (Basic) - Region PMOS.qsch

- NMOS
 - N-channel MOSFET



- PMOS
 - P-channel MOSFET



MOSFET Model Levels for NMOS | PMOS | VDMOS

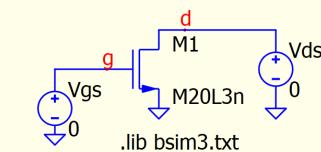
- Model Levels for MOSFET (NMOS | PMOS | VDMOS)
 - Monolithic N- or P- Mosfet : **.model <model> <NMOS|PMOS> Level=X**
 - Parameter Level specifies the model to be used for NMOS | PMOS
 - Vertical Double Diffused Power Mosfet : **.model <model> VDMOS <nchan|pchan>**
 - In default as nchan if not specify

Level	Name	Model	Comment
1	MOS1	Shichman-Hodges	MOS is generic model typically assumes long-channel devices
2	MOS2	Grove-Frohman	VDMOS is extended from MOS1 with additional parameters Cgdmin, Cgdmax, ETA, Ronx
3	MOS3	Semi-empirical model	MOS2 and MOS3 are intermediate and advance model of MOS1
-4	BSIM1	Berkeley Short-Channel IGFET Model	CMOS short-channel IGFET model, initial version, rarely used
-5	BSIM2		level number set negative in Qspice
7, 8, 49,53	BSIM3v3.3.2		Channel length down to 0.25um
14, 54	BSIM4v4.8.1		Channel length below 0.25um
5, 12, 55	Modified EKV v2.6	Enz-Krummenacher-Vittoz	CMOS
2010	SiC FET	Qorvo SiC FET	

NMOS MOS3 and BSIM3 Examples

Qspice : MOS Level=3 - MOS3.qsch | MOS Level=7 - BSIM3.qsch | bsim3.txt

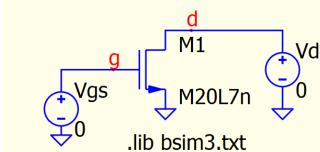
NMOS Level=3 MOS3 Example



```
.dc Vgs -5 5 0.01 Vds list 5  
.plot Id(M1)
```

```
.MODEL M20L3n NMOS LEVEL=3 PHI=0.700000 TOX=3.9100E-08 XJ=0.200000U TPG=1  
+ VTO=0.7909 DELTA=-7.2550E-01 LD=3.6790E-07 KP=5.4712E-05  
+ UO=619.5 THETA=4.2250E-02 RSH=3.2310E+01 GAMMA=0.5350  
+ NSUB=6.7240E+15 NFS=5.9090E+11 VMAX=1.9770E+05 ETA=8.3090E-02  
+ KAPPA=4.1240E-01 CGDO=4.8737E-10 CGSO=4.8737E-10  
+ CGBO=3.4582E-10 CJ=1.3214E-04 MJ=6.0852E-01 CJSW=5.2994E-10  
+ MJSW=2.5789E-01 PB=4.0492E-01
```

NMOS Level=7 BSIM3 Example



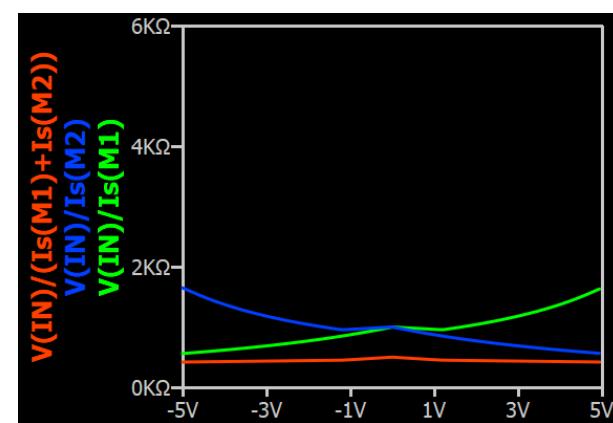
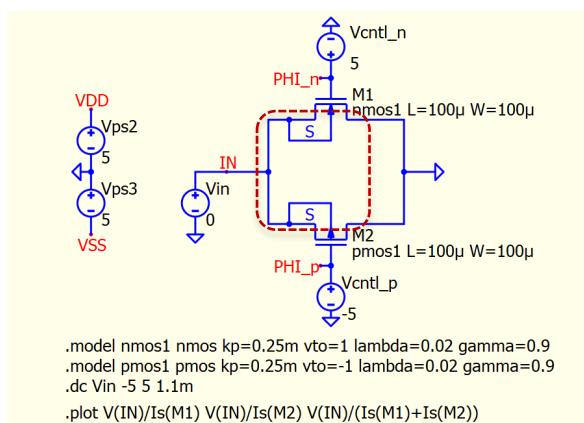
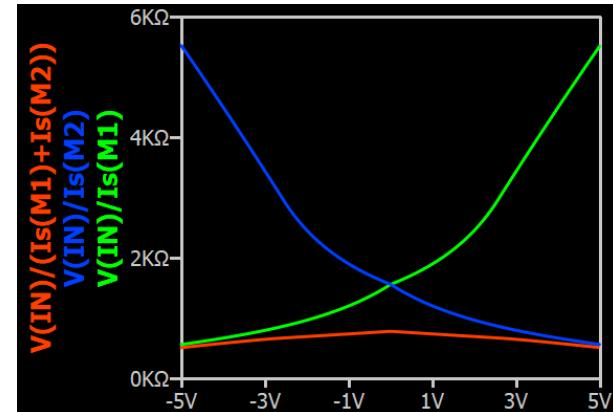
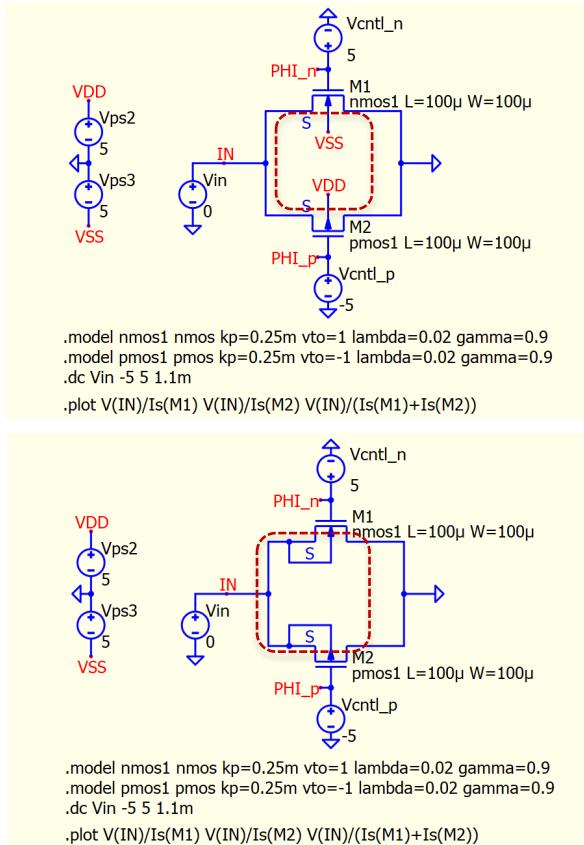
```
.dc Vgs -5 5 0.01 Vds list 5  
.plot Id(M1)
```

```
.MODEL M20L7n NMOS ( LEVEL= 7  
+*VERSION = 3.1  
+ TNOM = 27 TOX = 3.91E-8  
+ NCH = 8E16 VT0 = 0.7582903  
+ K1 = 1.2842394 K2 = -0.2616765 K3 = 1.8658079  
+ K3B = -6.3342185 W0 = 1E-8 NLX = 1E-9  
+ DVT0W = 0 DVT1W = 0 DVT2W = 0  
+ DVT0 = 0.8232689 DVT1 = 0.2798469 DVT2 = -0.3303888  
+ U0 = 686.7089438 UA = 2.30065E-9 UB = 1.887526E-19  
+ UC = 1.641046E-11 VSAT = 1.1522865 A0 = 0.4530999  
+ AGS = 0.143591 BO = 2.190772E-6 B1 = 3.8864578E-6  
+ KETA = -0.0185064 AI = 0 A2 = 1  
+ RDWSW = 915.0286945 PRWG = 1.170682E-4 PRWB = -1.258108E-7  
+ WR = 1 WINT = 1.354538E-7 LINT = 3.631938E-7  
+*XL = 0 XW = 0  
+ DWG = -4.259528E-8  
+ CIT = 0 VOFF = -0.0371577 NFACTOR = 0.0171325  
+ CDSCD = 0 CDSCD = 0  
+ CDSCB = 2.06298E-5 ETAB = 2.972609E-3 ETAB = -6.934953E-4  
+ DSUB = 6.9559E-3 PCLM = 4.6075119 PDBLC1 = 1.214532E-1  
+ PDIBLC2 = 1.404855E-6 PDIBLCB = -1E-3 DROUT = 0.5839765  
+ PSCBE1 = 2.291228E10 PSCBE2 = 6.675847E-7 PVAG = 1.8770406  
+ DELTA = 0.01 MOBMOD = 1 PRT = 0  
+ UTE = -1.5 KT1 = -0.11 KT1L = 0  
+ KT2 = 0.022 UAI = 4.31E-9 UBI = -7.61E-18  
+ UCL = -5.6E-11 AT = 3.3E4 WL = 0  
+ WLN = 1 WW = 0 WWN = 1  
+ NWL = 0 LL = 0 LLN = 1  
+ LW = 0 LWN = 1 LWL = 0  
+ CAPMOD = 2 XPART = 0.4 CGDO = 3.54E-10  
+ CGSO = 3.54E-10 CGBO = 0 CJ = 1.321396E-4  
+ FB = 0.4049196 MJ = 0.6085241 CJSW = 5.299371E-10  
+ PBSW = 0.6552296 MJSW = 0.2578644 PVTH0 = 0.0684739  
+ PRDSW = -1.8E3 PK2 = -0.0812182 WKETA = 0.0246323  
+ LKETA = -4.18493E-3 PAGS = 0.536 )
```

MOSFET model : Substrate or Body (B) Terminal

Qspice : MOSFET-CMOS-Substance (Circuit Example).qsch

- Substrate or Body (B)
 - MOSFET syntax
 - Mn_n D G S B <model>
 - For Power MOSFET, the B terminal is typically connected to the Source terminal
 - In CMOS, the substrate may be connected to potential different to Source terminal
 - This circuit example demonstrates how the substrate potential can affect the electronic characteristics of this CMOS amplifier
 - Reference :
<https://www.ece.mcgill.ca/~grobler4/SPICE/SPICE%20Decks/1st%20Edition%20LTSPICE/chapter5/Chapter%205%20MOSFETs%20web%20version.html>



Low Power IC (Integrated Circuit) MOSFET

- Modeling of Low Power CMOS
 - In Qspice, model is commonly found as : BSIM3 , BSIM4
- Low Power IC (Integrated Circuit) MOSFET
 - NMOS (Monolithic N-channel MOS)
 - PMOS (Monolithic P-channel MOS)
 - CMOS (Complementary Metal-Oxide-Semiconductor) : Employs both n-type and p-type MOSFETs (NMOS and PMOS) to achieve low power consumption and high noise immunity for the integration of digital logic, analog circuits and memory on a single chip
 - SOI (Silicon-On-Insulator MOSFET) : Utilizes a thin layer of silicon on top of an insulating layer to improve device performance and reducing parasitic capacitance for high-frequency performance and reduces cross-talk in mixed signal designs

High-Power MOSFET

- Modeling of High-Power MOSFET
 - In Qspice, model is commonly found as : VDMOS , Level=2010 (SiC) and .SUBCKT
- Common High-Power MOSFET
 - VDMOS (Vertical Double-Diffused MOSFET): Most common high-power MOSFET variant and widely used in a range of applications, including power supplies, motor control, and audio amplifiers
 - LDMOS (Laterally Diffused MOSFET): High-power applications such as RF power amplifiers, wireless communication systems, and automotive systems.
 - Trench MOSFET: Commonly used in power conversion, motor drives, and automotive applications
 - GaN HEMT (Gallium Nitride High Electron Mobility Transistor): High-frequency and high-power applications such as RF power amplifiers, radar systems, and wireless power transfer.
 - SiC MOSFET (Silicon Carbide MOSFET): High-power and high-temperature applications due to their excellent performance, particularly in electric vehicles, renewable energy systems, and industrial power electronics
 - DMOS (Double-Diffused MOSFET)
 - UMOS (Unipolar MOSFET)

M. MOSFET (VDMOS)

**** VDMOS with different
default as monolithic MOSFET
models, it popularly used in
board level SMPS**

MOSFET Level 1 (MOS1) Model Parameters

MOSFET Level 1 Model Parameters

Name	Description	Units	Default
A	Additional non-linear Gate-drain capacitance abruptness		1.0
AD	Default drain area	m ²	0.0
AF	Flicker noise exponent		1.0
AS	Default source area	m ²	0.0
BV	Body diode breakdown voltage	V	Infinite
CAPOP ⁹	Charge(Capacitance) model		1
CBD	Zero-bias B-D junction capacitance	F	0.0
CBS	B-S junction capacitance	F	0.0
CGBO	Gate-bulk overlap capacitance	F/m	0.0
CGDMAX ⁸	Maximum additional non-linear Gate-Drain capacitance	F	0.0
CGDMIN ⁸	Minimum additional non-linear Gate-Drain capacitance	F	0.0
CGDO	Gate-drain overlap capacitance	F/m	0.0
CGS	Gate-source capacitance that doesn't scale with width	F	0.0
CGSO	Gate-source overlap capacitance	F/m	0.0
CJ	Bottom junction cap per area	F/m ²	0.0
CJO	Body diode zero-bias capacitance	F	0.0
CJSW	Side junction cap per length	F/m	0.0
EG	Body diode activation energy	V	1.11
ETA ⁸	Philips, et al.-style subthreshold conduction parameter		0.0
ETA2	Inverse sharpness of Ids limit for non-square law variation		0.0
FC	Forward bias junction fit parameter		0.5
GAMMA	Bulk threshold parameter	V ^{1/2}	0.0
GDSNOI	Channel shot noise coefficient(nlev=3)		1.0
GM	Ideal transconductance for non-square law variation	Ω	none
GMAX	Maximum bulk PN conductivity	Ω	1000.
IBV	Body diode current at breakdown voltage	A	1e-10
IDS	Maximum drain current for non-square law variation	A	Infinite
IGSS	Gate-Source leakage current	A	0.0
IS	Bulk junction saturation current	A	1e-14
JS	Bulk junction saturation current density	A/m ²	0.0
K1 ¹⁰	Threshold voltage sensitivity to bulk node	V ^{1/2}	0.25
KF	Flicker noise coefficient		0.0
KP	Transconductance parameter	A/V ²	2e-5
L	Default channel length	m	1e-5
LAMBDA	Channel length modulation	V ⁻¹	0.0

LD	Lateral diffusion	m	0.0
MJ	Bulk grading coefficient		0.5
MJSW	Side grading coefficient		0.33
N	Bulk(or Body) PN junction emission coefficient		1.0
NBV	Body diode breakdown emission coefficient		1.0
NLEV	Noise level(equation selector)		0
NRD	Default drain squares		0.0
NRB	Default bulk squares		0.0
NRG	Default gate squares		0.0
NRS	Default source squares		0.0
NSS	Surface state density	cm ⁻²	0.0
NSUB	Substrate doping	cm ⁻²	0.0
PB	Bulk junction potential	V	1.0
PD	Default drain perimeter	m	0.0
PHI	Surface potential	V	1.0
PCHAN	Flag to specify vertical PMOS geometry		not set
PS	Default source perimeter	m	0.0
RB	Bulk resistance	Ω	0.0
RD	Drain resistance	Ω	0.0
RDS	Additional Drain-Source shunt resistance	Ω	Infinite
RG	Gate resistance	Ω	0.0
RON	Ron at zero drain current for non-square law variation	Ω	none
RONX ⁸	Channel conductivity multiplier in linear region		1.0
RS	Source resistance	Ω	0.0
RSH	Sheet resistance	Ω/□	0.0
TNOM	Parameter measurement temperature(aka TREF)	°C	27.0
TOX	Oxide thickness	m	1.5e-8
TPG	Gate type		1
TT	Bulk PN junction Transit-time	sec	0.0
U0	Surface mobility(aka U0)	cm ² /V×sec	600
VDMOS ⁸	Flag to specify vertical geometry		not set
VFB ¹⁰	Flat band voltage	V	-1.0
VIGSS	Voltage at which IGSS was measured	V	5.0
VJ	Body diode Junction potential	V	1.0
VT0	Threshold voltage(aka VTO)	V	0.0
W	Default channel width	m	1e-5
XPART ¹⁰	Channel charge partitioning		1
XTI	Body diode Saturation current temperature exponent		3

Display purpose only

- Vds : VDS rating
- Qq : Gate charge
- Mfg : manufacturer

Linear and Saturation Region : VTO, KP, W, L, LD, LAMBDA

- From Semiconductor Device Modeling with Spice (Section 4.2.3)

- Linear region : $V_{GS} > V_{TH}$ and $V_{DS} < V_{GS} - V_{TH}$
 - $I_{DS} = \frac{KP}{L-2X_{jl}} \left(V_{GS} - V_{TH} - \frac{V_{DS}}{2} \right) V_{DS} (1 + \lambda V_{DS})$
- Saturation region : $V_{GS} > V_{TH}$ and $V_{DS} > V_{GS} - V_{TH}$
 - $I_{DS} = \frac{KP}{2} \frac{W}{L-2X_{jl}} (V_{GS} - V_{TH})^2 (1 + \lambda V_{DS})$
- where
 - V_{TH} : VTO , zero-bias threshold voltage (Default VTO=0 V)
 - KP : KP , transconductance (Default KP=1 A/V²)
 - W : W, channel width (Default W=1e-4 m)
 - L : L, channel length (Default L=1e-4 m)
 - X_{jl} : LD, lateral diffusion (Default LD=0 m)
 - λ : LAMBDA channel-length modulation (Default LAMBDA=0 V⁻¹)

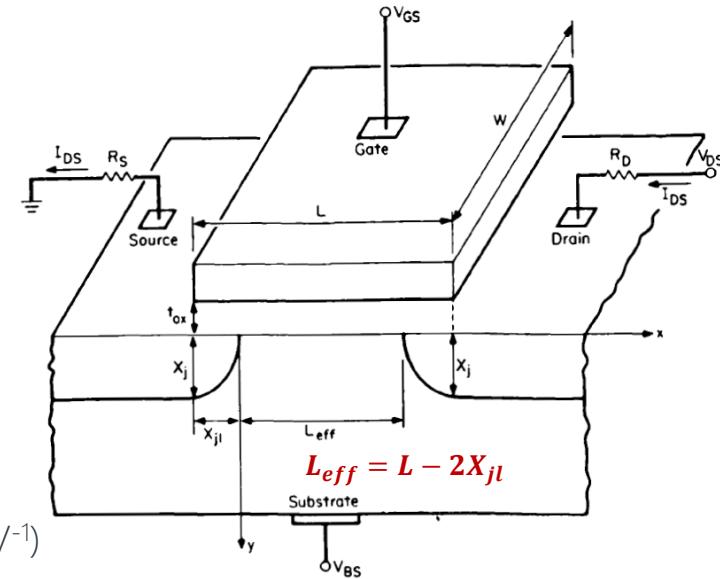


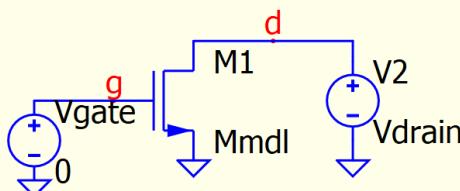
Figure 4-1 Structure of the MOST.

M. MOSFET Params : VTO, KP, W and L

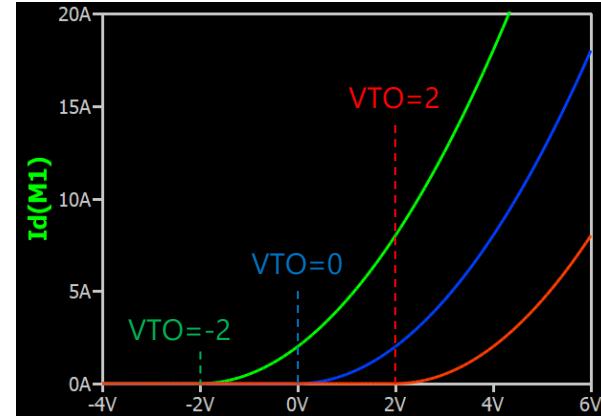
Qspice : VDMOS - VTO.qsch / VDMOS - KP.qsch / VDMOS - W.qsch / VDMOS - L.qsch

- VTO
 - VTO : Zero-bias threshold voltage
 - **Default VTO=0V**

```
.param Vdrain=10  
.dc Vgate -4 6 0.1 .plot Id(M1)
```

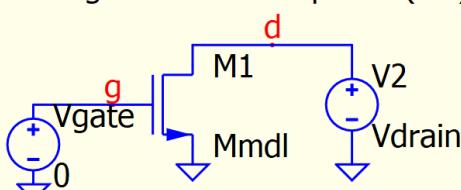


```
.step param vto list -2 0 2  
.model Mmdl VDMOS VTO=vto
```

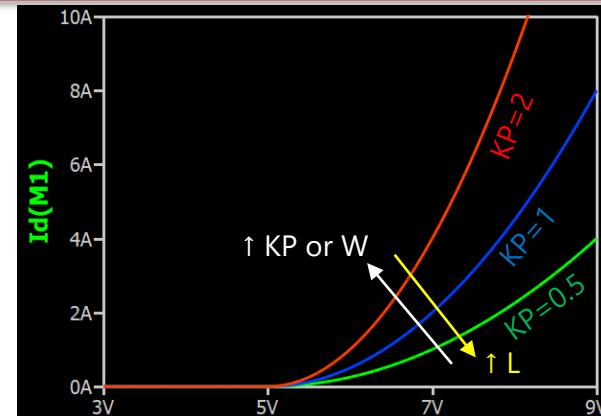


- KP
 - KP : transconductance
 - **Default KP=1 A/V²**

```
.param Vdrain=10  
.dc Vgate 3 9 0.1 .plot Id(M1)
```



```
.step param kp list 0.5 1 2  
.model Mmdl VDMOS VTO=5 KP=kp
```



- W and L
 - W : Channel Width (Default 1e-4)
 - L : Channel Length (Default 1e-4)
 - Effect is similar to KP as a gain
 - $\frac{KP}{2} \frac{W}{L-2X_{jl}}$ (for saturation region)

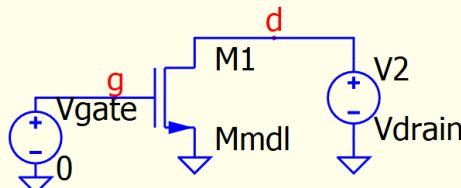
M. MOSFET Params : LD and ETA

Qspice : VDMOS - LD.qsch / VDMOS - ETA.qsch

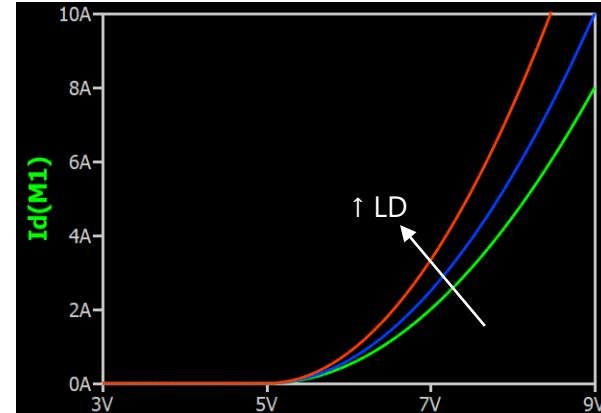
- LD

- LD : lateral diffusion
- **Default LD=0 m**
- $L_{eff} = L - 2LD > 0$
 - Therefore, $0 < LD < \frac{L}{2}$

```
.param Vdrain=10  
.dc Vgate 3 9 0.1 .plot Id(M1)
```



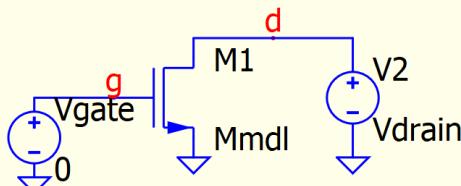
```
.step param Id list 0 0.1e-4 0.2e-4  
.model Mmdl VDMOS VTO=5 LD=Id
```



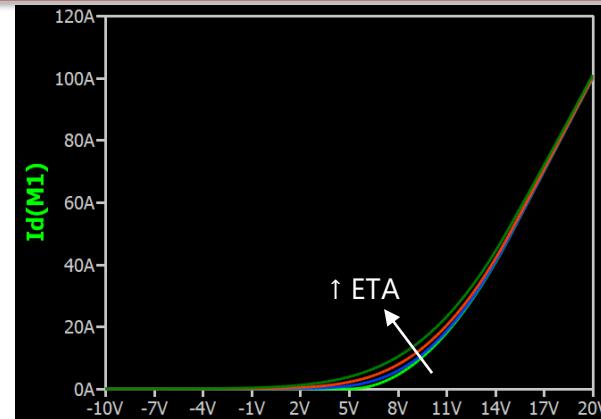
- ETA (aka ksubthres)

- ETA : Vds dependence of threshold voltage
- Static feedback on threshold voltage
- **Default ETA=0**
- Qspice accepts parameter name as ETA or ksubthres

```
.param Vdrain=10  
.dc Vgate -10 20 0.1.plot Id(M1)
```



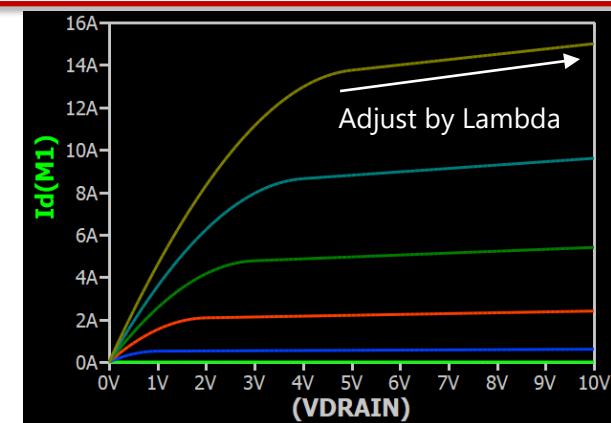
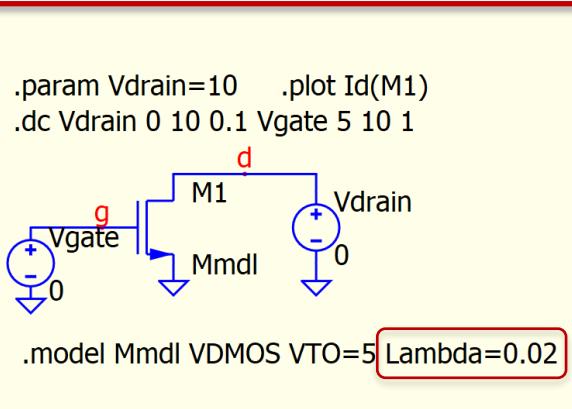
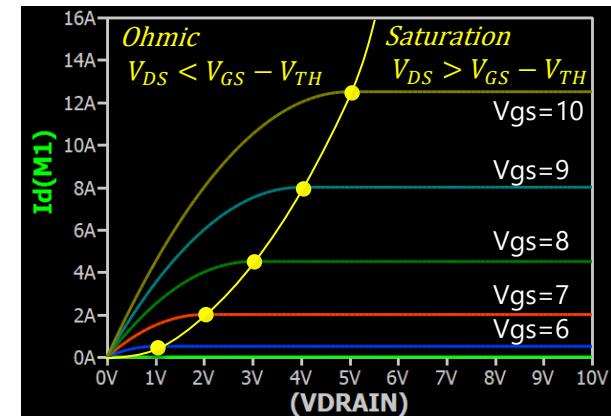
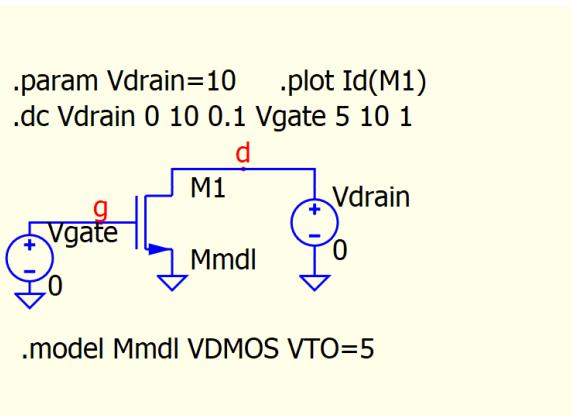
```
.step param eta list 0 2 3 4  
.model Mmdl VDMOS VTO=5 ETA=eta
```



M. MOSFET Params : Lambda

Qspice : VDMOS -LAMBDA.qsch

- LAMBDA
 - Labmda : channel-length modulation
 - Default LAMBDA=0 V⁻¹**



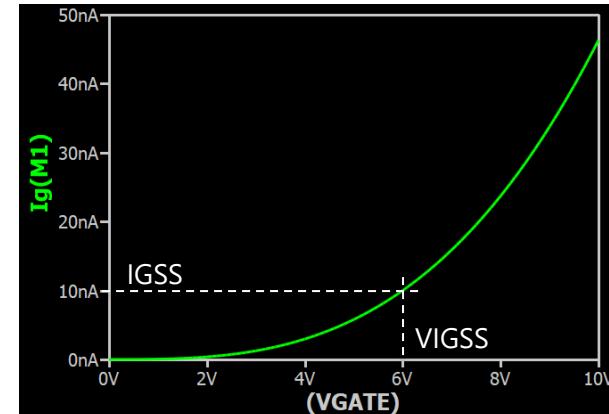
M. MOSFET Params (Gate) : VIGSS and IGSS, RG and CGS

Qspice : VDMOS - VIGSS IGSS.qsch / VDMOS - Rg Cgs.qsch

VIGSS and IGSS

- Vigss : Voltage at which IGSS was measured
- Igss : Gate-Source leakage current
- **Default VIGSS=5V**
- **Default IGSS=0A**
- Parameters to determine Igss in relates to Vgs

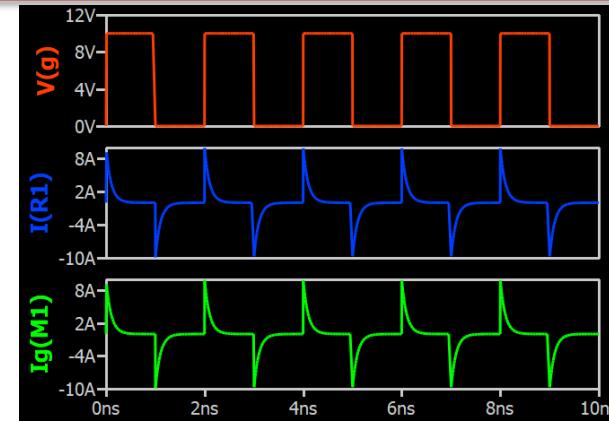
```
.param Vdrain=10  
.dc Vgate 0 10 0.1 .plot Ig(M1)  
  
M1  
Vdrain  
V2  
Vgate  
Mmdl  
d  
  
.model Mmdl VDMOS VTO=5 VIGSS=6 IGSS=10n
```



RG and CGS

- Rg : Gate Resistance
- Cgs : Gate-source capacitance that doesn't scale with width
- **Default RG=0Ω**
- **Default CGS=0F**
- Parameters to determine gate resistance and capacitoance

```
Equivalent Rg and Cgs  
R1  
C1  
100p  
1  
d  
M1  
Mmdl  
V2  
Vdrain  
Vgate  
pulse 0 10 0 0 0 1n 2n  
.model Mmdl VDMOS VTO=5 Rg=1 Cgs=100p
```



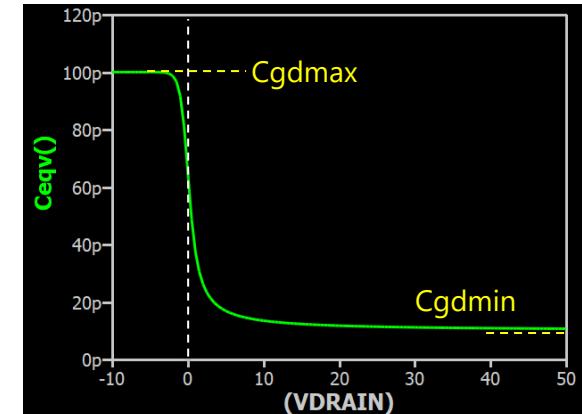
M. MOSFET Params (Cgd) : CGDMAX, CGDMIN and A

Qspice : VDMOS - CGDMIN CGDMAX.qsch / VDMOS - A.qsch

- CGDMAX and CGDMIN
 - Cgdmax : Maximum additional non-linear Gate-Drain capacitance
 - Cgdmin : Minimum additional non-linear Gate-Drain capacitance
 - Default Cgdmax=0F**
 - Default Cgdmin=0F**
 - Model non-linear of Cgd capacitance

```
.param f=10Meg
.ac list f
.step param Vdrain -10 50 0.5
Calculate Capacitance
.func imZ() imag(V(d)/Ig(M1))
.func Ceqv() -1/2/pi/f/imZ()
.plot Ceqv()

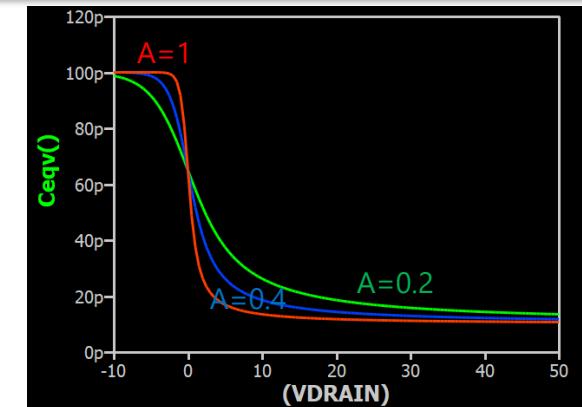
.model Mmdl VDMOS VTO=5 Cgdmin=10p Cgdmax=100p
```



- A
 - A : Additional non-linear Gate-drain capacitance abruptness
 - Default A=1**
 - Modify Cgd vs drain voltage profile

```
.param f=10Meg
.ac list f
.step param Vdrain -10 50 0.5
.step param a list 0.2 0.4 1
Calculate Capacitance
.func imZ() imag(V(d)/Ig(M1))
.func Ceqv() -1/2/pi/f/imZ()
.plot Ceqv()

.model Mmdl VDMOS VTO=5 Cgdmin=10p Cgdmax=100p A=a
```

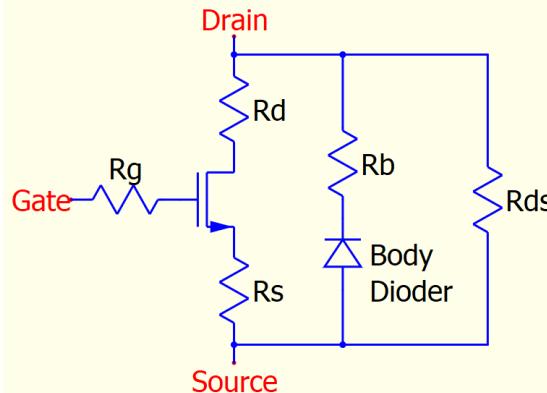


M. MOSFET Params : R_b, R_d, R_{ds}, R_g, R_s, Body Diode

Qspice : VDMOS - BodeDiode.qsch / VDMOS - R_b R_d R_{ds} R_g R_s.qsch

- Resistance

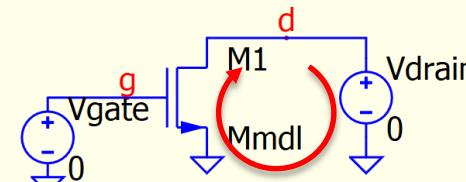
- R_b : Bulk resistance
- R_d : Drain resistance
- R_{ds} : Additional Drain-Source shunt resistance
- R_g : Gate resistance
- R_s : Source resistance
- **Default R_b=R_d=R_g=R_s=0Ω**
- **Default R_{ds}=Infinite**



- Body Diode

- Parameters same as diode model parameters
- Refer to section : D. Diode Diode Model Parameters
- This idea diode also provide C_{ds} capacitance with its junction capacitance C_j

```
.dc Vdrain -1 4 0.01  
.plot Id(M1)
```



```
.model Mmdl VDMOS VTO=5 N=0.3
```



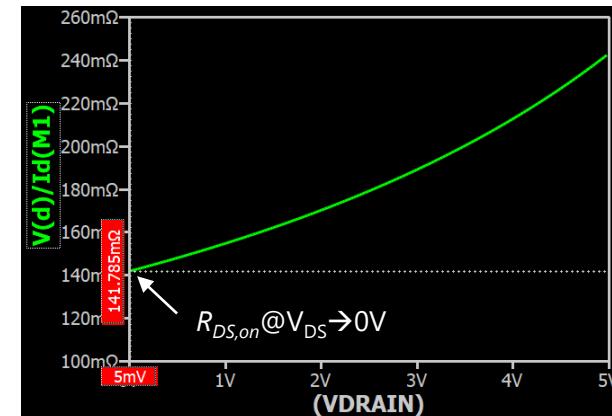
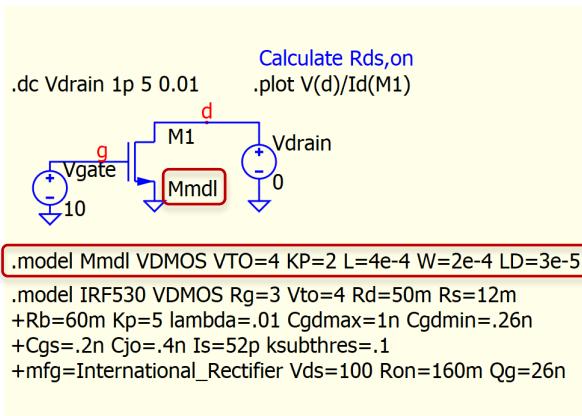
M. MOSFET : Drain-Source Turn ON Resistance : R_{ds,on}

- R_{ds,on}
 - This is not a direct parameters, but as to design SMPS, you may want to know what parameters in MOSFET model affect R_{ds,on}
 - In SMPS, R_{ds,on} is generally considered as MOSFET fully turn ON, where
 - $V_{GS} \gg V_{TH}$ and V_{DS} is low, MOSFET in linear region, and $R_{DS,ON} = \frac{V_{DS}}{I_{DS}}$
 - Linear region formula : $V_{GS} > V_{TH}$ and $V_{DS} < V_{GS} - V_{TH}$
 - $I_{DS} = KP \frac{W}{L-2X_{jl}} \left(V_{GS} - V_{TH} - \frac{V_{DS}}{2} \right) V_{DS} (1 + \lambda V_{DS})$
 - Therefore
 - $R_{DS,ON} = \frac{V_{DS}}{I_{DS}} = \frac{V_{DS}}{KP \frac{W}{L-2X_{jl}} \left(V_{GS} - V_{TH} - \frac{V_{DS}}{2} \right) V_{DS} (1 + \lambda V_{DS})} = \frac{1}{KP \frac{W}{L-2X_{jl}} \left(V_{GS} - V_{TH} - \frac{V_{DS}}{2} \right) (1 + \lambda V_{DS})}$
 - $\lim_{V_{DS} \rightarrow 0} R_{DS,ON} = \frac{1}{KP \frac{W}{L-2X_{jl}} \left(V_{GS} - V_{TH} - \frac{0}{2} \right) (1 + \lambda \times 0)} = \frac{1}{KP \frac{W}{L-2X_{jl}} (V_{GS} - V_{TH})} = \frac{L-2X_{jl}}{KP \cdot W \cdot (V_{GS} - V_{TH})}$
 - With Qspice model parameters, also consider drain and source resistance in model
 - @ $V_{DS} \rightarrow 0V$: $R_{DS,ON} = \frac{L-2 LD}{KP \cdot W \cdot (V_{GS} - VTO)} + RD + RS$
 - Where in default, VTO=0, KP=1, L=1e-4, W=1e-4, LD=0, RD=0 and RS=0

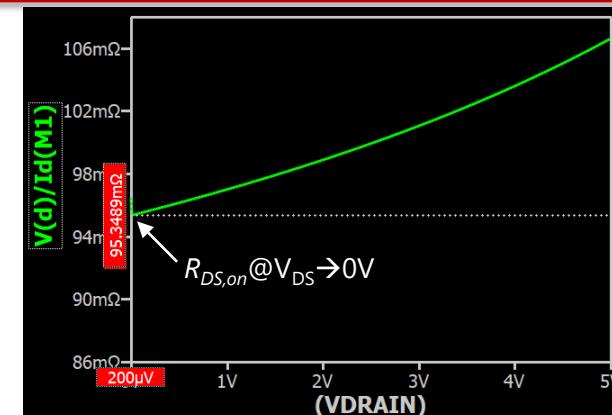
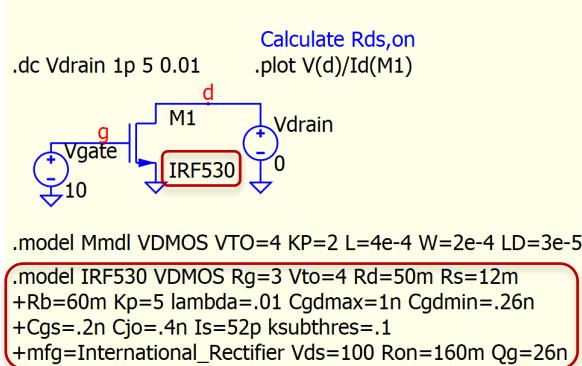
M. MOSFET : Drain-Source Turn ON Resistance : R_{ds,on}

Qspice : VDMOS - (Calculate) Rdson.qsch

- Example #1
 - Mmdl model
 - @V_{DS} → 0V
 - $R_{DS,ON} = \frac{L-2 LD}{KP \cdot W \cdot (V_{GS}-VTO)} + RD + RS$
 - RD=0
 - RS=0
 - $R_{DS,ON} @ V_{DS} \rightarrow 0V = 141.67m\Omega$



- Example #2
 - Mmdl model
 - @V_{DS} → 0V
 - $R_{DS,ON} = \frac{L-2 LD}{KP \cdot W \cdot (V_{GS}-VTO)} + RD + RS$
 - VTO=4, KP=5
 - L=W=1e-4, LD=0
 - RD=50m
 - RS=12m
 - $R_{DS,ON} @ V_{DS} \rightarrow 0V = 95.33m\Omega$



M. MOSFET
Level 2010 (SiC FET)
Model

M. MOSFET Level 2010 (SiC FET) Model

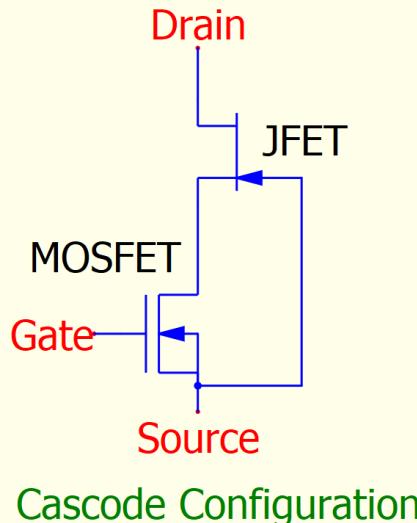
Name	Description	Units	Default
A	Sharpness of transition from CGDMIN to CGDMAX		1.0
AF	MOSFET Flicker noise exponent		1.0
BV	Body diode breakdown voltage	V	Infinite
CGDMAX	Gate-Drain maximum capacitance	F	0.0
CGDMIN	Gate-Drain minimum capacitance	F	0.0
CGS	Gate-source overlap capacitance	F	0.0
CJO	Body diode zero bias cap	F	0.0
EG	Body diode activation energy	V	1.11
ETA	Philips, et al.-style subthreshold conduction	V	0.0
ETATC1	ETA first order tempco	V/ $^{\circ}$ C ⁻¹	0.0
ETATC2	ETA second order tempco	V/ $^{\circ}$ C ⁻²	0.0
GDSNOI	Noise equation selector		0
GMAX	Maximum conductivity of any PN junction	Ω	1000.
IBV	Body diode current at breakdown voltage	A	1e-10
IGSS	Gate-Source leakage	A	0.0
IS	Body diode saturation current	A	1e-14
JAF	JFET Flicker Noise Exponent		1.0
JALPHA	JFET impact ionization coefficient	V ⁻¹	0.0
JB	JFET doping tail parameter		0.0
JBETA	JFET transconductance parameter	A/V ²	1.0
JBETATCE	JFET exponential temperature coefficient	%/ $^{\circ}$ C	0.0
JCGD	JFET G-D junction cap	F	0.0
JCGDO	JFET G-D junction cap	F	0.0
JCGS	JFET G-S junction capacitance	F	0.0
JCGSO	JFET G-S junction capacitance	F	0.0
JFC	JFET forward bias junction fit parm.		0.5
JIS	JFET gate junction saturation current	A	1e-14
JISR	JFET recombination current parameter	A	0.0
JKF	JFET Flicker Noise Coefficient		0.0
JLAMBDA	JFET Channel length modulation parameter	V ⁻¹	0.0

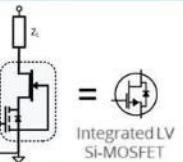
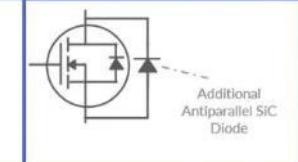
JM	JFET grading coeff.		0.5
JN	JFET emission coefficient		1.0
JNR	JFET Is _s emission coefficient		2.0
JPB	JFET gate junction potential	V	1.0
JRD	JFET drain ohmic resistance	Ω	0.0
JRDS	JFET additional Drain-Source leakage resistance	Ω	Infinite
JRDSTC1	JFET RDS first order tempco	$^{\circ}$ C ⁻¹	0.0
JRDSTC2	JFET RDS second order tempco	$^{\circ}$ C ⁻²	0.0
JRDTCl	JFET RD first order tempco	$^{\circ}$ C ⁻¹	0.0
JRDTC2	JFET RD second order tempco	$^{\circ}$ C ⁻²	0.0
JRG	JFET gate ohmic resistance	Ω	0.0
JRGTC1	JFET RG first order tempco	$^{\circ}$ C ⁻¹	0.0
JRGTC2	JFET RG second order tempco	$^{\circ}$ C ⁻²	0.0
JRONX	JFET channel conductivity multiplier in linear region		1.0
JRS	JFET source ohmic resistance	Ω	0.0
JRSTC1	JFET RS first order tempco	$^{\circ}$ C ⁻¹	0.0
JRSTC2	JFET RS second order tempco	$^{\circ}$ C ⁻²	0.0
JVK	JFET ionization knee current	V	0.0
JVTO	JFET threshold voltage	V	-2.0
JVTOTC	JFET V _{t0} 's temperature coefficient	$^{\circ}$ C ⁻¹	0.0
JXTI	JFET IS temperature coefficient		3.0
KF	MOSFET flicker noise coefficient		0.0
KP	MOSFET transconductance parameter	A/V ²	1.0
LAMBDA	MOSFET channel length modulation	V ⁻¹	0.0
LG	JFET gate inductance	H	0.0
LGRPAR	JFET gate inductance parallel loss	Ω	Infinite
LMID	Inductance making cascode connection	H	0.0
LS	MOSFET Source Inductance	H	0.0
LSRPAR	MOSFET Source inductance parallel loss	Ω	Infinite
LMIDRPAR	Cascode inductance parallel loss	Ω	Infinite
M	Body diode grading coefficient(MJ)	Ω	0.5

N	Bulk diode emission coefficient		1.0
NBV	Body diode breakdown emission coeff		1.0
NLEV	MOSFET noise equation selector		0
NOISELESS	The device does not contribute to a noise		
RB	Body diode series resistance	Ω	0.0
RBTC1	MOSFET RB first order tempco	$^{\circ}$ C ⁻¹	0.0
RBTC2	MOSFET RB second order tempco	$^{\circ}$ C ⁻²	0.0
RD	MOSFET drain ohmic resistance	Ω	Infinite
RDS	MOSFET drain-source shunt resistance	Ω	Infinite
RDTC1	MOSFET RD first order tempco	$^{\circ}$ C ⁻¹	0.0
RDTC2	MOSFET RD second order order	$^{\circ}$ C ⁻²	0.0
RG	MOSFET gate resistance	Ω	0.0
RONX	MOSFET conductivity multiplier in linear region		1.0
RS	MOSFET Source ohmic resistance	Ω	0.0
RSTC1	MOSFET RS first order tempco	$^{\circ}$ C ⁻¹	0.0
RSTC2	MOSFET RS second order tempco	$^{\circ}$ C ⁻¹	0.0
THETA	MOSFET V _{gs} dependence on mobility ala mos3	V ⁻¹	0.0
TNOM	Parameter measurement temperature(TNOM)	$^{\circ}$ C	27.0
TRB1	MOSFET RB first order tempco	$^{\circ}$ C ⁻¹	0.0
TRB2	MOSFET RB second order tempco	$^{\circ}$ C ⁻²	0.0
TRD1	MOSFET RD first order tempco	$^{\circ}$ C ⁻¹	0.0
TRD2	MOSFET RD second order tempco	$^{\circ}$ C ⁻²	0.0
TRS1	MOSFET RS first order tempco	$^{\circ}$ C ⁻¹	0.0
TRS2	MOSFET RS second order tempco	$^{\circ}$ C ⁻²	0.0
TT	Bulk diode transit time	s	0.0
VJ	Body diode Junction potential	V	1.0
VTO	MOSFET threshold voltage	V	0.0
VTOTC	MOSFET's V _{t0} tempco	$^{\circ}$ C ⁻¹	0.0
XTI	Body diode Saturation current temperature exp.		3.0

M. MOSFET Level 2010 (SiC FET) Cascode Configuration

- MOSFET Level 2010 (SiC FET) Model Parameters
 - SiC Cascode Configuration for SiC FET, which contains a JFET and MOSFET
 - SiC JFET
 - Si MOSFET
 - Reference
 - "Cascode Configuration Eases Challenges of Applying SiC JFETs", United SiC, App Note USCI_AN0004
 - "Origins of SiC FETs and their evolution towards the perfect switch", United SiC, White Paper

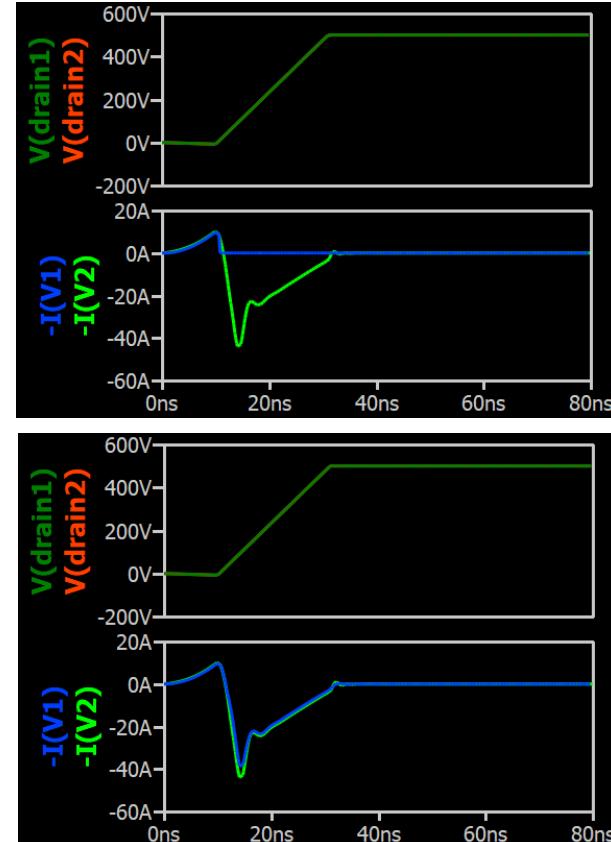
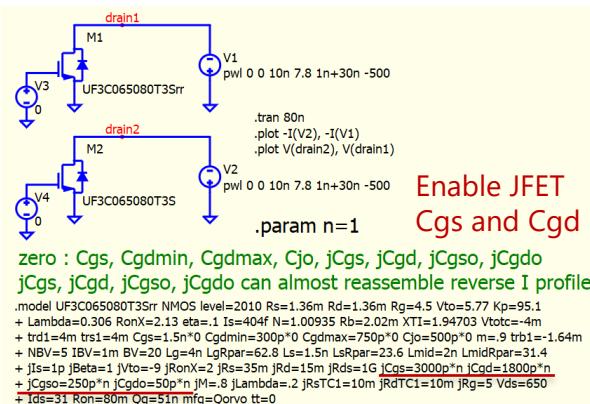
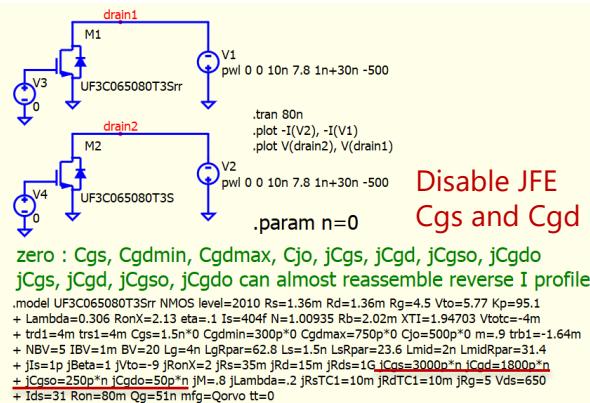


Normally Off UnitedSiC Cascode		Normally Off Typical SiC MOSFET
SiC Cascode Configuration	 = 	
Die Size	(Smaller) $R_{DS(A)} \sim 1.75 \text{ m}\Omega\cdot\text{cm}^2$	(Larger) $R_{DS(A)} \sim 3.1 - 4.5 \text{ m}\Omega\cdot\text{cm}^2$
Gate Drive	(Standard) $V_{GS} = 0V$ to $12V$ OR (SiC) $V_{GS} = -10V$ to $20V$	$V_{GS} = -5V$ to $20V$
Threshold	$V_{GS(TH)} = 5V$ Typical	$V_{GS(TH)} = 2.2V$ Typical
Intrinsic Diode	Low Qrr, +10% Over Temperature	High Qrr, High VF 3X Over Temperature
Avalanche	Yes	Yes
Short Circuit	Yes	Low

M. MOSFET Level 2010 : Reverse Current

Qspice : UF3C065080T3S Reverse Current.qsch

- Reverse Current
 - TT (transit-time) is set to 0 in Qorvo SiC FET, reverse recovery of bulk diode is not be used
 - Reverse current is simulated by parasitic capacitance in SiC FET
 - From Qorvo SiC FET model, reverse current is mainly contributed from Cgs and Cgd of JFET
 - j_{Cgs}, j_{Cgso}
 - j_{Cgd}, j_{Cgdo}

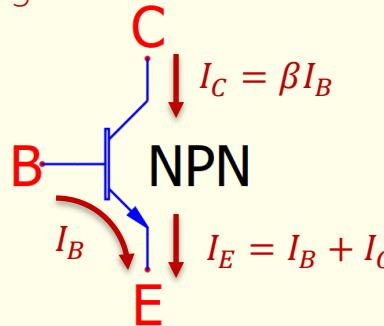


**Q. Bipolar Transistor
(Level 1, Extended
SPICE Gummel-Poon)**

Q. Bipolar Transistor : NPN and PNP

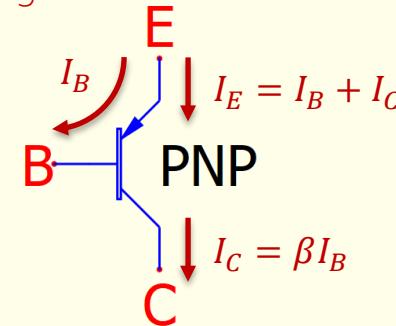
Active Region

$$V_C > V_E$$



Active Region

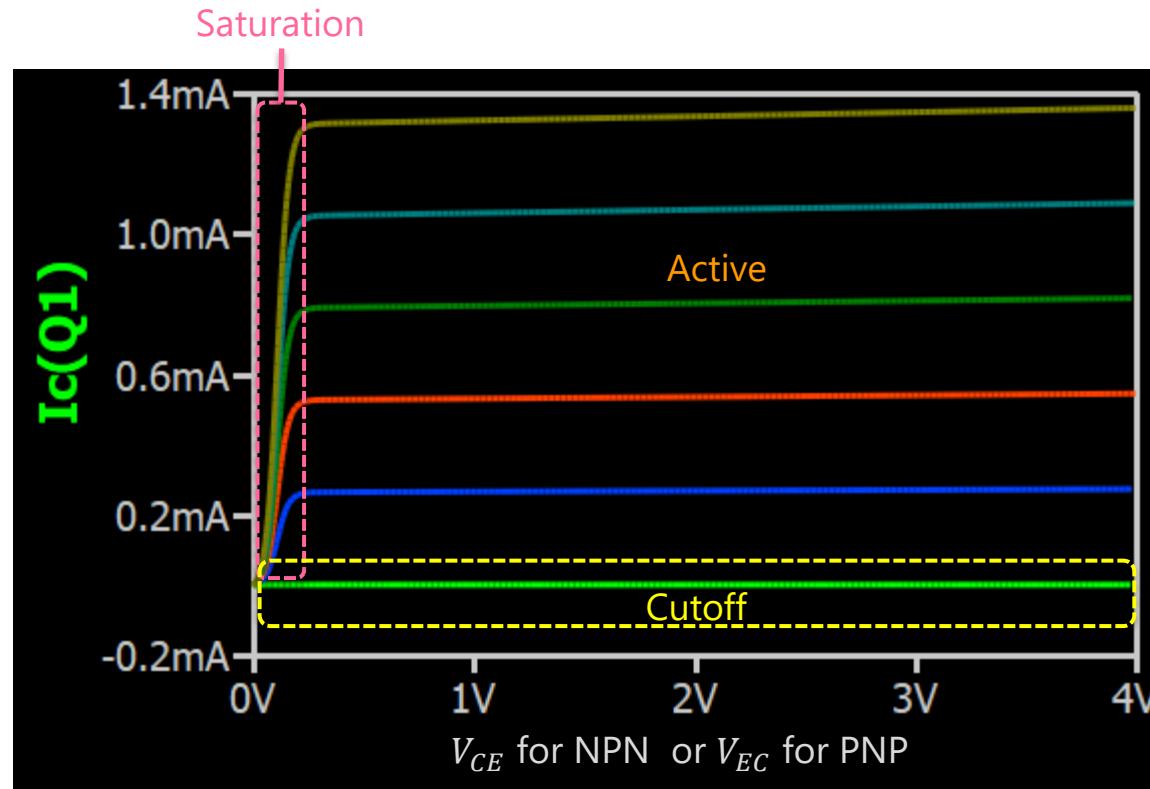
$$V_E > V_C$$



Voltage Relations	NPN
$V_E < V_B < V_C$	Active
$V_E < V_B > V_C$	Saturation
$V_E > V_B < V_C$	Cutoff
$V_E > V_B > V_C$	Reverse

Voltage Relations	PNP
$V_E < V_B < V_C$	Reverse
$V_E < V_B > V_C$	Cutoff
$V_E > V_B < V_C$	Saturation
$V_E > V_B > V_C$	Active

Q. Bipolar Transistor : NPN and PNP : Active, Saturation and Cutoff



Q. Bipolar Transistor Model Parameters

Bipolar Transistor Model Parameters			
Name	Description	Units	Default
AF	Flicker Noise Exponent		1.0
BF	Ideal forward beta		100.
BR	Ideal reverse beta		1.0
BRS	Substrate parasitic transistor beta		.0
CJC	Zero bias B-C capacitance	F	0.0
CJE	Zero bias B-E capacitance	F	0.0
CJS	Zero bias C-S capacitance(aka CCS)	F	0.0
CN ¹	Tempco for hole mobility	°C ⁻¹	NPN: 2.42 PNP: 2.20
D ¹	Tempco for scattering-limited hole carrier velocity	V ⁻¹	NPN: 0.87 PNP: 0.52
EG	Energy gap for IS temp. dependency	V	1.11
FC	Forward bias junction fit parameter		0.5
GAMMA ¹	Epitaxial region doping factor		1e-11
GMAX	Maximum PN conductivity(straight-line extension)	Ω	1000.
IBC	B-C saturation current	A	0.0
IBE	B-E saturation current	A	0.0
IKF	Forward beta roll-off corner current(aka IK)	A	Infinite
IKR	Reverse beta roll-off corner current	A	Infinite
IRB	Current for base resistance=(rb+rbm)/2	A	Infinite
IS	Saturation Current	A	1e-16
ISC	B-C leakage saturation current(aka C4)	A	IS
ISE	B-E leakage saturation current(aka C2)	A	IS
ISS	Substrate junction saturation current	A	0.0 ²
ITF	High current dependence of TF	A	0.0
KF	Flicker Noise Coefficient		0.33
MJC	B-C junction grading coefficient(aka MC)		0.33
MJE	B-E junction grading coefficient(aka ME)		0.0
MJS	Substrate junction grading coefficient(aka MS)		0.0
NC	B-C leakage emission coefficient		2.0
NE	B-E leakage emission coefficient		1.5
NEPI ¹	Epitaxial region emission coefficient		1.0
NF	Forward emission coefficient		1.0
NK	High-current roll-off coefficient		0.5
NR	Reverse emission coefficient		1.0
NS	Substrate junction emission coefficient		1.0
PTF	Excess phase	°	0.0
QCO ¹	Epitaxial region charge factor	C	0.0

QUASIMOD ¹	Temperature dependence equation selector		0
RB	Zero bias base resistance	Ω	0.0
RBM	Minimum base resistance	Ω	0.0
RC	Collector resistance	Ω	0.0
RCO ¹	Epitaxial region resistance	Ω	0.0
RE	Emitter resistance	Ω	0.0
SUBS	Set to 2 to specify lateral geometry.		1
TF	Ideal forward transit time	sec	0.0
TNOM	Parameter measurement temperature(aka TREF)	°C	27.0
TR	Ideal reverse transit time	sec	0.0
TRB1	Rb 1st order temperature coefficient	°C ⁻¹	0.0
TRB2	Rb 2nd order temperature coefficient	°C ⁻²	0.0
TRBM1	Rbm 1st order temperature coefficient(aka TRM1)	°C ⁻¹	0.0
TRBM2	Rbm 2nd order temperature coefficient(aka TRM2)	°C ⁻²	0.0
TRC1	RC 1st order temperature coefficient	°C ⁻¹	0.0
TRC2	RC 2nd order temperature coefficient	°C ⁻²	0.0
TRE1	RE 1st order temperature coefficient	°C ⁻¹	0.0
TRE2	RE 2nd order temperature coefficient	°C ⁻²	0.0
TVAF1	1st order tempco of forward Early voltage	V/°C ¹	0.0
TVAF2	2nd order tempco of forward Early voltage	V/°C ²	0.0
TVAR1	1st order tempco of reverse Early voltage	V/°C ¹	0.0
TVAR2	2nd order tempco of reverse Early voltage	V/°C ²	0.0
VAF	Forward Early voltage(aka VA)	V	Infinite
VAR	Reverse Early voltage(aka VB)	V	Infinite
VG ¹	Extrapolated band gap voltage at 0°K	V	1.206
VJC	B-C junction built in potential(aka PC)	V	0.75
VJE	B-E junction built in potential(aka PE)	V	0.75
VJS	Substrate junction built in potential(aka PS)	V	0.75
VO ¹	Carrier mobility knee voltage	V	10.0
VTF	Voltage giving VBC dependence of TF	V	Infinite
XCJC	Fraction of CJC connected to intrinsic base ³		1.0
XCJC2	Fraction of CJC connected to intrinsic base ⁴		1.0
XCJS	Fraction of CJS connected internally to RE		1.0
XTB	Forward and reverse beta temp. exp.		0.0
XTF	Coefficient for bias dependence of TF		0.0
XTI	Temperature exponent for IS(aka PT)		3.0

Q. Bipolar Transistor Basic Equation

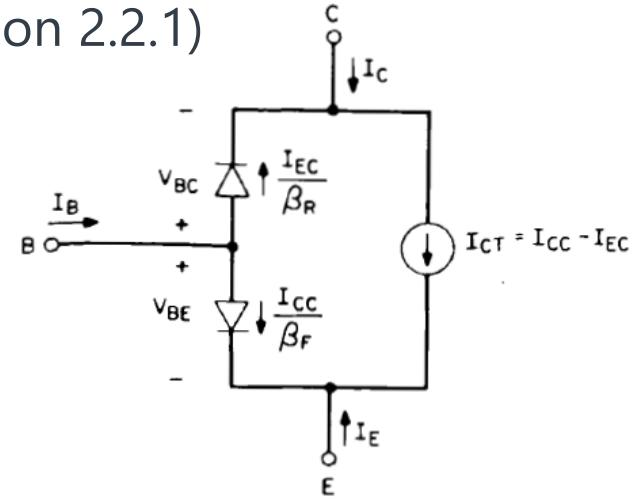
- Semiconductor Device Modeling with SPICE (Section 2.2.1)

- Basic equation from BJT Ebers-Moll static model

- $$\begin{aligned} I_C &= I_{CT} - \frac{I_{EC}}{\beta_R} \\ I_{CT} &= I_{CC} - I_{EC} \\ I_E &= -\frac{I_{CC}}{\beta_F} - I_{CT} \\ I_B &= \frac{I_{CC}}{\beta_F} + \frac{I_{EC}}{\beta_R} \end{aligned}$$

- Therefore

- $$\begin{aligned} I_C &= I_{CC} - I_{EC} - \frac{I_{EC}}{\beta_R} = \beta_F \left(I_B - \frac{I_{EC}}{\beta_R} \right) - I_{EC} - \frac{I_{EC}}{\beta_R} \\ I_C &= \beta_F I_B - \left(\frac{\beta_F}{\beta_R} + \frac{1}{\beta_R} + 1 \right) I_{EC} \end{aligned}$$



- Understanding (Approximation approach)

- If $V_{CE} \gg V_{BE}$, diode D_{BC} is reverse bias, where $I_{EC} \rightarrow 0$
 - $I_C = \beta_F I_B$
 - If $V_{BE} \gg V_{CE}$, diode D_{BC} is forward bias, and with $\beta_F \gg \beta_R$
 - $I_C = \beta_F I_B - \frac{\beta_F}{\beta_R} I_{EC}$

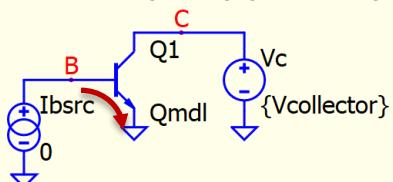
Q. Bipolar Params ($\beta_F | \beta_R$) : BF and BR

Qspice : NPN - BF.qsch / NPN - BR.qsch

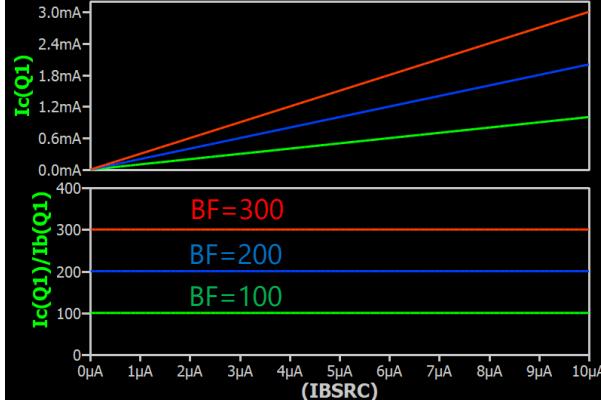
- BF
 - BF : Ideal forward beta
 - **Default BF=100**
 - $I_C = \beta_F I_B$ for $V_{CE} \gg V_{BE}$

- BR
 - BR : Ideal reverse beta
 - **Default BR=1**
 - $I_C = \beta_F I_B - \frac{\beta_F}{\beta_R} I_{EC}$
 - This effect is mainly observed when both BE and BC diode are forward bias, where collector-emitter voltage is close to 0V
 - Smaller β_R , larger $\frac{\beta_F}{\beta_R}$ and less I_C and less $\frac{I_C}{I_B}$

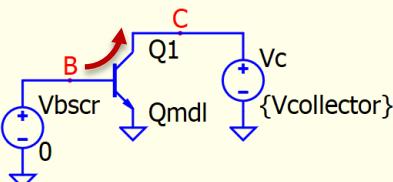
Sweep Parameters
`.param Vcollector = 10
.param Ibmax=10μ
.dc Ibsrc 10n {Ibmax} {Ibmax/100}`



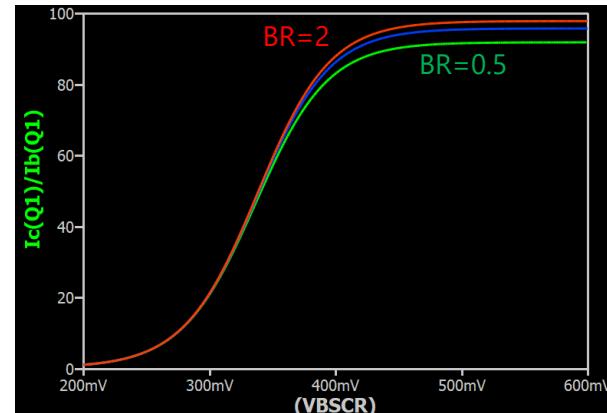
`.step param bf list 100 200 300
.model Qmdl NPN BF={bf}`



Sweep Parameters
`.param Vcollector = 0.2
.param Ibmin=10p
.dc Vbscr 0.2 0.6 0.001`



`.step param br list 0.5 1 2
.model Qmdl NPN BR={br} BF=100`

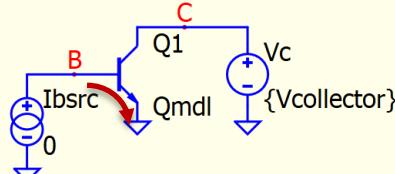


Q. Bipolar Params ($\beta_F | \beta_R$) : IKF

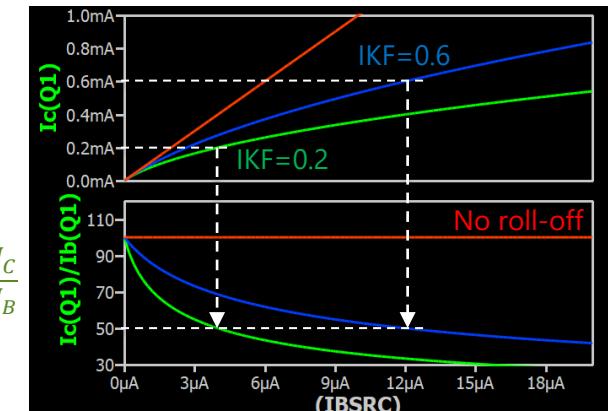
Qspice : NPN - IKF.qsch / NPN - IKR.qsch

- IKF
 - IKF : Forward beta roll-off corner current
 - Default IKF=infinite (A)**
 - IKF models β_F drop when I_C increase
 - IKF is I_C where effective BF (β_F) reduces multiple approximate by $(1-NK)$
 - This example Default NK=0.5, effective BF is reduced to 50 @ $I_C=IKF$

Sweep Parameters
`.param Vcollector = 10
.param Ibmax=20μ
.dc Ibsrc 10n {Ibmax} {Ibmax/100}`

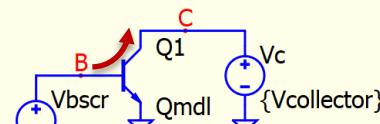


`.step param ikf list 0.2m 0.6m 1e12
.model Qmdl NPN BF=100 IKF=ikf`

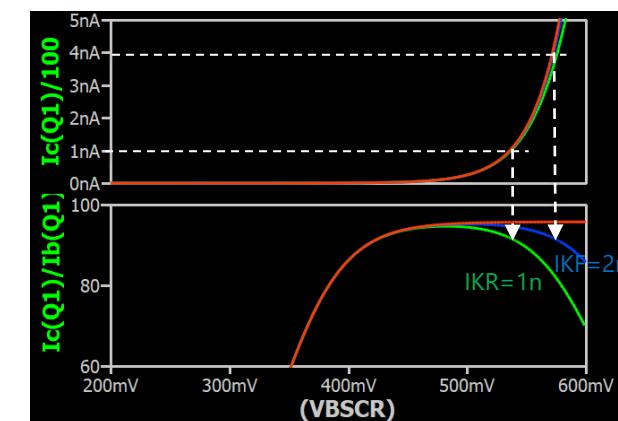


$$\beta_{F,\text{eff}} = \frac{I_C}{I_B}$$

Sweep Parameters
`.param Vcollector = 0.2
.param Ibmin=10p
.dc Vbscr 0.2 0.6 0.001`



`.param bf=100
.step param ikr list 1n 4n 1e12
.model Qmdl NPN BR=1 BF=bf IKR=ikr`



- IKR
 - IKR : Reverse beta roll-off corner current
 - Default IKR=infinite (A)**
 - IKR models β_F drop when I_C increase
 - IKR is $\frac{I_C}{BF}$ where effective BR (β_R) reduces to 50%

Q. Bipolar Params ($\beta_F | \beta_R$) : NK

Qspice : NPN - NK.qsch

- NK
 - NK : High-current roll-off coefficient
 - **Default NK=0.5**
 - This parameter is only be used if IKF not infinite

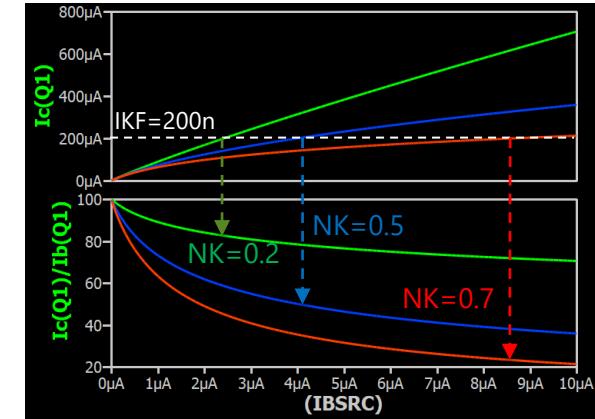
Sweep Parameters
.param Vcollector = 10
.param Ibmax=20 μ
.dc Ibsrc 10n {Ibmax} {Ibmax/100}

Plot Output
.plot Ic(Q1)/Ib(Q1)
.plot Ic(Q1)

Diagram

Model Definition

```
.step param nk list 0.2 0.5 0.7  
.model Qmdl NPN BF=100 IKF=200 $\mu$  NK=nk
```



Q. Bipolar Params (B-E and B-C Diode) : IS, NF, BF, NR, BR

Qspice : NPN - IS NF BF.qsch / NPN - IS NR BR.qsch

- Diode of Base-Emitter
 - **IS** : Saturation Current
 - **NF** : Forward emission coefficient
 - Default **IS** = $1e-16A$
 - Default **NF** = 1
 - In this case
 - $I_B = I_{BE} = \frac{I_{CC}}{\beta_F}$
 - $= \frac{1}{\beta_F} I_S \left(e^{\frac{qV_{BE}}{n_F kT}} - 1 \right)$
 - where β_F is **BF**

$$I_B = I_{BE} = \frac{I_{CC}}{\beta_F}$$

$$= \frac{1}{\beta_F} I_S \left(e^{\frac{qV_{BE}}{n_F kT}} - 1 \right)$$

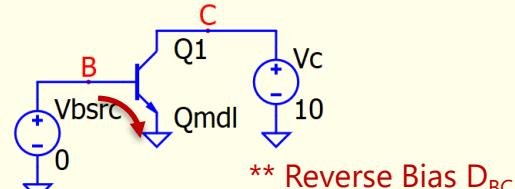
- Diode of Base-Collector
 - **IS** : Saturation Current
 - **NR** : Reverse emission coefficient
 - Default **IS** = $1e-16A$
 - Default **NR** = 1
 - In this case
 - $I_B = I_{BC} = \frac{I_{EC}}{\beta_R}$
 - $= \frac{1}{\beta_R} I_S \left(e^{\frac{qV_{BE}}{n_R kT}} - 1 \right)$
 - where β_R is **BR**

$$I_B = I_{BC} = \frac{I_{EC}}{\beta_R}$$

$$= \frac{1}{\beta_R} I_S \left(e^{\frac{qV_{BE}}{n_R kT}} - 1 \right)$$

Sweep Parameters
.param Vcollector = 10

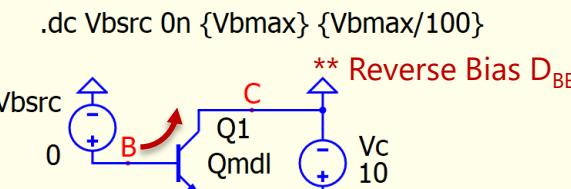
.param Vbmax=0.8
.dc Vbsrc 0n {Vbmax} {Vbmax/100}



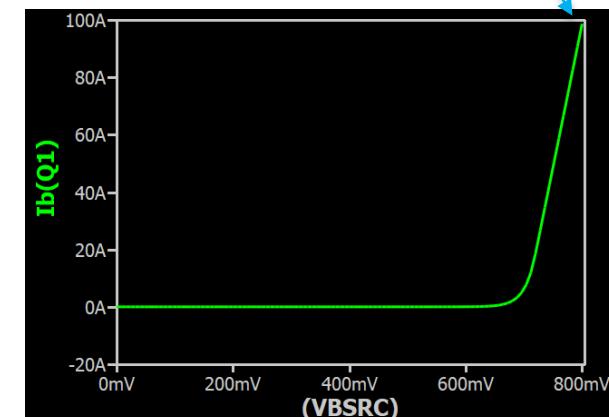
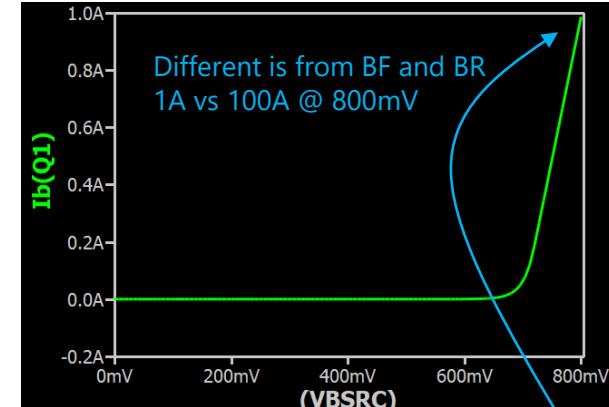
.model Qmdl NPN IS=1e-16 NF=0.7 BF=100

Sweep Parameters
.param Vcollector = 10

.param Vbmax=0.8
.dc Vbsrc 0n {Vbmax} {Vbmax/100}



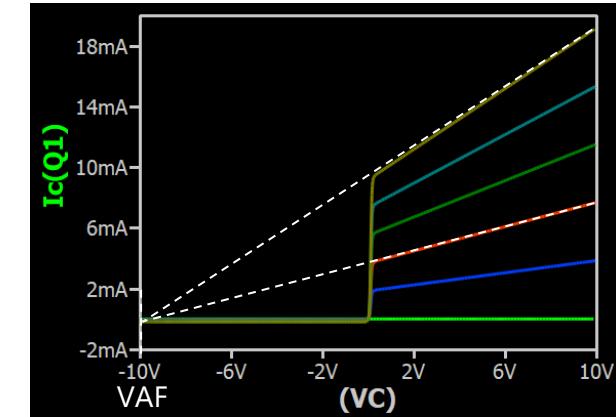
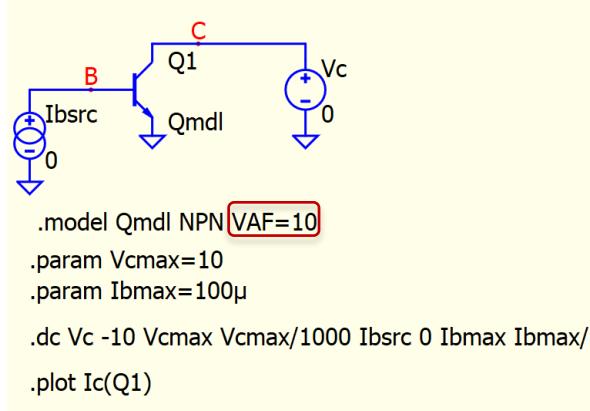
.model Qmdl NPN IS=1e-16 NR=0.7 BR=1



Q. Bipolar Params (Active Region) : VAF

Qspice : NPN - VAF.qsch

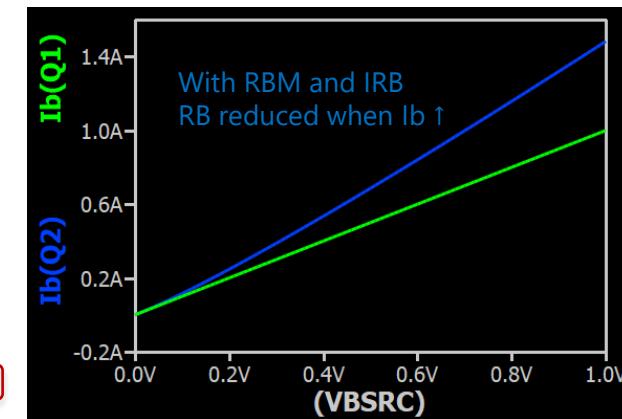
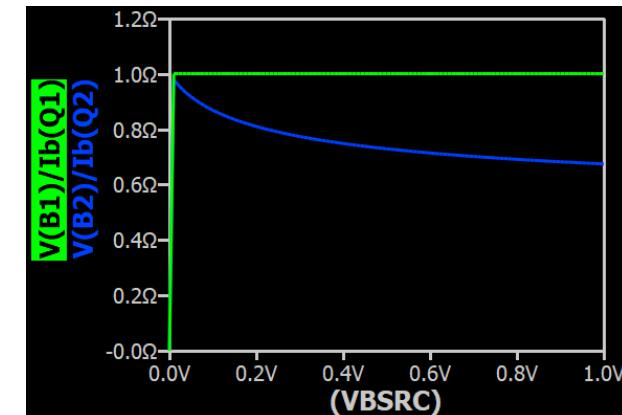
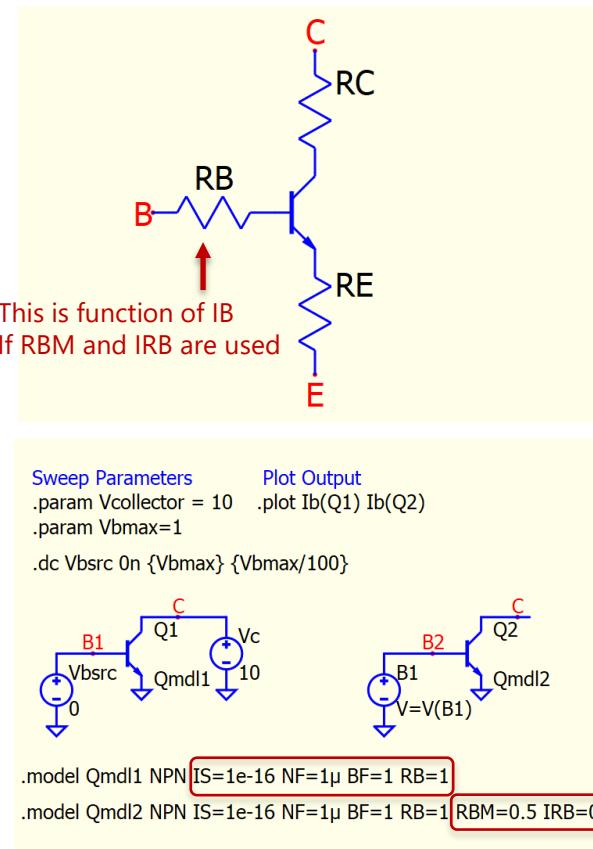
- VAF (aka VA)
 - VAF : Forward Early voltage
 - **Default VAF=Infinite (V)**



Q. Bipolar Params (Resistance): RB, RC, RE, RBM and IRB

Qspice : NPN - RBM IRB.qsch

- RB, RC, RE
 - RB : Zero bias base resistance
 - If RBM and IRB are used, base resistor is current dependent
 - RC : Collector resistance
 - RE : Emitter resistance
- RBM, IRB
 - RBM : Minimum base resistance
 - IRB : Current for base resistance
 - $R_{B, \text{effective}} @ \text{IRB} = \frac{1}{2} (\text{RB} + \text{RBM})$
 - Default RBM=0Ω
 - Default IRB=Infinite(A)
 - If these 2 parameters are defined, base resistance is function of base current



Q. Bipolar Params (Capacitance) : CJC, MJC, VJC, CJE, MJE, VJE

- B-C, B-E and C-S nonlinear capacitance
 - Model nonlinear capacitor between B-C, B-E and C-S
 - Parameters definition follows diode CJO, M and VJ
 - $C_j = \frac{\text{CJO}}{(1 - \frac{V_D}{V_J})^M}$
 - CJO : Zero-bias junction capacitance
 - M : Grading coefficient
 - VJ : Junction potential

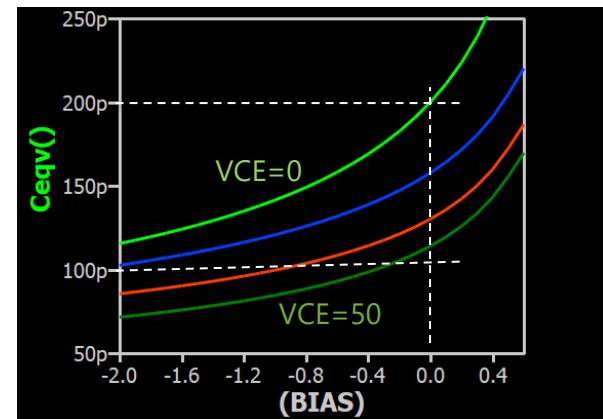
Diode	CJO	M	VJ
B-C	CJC	MJC	VJC
B-E	CJE	MJE	VJE
C-S	CJS	MJS	VJS

- Refer to D. Diode CJO, M and VJ
- C-S normally not modeled

```
.param f=1Meg
.ac list f
.step param bias -2 0.6 0.1
.step param VCE list 0 2 10 50
.func Zim() imag(V(B)/Ib(Q1))
.func Cequiv() -1/2/pi/f/Zim()
.plot Cequiv()

.Circuit Diagram
A bipolar junction transistor (Q1) is shown with its base (B), collector (C), and emitter (E) terminals. The base terminal is connected to a DC bias source labeled 'DC bias AC 1'. The collector terminal is connected to a voltage source labeled 'V2'. The emitter terminal is connected to ground through a load resistor labeled 'Qmdl' and to an output port labeled 'VCE'. The collector-emitter voltage is also labeled 'VCE'.
```

.model Qmdl NPN CJE=100p MJE=0.5 VJE=1
+CJC=100p MJC=0.5 VJC=1



Q. Bipolar Params (Capacitance) : CJC, MJC, VJC, CJE, MJE, VJE

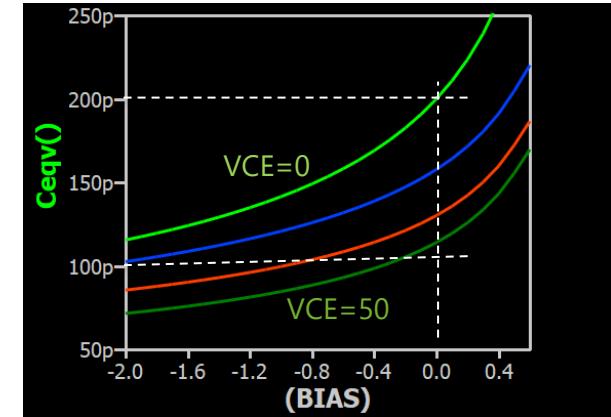
Qspice : NPN - CJC CJE.qsch

- B-C, B-E and C-S nonlinear capacitance
 - Model nonlinear capacitor between B-C, B-E and C-S
 - Parameters definition follows diode CJO, M and VJ
 - $C_j = \frac{C_{JO}}{(1 - \frac{V_D}{V_J})^M}$
 - CJO : Zero-bias junction capacitance
 - M : Grading coefficient
 - VJ : Junction potential
- Simulation
 - This simulation modeled both capacitance between B-C and B-E. Change VCE to observe overall capacitance effect in different bias voltage

```
.param f=1Meg
.ac list f
.step param bias -2 0.6 0.1
.step param VCE list 0 2 10 50
.model Qmdl NPN CJE=100p MJE=0.5 VJE=1
+CJC=100p MJC=0.5 VJC=1
```

Calculate Equivalent C

```
.func Zim() imag(V(B)/Ib(Q1))
.func Ceqv() -1/2/pi/f/Zim()
.plot Ceqv()
```



Diode	CJO	M	VJ
B-C	CJC	MJC	VJC
B-E	CJE	MJE	VJE
C-S	CJS	MJS	VJS

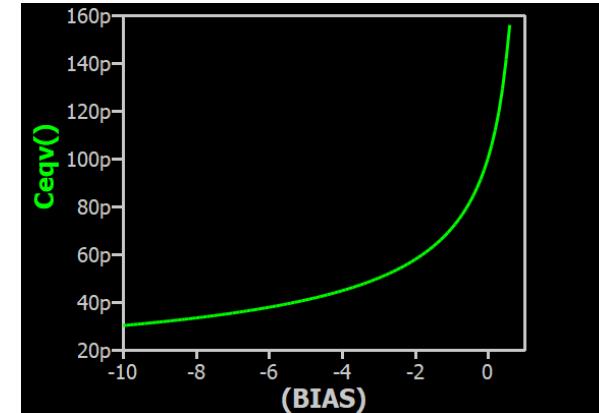
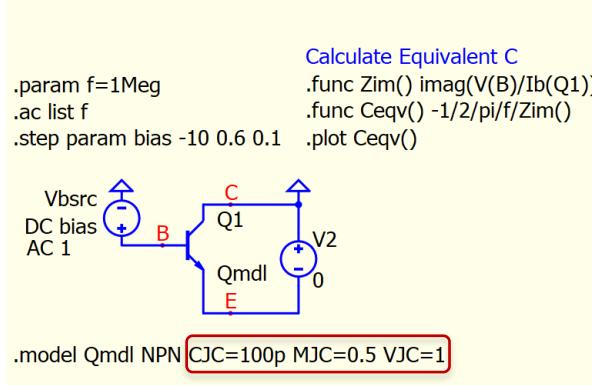
- Refer to D. Diode CJO, M and VJ
- C-S normally not modeled

- Simulation Explanation
 - CBC and CBE are nonlinear capacitance of junction diode from B to C and B to E
 - Higher reverse voltage, lower capacitance
 - Therefore, increase VCE, increase reverse voltage of B-C and affects B-C capacitance. However, increase VCE doesn't affect VBE, and no effects in B-E capacitance
 - @VB=0V, when VCE=0, no reverse in both B-C and B-E and capacitance equals CJC+CJE

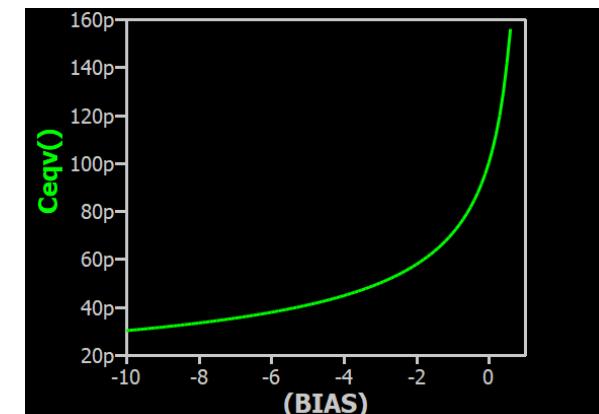
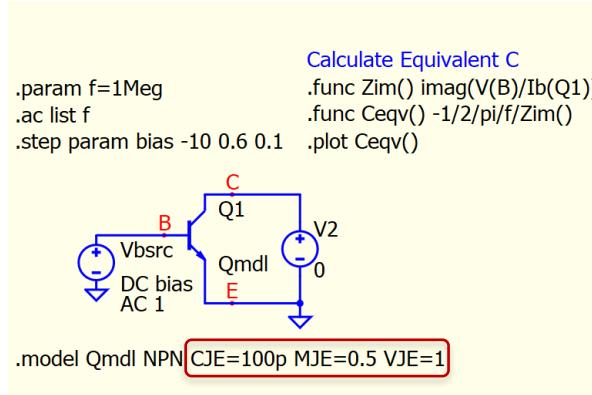
Q. Bipolar Params (Capacitance) : CJC, MJC, VJC, CJE, MJE, VJE

Qspice : NPN - CJC MJC VJC.qsch / NPN - CJE MJE VJE.qsch

- CJC, MJC and VJC
 - CJC : Zero bias B-C capacitance
 - MJC : B-C junction grading coefficient
 - VJC : B-C junction built in potential
 - **Default CJC=0F**
 - **Default MJC=0.5**
 - **Default VJC=1**



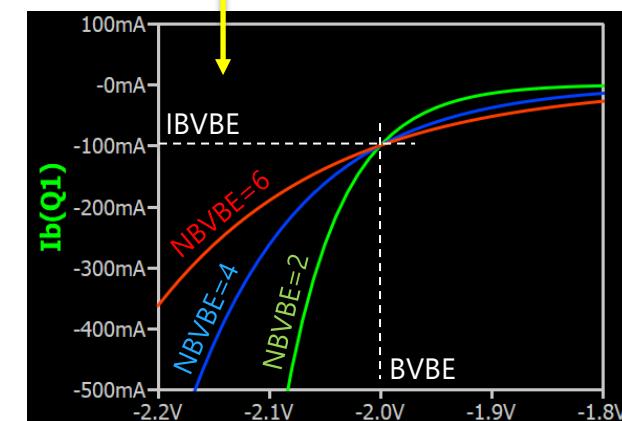
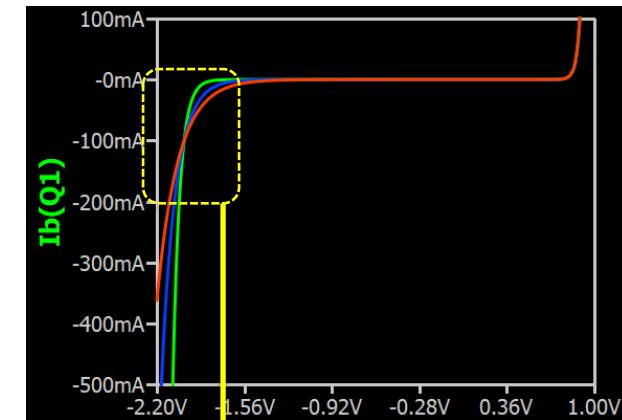
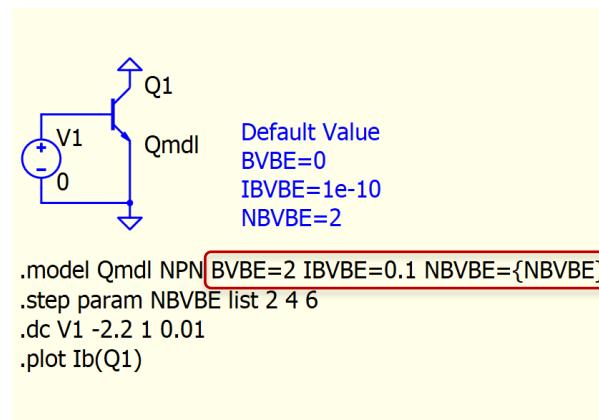
- CJE, MJE and VJE
 - CJE : Zero bias B-E capacitance
 - MJE : B-E junction grading coefficient
 - VJE : B-E junction built in potential
 - **Default CJE=0F**
 - **Default MJE=0.5**
 - **Default VJE=1**



Q. Bipolar Params (B-E Diode) : BVBE, IBVBE, NBVBE

Qspice : NPN - BVBE IBVBE NBVBE.qsch

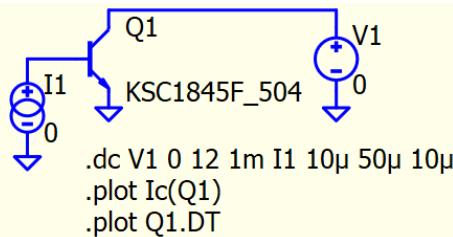
- BVBE, IBVBE, NBVBE
 - Qspice Revision History
 - 12/30/2023 Implemented bipolar B-E breakdown via model parameters BVBE, IBVBE, AND NBVBE.
 - Parameters to model breakdown characteristic of Base-Emitter Diode
 - BVBE : Reverse breakdown voltage
 - IBVBE : Current at breakdown voltage
 - NBVBE : Emission coefficient
 - **Default BVBE=0V**
 - **Default IBVBE=1e-10A**
 - **Default NBVBE=2**



**Q. Bipolar Transistor
(MEXTRAM 504, Level
504 by NXP)**

Q. Transistor (MEXTRAM 504)

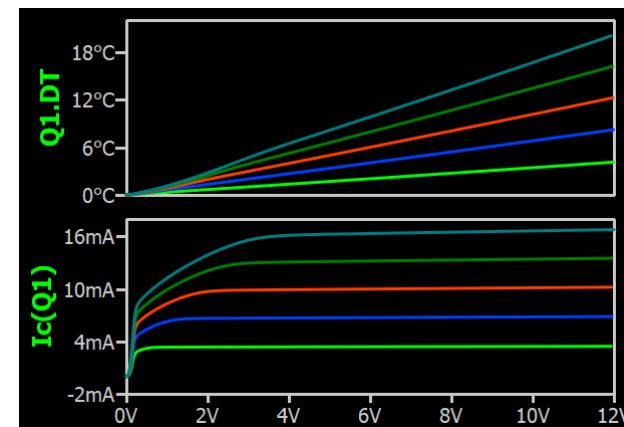
- **MEXTRAM 504**
 - Release history
 - Qspice Revision History : 11/29/2023 Released a MEXTRAM 504(rev 12) implementation
 - <https://forum.qorvo.com/t/models-of-transistors-with-thermal-parameters/15809/5>
 - Comment from Mike Engelhardt
 - It's the current minor revision level, 12
 - It should be able to properly run that model without the collector current going to zero
 - If no self heating node is specified, it will make one called Q1.DT. Otherwise you can make a five terminal transistor and connect a thermal network the temperature node



```

.model KSC1845F_504 npn level=504 is=1.075431e-013 bf=362.1
+ bri=1.3565 vef=267 ver=20.6691 ik=0.25 ibf=1e-012 ibr=1e-012 mlf=2 rbv=144.908
+ rbc=12.092 re=1.5 rcc=1 rcv=150 scrv=225 ihc=1.5m axi=.1 cje=7p cjc=4.525739e-012
+ pe=0.36 pc=0.3659045 vde=0.6 vdc=0.5 taue=250p taub=2.1e-011 af=1 kf=0 vgb=1.1809
+ vgc=1.1809 vgs=-1.1809 v gj=1.1809 exavl=0 wavl=1K Xcje=0.25 Cheo=2p
+ Rth=100 Cth=100n

```



R. Resistor

R. Resistor Instance and Model Parameters

- Resistor Syntax
 - Rnnn N1 N2 [<model>] <resistance> [instance parameters]
 - .model <model> RES [model parameters]

Resistor Instance Parameters

Name	Description	Units	Default
AC	Value to use for .ac analysis	Ω	RESISTANCE
B ¹	NTC coefficient		0.0
CTH ²	Thermal capacitance	F	Model value
RESISTANCE	Resistance	Ω	none
RTH ²	Thermal resistance	Ω	Model value
L ³	Length	m	1.0
W ³	Width	m	1.0
M	Number of identical parallel instances		1.0
TC ¹	Polynomial temperature coefficient list		0.0
TC1 ¹	1nd order temperature coefficient	$^{\circ}\text{C}^{-1}$	0.0
TC2 ¹	2nd order temperature coefficient	$^{\circ}\text{C}^{-2}$	0.0
TEMP	Instance temperature	$^{\circ}\text{C}$	Circuit temperature
TNOM	Temperature resistance was measured(aka TREF)	$^{\circ}\text{C}$	Circuit TNOM

Resistor Model Parameters

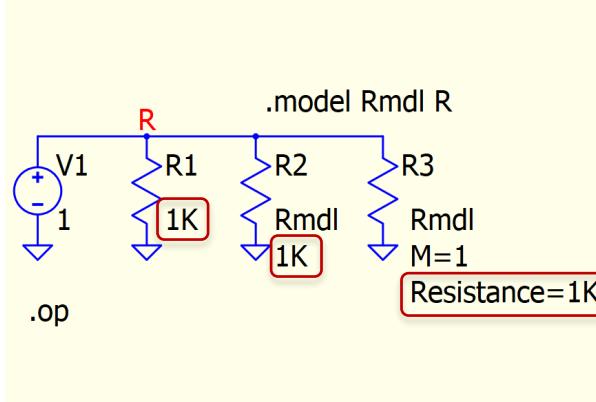
Name	Description	Units	Default
CTH ²	Thermal capacitance	F	0.0
DEFW	Default device width	m	1.0
NARROW ³	Narrowing of resistor	m	1.0
R	Resistor multiplier		1.0
RTH ²	Thermal resistance	Ω	0.0
RSH ³	Sheet resistance(for instance L and W)	Ω/\square	0.0
TC ¹	Polynomial temperature coefficient list		0.0
TC1 ¹	1nd order temperature coefficient	$^{\circ}\text{C}^{-1}$	0.0
TC2 ¹	2nd order temperature coefficient	$^{\circ}\text{C}^{-2}$	0.0
TCE ¹	Exponential order temperature coefficient	$^{\circ}/\text{C}$	0.0
TNOM	Parameter measurement temperature(aka TREF)	$^{\circ}\text{C}$	Circuit TNOM

R. Resistor – Resistance and AC

Qspice : R - Resistance.qsch | R - AC.qsch

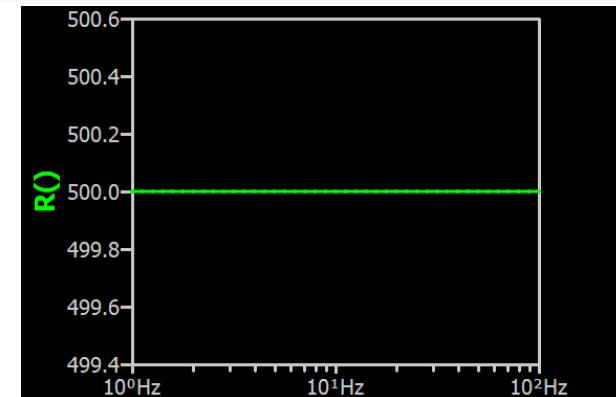
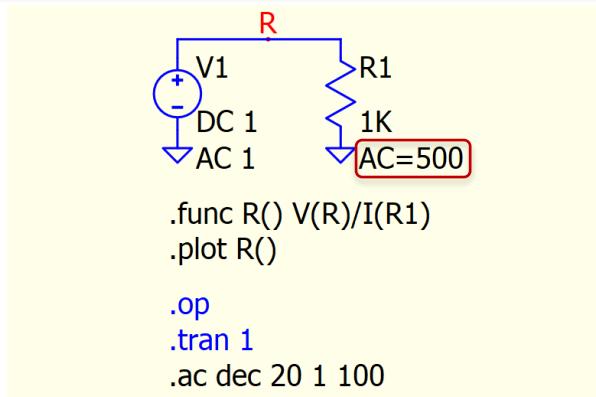
- Resistance

- Resistance can be specified in three way
 - #1 : Resistance value at 1st attribute
 - #2 : <model> at 1st attribute and resistance value at 2nd attribute
 - #3 : <model> at 1st attribute, resistance value after 2nd attribute with **Resistance=<value>**



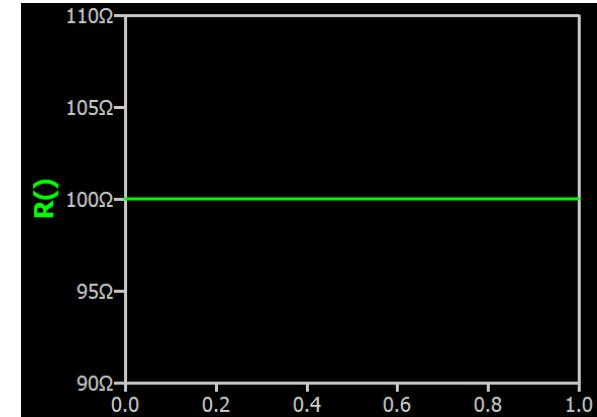
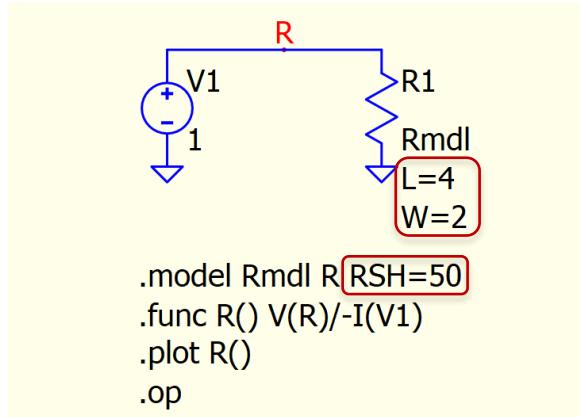
- AC

- Value to use for .ac analysis
- **Default = RESISTANCE**
- In this example, .op or .tran set R1=1Kohms but .ac set R1=500ohms



R. Resistor – RSH, L and W (Sheet Resistance)

- RSH, L and W
 - RSH : Sheet Resistance
 - L : Length
 - W : Width
 - RSH is model param and L, W are instance params
 - If RESISTANCE is defined, RSH, L and W will be ignored
 - Sheet resistance is the resistance of a square of the conductive thin film with uniform thickness
 - $R = R_{SH} \times \frac{L}{W}$



R. Resistor – Thermal Related Parameters

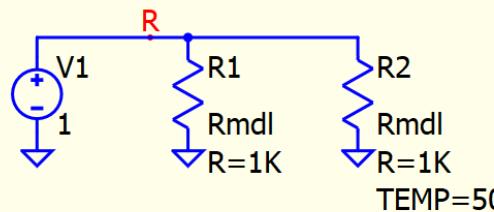
- Resistor Thermal Equation
 - Formula with temperature coefficient list TC : $R_T = R_{nom}(1 + \sum T_{Cn}\Delta T^n)$
 - TC supports a list of temperature coefficient in format TC=<value1>,<value2>,<value3>,...
 - Formula with temperature coefficient TC1 and TC2 : $R_T = R_{nom}(1 + T_{C1}\Delta T + T_{C2}\Delta T^2)$
 - Formula with temperature coefficient TCE : $R_T = R_{nom} e^{\frac{T_{CE}}{100} \Delta T}$
 - Formula with B (or beta) for thermistor (NTC) : $R_T = R_{nom} e^{B \times \left(\frac{1}{T} - \frac{1}{T_{nom}}\right)}$
 - where Temperature in above formula is in Kelvin, $\Delta T = T - T_{nom}$

R. Resistor Params : Tnom and TEMP (Instance param), TC

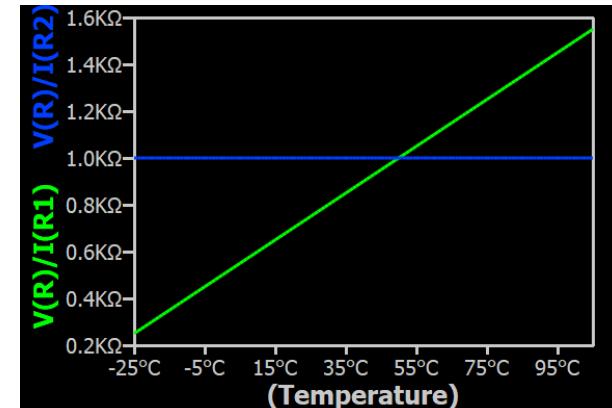
Qspice : R - TNOM TEMP.qsch | R - TC.qsch

Tnom and TEMP

- Tnom : Parameter measurement temperature
- TEMP : Instance temperature in Instance param
- **Default Tnom=27oC**
- **Default TEMP=Circuit** Temperature
- In this example, instance temperature TEMP is assigned for R2, which forced R2 at TEMP instead of circuit temperature

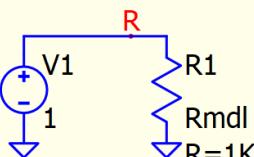


```
.model Rmdl R Tnom=50 TC1=0.01  
.plot V(R)/I(R1) V(R)/I(R2)  
.dc Temp -25 105 1  
.op
```

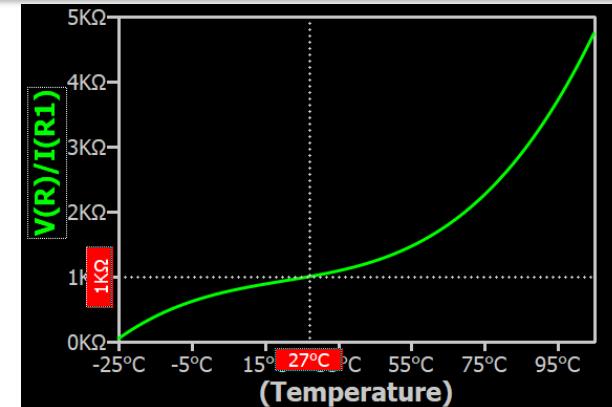


TC

- TC : Polynomial temperature coefficient list
- **Default TC=0**
- $TC = <value1>, <value2>, <value3>, \dots$
- $R_T = R_{nom}(1 + \sum T_{cn} \Delta T^n)$
- where Tnom is R defined measurement temperature



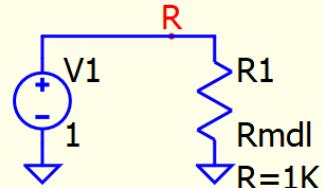
```
.model Rmdl R TC=0.01,0.0001,0.000005  
.plot V(R)/I(R1)  
.dc Temp -25 105 0.001  
.op
```



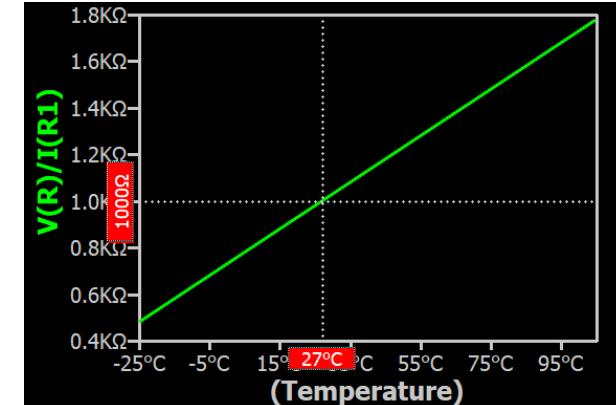
R. Resistor Params : TC1 and TC2

Qspice : R - TC1.qsch / R - TC2.qsch

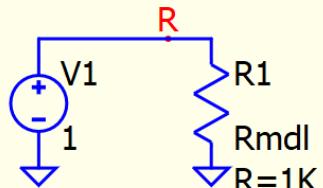
- TC1
 - TC1 : 1nd order temperature coefficient
 - **Default TC1=0°C⁻¹**
 - $RT = R * (1 + TC1 * (T - T_{nom}))$
 - Where T_{nom} is R defined measurement temperature



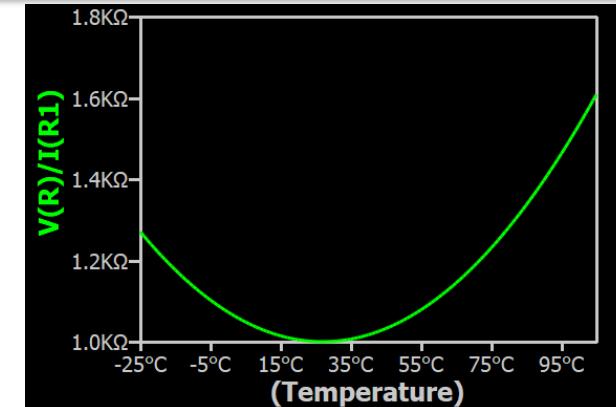
```
.model Rmdl R TC1=0.01  
.plot V(R)/I(R1)  
.dc Temp -25 105 0.001  
.op
```



- TC2
 - TC2 : 2nd order temperature coefficient
 - **Default TC2=0°C⁻²**
 - $RT = R * (1 + TC2 * (T - T_{nom})^2)$
 - TC2 and TC1 can be used together



```
.model Rmdl R TC2=0.0001  
.plot V(R)/I(R1)  
.dc Temp -25 105 1  
.op
```

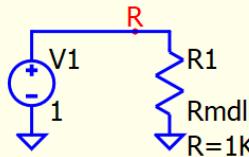


R. Resistor Instance Param : TCE and B for Thermistor (NTC)

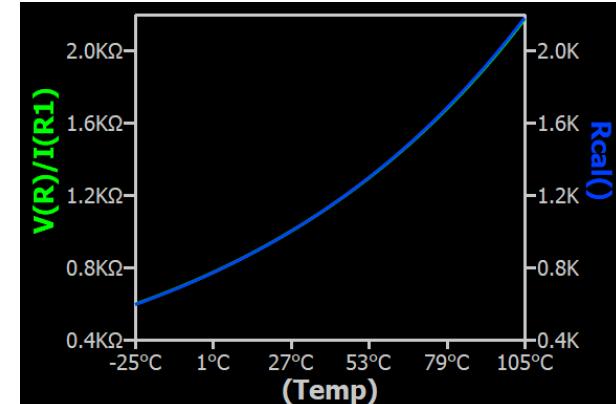
Qspice : R - TCE.qsch | R - B.qsch

TCE

- TCE : Exponential order temperature coefficient
- **Default TCE=0%/ $^{\circ}\text{C}$**
- $R_T = R_{\text{nom}} \exp((T-T_{\text{nom}})/100 \cdot \text{TCE})$
- If TCE is specified non-zero, TC1 and TC2 are ignored

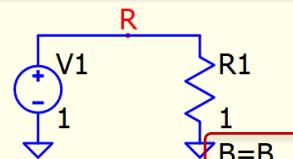


```
.model Rmdl R TCE=1  
.plot V(R)/I(R1) Rcal()  
.dc Temp -25 105 1  
.step param Temp -25 105 1  
.op  
.func Rcal() 1K*exp((Temp-27)/100*1)
```

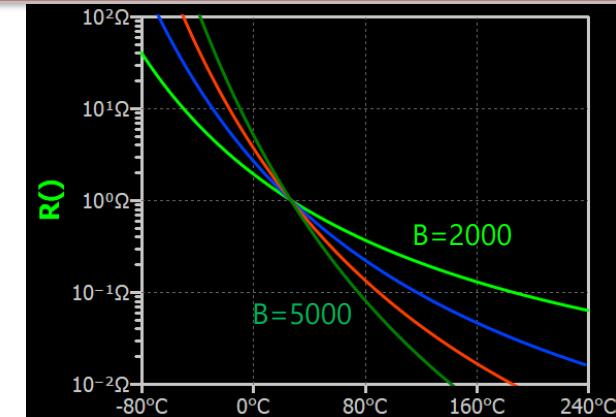


B (for thermistor/NTC)

- NTC Coefficient
- **Default B=0**
- $R_T = R_{\text{nom}} e^{B \times \left(\frac{1}{T} - \frac{1}{T_{\text{nom}}}\right)}$
- Refer to TDK NTC thermistor general information, B value of common NTC materials range is from 3000 to 5000



```
.op  
.step param TEMP -80 240 1  
.step param B 2000 5000 1000  
.func R() V(R)/I(R1)  
.plot R()
```

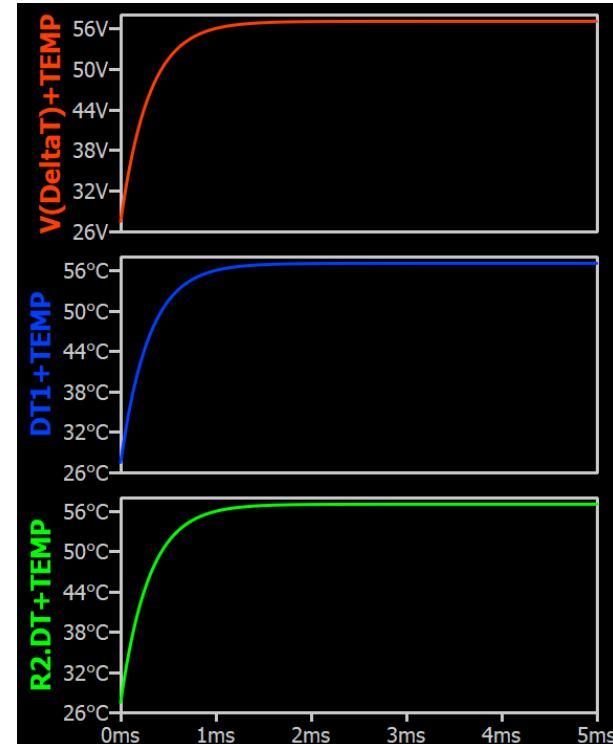
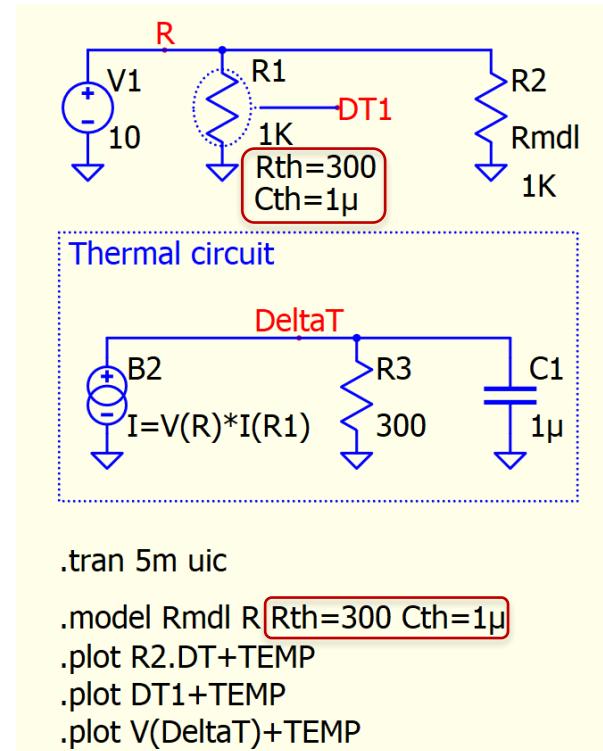


R. Resistor Params : Rth and Cth (Thermal Resistance and Capacitance)

Qspice : R - Rth Cth (Thermal Circuit).qsch

- RTH and CTH

- RTH : Thermal Resistance
- CTH : Thermal Capacitance
- **Default RTH=0**
- **Default CTH=0**
- Cth and Cth supports both instance (e.g. R1) and .model parameters (e.g. R2)
- DT (Delta Temperature ΔT)
 - DT is rise in temperature above ambient of resistor
 - 3-terminal resistor (3rd node in square braces) : ΔT is returned at 3rd node
 - 2-terminal resistor : ΔT is returned as Rnnn.DT

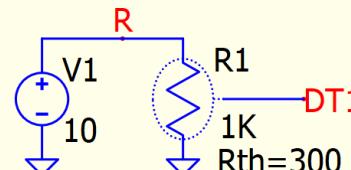


R. Resistor Params : Rth and Cth (Thermal Resistance and Capacitance)

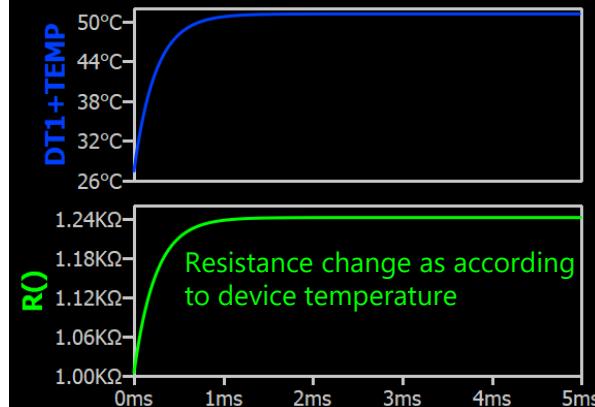
Qspice : R - Rth Cth (Self Heating).qsch

- Self Heating Resistor
 - This is an example for resistor with positive temperature coefficient
 - Resistance and temperature relationship is controlled by temperature coefficient TC. Rth and Cth determine thermal response to achieve self heating simulation

Self Heating Resistor Modeling

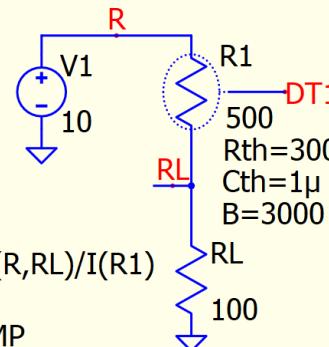


```
.tran 5m uic  
.func R() V(R)/I(R1)  
.plot R()  
.plot DT1+TEMP
```

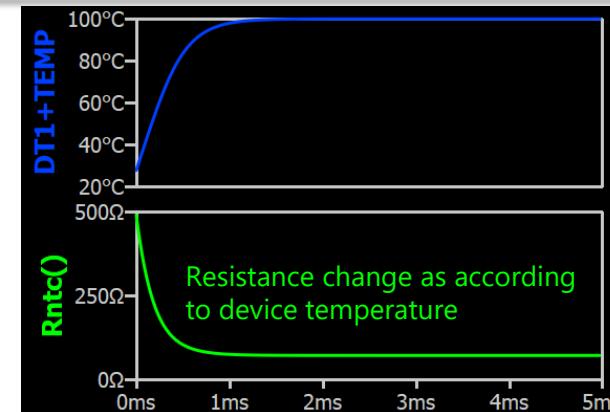


- Thermistor Self Heating
 - This example use NTC coefficient B to setup a thermistor for self heating simulation
 - A loading resistor is required to limit maximum current for simulation to reach steady state with using NTC

Self Heating Thermistor Modeling



```
.tran 5m uic  
.func Rntc() V(R,RL)/I(R1)  
.plot Rntc()  
.plot DT1+TEMP
```



R. Resistor : Behavioral Resistor (R)

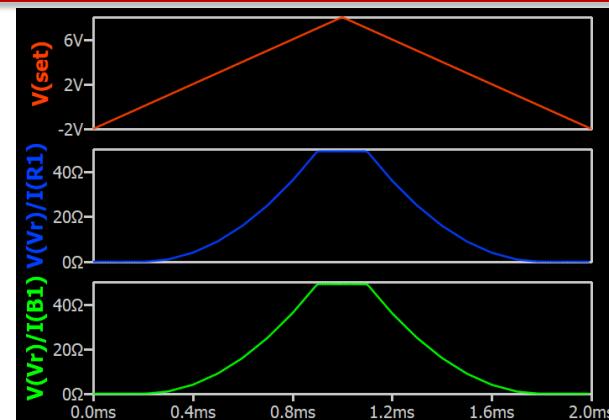
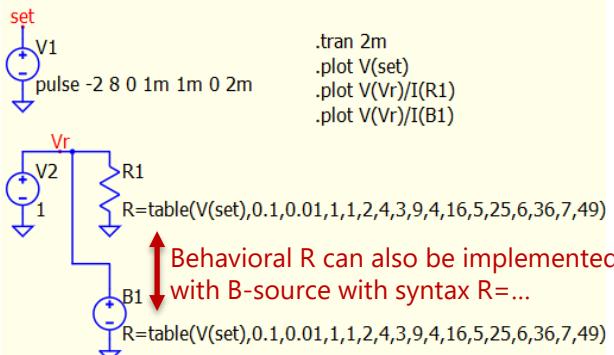
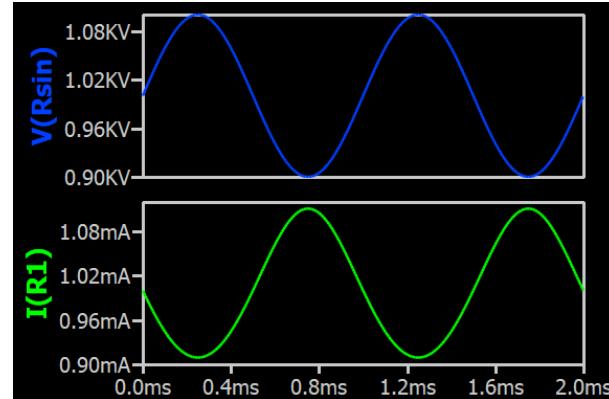
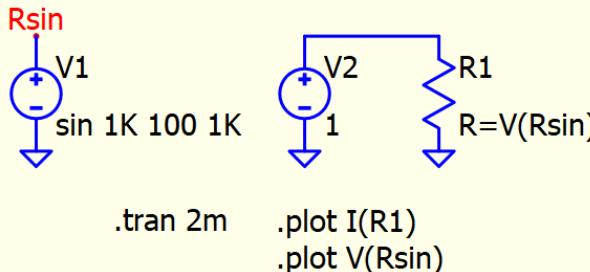
Qspice : R - Behavioral R Demo 01.qsch | R - Behavioral R Demo 02.qsch

- Behavioral Resistor

- To use formula or voltage/current node for resistance, type $R=...$ in $<\text{val}>$ of resistor
- Also support to use Behavioral source (B) for behavioral resistor

- Replace $V=\text{expression}$ with $R=\text{expression}$

Behavioral Resistance with $R=$ <eqn>



S. Voltage Controlled Switch

S. Voltage Controlled Switch Model Parameters

- S. Voltage Controlled Switch Model Parameters
 - It is common to define Switch Model for usage as multiple switches in a schematic
 - Syntax: Snnn N1 N2 NC+ NC- <model> [instance parameters]
 - .model <model> SW [model parameters]

Voltage Controlled Switch Model Parameters

Name	Description	Units	Default
ETA ¹	Sub-/over-Threshold conduction	V	0.0
ROFF	Off resistance	Ω	1e6
RON	On resistance	Ω	1.0
TTOL	Temporal tolerance	sec	1e308
VH	Hysteresis voltage	V	0.0
VOFF	Voltage when open	V	0.0
VON	Voltage when closed		
VT	Threshold voltage		

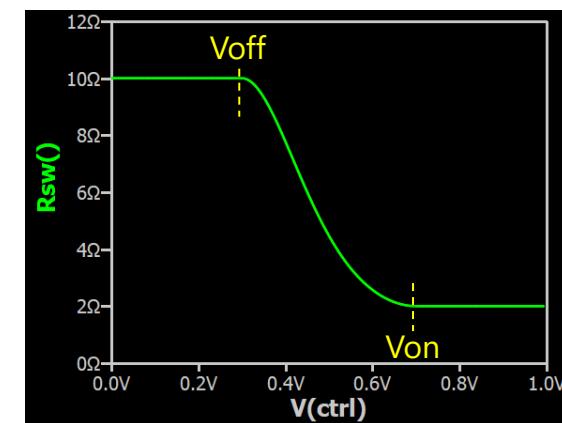
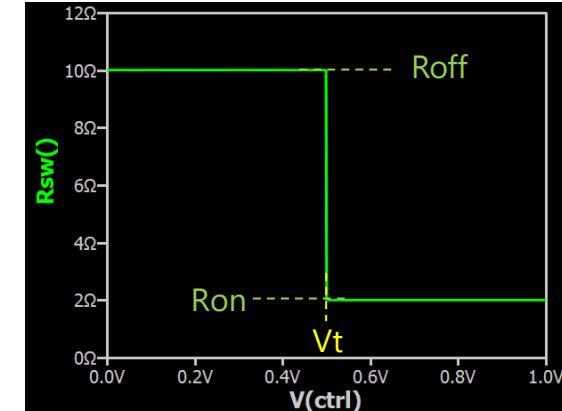
S. Switch Model Params : Ron, Roff, VT, Von and Voff

Qspice : Switch - Ron Roff VT.qsch

- RON, ROFF, VT
 - Ron : On resistance
 - Roff : Off resistance
 - VT : Threshold voltage
 - **Default RON=1Ω**
 - **Default ROFF=1MegΩ**
 - **Default VT=0V**
- VON, VOFF
 - Von : Voltage when closed
 - Voff : Voltage when open
 - **Default VON=0V**
 - **Default VOFF=0V**
 - switch smoothly transitions between on and off
 - If VT and VH are specified, VON and VOFF are ignored

```
.model mSW SW Ron=2 Roff=10 Vt=0.5 VH=0
pulse 0 1 0 1 1 1 4
.tran 4
.func Rsw() V(sw)/I(I1)
.plot Rsw()
.plot V(ctrl)
```

```
.model mSW SW Ron=2 Roff=10 Von=0.7 Voff=0.3
pulse 0 1 0 1 1 1 4
.tran 4
.func Rsw() V(sw)/I(I1)
.plot Rsw()
.plot V(ctrl)
```



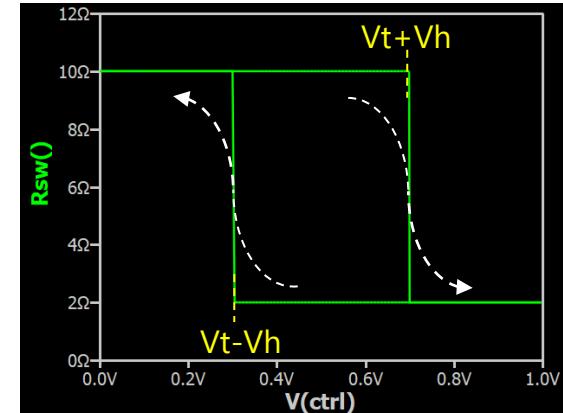
S. Switch Model Params : VH

Qspice : Switch - VH.qsch

- VH
 - V_h : Hysteresis voltage
 - **Default VH=0V**
 - Switch is ON
 - $V(+)-V(-) > V_t + V_h$
 - Switch is OFF
 - $V(+)-V(-) < V_t - V_h$
 - Switch maintain its state
 - $V_t - V_h < V(+)-V(-) < V_t + V_h$

```
.model mSW SW Ron=2 Roff=10 Vt=0.5 Vh=0.2  
+ve Vh
```

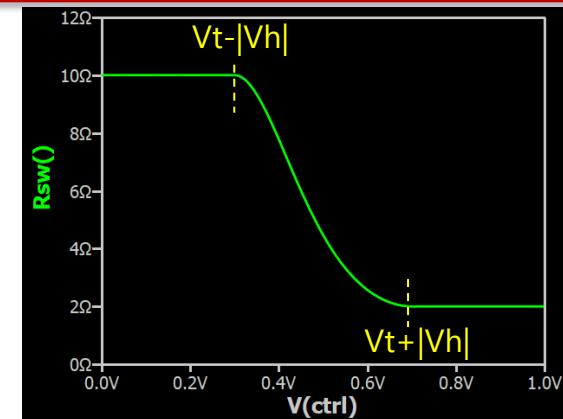
```
pulse 0 1 0 1 1 1 4  
.tran 4  
.func Rsw() V(sw)/I(I1)  
.plot Rsw()  
.plot V(ctrl)
```



- VH (-ve explained)
 - Negative V_h
 - If V_H is negative the switch smoothly transitions between on and off

```
.model mSW SW Ron=2 Roff=10 Vt=0.5 Vh=-0.2  
-ve Vh
```

```
pulse 0 1 0 1 1 1 4  
.tran 4  
.func Rsw() V(sw)/I(I1)  
.plot Rsw()  
.plot V(ctrl)
```



S. Switch Model Params : (VON, VOFF) vs (VT, VH)

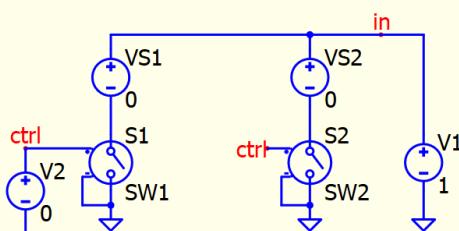
- Change between [VON, VOFF] and [VT, VH]
 - Important Note
 - VH must be negative for smooth transition
 - VON and VOFF is Pspice syntax which must be a smooth transition
 - For VON > VOFF
 - $VT = (VON + VOFF)/2$
 - $VH = |VON - VOFF|/2 * (-1)$: negative for smooth transition
 - For discrete switching action, remove the negative sign, but this is not an exact equivalent change.
 - For VON < VOFF
 - VT and VH : Same as above
 - Swap ROFF and RON

S. Switch Model Params : (VON, VOFF) vs (VT, VH)

Qspice : Switch - VH neg formula.qsch

- Formula in Smooth Transition Region

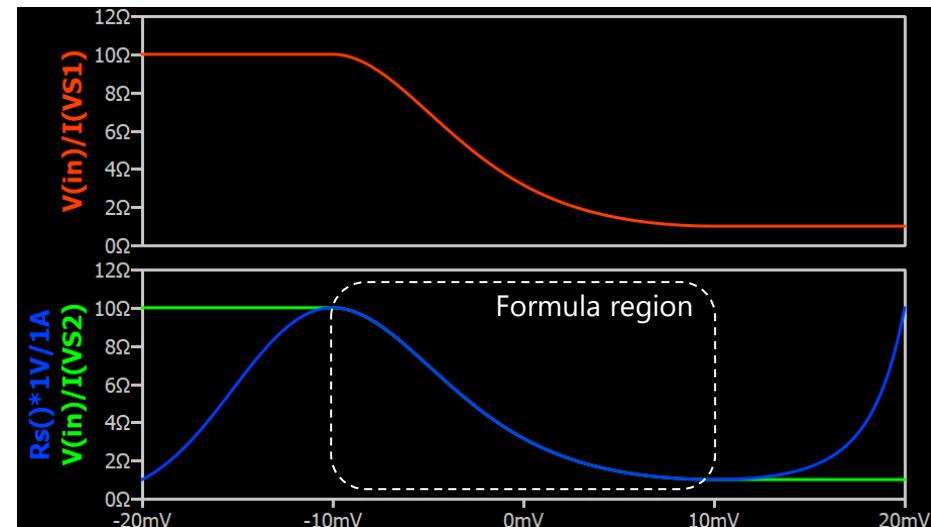
- $L_m = \ln(\sqrt{R_{ON} \times R_{OFF}})$, $L_r = \ln\left(\frac{R_{ON}}{R_{OFF}}\right)$, $V_m = \frac{V_{ON}+V_{OFF}}{2}$, $V_d = V_{ON} - V_{OFF}$
- For $V_{ON} > V_{OFF}$: $R_s = e^{L_m + \frac{3 L_r (V_c - V_m)}{2 V_d} - 2 L_r \left(\frac{V_c - V_m}{V_d}\right)^3}$
- For $V_{ON} < V_{OFF}$: $R_s = e^{L_m - \frac{3 L_r (V_c - V_m)}{2 V_d} + 2 L_r \left(\frac{V_c - V_m}{V_d}\right)^3}$



```

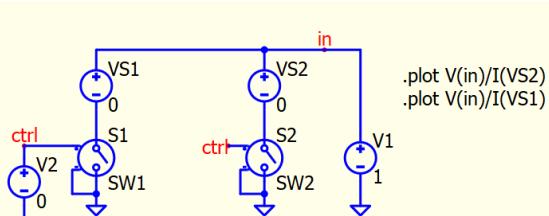
.model SW1 SW ROFF=10 RON=1 Vt=Vt Vh=Vh
.model SW2 SW ROFF=Roff RON=Ron VOFF=Voff VON=Von
.dc V2 -20m 20m 0.1m
.func Lm() ln(sqrt(Ron*Roff))
.func Lr() ln(Ron/Roff)
.func Vm() (Von+Voff)/2
.func Vd() (Von-Voff)
.func Rs() exp(Lm() + 3*Lr()*(V(ctrl)-Vm())/(2*Vd()) - 2*Lr()*((V(ctrl)-Vm())/Vd())^3)
.plot V(in)/I(VS2) Rs()*1V/1A
.plot V(in)/I(VS1)
.param Roff=10
.param Ron=1
.param Voff=-10m
.param Von=10m
.param Vt=(Von+Voff)/2
.param Vh=abs(Von-Voff)/2*-1

```



S. Switch Model Params : (VON, VOFF) vs (VT, VH)

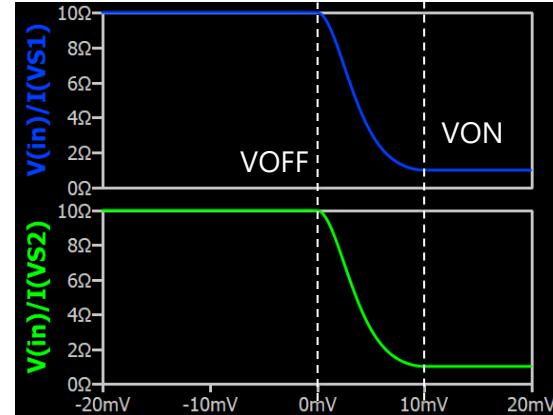
Qspice : Switch - Von Voff VT VH.qsch



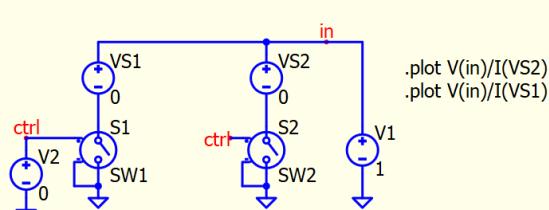
```
.model SW1 SW ROFF=10 RON=1 Vt=5m Vh=-5m
.model SW2 SW ROFF=10 RON=1 VOFF=0 VON=10m

.model SW1 SW ROFF=1E12 RON=10m Vt=5m Vh=-5m
.model SW2 SW ROFF=1E12 RON=10m VOFF=0 VON=10m

.dc V2 -20m 20m 0.1m
```



- Two examples

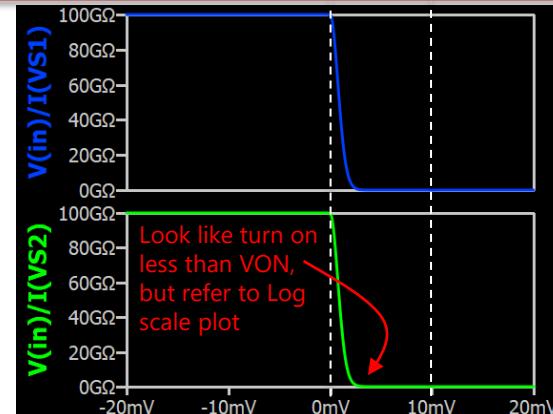


```
.model SW1 SW ROFF=10 RON=1 Vt=5m Vh=-5m
.model SW2 SW ROFF=10 RON=1 VOFF=0 VON=10m

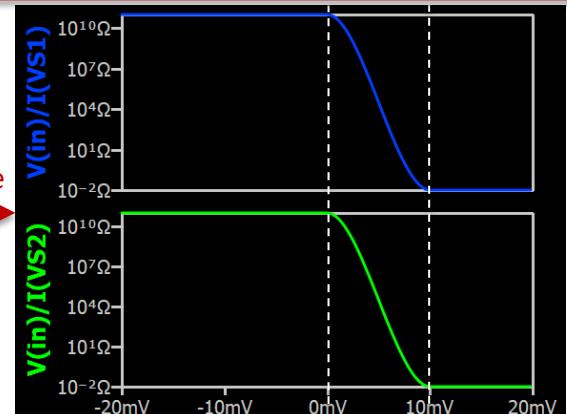
.model SW1 SW ROFF=1E12 RON=10m Vt=5m Vh=-5m
.model SW2 SW ROFF=1E12 RON=10m VOFF=0 VON=10m

.dc V2 -20m 20m 0.1m
```

ROFF and RON is extreme



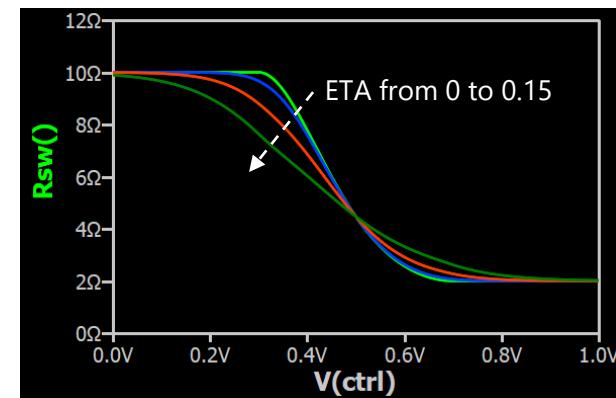
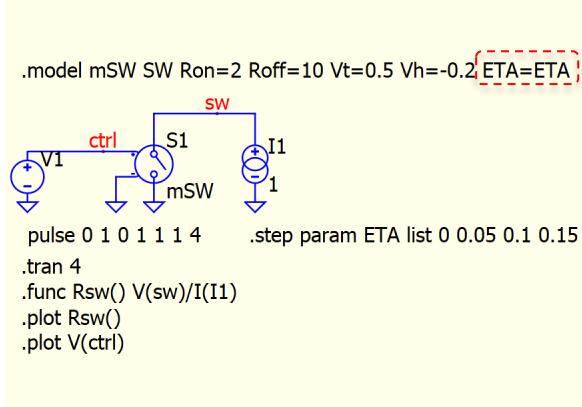
LOG Scale



S. Switch Model Params : ETA

Qspice : Switch - ETA.qsch

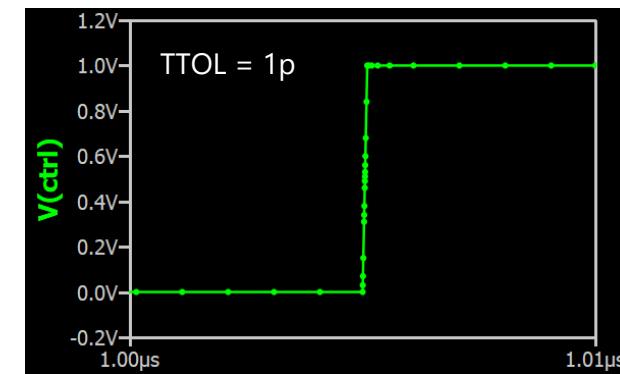
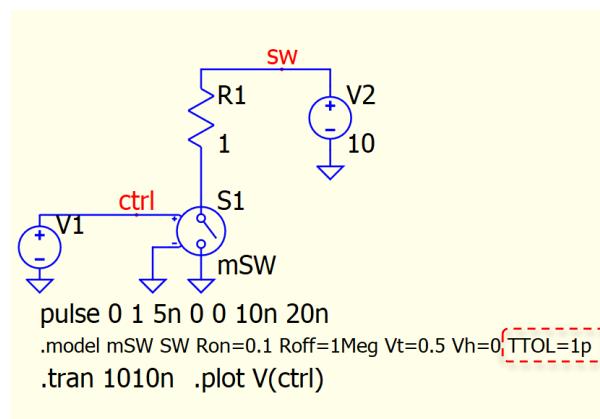
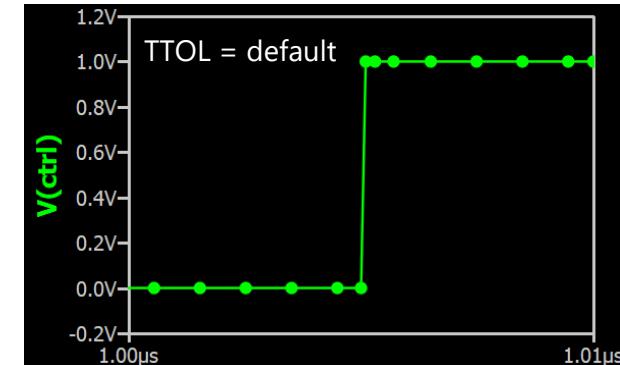
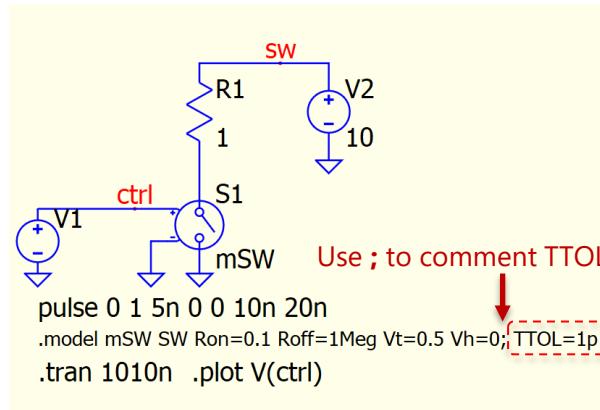
- **ETA**
 - ETA : Sub-/over- Threshold conduction
 - **Default ETA=0**
 - Prevents the control voltage Jacobian from vanishing
 - Only effective in smoothly transitions cases
 - V_t is negative
 - V_{on} / V_{off} are used without V_t and V_h



S. Switch Model Params : TTOL

Qspice : Switch - TTOL.qsch

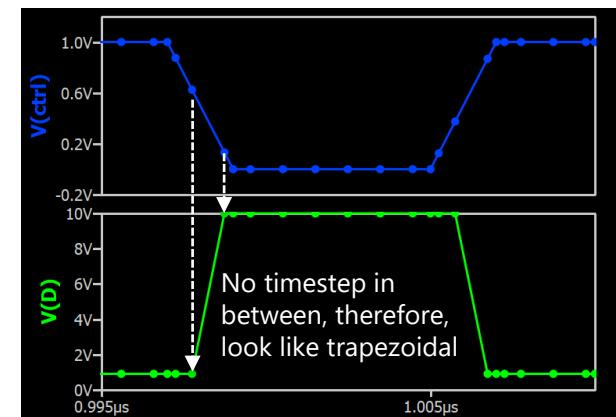
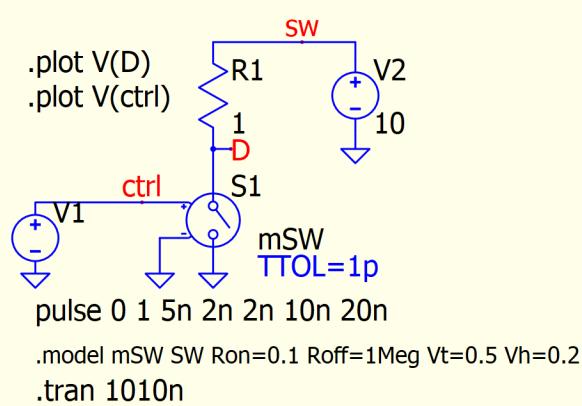
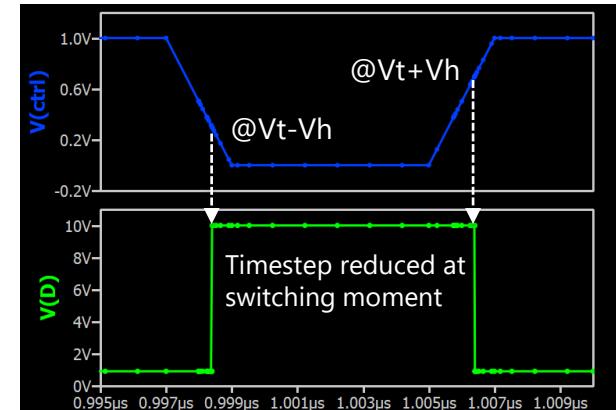
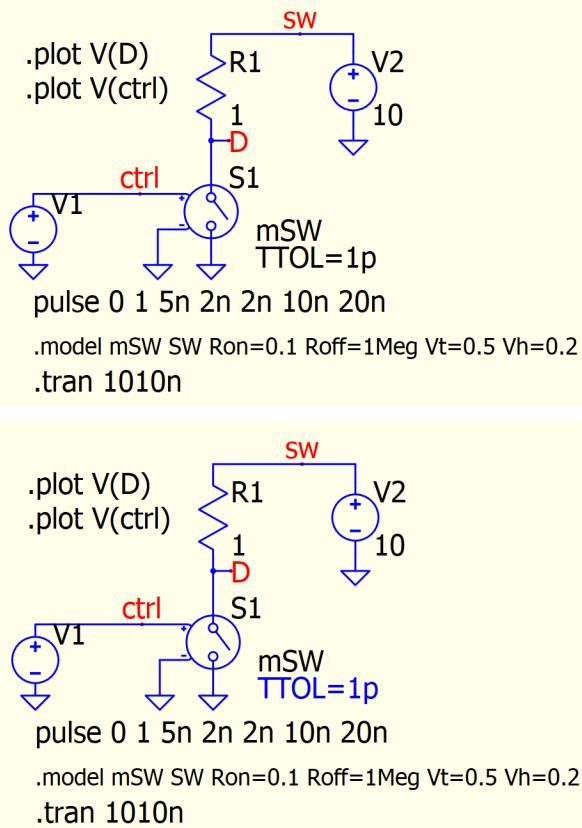
- TTOL
 - Ttol : Temporal tolerance
 - **Default TTOL=1e308s**
- Usage
 - TTOL allows one to determine how accurately the switch time should be found
 - It only affect timestep at switch time, which maintain simulation speed but improve accuracy at switching or logic action



S. Switch Model Params : TTOL (with VH hysteresis)

Qspice : Switch - TTOL with VH.qsch

- TTOL
 - Ttol : Temporal tolerance
 - **Default TTOL=1e308s**
- With Vh hysteresis
 - Extra timestep occurs according to switching action with hysteresis
 - ** TTOL may not response to negative Vh (-Vh) as switch is defined as smoothly transit instead of discrete state



T. Lossless Transmission Line

T. Lossless Transmission Line Instance Parameters

- T. Lossless Transmission Line
 - Syntax: Tnnn L+ L- R+ R- Zo=<value> Td=<value>

Lossless Transmission Line Instance Parameters

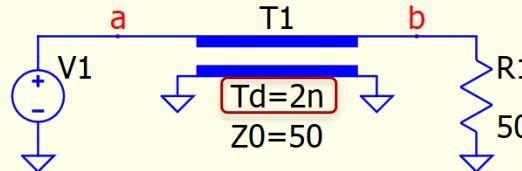
Name	Description	Units	Default
F ¹	Frequency	Hertz	1GHz
NL ¹	Normalized length at frequency given	wavelengths	1/4
TD	Transmission delay	sec	
Z0	Characteristic impedance(aka ZO)	Ω	50 Ω

T. Instance Params : TD, F and NL

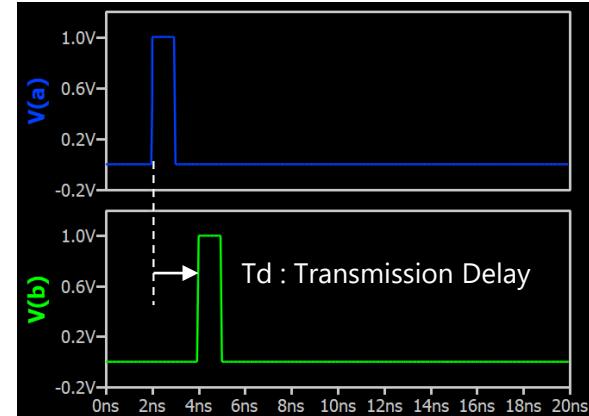
Qspice : Tline - Td.qsch ; Tline - F NL.qsch

- TD and Z0

- Td : Transmission delay
- Z0 : Characteristic Impedance
- **Default TD is not set**
- **Default Z0=50Ω**
- This simulation terminate transmission line with characteristic impedance Z0, no reflection of signal
- If TD is given, F and NL are ignored



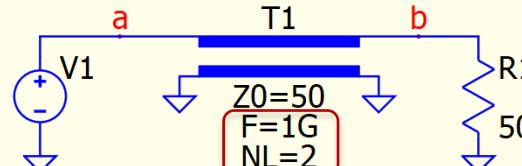
```
pulse 0 1 2n 0 0 1n 1 1  
.options MAXSTEP=1p  
.tran 20n  
.plot V(b)  
.plot V(a)
```



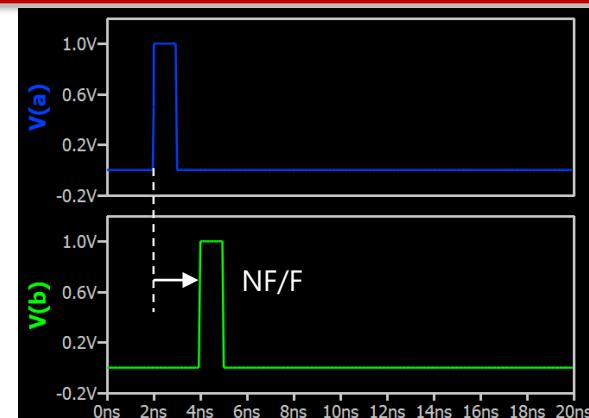
- F and NL

- F : Frequency
- NL : Normalized length at frequency given
- **Default F=1GHz**
- **Default NL=1/4**
- Equation

$$\begin{aligned} NL &= \frac{Length}{Wavelength} = \frac{Length}{\lambda} \\ \text{Period per } \lambda &: T = \frac{1}{F} \\ \text{Delay } T_d &= T \times \frac{Length}{\lambda} = \frac{NL}{F} \end{aligned}$$



```
pulse 0 1 2n 0 0 1n 1 1  
.options MAXSTEP=1p  
.tran 20n  
.plot V(b)  
.plot V(a)
```



V. Voltage Source

V. Voltage Source - Instance Params

- V. Voltage Source
 - Syntax: Vnnn N+ N- <voltage> [Additional Instance Parameters]

Voltage Source Instance Parameters				
Name	Description	Units	Default	
AC	AC magnitude, optionally followed by phase angle	V, °	0.	
ACMAG	AC Magnitude	V	0.	
ACPHASE	AC Phase	°	0.	
DC	DC source value	V	0.	
EXP	Exponential source description			
LOG	Interpolate between PWL and CHIRP points		(not set)	
PULSE	Pulse description			
PWL	Piecewise linear description			
RSER	Internal series resistance			
SFFM	Single frequency FM description			
SINE	Sinusoidal source description(aka SIN)			
TIMECTRL	Time step control, one of NONE, LIMITS ¹ , BREAKS ² , BOTH	String	LIMITS	
TIME_SCALE_FACTOR	Multiplies times, divides frequencies		1.	
VALUE_SCALE_FACTOR	Multiplies voltages		1.	
XTRAP	Extrapolate beyond PWL and CHIRP points		(not set)	

V. Voltage Source (Instance Params) : DC

- DC
 - DC source value
 - This DC value is used in .dc analysis
 - Special Usage
 - For pulse in .tran, DC value can define voltage before Tdelay or at 0s
 - Without DC, this voltage equals <value1> in pulse

```
.tran 3  
.param Td=1  
.plot V(pulse-WithDC)  
.plot V(pulse-WithoutDC)
```

pulse-WithoutDC **Special Usage in Pulse**

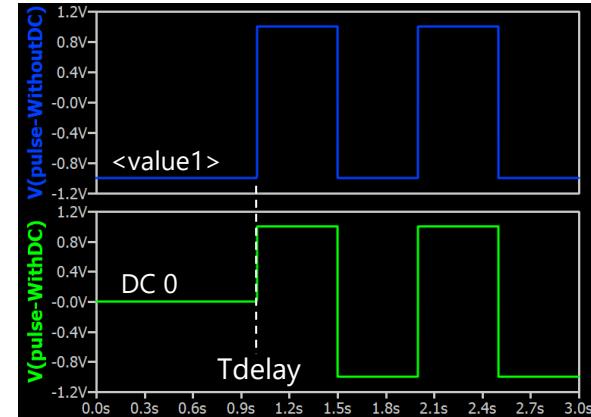


pulse -1 1 Td 0 0 0.5 1

pulse-WithDC



DC 0

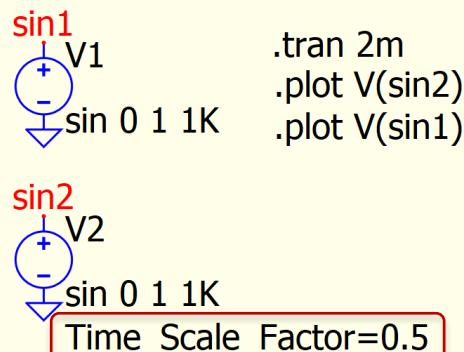


V. Voltage Source (Instance Params) : Time/Value_Scale_Factor

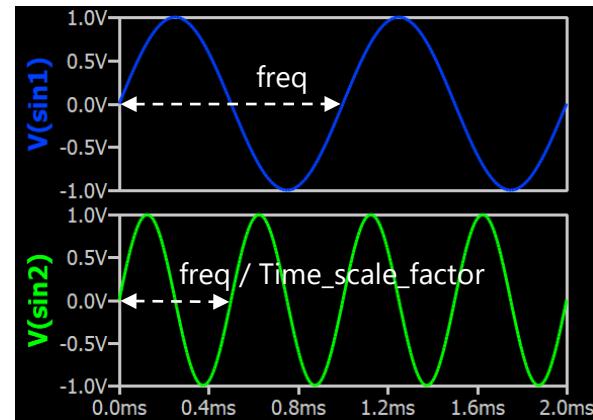
Qspice : Vsource - Time_Scale_Factor.qsch / Vsource - Value_Scale_Factor.qsch

- TIME_SCALE_FACTOR

- Time_Scale_Factor : multiples times, divides frequency
- Default Time_Scale_Factor=1

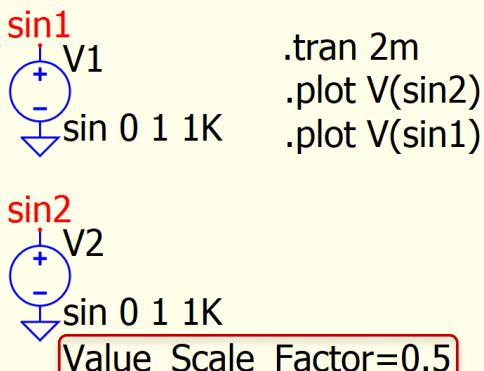


.tran 2m
.plot V(sin2)
.plot V(sin1)

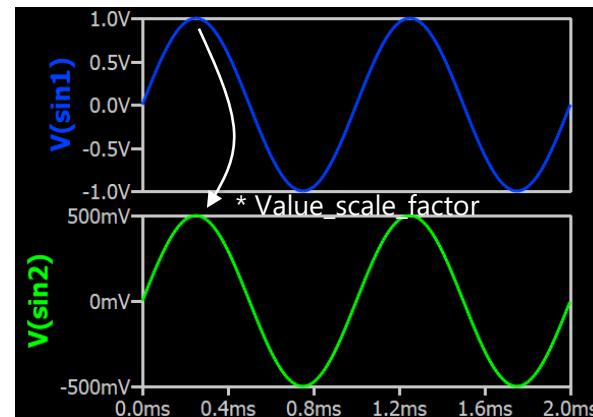


- VALUE_SCALE_FACTOR

- Value_Scale_Factor : multiples voltages
- Default Value_Scale_Factor=1



.tran 2m
.plot V(sin2)
.plot V(sin1)

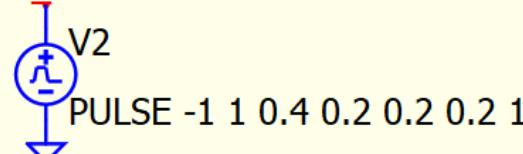


V. Voltage Source : PULSE (Pulse)

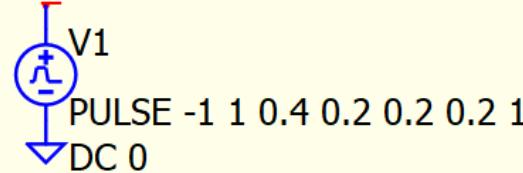
Qspice : Vsource PULSE.qsch

Syntax : PULSE V1 V2 Td Trise Tfall Ton Tperiod

pulse_woDC

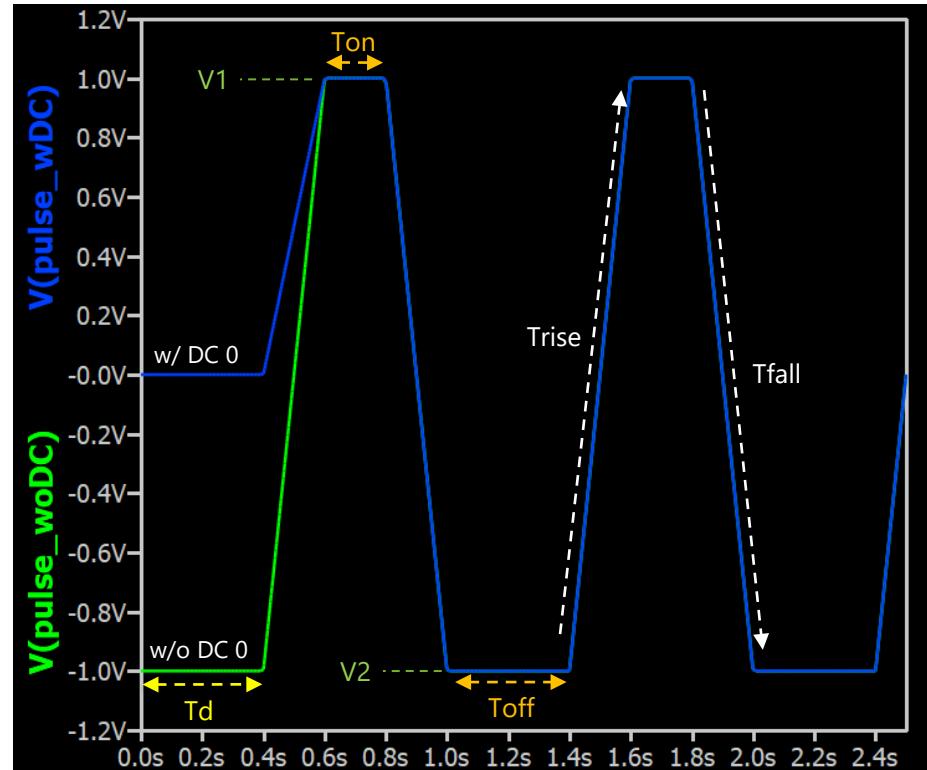


pulse_wDC



.tran 2.5

.plot V(pulse_woDC) V(pulse_wDC)



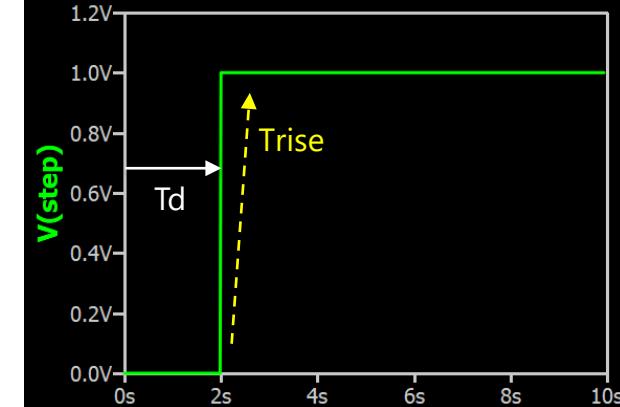
V. Voltage Source : PULSE (Pulse) : Usage

Qspice : Vsource PULSE-Step.qsch / Vsource PULSE-SinglePulse.qsch

- Step with PULSE
 - To generate a step, only input value to **Trise**

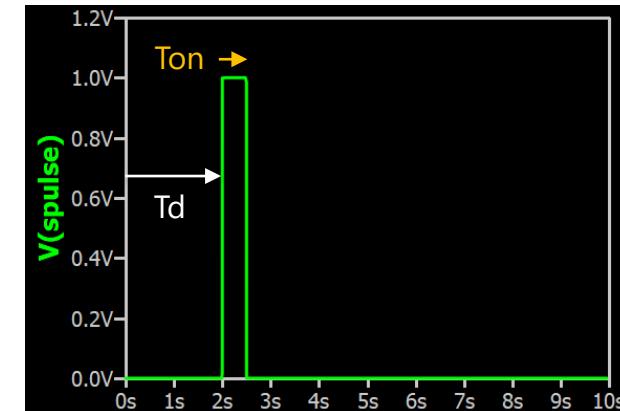
step
V2
 PULSE V1 V2 Td Trise
pulse 0 1 2 0

.tran 10
.plot V(step)



- Single Pulse with PULSE
 - To generate a single non-repeating pulse, does not specify **Tperiod** in pulse statement

spulse
V1
 pulse 0 1 2 0 0 0.5
PULSE V1 V2 Td Trise Tfall Ton
.tran 10
.plot V(spulse)

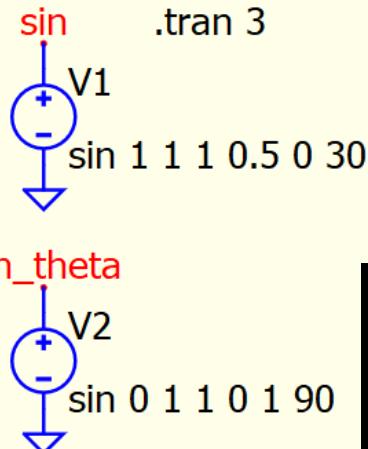


V. Voltage Source : SIN (Sine Wave)

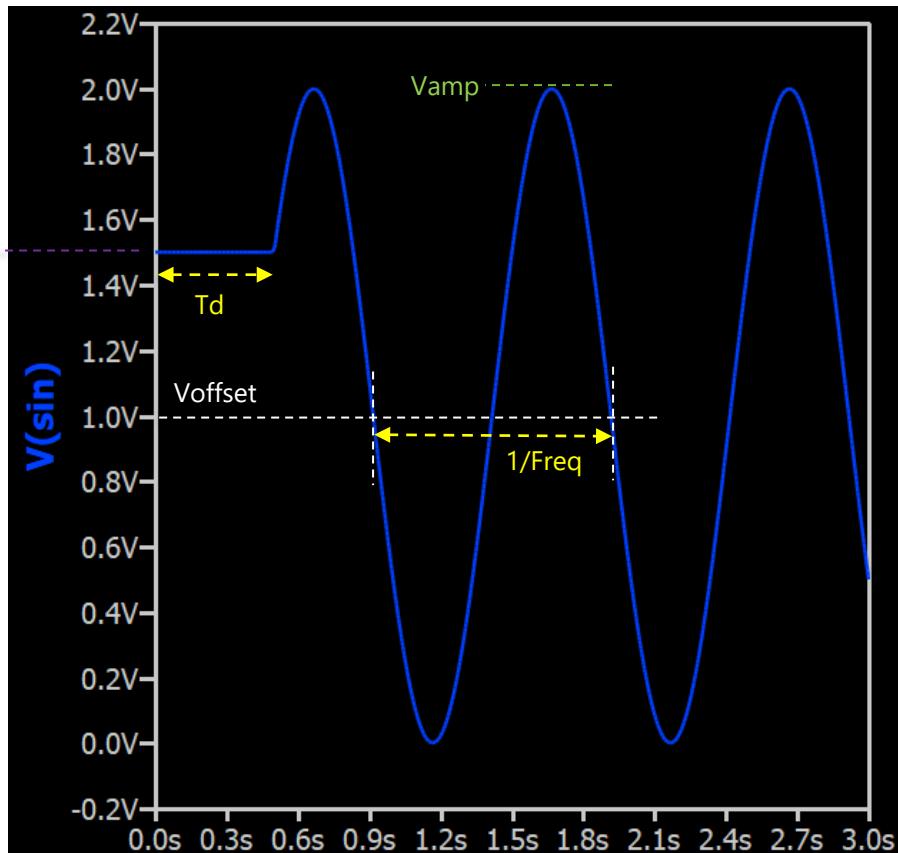
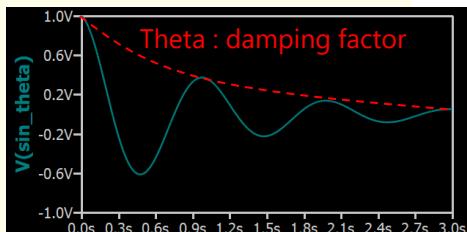
Qspice : Vsource SIN.qsch

Phi : level = $V_{offset} + \sin(\Phi)$
e.g.: $=1+\sin(30^\circ) = 1.5$

Syntax : SIN Voffset Vamp Freq Td Theta Phi



Amplitude drops by $e^{-1} \sim 0.378$ in $1/\Theta$ seconds



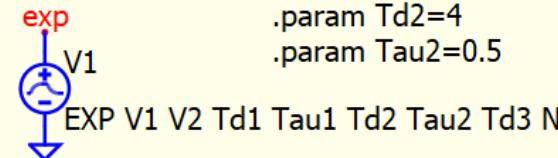
V. Voltage Source : EXP (Exponential)

Qspice : Vsource EXP.qsch

```
.plot V(expTperiod) V(exp)
```

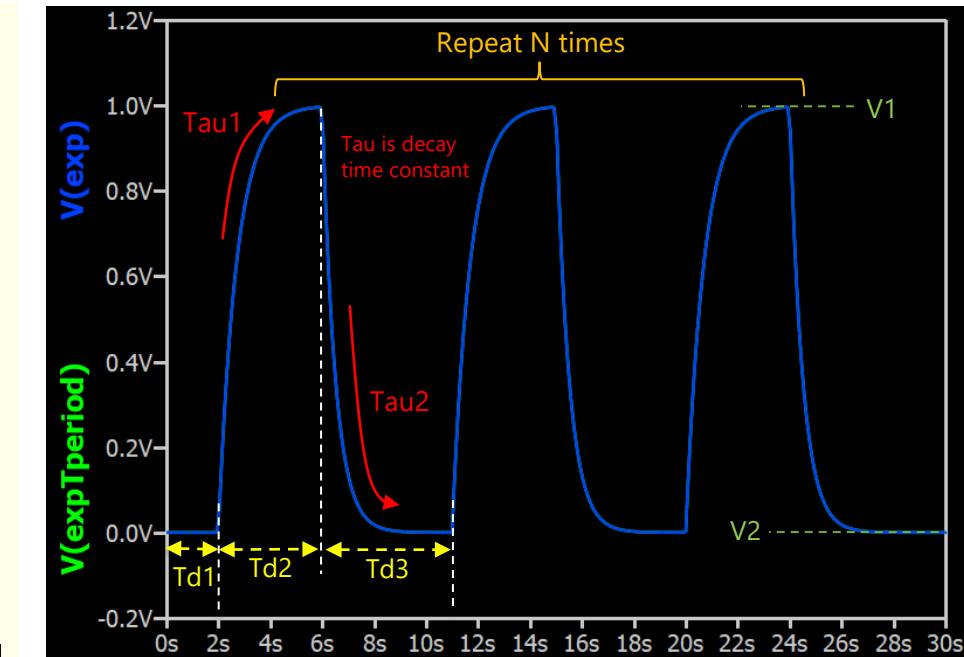
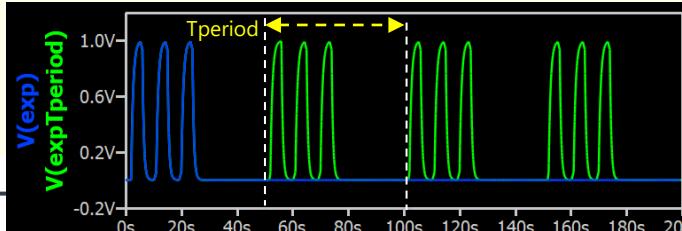
Syntax : EXP V1 V2 Td1 Tau1 Td2 Tau2 Td3 N Tperiod

```
.tran 200          .param V1=0      .param Td3=9  
                   .param V2=1      .param N=3  
                   .param Td1=2      .param Tperiod=50  
                   .param Tau1=0.7  
                   .param Td2=4  
                   .param Tau2=0.5
```



expTperiod

```
EXP V1 V2 Td1 Tau1 Td2 Tau2 Td3 N Tperiod
```



V. Voltage Source : EXP (Exponential)

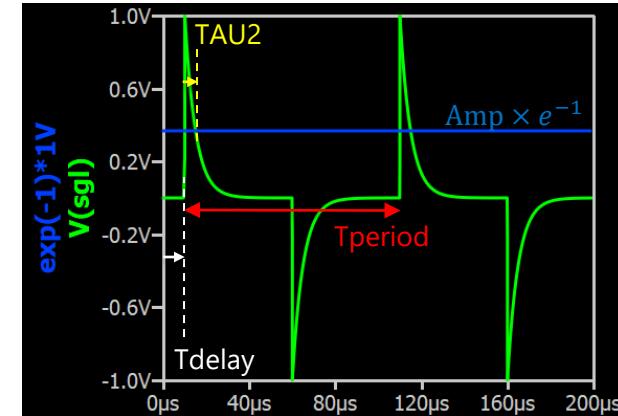
Qspice : Vsource EXP-DualSrc | Vsource EXP-DDT.qsch

- EXP (derivative)
 - Two exponential sources can be used to generate this exponential derivative signal

.param Amp=1
.param Tdelay=10μ
.param TAU2=5μ
.param Tperiod=100μ
.param N=1e6 Number of times repeated

EXP 0 Amp Tdelay 1n 2n TAU2 Tperiod N
EXP 0 -Amp Tdelay+Tperiod/2 1n 2n TAU2 Tperiod N

.tran 4*Tperiod
.plot V(sgl) exp(-1)*1V

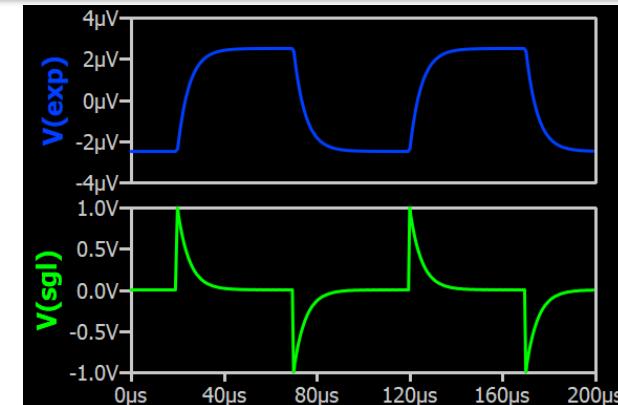


- EXP (derivative)
 - Use Behavioral source with derivative function ddt() to process exponential source output

sgl
B1
V=ddt(V(exp))
exp
V1
EXP -AMP*TAU/2 AMP*TAU/2 Tdelay TAU Tperiod/2 TAU Tperiod N

.param Amp=1
.param Tdelay=20μ
.param TAU=5μ
.param Tperiod=100μ
.param N=1e6

.tran 2*Tperiod
.plot V(sgl)
.plot V(exp)

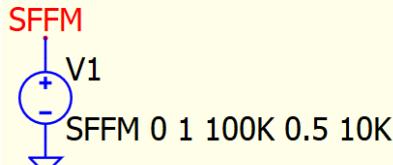


V. Voltage Source : SFFM (Single Frequency FM)

Qspice Vsource SFFM.qsch

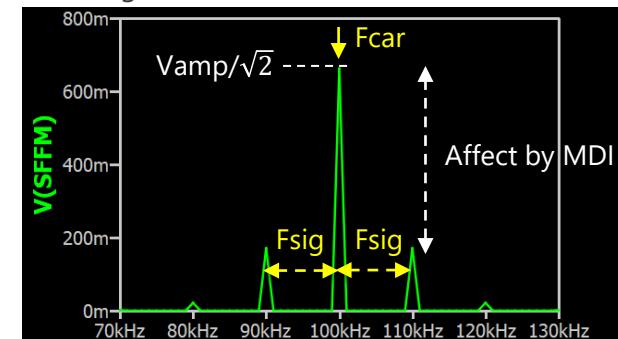
- SFFM
 - Single Frequency FM
 - It is hard to observe FM signal in time domain waveform
 - FFT is used to explain its nature

Syntax : SFFM Voff Vamp Fcar MDI Fsig



.tran 10/10K
.plot V(SFFM)

FFT magnitude is RMS

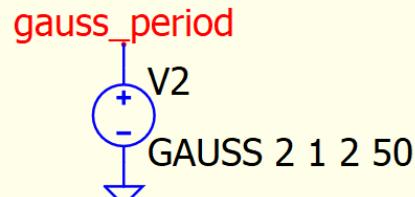
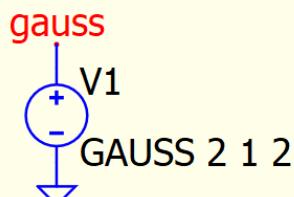


- Transient formula
 - $V_{off} + V_{amp} \sin((2\pi F_{car} \cdot time) + MDI \sin(2\pi F_{sig} \cdot time))$

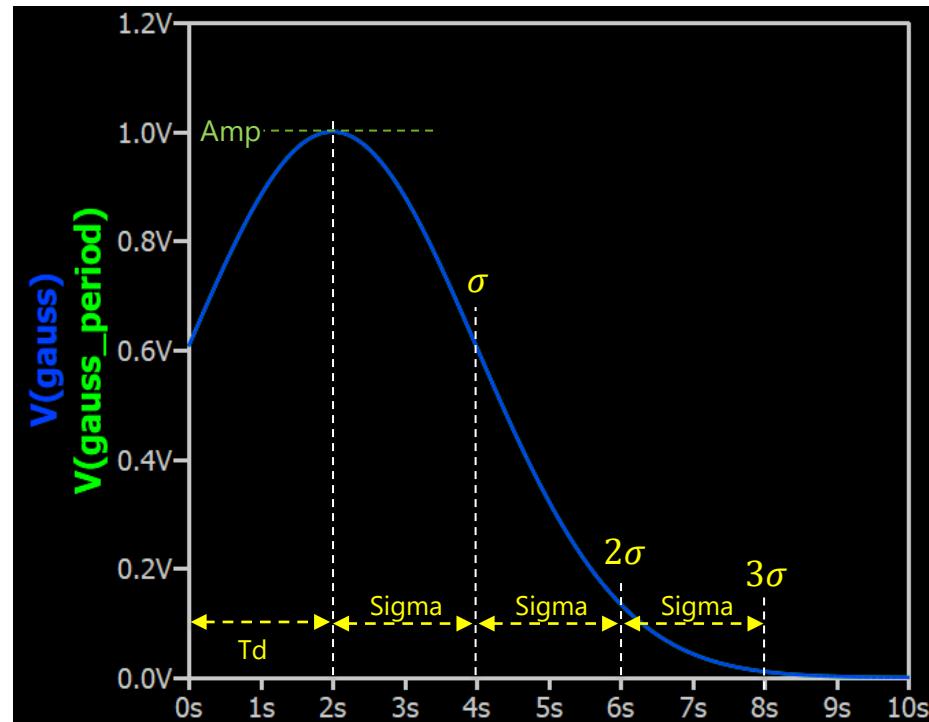
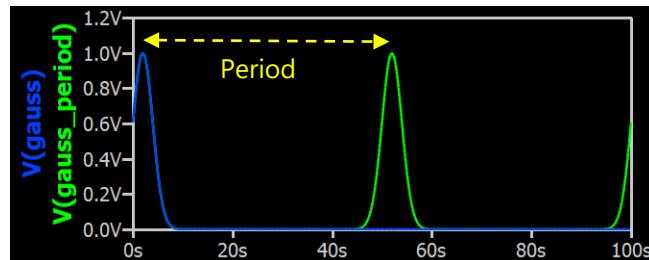
V. Voltage Source : GAUSS (Gaussian Pulse)

Qspice Vsource GAUSS.qsch

Syntax : GAUSS Td Amp Sigma [Period]



```
.plot V(gauss_period) V(gauss)
.tran 100
```

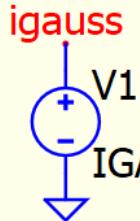


V. Voltage Source : IGAUSS (Imaginary Gaussian Pulse)

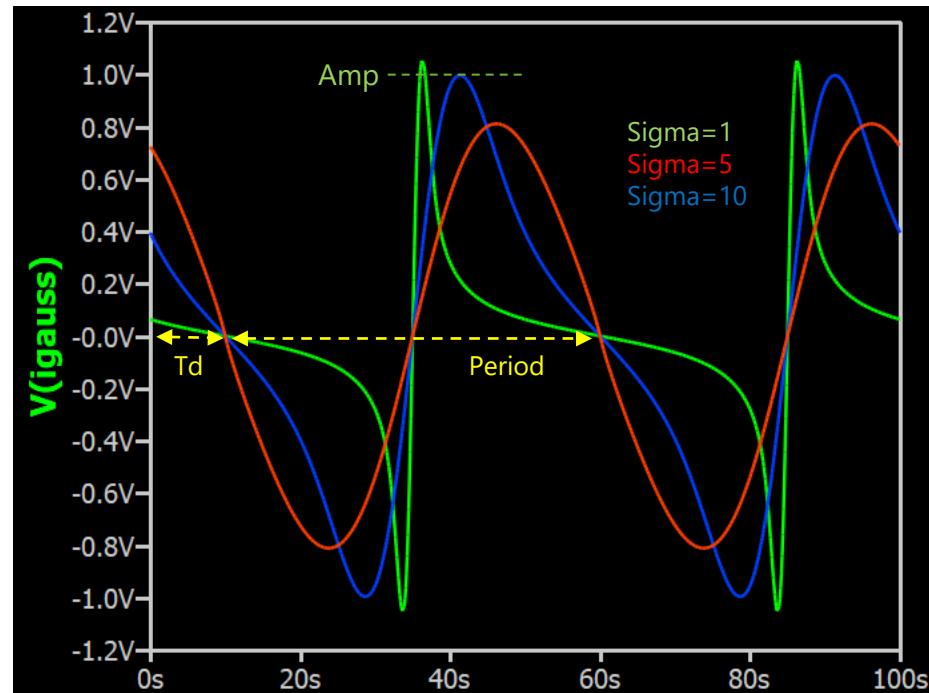
Qspice Vsource IGAUSS.qsch

Syntax : IGAUSS Td Period Sigma Amp

.step param Sigma list 1 5 10



.plot V(igauss)
.tran 100



V. Voltage Source : CHIRP (Piece-wise Linear Chirp)

Qspice Vsource Chirp.qsch

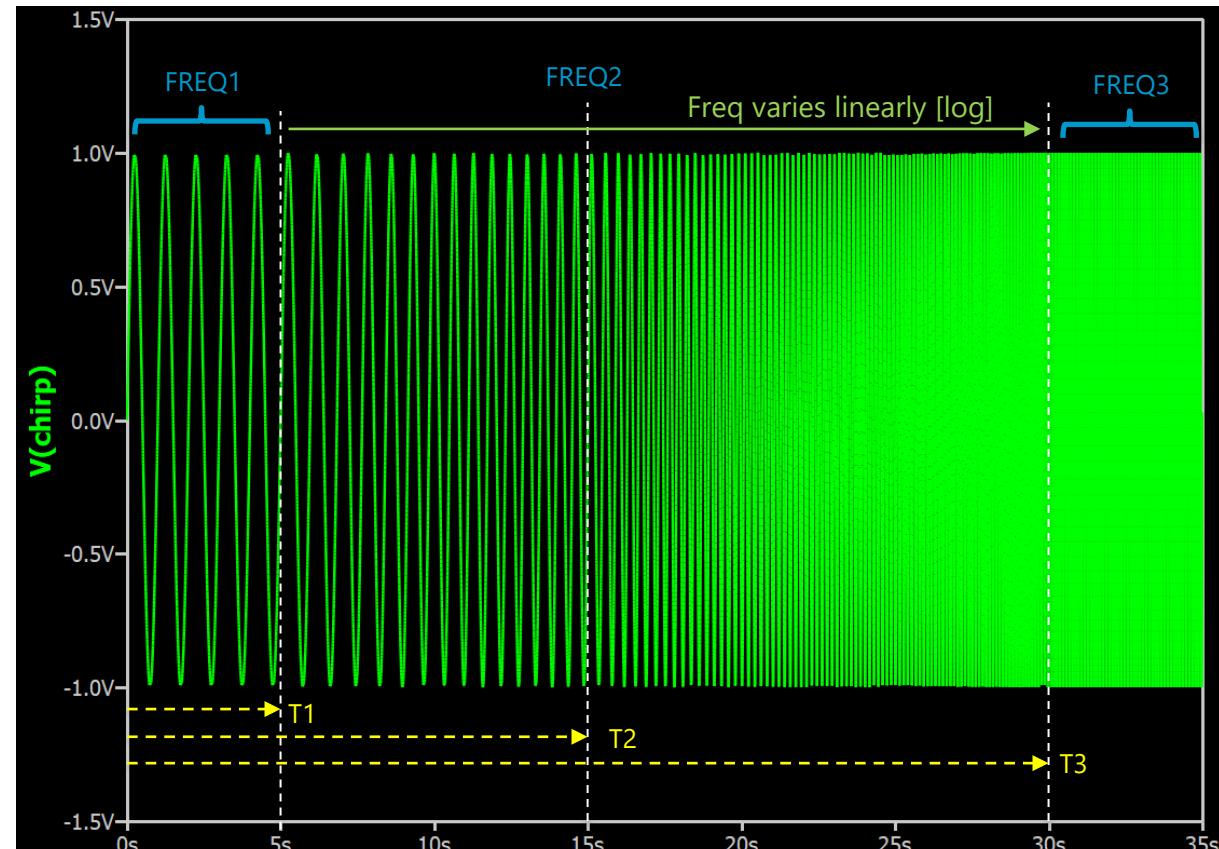
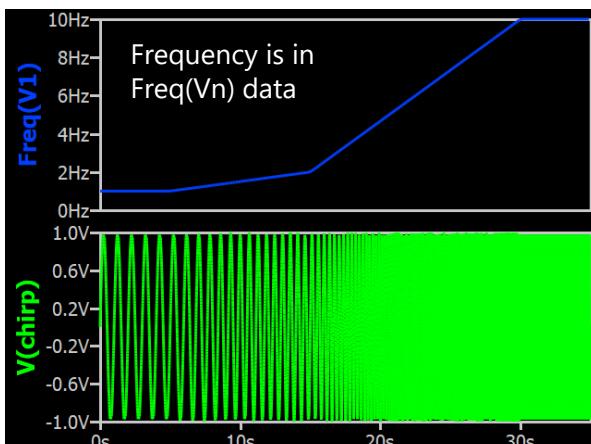
Syntax : CHIRP(AMP T1 FREQ1 T2 FREQ2 [...]) [LOG] [XTRAP]

```
.param AMP=1  
.param T1=5  
.param FREQ1=1  
.param T2=15  
.param FREQ2=2  
.param T3=30  
.param FREQ3=10
```

chirp
V1
CHIRP AMP T1 FREQ1 T2 FREQ2 T3 FREQ3

```
.plot V(chirp)  
.tran 35  
.options MAXSTEP=1/1000
```

XTRAP : extrapolate beyond PWL and CHIRP points



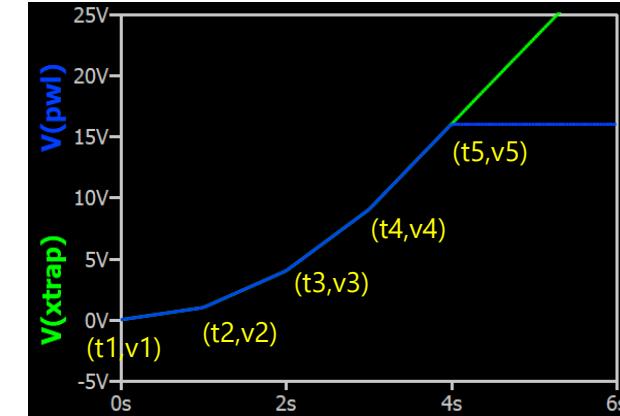
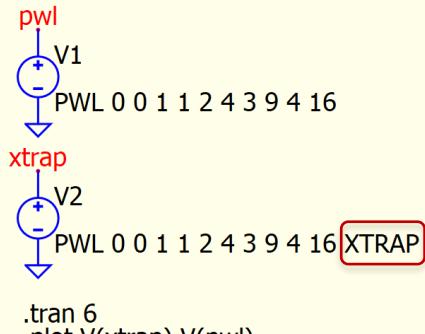
V. Voltage Source : PWL (Piece-wise Linear) – XTRAP and LOG

Qspice : Vsource PWL-Xtrap.qsch/ Vsource PWL-Log.qsch

- Basic Usage and XTRAP

- Standard
 - last value will hold
- Xtrap
 - Extrapolate beyond PWL and CHIRP points

Syntax : PWL(t1 v1 t2 v2 t3 v3...) [LOG] [XTRAP]

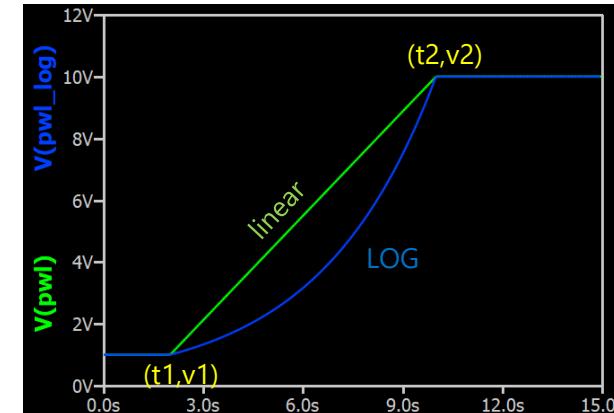
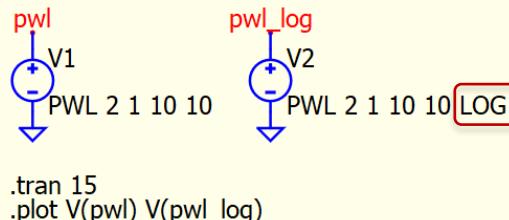


- LOG

- Log

- Interpolate between PWL and CHIRP points with log function

Syntax : PWL(t1 v1 t2 v2 t3 v3...) [LOG] [XTRAP]



V. Voltage Source : PWL (Piece-wise Linear) – REPEAT

Qspice : Vsource PWL-Repeat.qsch

- PWL Repeat Syntax

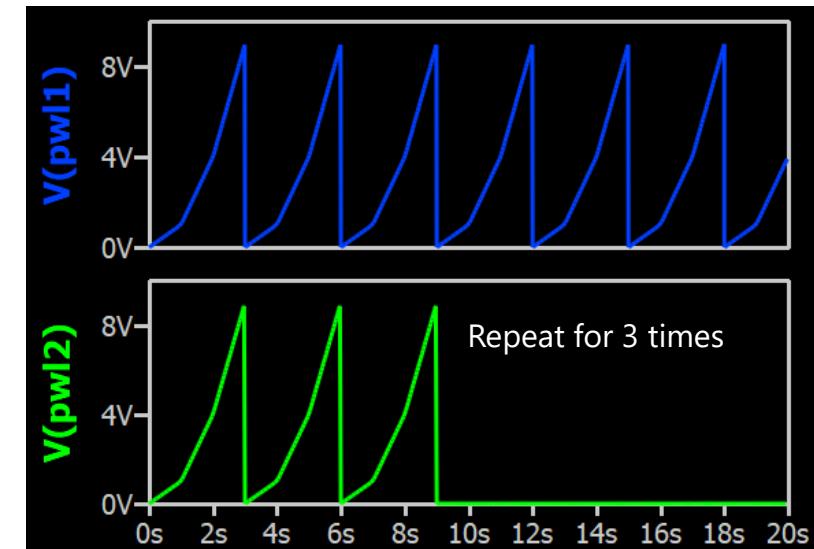
- Vnnn N+ N- PWL **REPEAT FOREVER** t1 v1 t2 v2 t3 v3... **ENDREPEAT**
- Vnnn N+ N- PWL **REPEAT FOR N** t1 v1 t2 v2 t3 v3... **ENDREPEAT**
 - N is number of times
 - ** last voltage value of a repeated PWL will be ignored and forced to be equal to the first value**

Syntax : PWL FOR[EVER] [times] (t1 v1 t2 v2 t3 v3...) Endrepeat

pwl1
V1
PWL REPEAT FOREVER (0 0 1 1 2 4 3 9 3+1p 0) Endrepeat

pwl2
V2
PWL REPEAT FOR 3 (0 0 1 1 2 4 3 9 3+1p 0) Endrepeat

.tran 20
.plot V(pwl2)
.plot V(pwl1)

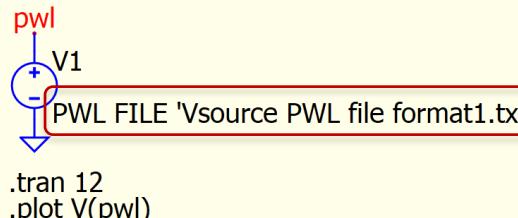


V. Voltage Source : PWL (Piece-wise Linear) – Load from file

Qspice : Vsource PWL file.qsch / Vsource PWL-Repeat-File.qsch

- PWL : load from file
 - Filename is quoted with single ('filename') or double ("filename") quotation
 - Delimiter can be space [] or comma [,]
 - To load from file, syntax is
 - FILE filename
 - Support repeat syntax, but remember last value in repeated PWL is ignored and forced to be equal to first value
- File internal format
 - Only two column of data
 - 1st column is TIME
 - 2nd column is Voltage/Current
 - No headers line

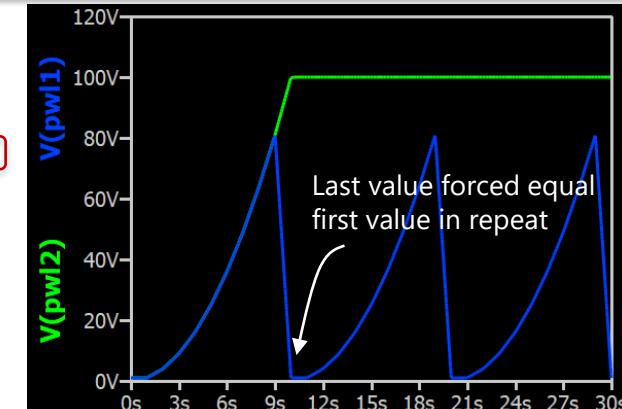
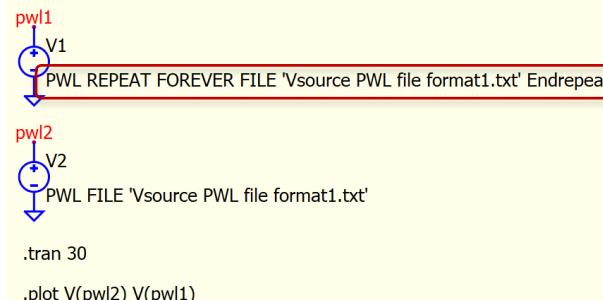
Syntax : PWL FILE file.txt [LOG] [XTRAP]



1	1	1
2	2	4
3	3	9
4	4	16
5	5	25
6	6	36
7	7	49
8	8	64
9	9	81
10	10	100

1	1,1
2	2,4
3	3,9
4	4,16
5	5,25
6	6,36
7	7,49
8	8,64
9	9,81
10	10,100

Syntax : PWL FOR[EVER] [times] FILE 'filename' Endrepeat



V. Voltage Source : PWL (Piece-wise Linear) – Usage

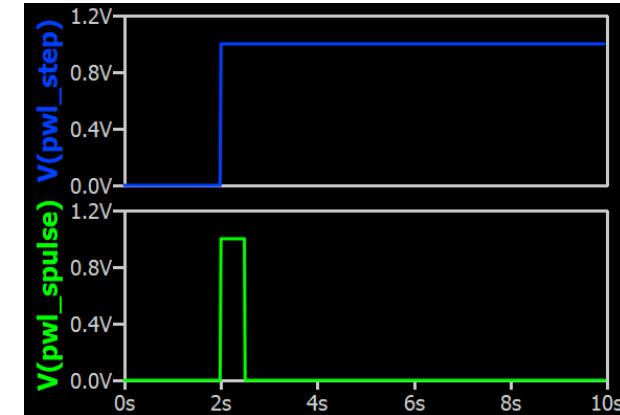
Qspice : Vsource PWL-SinglePulse.qsch

- Step and Single Pulse
 - To create step or single pulse with PWL, a datapoint to maintain voltage level before change is required
 - For example, if change occurs at 2s, define an extra datapoint at 1.999s or (2-1p)

pwl_step
V1
pwl 0 0, 2-1p 0, 2 1

pwl_spulse
V2
pwl 0 0, 2-1p 0, 2 1, 2.5-1p 1, 2.5 0

.tran 10
.plot V(pwl_spulse)
.plot V(pwl_step)



**W. Current Controlled
Switch**

W. Current Controlled Switch

- W. Current Controlled Switch

- Syntax: Wnnn N1 N2 <name> <model> [ttol=<value>]

- The current sensed in device <name> controls the switch. The sense device can be any element internally represented as a Thévenin equivalent circuit, i.e., E-, H-, L-, or V-devices.

- .model <model> CSW [model parameters]

Current Controlled Switch Model Parameters

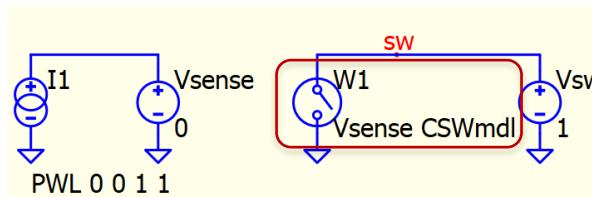
Name	Description	Units	Default
IH	Hysteresis current	A	0.0
IOFF	Current when open	A	0.0
ION	Current when closed	A	0.0
IT	Threshold current	A	0.0
M	Number of parallel devices		1.0
ROFF	Open resistance	Ω	1/Gmin
RON	Closed resistance	Ω	1.0
TTOL	Temporal tolerance	sec	1e308

If IT and IH are specified, ION and IOFF are ignored. If IH is negative the switch smoothly transitions between on and off.

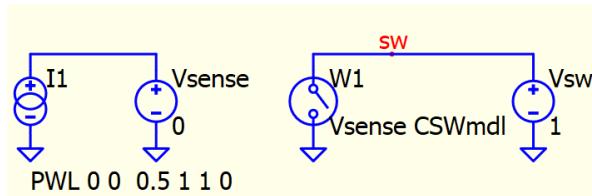
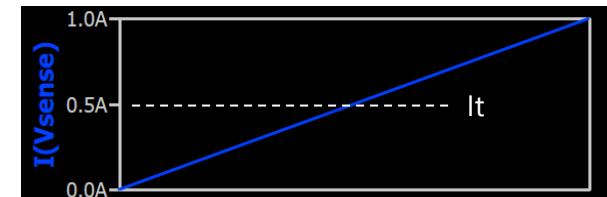
W. Current Controlled Switch

Qspice : CSW - RON ROFF IT IH.qsch | CSW - IH -ve.qsch

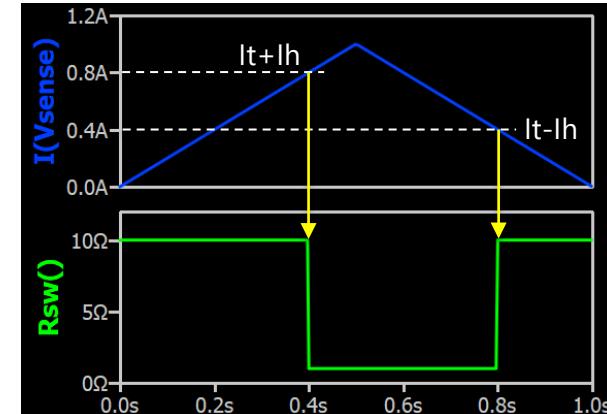
- RON, ROFF, IT, IH
 - RON : Closed resistance
 - ROFF : Open resistance
 - IT : Threshold current
 - IH : hysteresis current
 - Discrete transition with +ve IH, smoothly transition with -ve IH
 - **Default Ron=1**
 - **Default Roff=1/Gmin**
 - **Default It=0**
 - **Default Ih=0**



```
.model CSWmdl CSW Ron=1 Roff=10 It=0.5 Ih=0
.func Rsw() V(sw)/-I(Vsw)
.tran 1
.plot Rsw()
.plot I(Vsense)
```



```
.model CSWmdl CSW Ron=1 Roff=10 It=0.6 Ih=0.2
.func Rsw() V(sw)/-I(Vsw)
.tran 1
.plot Rsw()
.plot I(Vsense)
```

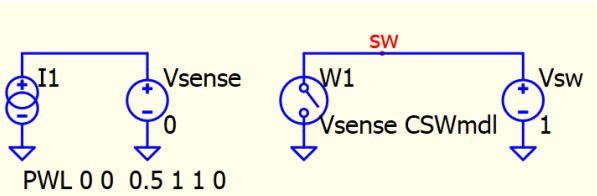


W. Current Controlled Switch

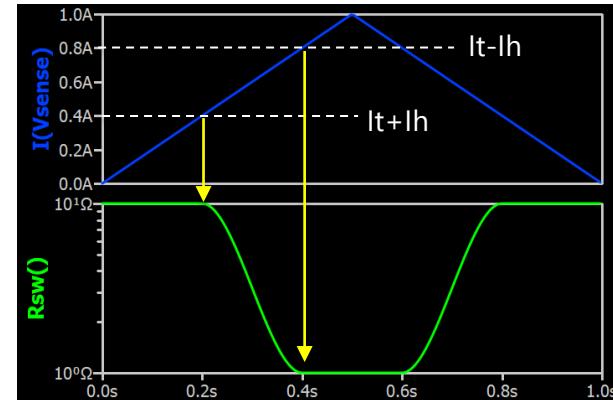
Qspice : CSW - IH -ve.qsch | CSW - ION IOFF.qsch

- IH

- IH : hysteresis current
- IH is negative the switch smoothly transitions between on and off

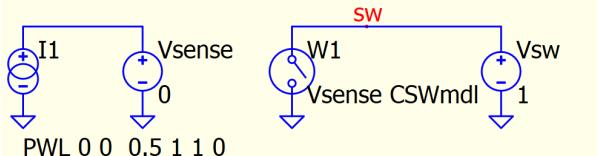


```
.model CSWmdl CSW Ron=1 Roff=10 It=0.6 Ih=-0.2
.func Rsw() V(sw)/-I(Vsw)
.tran 1
.plot Rsw()
.plot I(Vsense)
```

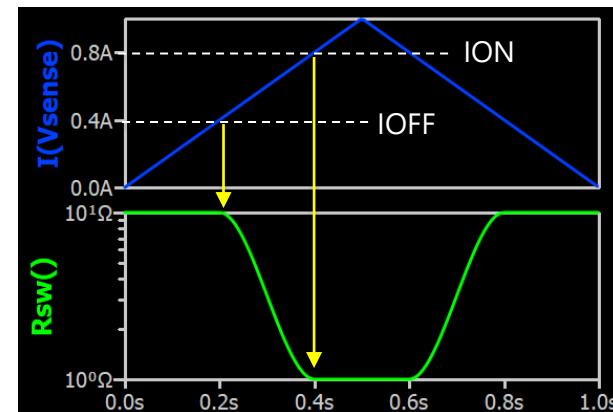


- ION and IOFF

- ION : Current when closed
- IOFF : Current when open
- If ION and IOFF are specified, the switch smoothly transitions between on and off



```
.model CSWmdl CSW Ron=1 Roff=10 Ion=0.8 Ioff=0.4
.func Rsw() V(sw)/-I(Vsw)
.tran 1
.plot Rsw()
.plot I(Vsense)
```

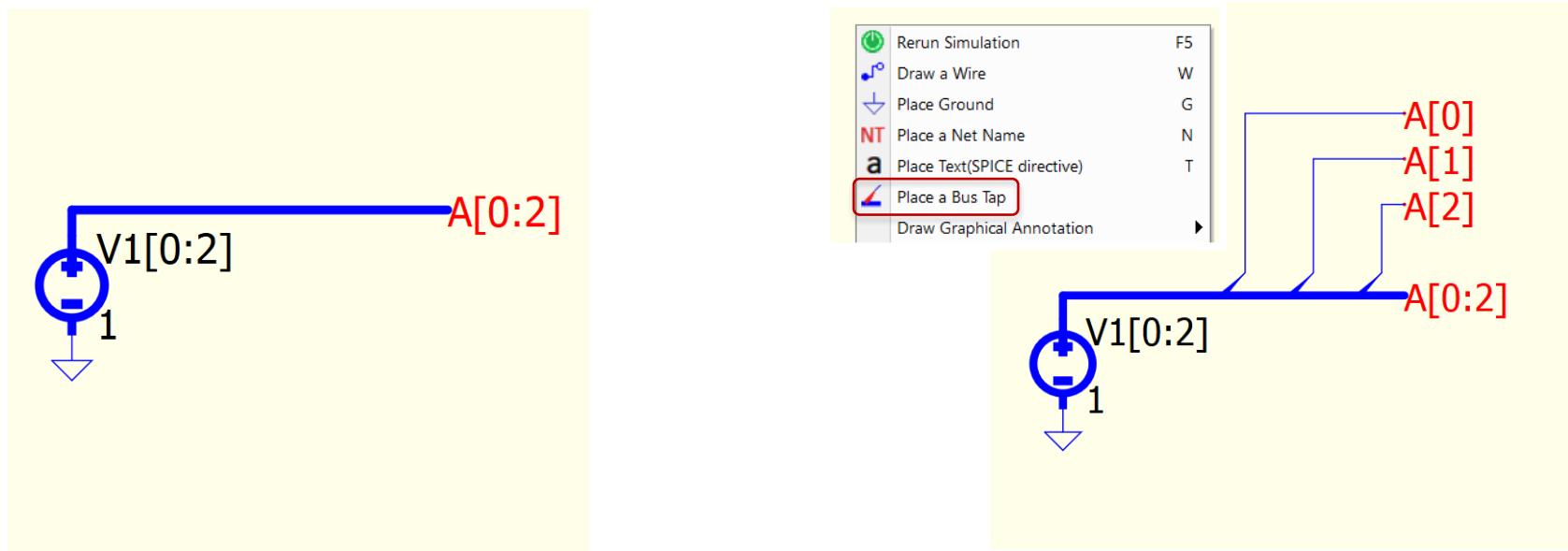


W. Wire and BUS

W. Wire and Bus : Introduction

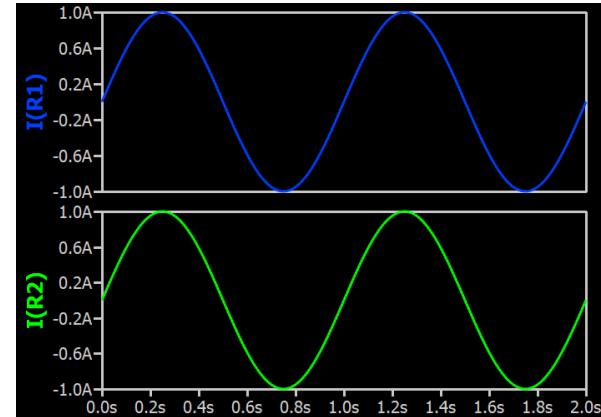
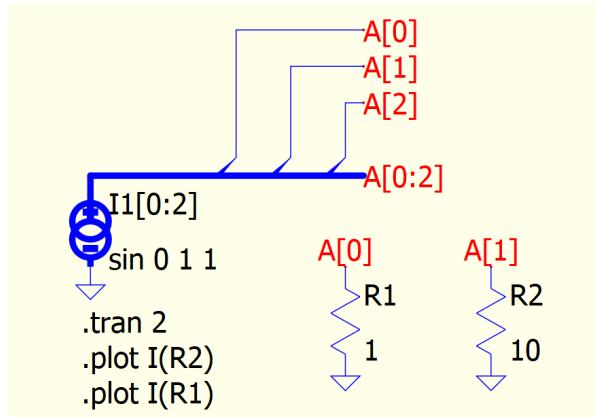
- [1] Place a voltage source and draw wire
- [2] Rename voltage source to V1[0:2]
- [3] Place net name as A[0:2]
- [4] Now, the wire becomes a bus, in this example, A[m] is voltage of V1[m]

- [5] Right click and select "Place a Bus Tap"
- [6] Place net name to bus tap wire



W. Wire and Bus : Bus for V/I-source

- Identical I-source
 - File : BUS - Isrc.qsch
 - Bus can replicate current or voltage source for multiple nodes usage
 - In netlist
 - $I1[0] 0 A[0] \sin 0 1 1$
 - $I1[1] 0 A[1] \sin 0 1 1$
 - $I1[2] 0 A[2] \sin 0 1 1$
 - ** .dc for $I1$ won't work as three I-sources $I1[0]$, $I1[1]$ and $I1[2]$ in this format



W. Wire and Bus : Bus for Ø-Device

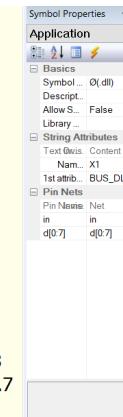
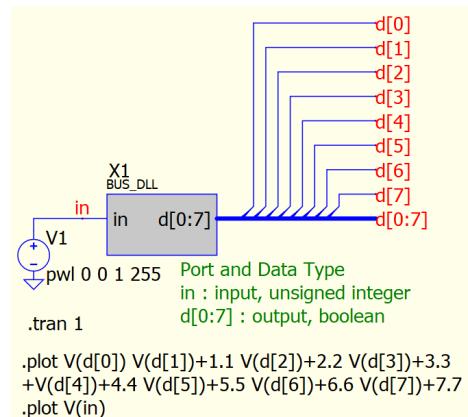
- Bus for Ø-Device

- Files

- BUS_DLL.qsch
 - bus_dll.cpp
 - bus_dll.dll

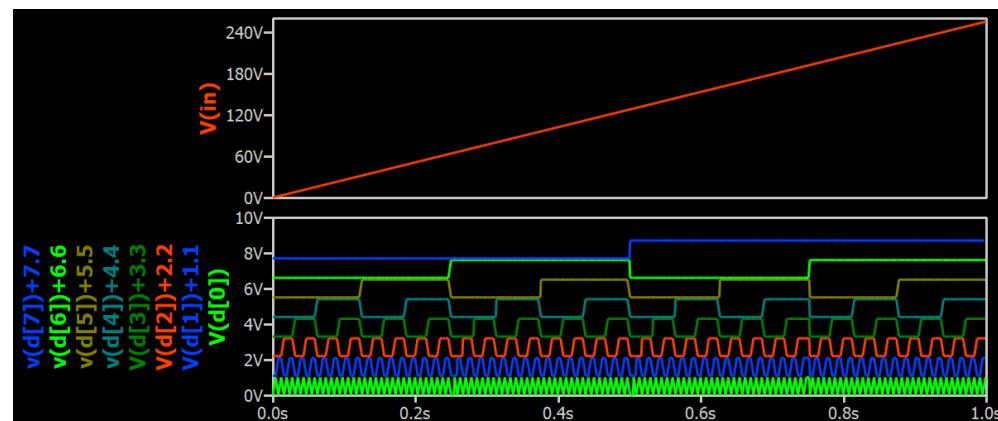
- Procedure

- For Ø-Device, defines an output port with label name with net[0:7] array
 - To output bit, data type should be boolean
 - In template generation, it creates variable name as `net_0_` for bit 0 and `net_7_` for bit 7



```
extern "C" __declspec(dllexport) void bus_dll
{
    unsigned int in = data[0].ui; // input
    bool &d_0 = data[1].b; // output
    bool &d_1 = data[2].b; // output
    bool &d_2 = data[3].b; // output
    bool &d_3 = data[4].b; // output
    bool &d_4 = data[5].b; // output
    bool &d_5 = data[6].b; // output
    bool &d_6 = data[7].b; // output
    bool &d_7 = data[8].b; // output

    // Implement module evaluation code here:
    d_0 = in & 0x01;
    d_1 = in & 0x02;
    d_2 = in & 0x04;
    d_3 = in & 0x08;
    d_4 = in & 0x10;
    d_5 = in & 0x20;
    d_6 = in & 0x40;
    d_7 = in & 0x80;
}
```



Y. Piezoelectric Crystal

Y. Piezoelectric Crystal : Instance Parameters

- Y. Piezoelectric Crystal
 - Syntax: Ynnn N+ N- <frequency1> dF=<value> Ctot=<value> [Q=<value>]

Piezoelectric Crystal Instance Parameters

Name	Description	Units	Default
CTOT	Total capacitance as measured at DC	F	
DF ¹	Difference between series and parallel resonant frequencies	Hz	
FREQUENCY ¹	Resonant frequency	Hz	
IC	Initial internal current(Used with UIC on the .tran)	A	0.0
M	Number of parallel devices		1.0
RSER	Series resistance	Ω	Determined from Q
Q	Quality factor		$1.6e13 \div \text{FREQUENCY}^2$

$$Q = \min(1e6, \frac{1e13}{\text{FREQUENCY}^2})$$

If default equation is used

- If DF > 0 : **Series Resonant Freq = Frequency** and **Parallel Resonant Freq = Frequency + DF**
- If DF < 0 : **Series Resonant Freq = Frequency + DF** and **Parallel Resonant Freq = Frequency**

Y. Piezoelectric Crystal : Formula and Equivalent Circuit

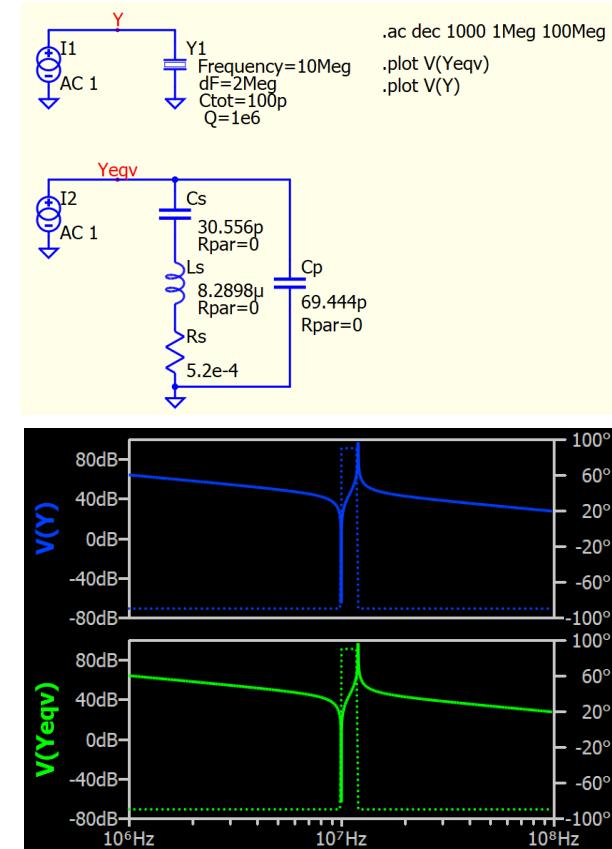
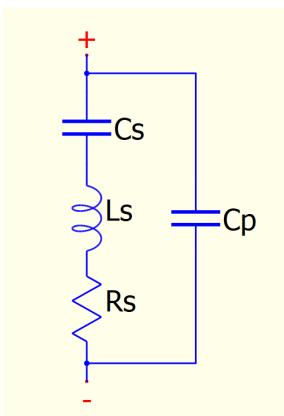
Qspice : Y Crystal - Equivalent Circuit.qsch

- Piezoelectric Crystal Equation

- Series Resonant Frequency : $f_s = \frac{1}{2\pi\sqrt{L_s C_s}}$
- Parallel Resonant Frequency : $f_p = \frac{1}{2\pi\sqrt{\frac{C_p C_s}{C_p + C_s}}}$
- Crystal Oscillators Q-factor : $Q = \frac{X_L}{R} = \frac{2\pi f L_s}{R_s}$
- Total Capacitance : $C_{TOT} = C_p + C_s$

- Calculated Value

- $C_p = \left(\frac{f_s}{f_p}\right)^2 C_{TOT}$
- $C_s = C_{TOT} - C_p$
- $L_s = \frac{1}{(2\pi f_s)^2 C_s}$
- $R = \frac{2\pi f L}{Q}$



\tilde{A} -Device
Type : MultGmAmp

\tilde{A} -Device : MultGmAmp and RRopAmp

- \tilde{A} -Device
 - Syntax

$\tilde{A}nnn \ VDD \ VSS \ OUT \ IN- \ IN+ \ MULT+ \ MULT- \ IN-- \ IN++ \ EN \ \# \ \# \ \# \ \# \ \# \ \# \ \# \ <TYPE> \ [INSTANCE \ PARAMETERS]$

- \tilde{A} -device models a highly configurable Gm block than can mimic the behavior of a complementary MOSFET output, there are two types MULTGMAMP and RRROPAMP

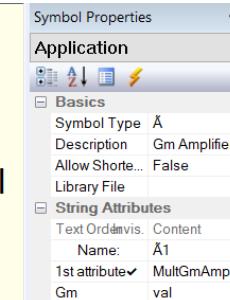
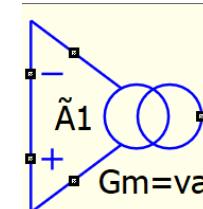
\tilde{A} -Device Types

TYPE	Behavior
MULTGMAMP	Multiplying Gm Amplifier
RRROPAMP	Rail-to-Rail Output OpAmp

MULTGMAMP is Operational Transconductance Amplifier (OTA)

RRopAmp is implemented with two Gm amps (MULTGMAMP) with an internal node for a Miller capacitor connected to the output

- To Identify what $<TYPE>$ a symbol is
- In Symbol Properties > 1st attribute
 - View > Netlist : from device syntax



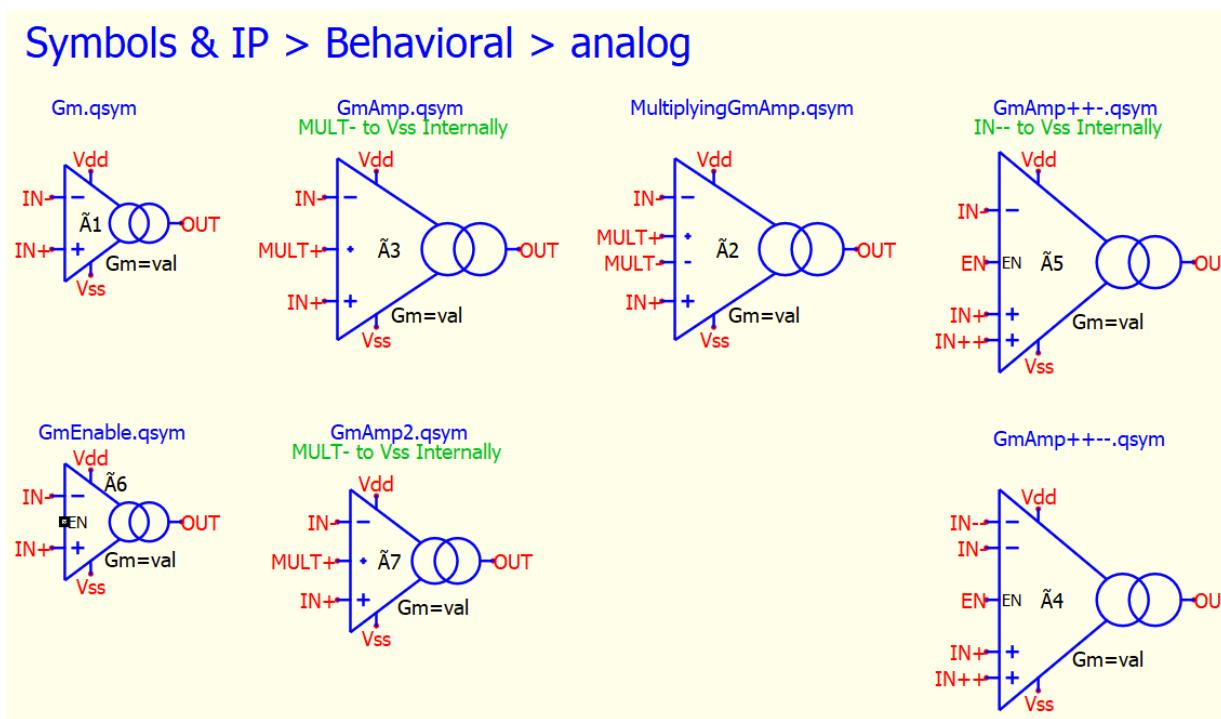
```
* C:\Users\kelvinleung\Documents\QSPICE\Untitled.qsch
A1 Y0 Y1 Y2 Y3 Y4 Y Y Y Y Y Y Y Y Y Y Y Y Y Y MultGmAmp Gm=val
.end
```

\tilde{A} -Device : MultGmAmp

- \tilde{A} -Device

- Syntax: $\tilde{A}nnn \text{ VDD VSS OUT IN- IN+ MULT+ MULT- IN-- IN++ EN } \dots <\text{TYPE}> [\text{INSTANCE PARAMETERS}]$
- Formula in Linear Region : $i_{out} = GM * V(\text{MULT+}, \text{MULT-}) * V(\text{MIN}(\text{IN+}, \text{IN++}), \text{MAX}(\text{IN-}, \text{IN--}))$

Symbols & IP > Behavioral > analog



À-Device Instance Parameters in MultGmAmp

À-Device Instance Parameters

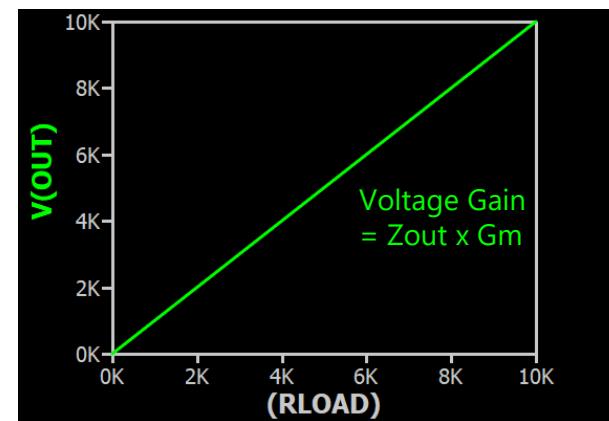
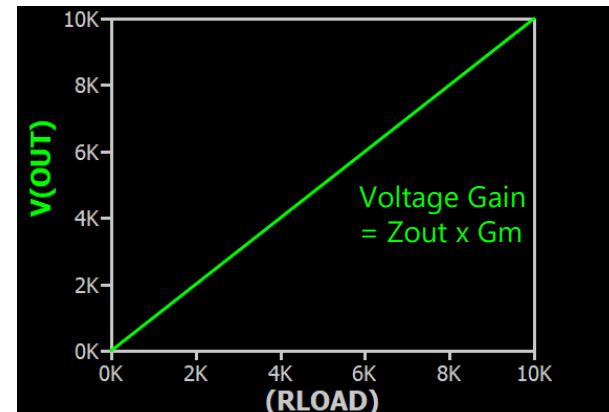
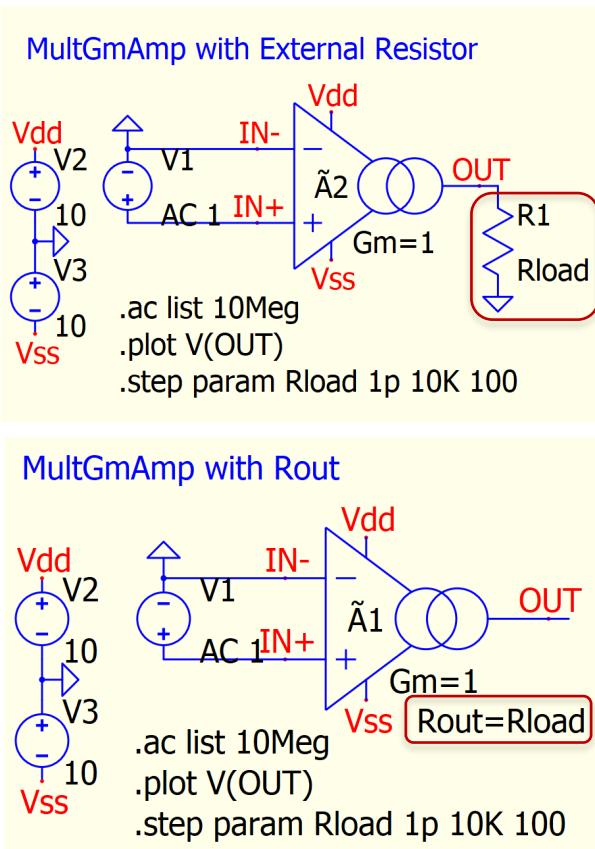
Name	Description
CAPINCM	Common eigenmode input capacitance
CAPINNM	Normal eigenmode input capacitance
CAPVDD	Capacitance from output to Vdd
CAPVSS	Capacitance from output to Vss
EN	Equivalent input voltage noise density
ENK	EN corner frequency
FT	3dB bandwidth of transconductance with no voltages slewing
GM	Ideal transconductance
IC	Initial condition of $V_{in} \times V_{mult}$
IN	Equivalent input current noise density
INF	Common mode input current noise density proportional to frequency
INK	IN corner frequency
IOUT	Maximum sourcing current
ISNK	Maximum sinking current
ISNKKNEE	Sharpness of Maximum sinking current limit
ISRC	Maximum sourcing current
ISRCKNEE	Sharpness of max sourcing current limit
M	Number of parallel devices

REF	Logic threshold for enable(from Vss)
ROUT	Additional impedance added to output(2*R to Vdd, 2*R to Vss)
TEMP	Instance temperature
TTOL	Temporal tolerance for enable & UVLO
UVLO	Minimum supply voltage
VCROSS	Cross conduction voltage range
VDSAT	Voltage where gm starts to switch over to a resistance
VDSAT1	Voltage where gm starts to switch over to a resistance(top FET)
VDSAT2	Voltage where gm starts to switch over to a resistance(bottom FET)
VINHIGH	Output range measured from positive rail
VINHIGHKNEE	Sharpness of positive input range limit
VINLOW	Input range measured from negative rail
VINLOWKNEE	Sharpness of negative input range limit
VOS1	Offset voltage for input
VOS2	Offset voltage for multiplying input
VOUTMAX	Maximum output voltage measured from negative rail
VOUTMIN	Minimum output voltage measured from negative rail

MultGmAmp : Basic

Qspice : Multgmamp - Basic.qsch

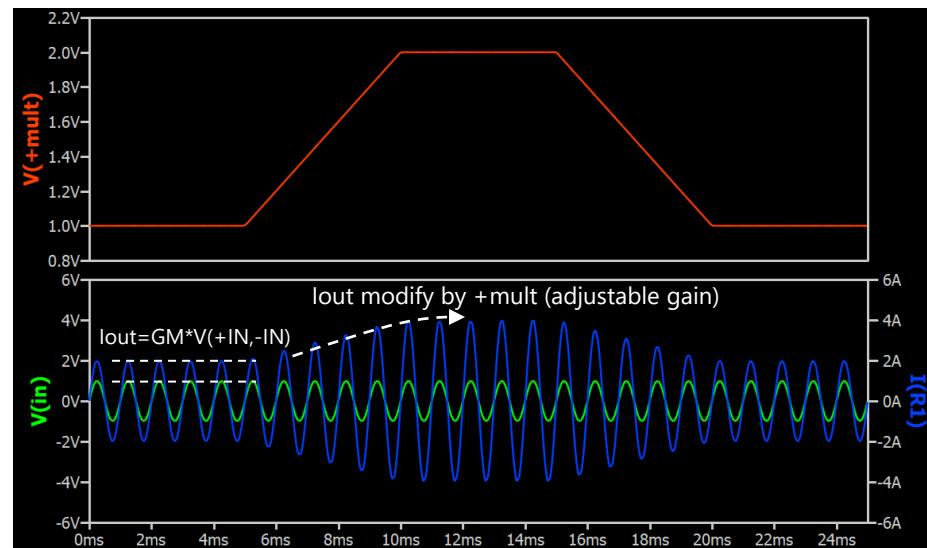
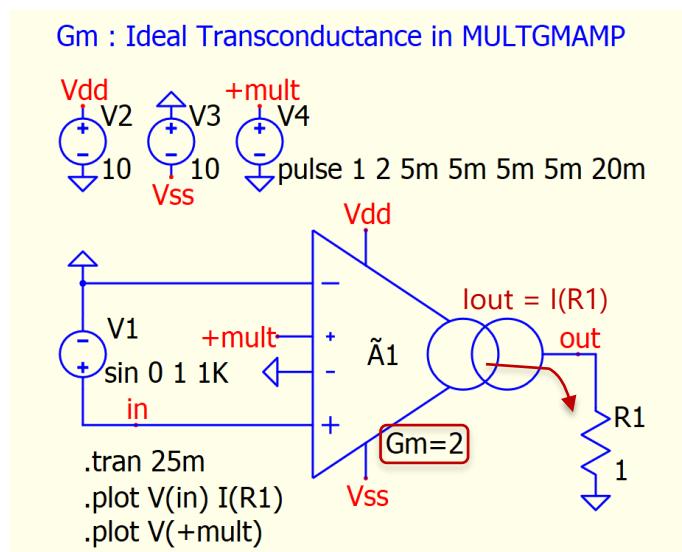
- Basic
 - MULTGMAMP is Operational Transconductance Amplifier (OTA) whose differential input voltage produces an output current
 - By simplify its input only with IN- and IN+
 - $I_{out} = Gm \times (V_{IN+} - V_{IN-})$
 - As OTA output a current, its output voltage depends on loading impedance, where
 $V_{out} = Z_{out} \times I_{out}$
 $V_{out} = Z_{out} Gm \times (V_{IN+} - V_{IN-})$
 - Zout can be defined in two ways
 - External Resistor
 - Instance parameter Rout



MultGmAmp : GM (Ideal transconductance)

Qspice : Multgmamp – Gm with mult.qsch

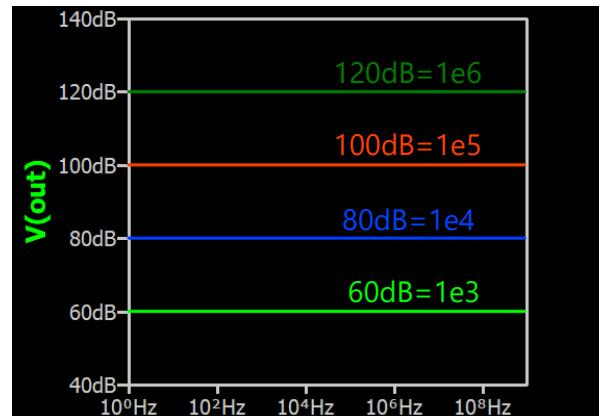
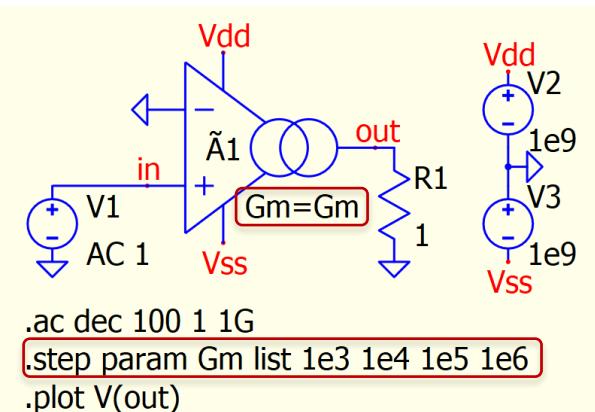
- Gm : Ideal transconductance
 - Operational Transconductance Amplifier (OTA) is an amplifier whose differential input voltage produces an output current
 - Without IN++ and IN--, formula is $\text{Iout} = \mathbf{GM} * \mathbf{V(MULT+,MULT-)} * \mathbf{V(IN+,IN-)}$
 - Gm can be positive or negative, but must be non-zero



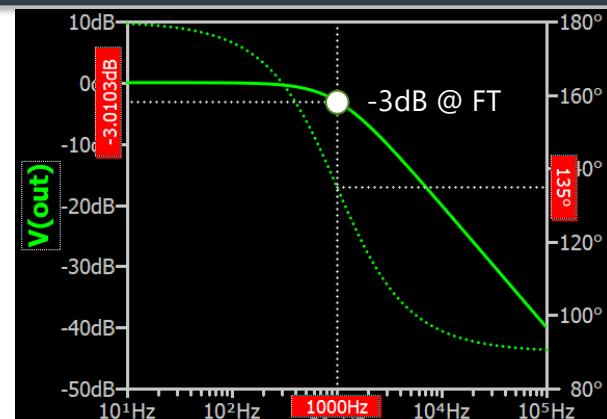
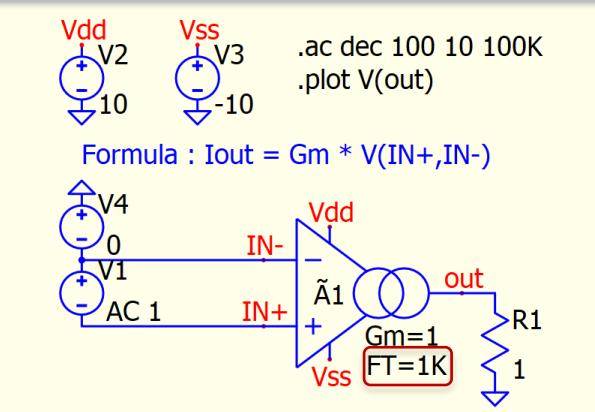
MultGmAmp : GM (Ideal transconductance) and FT (3dB Bandwidth)

Qspice : Multgmamp - Gm.qsch | Multgmamp - FT.qsch

- Gm Ideal transconductance
 - No default value of Gm
 - Must be user provided
 - MULTGMAMP has ideal frequency response if other instance parameters are in default



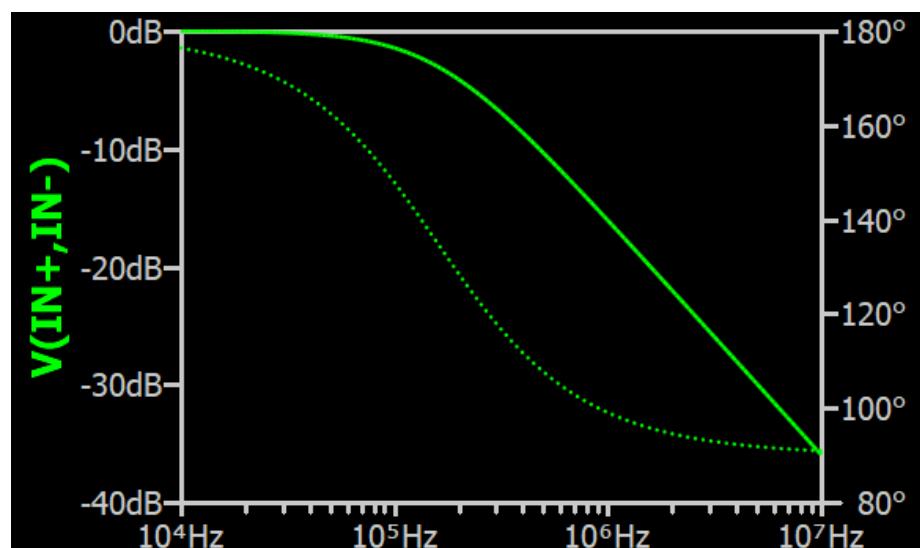
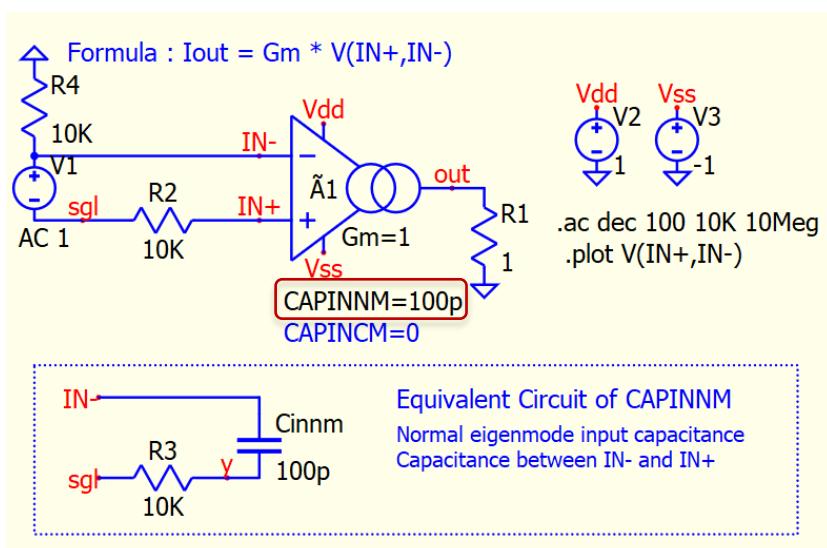
- FT (3dB Bandwidth)
 - FT : 3dB bandwidth of transconductance with no voltages slewing
 - Default FT=0** (i.e. infinite)
 - FT is frequency



MultGmAmp : CAPINNM (Normal eigenmode input capacitance)

Qspice : Multgmamp - Capinnm.qsch

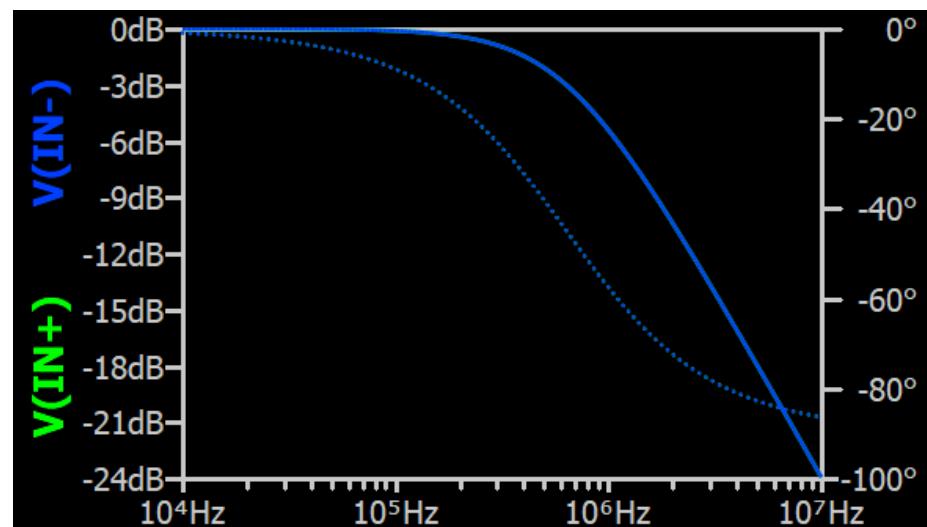
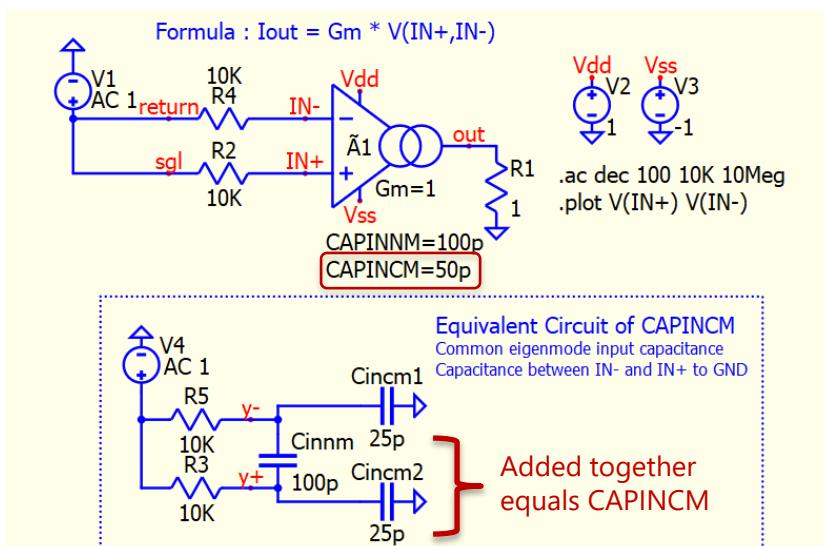
- CAPINNM : Normal eigenmode input capacitance
 - Default CAPINNM=0
 - This capacitance is between IN- and IN+



MultGmAmp : CAPINCM (Common eigenmode input capacitance)

Qspice : Multgmamp - Capincm.qsch

- CAPINCM : Common eigenmode input capacitance
 - Default CAPINCM=0
 - This capacitance is between IN- to GND and IN+ to GND

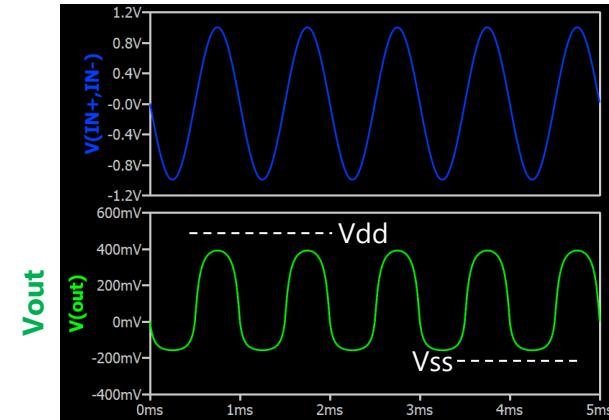
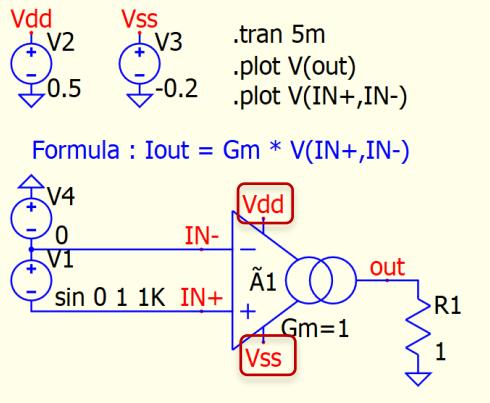


MultGmAmp : Vdd, Vss and VDSAT – Output Voltage Swing

Qspice : Multgmamp - Vdd Vss.qsch | Multgmamp - VDSAT.qsch

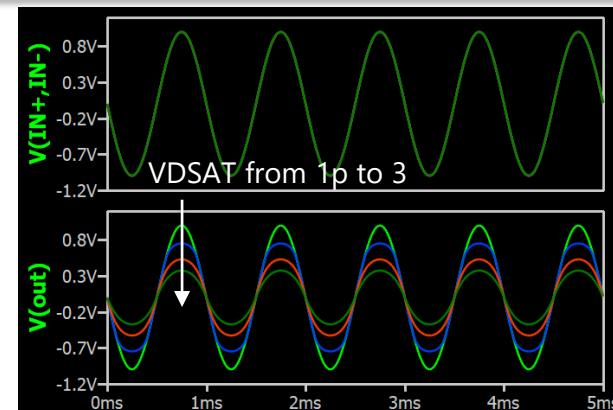
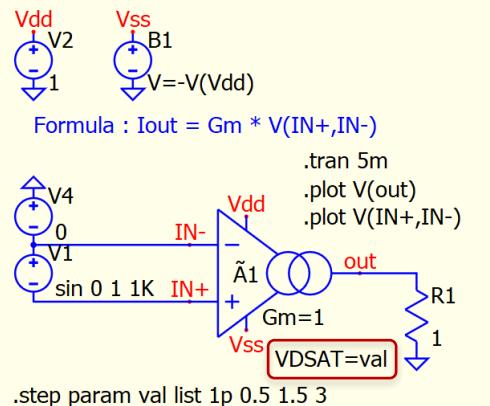
Vdd and Vss Nets

- This is not parameters but Net 1 and Net 2 in \tilde{A} -Device
- Output voltage swing is limited by Vdd and Vss
- ** In this example, Vout cannot reach Vdd and Vss because Default VDSAT is set in Qspice



VDSAT

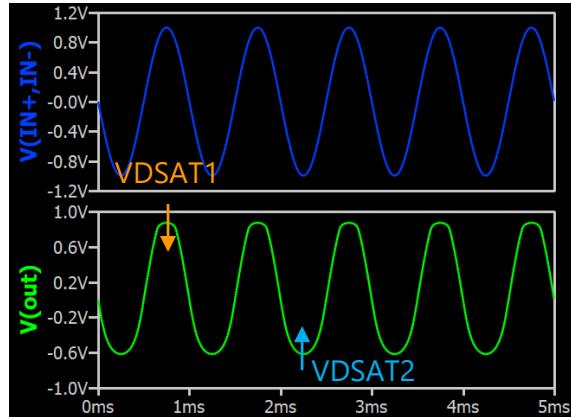
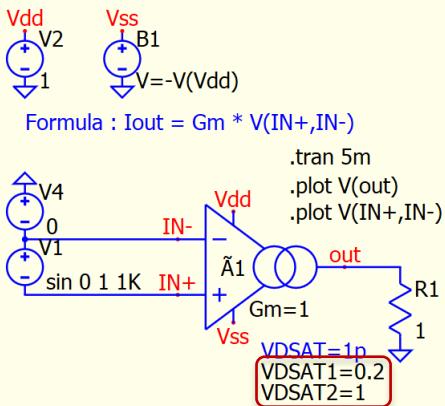
- V_{dsat} : Voltage where gm starts to switch over to a resistance
- Default VDSAT = 0.5**
- VDSAT=0** forced this value to default!
- Set VDSAT to small value (e.g. 1p) for no saturation**



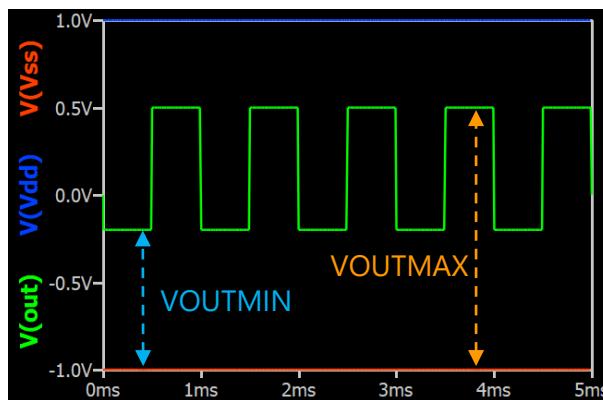
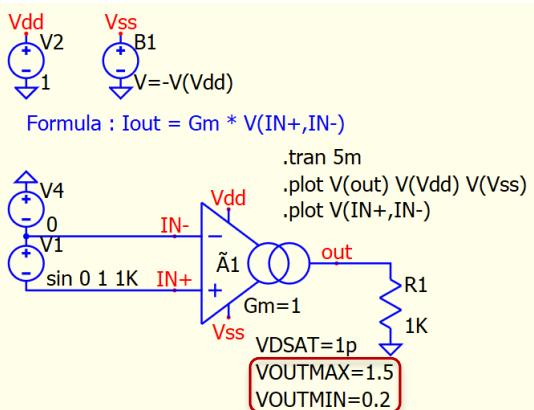
MultGmAmp : VDSAT1, VDSAT2, VOUTMIN, VOUTMAX – Output Voltage

Qspice : Multgmamp - VDSAT1 VDSAT2.qsch ; Multgmamp | VOUTMAX VOUTMIN.qsch

- VDSAT1 and VDSAT2
 - VDSAT1 : Voltage where gm starts to switch over to a resistance (top FET)
 - VDSAT2 : Voltage where gm starts to switch over to a resistance (bottom FET)
 - **Default VDSAT1=VDSAT**
 - **Default VDSAT2=VDSAT1**



- VOUTMIN and VOUTMAX
 - V_{outmin} : Minimum output voltage measured from negative rail
 - V_{outmax} : Maximum output voltage measured from negative rail

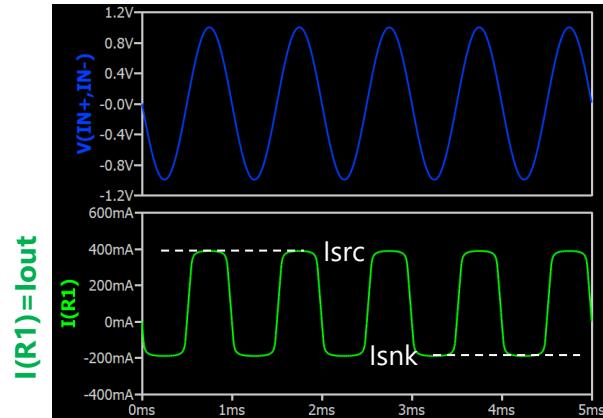
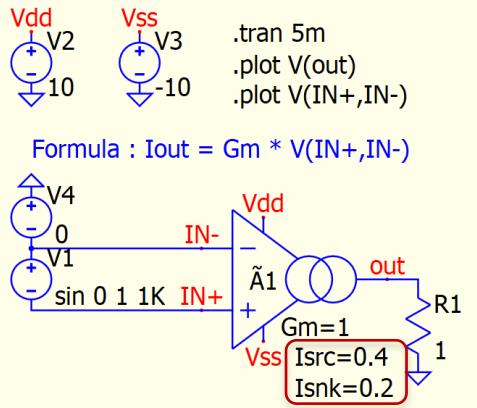


MultGmAmp : Iout/Isrc, Isnk – Output Sink and Src Current

Qspice : Multgmamp - ISRC ISNK.qsch ; Multgmamp - ISRCKNEE ISNKKNEE.qsch

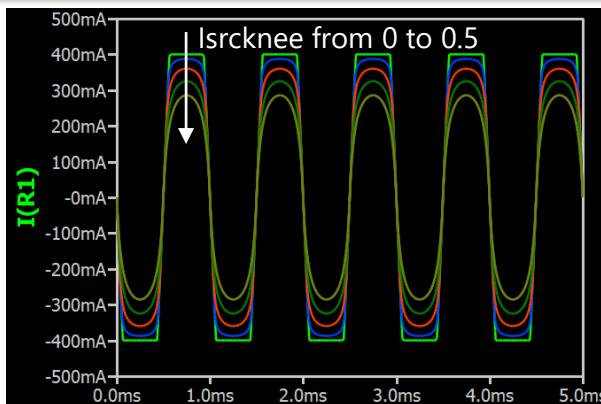
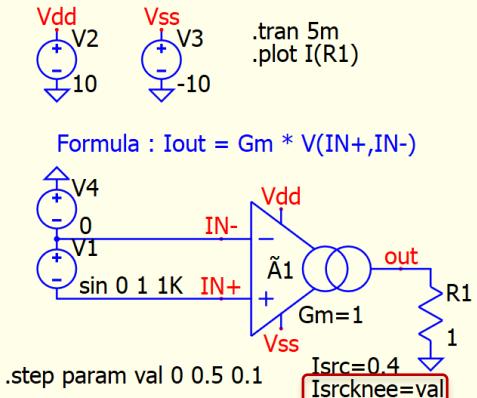
- IOUT/ISRC and ISNK

- Iout/Isrc : Maximum sourcing current (toward load)
- Isnk : Maximum sinking current (toward device)
- **Default ISRC = Infinite**
- **Default ISNK = IOUT or ISRC**
 - i.e. if ISNK not specified, ISNK equals IOUT or ISRC



- ISRCKNEE and ISNKKNEE

- Isrcknee : Sharpness of max sourcing current limit
- Isnkknee : Sharpness of Maximum sinking current limit
- **Default Isrckness = 0.1**
- **Default Isnkkness = Isrcknee**



- Important Note

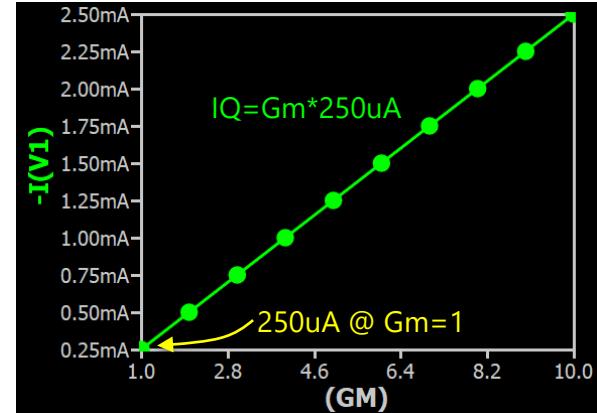
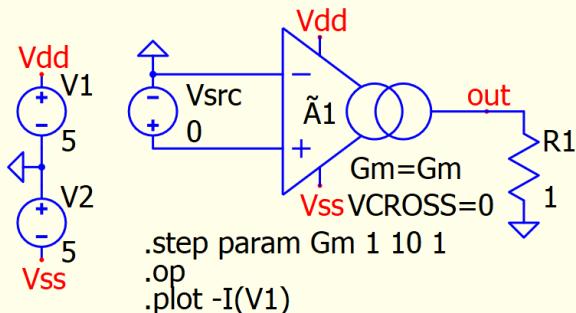
- To have effect, must defines ISRC or ISNK

MultGmAmp : Quiescent Current and VCROSS

- Quiescent Current

- MultGmAmp runs in class AB, there is a quiescent current since both the top and bottom pass elements are conducting at the same time
- $I_Q = GM \times 250\mu A$
 - for $VCROSS=0$

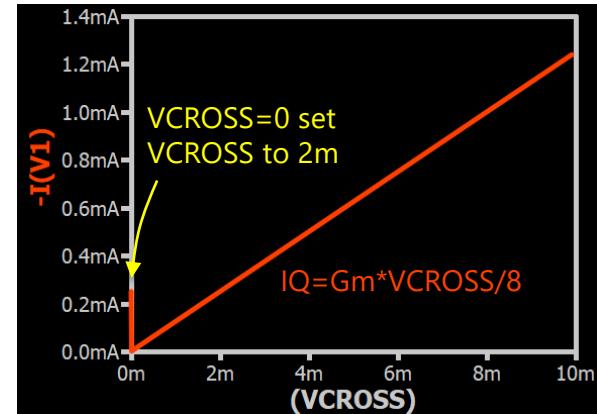
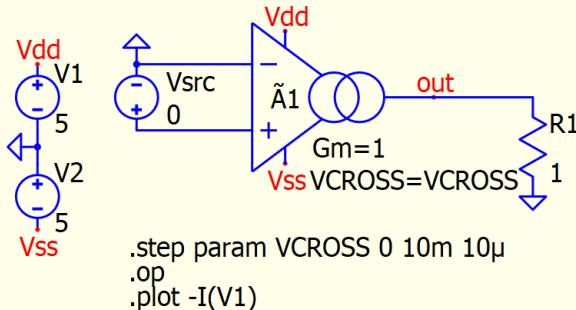
Quiescent Current in MultGmAmp



- VCROSS

- Cross conduction voltage range
- Default $VCROSS=0$**
 - It will force $VCROSS=2mV$ if $VCROSS$ set to default or 0
 - If $VCROSS=1p$, quiescent current will $\sim 0A$
- $I_Q = GM \times \frac{VCROSS}{8}$

VCROSS in MultGmAmp (Quiescent Current)

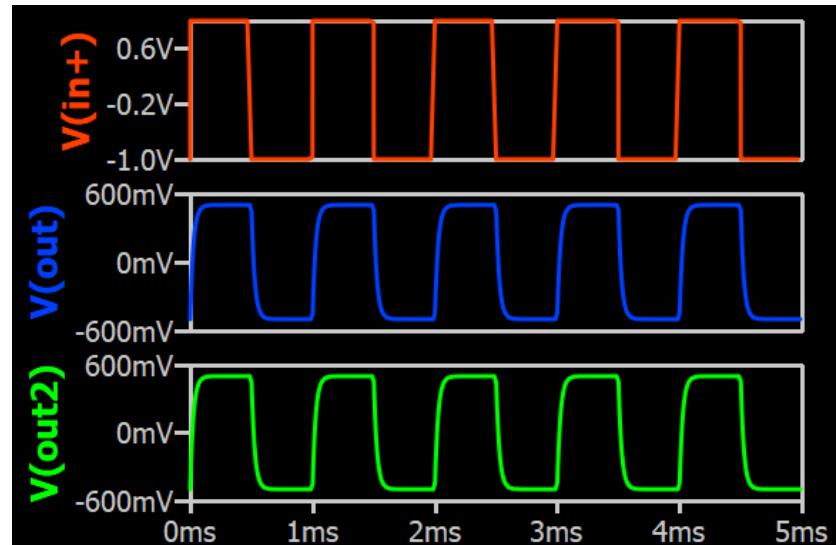
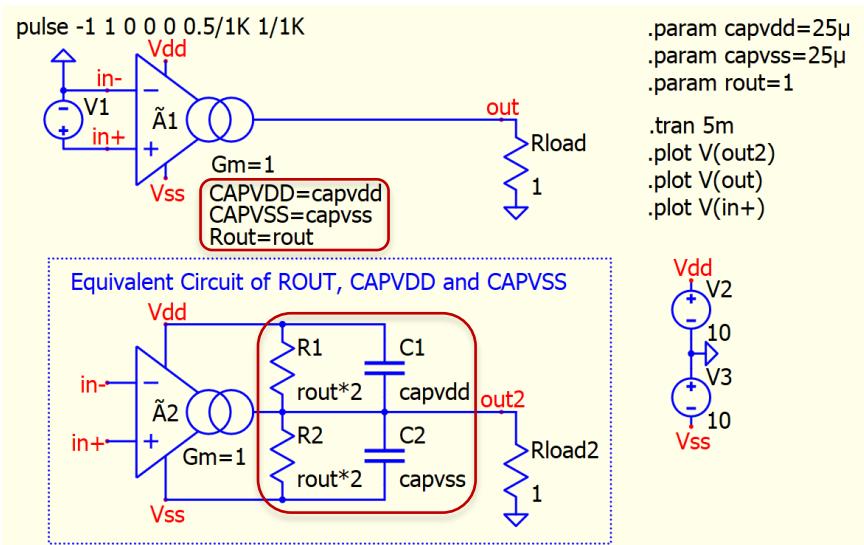


MultGmAmp : ROUT, CAPVDD and CAPVSS (Output Stage)

Qspice : Multgmamp - Rout CAPVDD CAPVSS.qsch

- ROUT, CAPVDD and CAPVSS

- ROUT : Additional impedance added to output ($2 \times R$ to Vdd, $2 \times R$ to Vss) (**Default ROUT=0, which is INF**)
- CAPVDD : Capacitance from output to Vdd (**Default CAPVDD=0**)
- CAPVSS : Capacitance from output to Vss (**Default CAPVSS=0**)

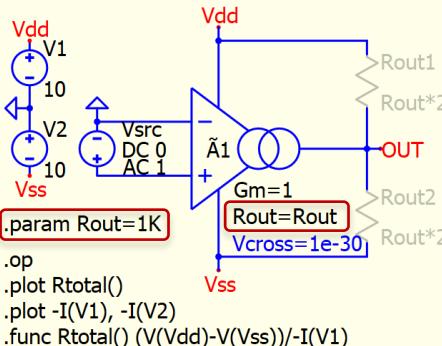


MultGmAmp : ROUT

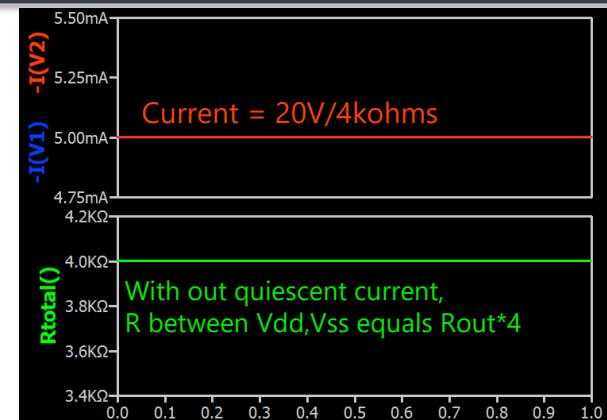
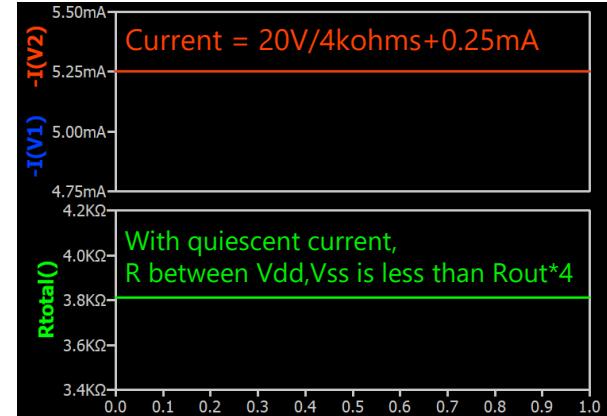
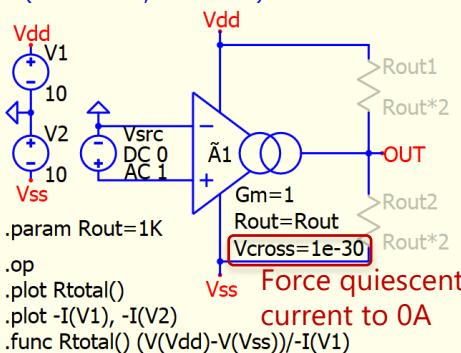
Qspice : Multgmamp - ROUT (.op).qsch

- ROUT
 - Additional impedance added to output ($2 \cdot R_{out}$ to V_{dd} , $2 \cdot R_{out}$ to V_{ss})
 - **Default ROUT=0**
 - ROUT equals infinite
 - In DC analysis, supply current equals current through ROUT + Quiescent Current
 - Total resistance between V_{dd} and V_{ss} is **Rout*4** if ignore quiescent current
 - In studying Rout, this section set $V_{cross}=1e-30$ to eliminate quiescent current

Rout : Additional impedance added to output
($2 \cdot R$ to V_{dd} , $2 \cdot R$ to V_{ss})



Rout : Additional impedance added to output
($2 \cdot R$ to V_{dd} , $2 \cdot R$ to V_{ss})

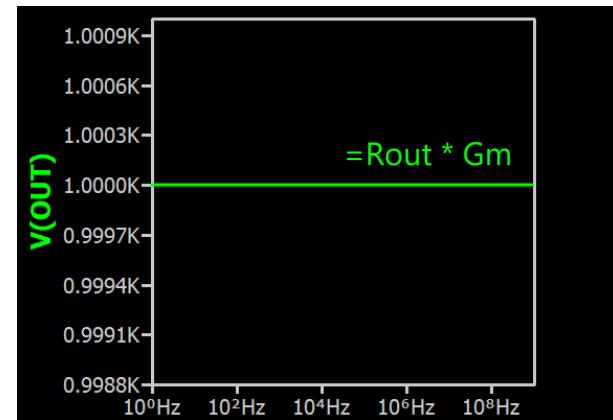
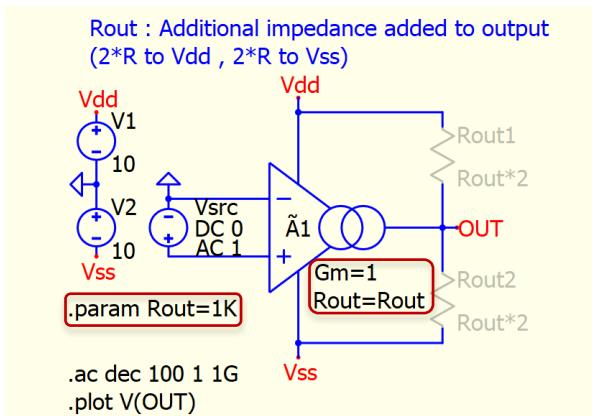


MultGmAmp : ROUT

Qspice : Multgmamp - ROUT (.ac).qsch

- ROUT in .ac
 - In .ac analysis, dc component likes quiescent current is ignored

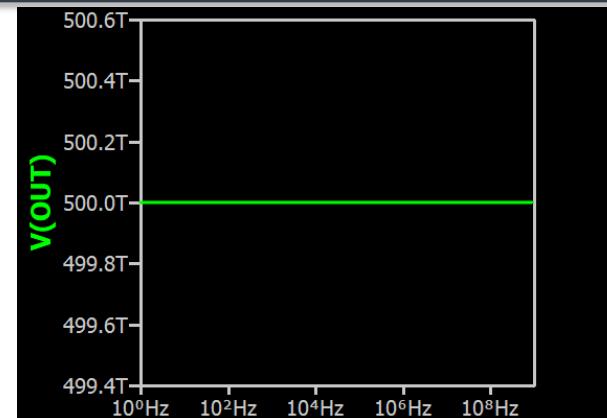
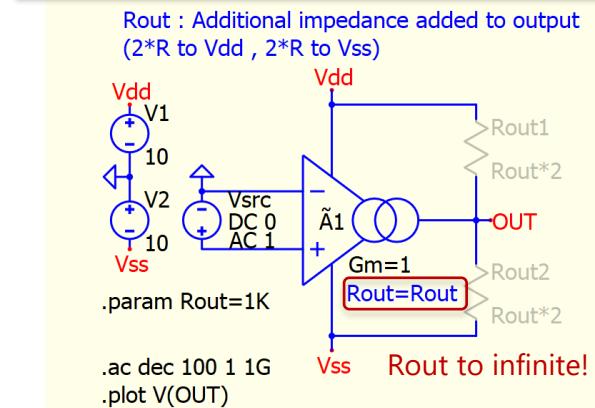
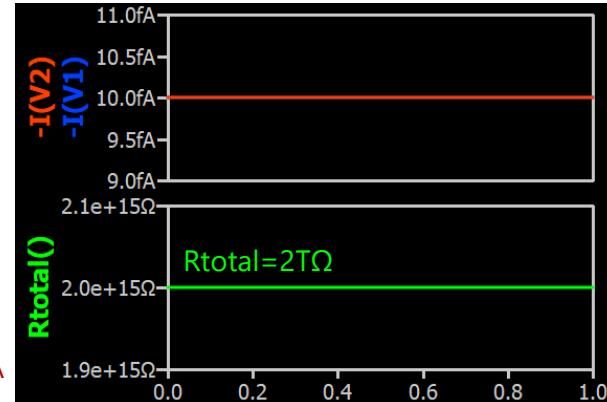
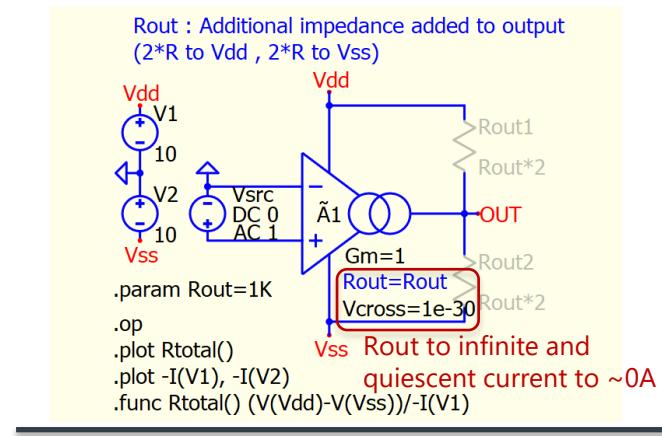
- Formula
 - By $I_{out} = Gm \times (V_{IN+} - V_{IN-})$
 - With no external resistance,
 $V_{out} = Rout \times I_{out}$
 $= Rout \times Gm \times (V_{IN+} - V_{IN-})$
 - .ac Set $V_{IN+} - V_{IN-} = 1$
 - $V_{out} = Rout \times Gm$



MultGmAmp : ROUT=Infinite

Qspice : Multgmamp - ROUT - Infinite (.op).qsch | Multgmamp - ROUT - Infinite (.ac).qsch

- Case with $R_{out} = \text{Infinite}$
 - If R_{out} is set to default, R_{out} is infinite
 - However,
 - In .op analysis, R_{total} between V_{dd} to V_{ss} is $2T\Omega$
 - In .ac analysis, V_{out} will still read a finite value which is $500T$
 - In both cases, it proved Qspice with additional $1T\Omega$ between output- V_{dd} and output- V_{ss} by $R_{out} = \text{infinite}$

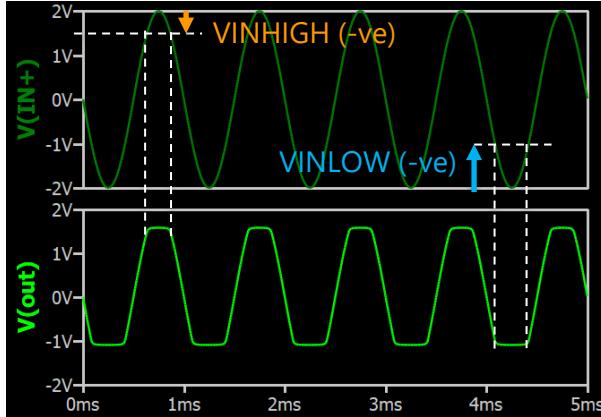
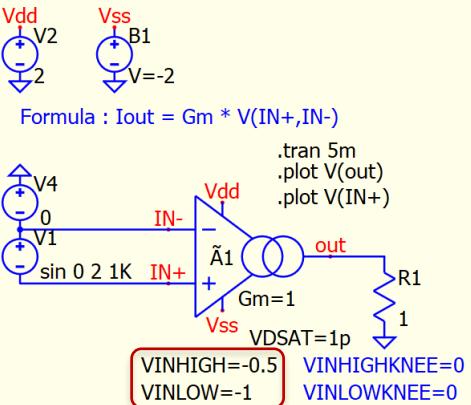


MultGmAmp : Input Range VINLOW, VINHIGH, VINHIGHKNEE, VINLOWKNEE

Qspice : Multgmamp - VINHIGH VINLOW.qsch ; Multgmamp - VINHIGHKNEE VINLOWKNEE.qsch

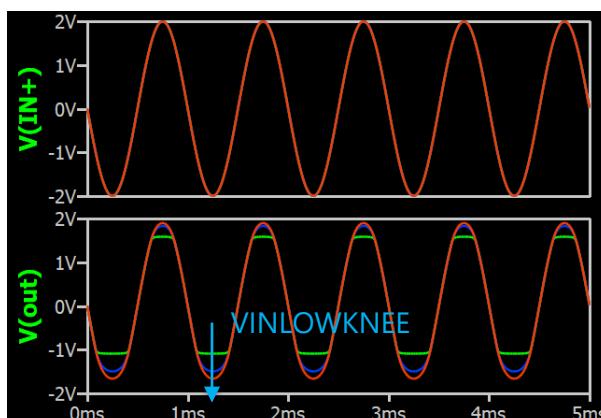
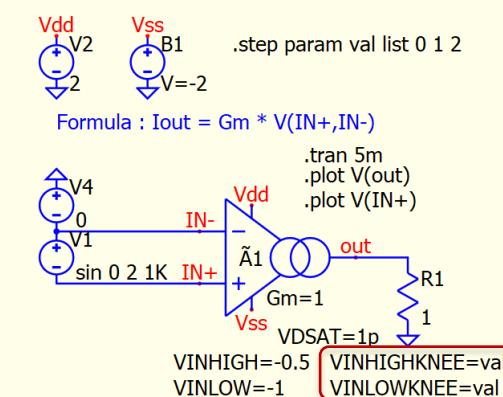
- VINLOW and VINHIGH

- VINLOW : Input range measured from negative rail
- VINHIGH : Input range measured from positive rail
- Default VINLOW=0**
- Default VINHIGH=0**
- Value is negative**, which limit input range. For example, VINHIGH=-0.5, Input HIGH is limited to $Vdd + VINHIGH = 2 - 0.5 = 1.5$ in this example



- VINLOWKNEE
VINHIGHKNEE

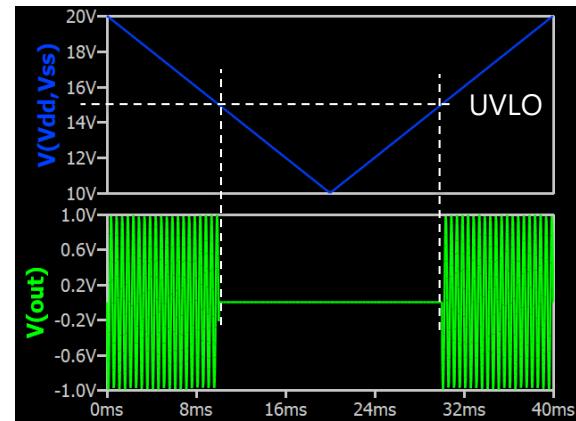
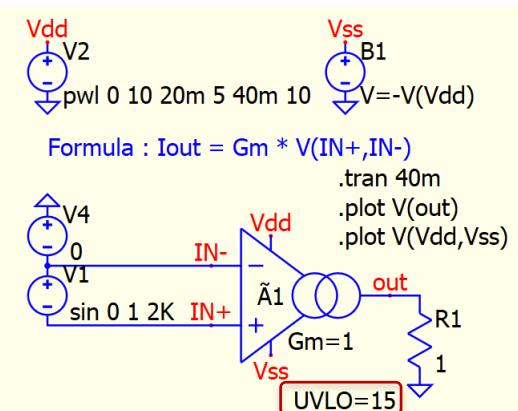
- Vinlowknee : Sharpness of negative input range limit
- Vinhightknee : Sharpness of positive input range limit
- Default VINHIGHKNEE=0**
- Default VINLOWKNEE=0**
- Increase KNEE soften the sharpness of input range, more output signal to come



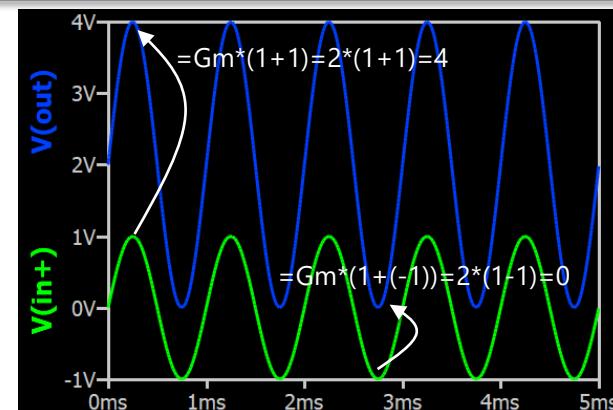
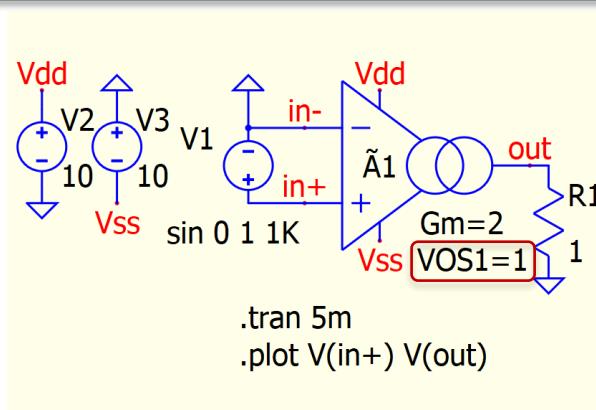
MultGmAmp : UVLO and VOS1

Qspice : Multgmamp - UVLO.qsch ; Multgmamp - VOS1.qsch

- UVLO
 - UVLO : Under Voltage Lock Out - Minimum supply voltage
 - Default UVLO is Infinite**
 - UVLO is compared to supply voltage = $V_{dd} - V_{ss}$



- VOS1
 - VOS1 : Offset voltage for input
 - $I_{out} = GM * (VOS1 + V(IN+, IN-))$
 - This parameter is not in HELP formula, but it actually implemented
 - Default VOS1 = 0**

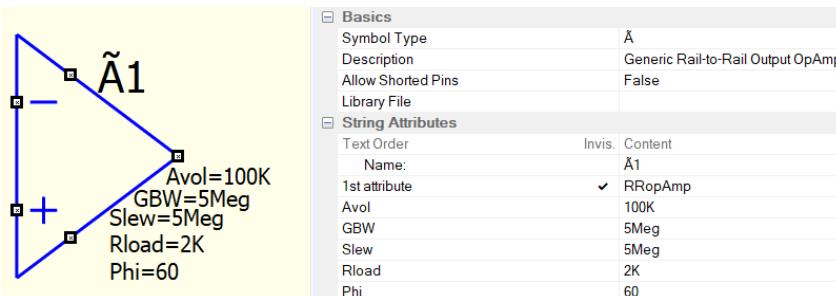


\tilde{A} -Device

Type : RRopAmp

\tilde{A} -Device RRopAmp Amplifier

- \tilde{A} -Device RRopAmp Amplifier
 - Syntax: $\tilde{A}nnn$ VDD VSS OUT IN- IN+ MULT+ MULT- IN-- IN++ EN $\$ \$ \$ \$ \$ \$ \$$ RROPAMP [INSTANCE PARAMETERS]
 - A generic rail-to-rail output opamp specified by Avol, GBW, slew rate and phase margin. **It is implemented with two Gm amps** as above with an internal node for a Miller capacitor connected to the output.
 - Therefore, we can expect some parameters are carried from MULTGMAMP

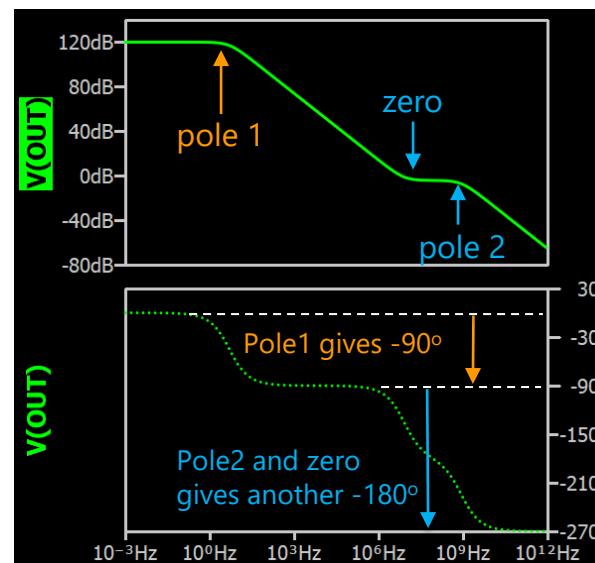
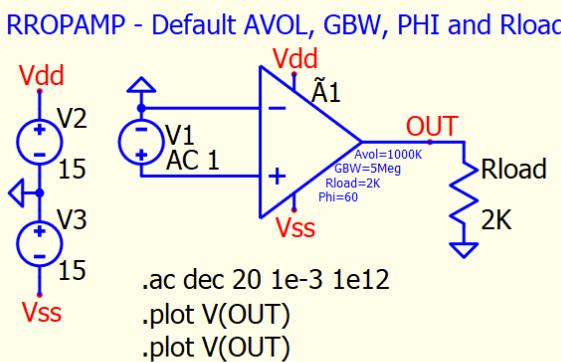


\tilde{A}-Device Instance Parameters	
Name	Description
AVOL	Open loop voltage gain when loaded with RLOAD
CAPINCM	Common eigenmode input capacitance
CAPINNM	Normal eigenmode input capacitance
CAPVDD	Capacitance from output to Vdd
CAPVSS	Capacitance from output to Vss
EN	Equivalent input voltage noise density
ENK	EN corner frequency
FT	3dB bandwidth of transconductance with no voltages slewing
GBW	Dominant pole gain-bandwidth
IC	Initial condition of $V_{in} \times V_{mult}$
IN	Equivalent input current noise density
INF	Common mode input current noise density proportional to frequency
INK	IN corner frequency
IOUT	Maximum sourcing current
ISNK	Maximum sinking current
ISNKKNEE	Sharpness of max sinking current limit
ISRC	Max sourcing current
ISRCKNEE	Sharpness of max sourcing current limit
M	Number of parallel devices
PHI	Nominal phase margin
REF	Logic threshold for enable(from Vss)
RLOAD	Load resistance used in AVOL, GBW specification
SLEW	Slew rate in Volts per second
TEMP	Instance temperature
TTOL	Temporal tolerance for enable & UVLO
UVLO	Minimum supply voltage
VCROSS	Cross conduction voltage range
VDSAT	Voltage where gm starts to switch over to a resistance
VDSAT1	Voltage where gm starts to switch over to a resistance(top FET)
VDSAT2	Voltage where gm starts to switch over to a resistance(bottom FET)
VINHIGH	Output range measured from positive rail
VINHIGHKNEE	sharpness of positive input range limit
VINLOW	Input range measured from negative rail
VINLOWKNEE	Sharpness of negative input range limit
VOS1	Offset voltage for input
VOS2	Offset voltage for multiplying input
VOUTMAX	Maximum output voltage measured from negative rail
VOUTMIN	Minimum output voltage measured from negative rail

RropAmp : RLOAD, AVOL, GBW and PHI

Qspice : RROPAMP - Second-Order TF.qsch

- RROPAMP models $G_{opamp}(s)$ with second-order transfer function
 - Opamp Open-Loop Transfer Function : $v_{out} = G_{opamp}(s) (v_+ - v_-)$
 - RROPAMP model this transfer function with two poles and one zero
 - AVOL (open loop gain), GBW (gain bandwidth) and PHI (phase margin) are defined with RROPAMP loaded with a load resistor as RLOAD



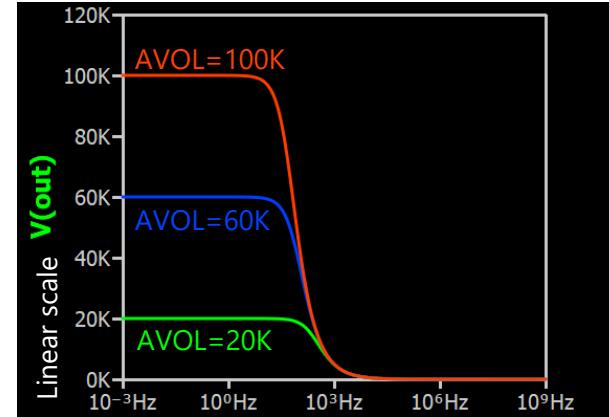
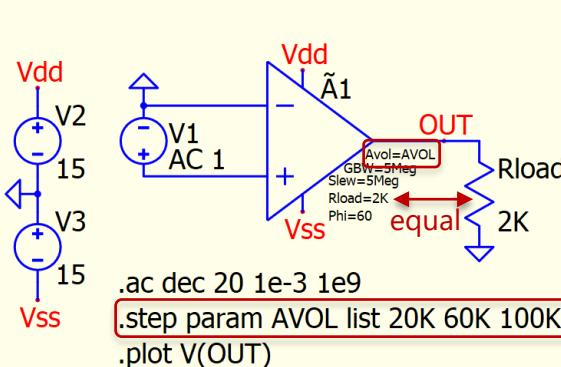
- **Pole 1**
 - Determine by **AVOL** and **GBW**
- **Pole 2 and Zero**
 - Determine by **PHI**
 - pole 2 and zero are apart by two decades which seems to be fixed by Qspice
 - Therefore, PHI cannot change how far they apart from each other, but move it through frequency to set phase margin

RropAmp : RLOAD, AVOL, GBW and PHI

Qspice : RROPAMP - AVOL.qsch | RROPAMP - GBW.qsch

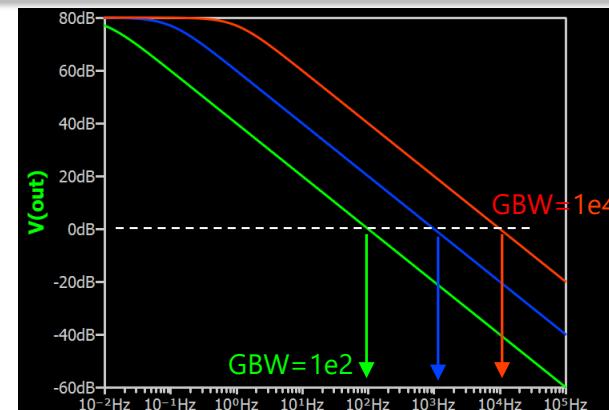
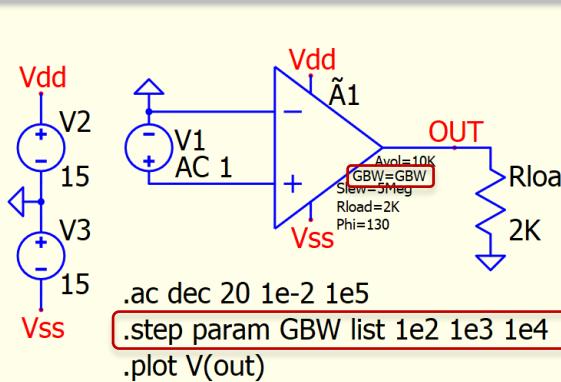
RLOAD

- Load resistance used in AVOL, GBW and PHI specification
- **Default Rload=2K**
- Output resistor with $R=Rload$ is required to obtain frequency response as according to these parameters specified



AVOL

- Open loop voltage gain when loaded with RLOAD
- **Default AVOL=1000k (120dB)**
- Gain = $\frac{V_{out}}{V_+ - V_-}$
- AVOL is gain @ 0Hz



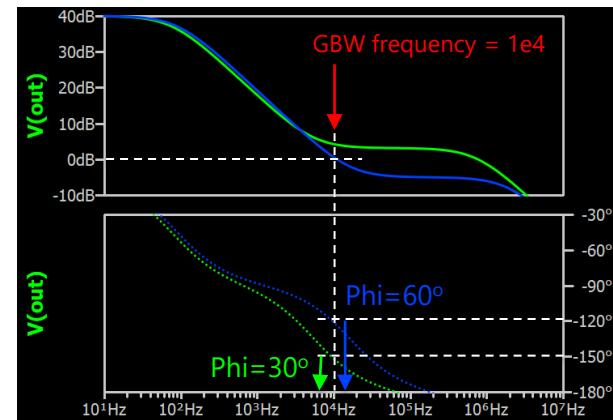
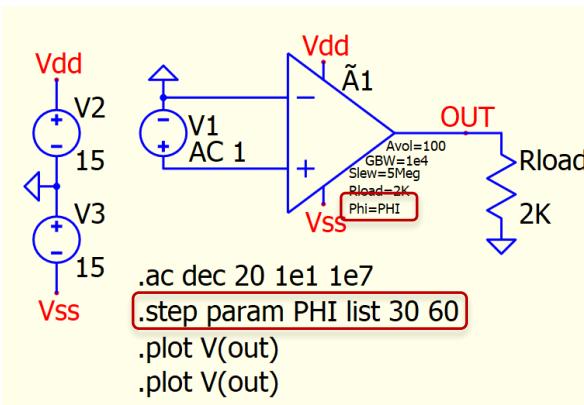
GBW

- Dominant pole gain-bandwidth
 - GBW means frequency where gain of opamp falls to unity (0dB or 1)
- **Default GBW=5Meg**

RropAmp : RLOAD, AVOL, GBW and PHI

Qspice : RROPAMP - PHI.qsch | RROPAMP - AVOL GBW PHI RLOAD.qsch

- PHI
 - Nominal phase margin
 - **Default PHI=60°**
 - Phase margin is measured of phase to -180° at 0dB (or at GBW frequency)
 - PHI should limit in the range of [0° , 90°]
 - PHI=0 or negative will force PHI to default at 60°
 - PHI>90° will limit at 90°

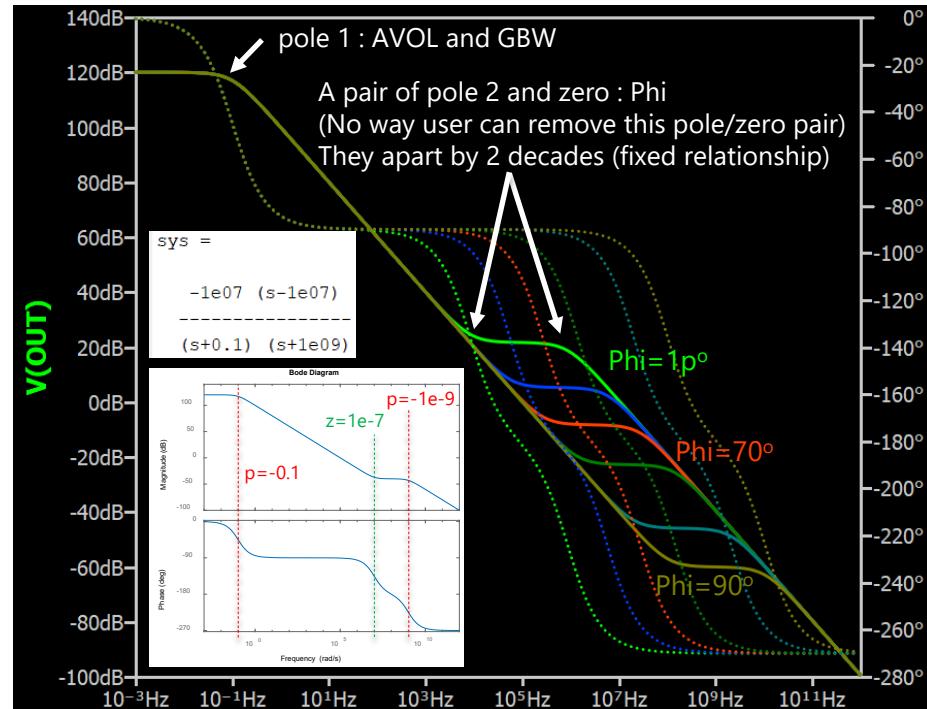
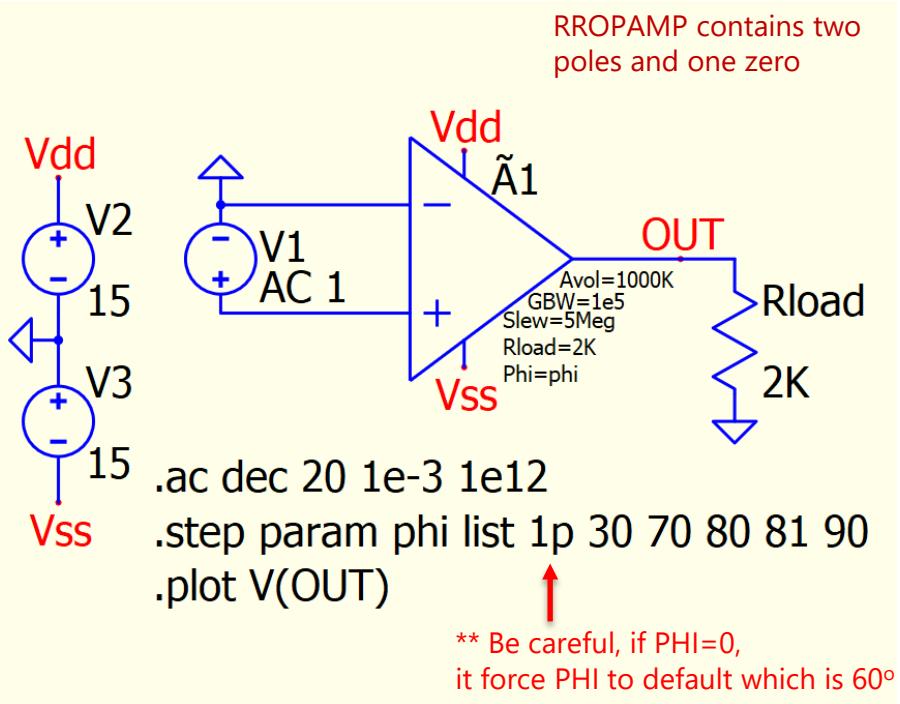


- AVOL, GBW and PHI
 - AVOL, GBW, PHI are three parameters to determine open-loop frequency response of RROPAMP
 - RLOAD
 - These three parameters are specified at this Rload condition



RropAmp : Poles and Zero Location

Qspice : RROPAMP - PHI - Pole Zero Pair.qsch

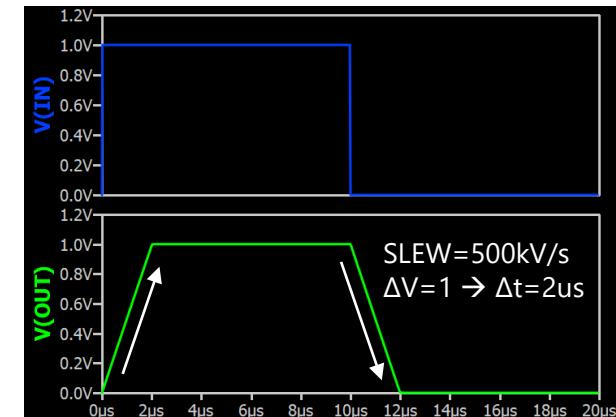
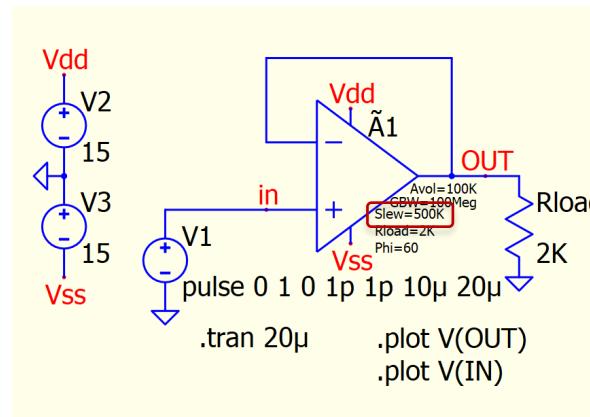


This matlab is not to replicate exact Qspice result but to demonstrates this profile is created with two -ve poles and one +ve zero

RropAmp : SLEW

Qspice : RROPAMP - SLEW.qsch

- SLEW
 - Slew rate in Volts per second (maximum change rate)
 - $SLEW = \frac{\Delta V_{out}}{\Delta t}$
- **Default SLEW=5Meg**



¥-Device

¥-Device

- ¥-Device
 - Syntax:

`¥nnn N1 N2 N3 N4 N5 N6 N7 N8 N9 N10 N11 N12 N13 N14 N15 N16 <TYPE> [INSTANCE PARAMETERS]`

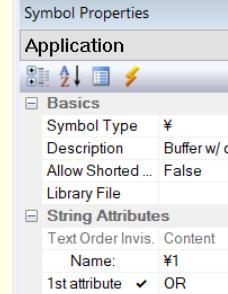
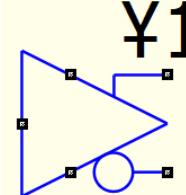
- The ¥-device supplies gate, flop, and a few other types of functional behaviors. The device expects exactly 16 pins, but not all are used. Unused pins must be specified connected to "¥".

¥-Device Types

TYPE	Behavior
AND	AND gate
CLOCKSYNC	Selects between a Sync and Clock inputs
D-FLOP	D-type flip-flop
EXTOSC	Oscillator programmed with an external resistor
HMITT	Schmitt trigger
JK-FLOP	JK-type flip-flop
MONOSTABLE	Retriggerable monostable
OR	OR gate
PS-FLOP	SMPS flip-flop
RS-FLOP	RS-type flip-flop
T-FLOP	Toggle flip-flop
XOR	XOR gate
Φ-DET	Phase/Frequency detector

To Identify what <TYPE> a symbol is

- In Symbol Properties > 1st attribute
- View > Netlist : from device syntax

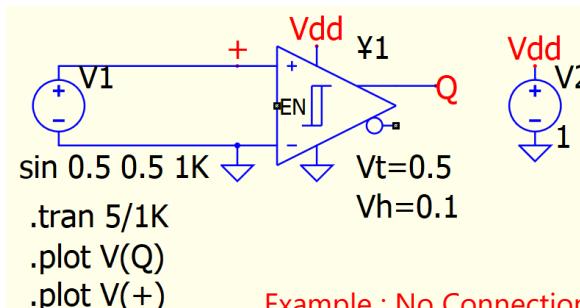


```
* C:\Users\kelvinleung\Documents\QSPICE\Unt
¥1 ¥0 ¥1 ¥2 ¥3 ¥4 ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ OR
.end
```

¥-Device : How EN pin works

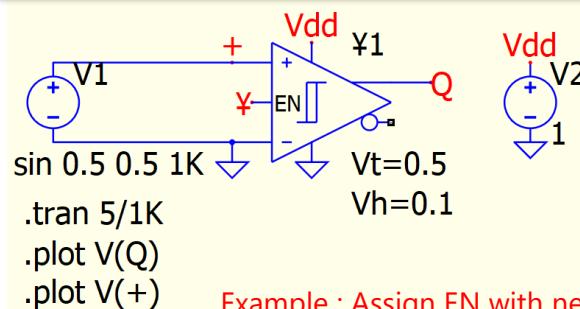
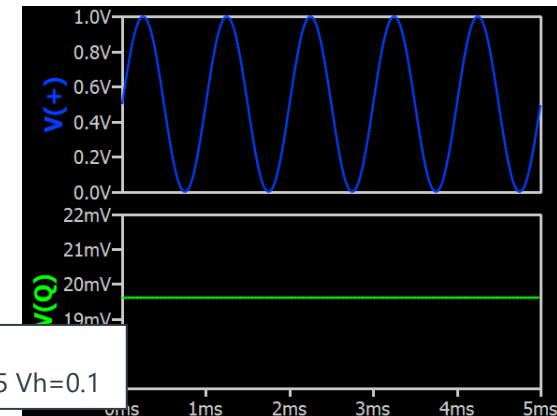
Qspice - Logic - EN.qsch

- How EN works
 - If EN is preset in symbol, normally, a signal is used to control its status. Here discuss two situations
 - #1 No connect to EN pin
 - Netlist assign ¥n as net name. EN pin is active to monitor EN signal. In this case, no output will generate
 - #2 Assign EN pin with net ¥
 - ¥ net name is equivalent to unassigned in ¥-device
 - Unassigned EN pin will be considered as Default ENABLE (except Latch)
 - Therefore, a symbol can be created with pin assigned to ¥ for their default



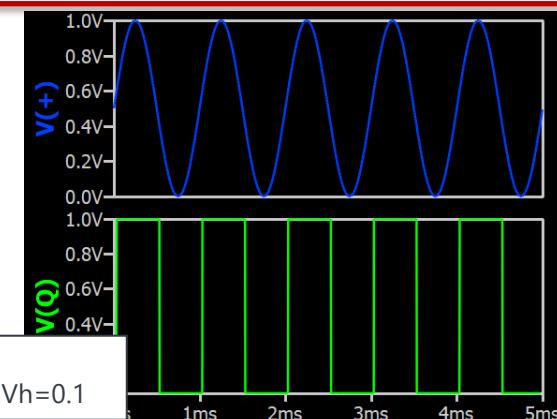
Example : No Connection

Netlist
¥1 Vdd 0 Q ¥0 + 0 ¥1 ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ HMITT Vt=0.5 Vh=0.1



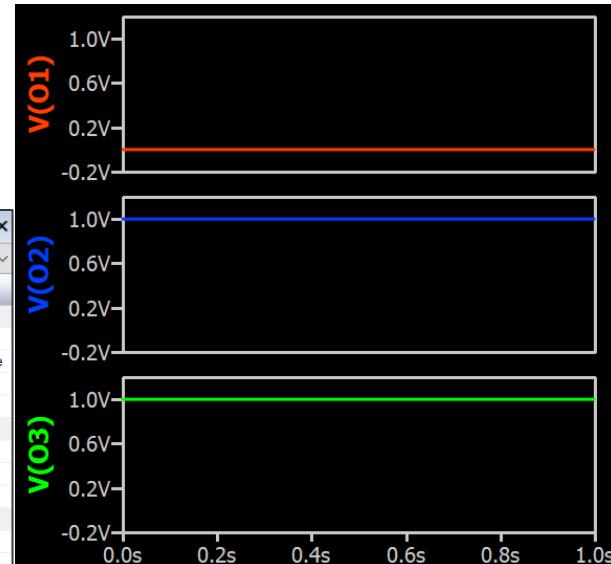
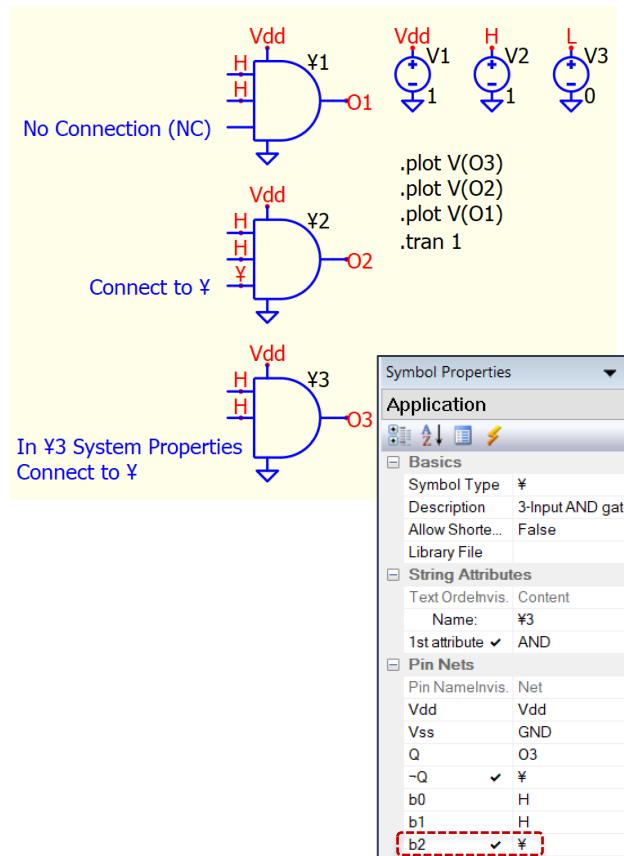
Example : Assign EN with net ¥

Netlist
¥1 Vdd 0 Q ¥0 + 0 ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ HMITT Vt=0.5 Vh=0.1



¥-Device : Net ¥

- Net ¥
 - Unconnected Pin and Pin connected to Net ¥ is different
 - Net ¥ is a special net name, in HELP of ¥-Device, it specified that unused pins must be specified connected to "¥"
 - Two methods to force a pin to ¥
- This is an example of AND gate
 - Device ¥1 : NC pin is equivalent to 0V and AND gate output 0
 - Device ¥2 : ¥ is assigned as Net in schematic and this input specified unused for this AND gate
 - Device ¥3 : ¥ is assigned but in System Properties, this input specified unused and become invisible in symbol



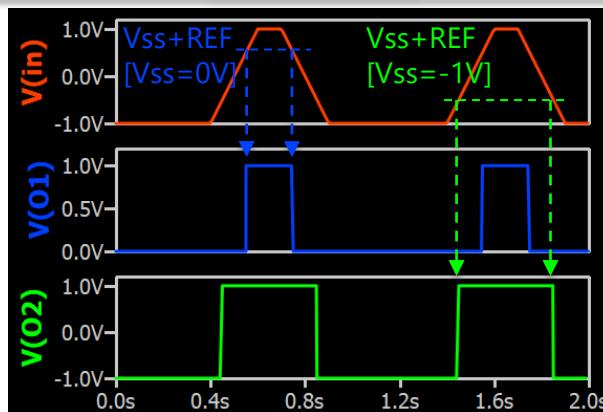
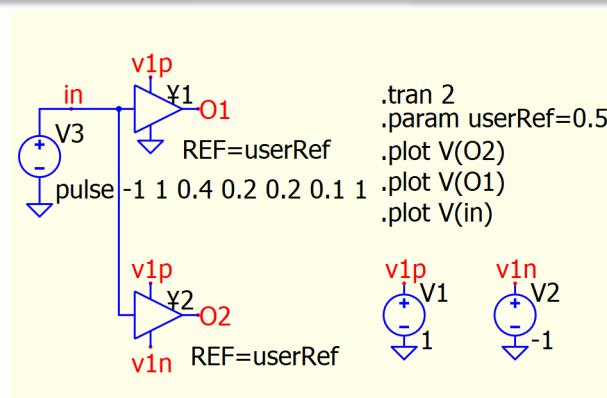
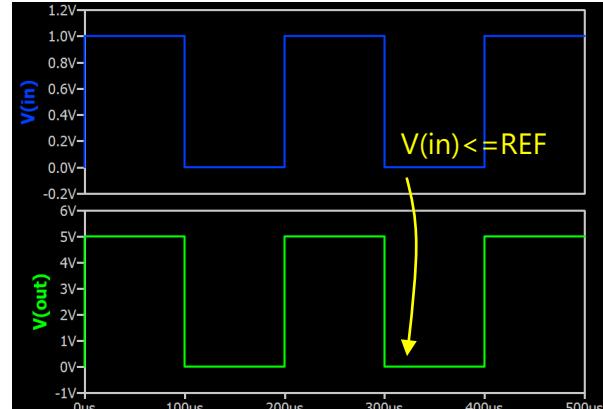
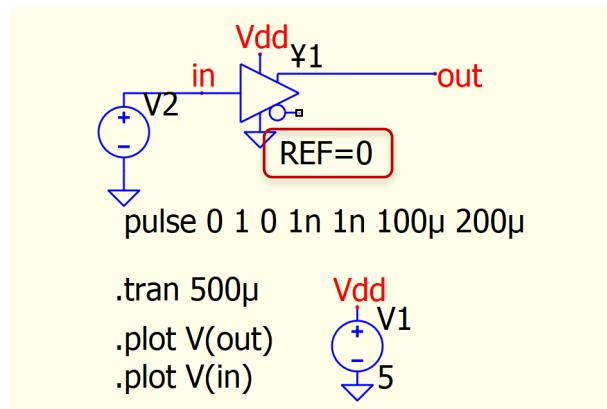
¥-Device : HELP > Simulator > Device Reference > ¥-Device
 Common Instance Parameters (example from AND Gate Instance Param)

Name	Description	Units	Default
CAPVDD	Capacitance from an output to Vdd	F	0.
CAPVSS	Capacitance from an output to Vss	F	0.
IC	Initial condition(needed, e.g., for a ring osc)		
M	Number of parallel devices		1.
REF	Logic reference voltage	V	$(Vdd + Vss) \div 2$
RSINK	Resistance to Vss when output high	Ω	RSRC
RSRC	Resistance to Vdd when output low(aka ROUT)	Ω	100.
TD	Delay(aka TD1)	s	0.
TD2	Asymmetrical delay	s	TD
TEMP	Instance temperature	$^{\circ}C$	27.
TFALL	Fall time	s	0.
TRISE	Rise time	s	0.
TTOL	Temporal tolerance	s	$1\mu s$
UVLO	Minimum Vdd-Vss voltage to operate	V	0.
ZMULT	Impedance multiplier when biased half way		1.

¥ Instance Params : REF (Logic Reference Voltage)

Qspice : Logic - REF.qsch | Logic - REF (Dual Supply).qsch

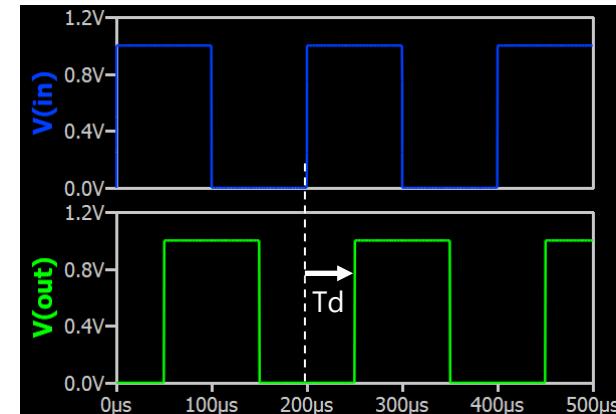
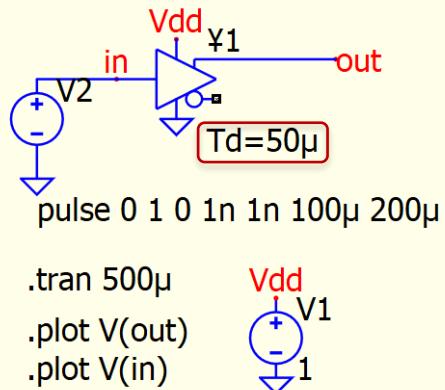
- REF
 - Logic Reference Voltage
 - **Default REF** = $\frac{Vdd + Vss}{2}$
- Threshold definition
 - Low : $V(IN) \leq \text{REF}$
 - High : $V(IN) > \text{REF}$
- Special Note
 - REF is not absolute voltage to node 0, but reference to VSS node
 - In this example, both ¥- devices have same REF, but as VSS with different potential, their logic threshold are different



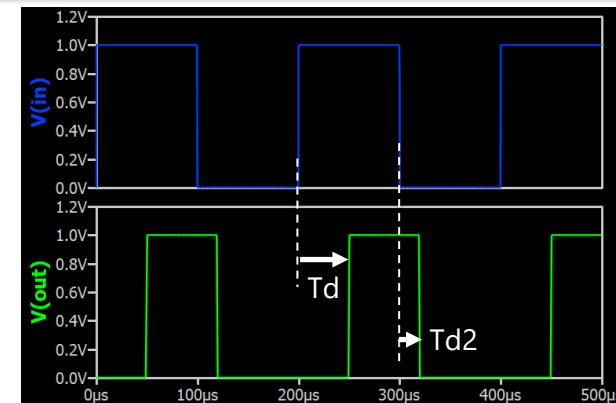
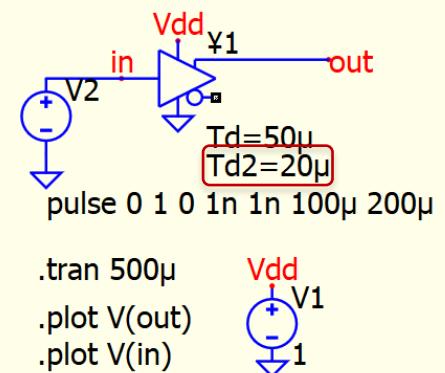
Instance Params : TD (Delay) and TD2 (Asymmetrical Delay)

Qspice : Logic - Td.qsch ; Logic - Td Td2.qsch

- TD (Delay)
 - Td : Delay
 - **Default TD=0s**
 - ** If TD2 is not set, both rising and falling delay times are same
 - ** If TD > logic H duration or delay TD2 > logic L duration, output always LOW or HIGH



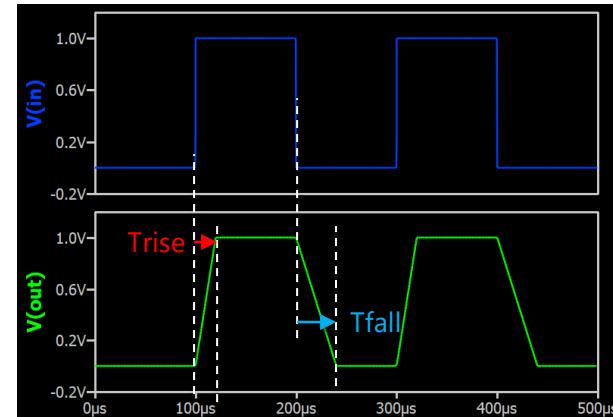
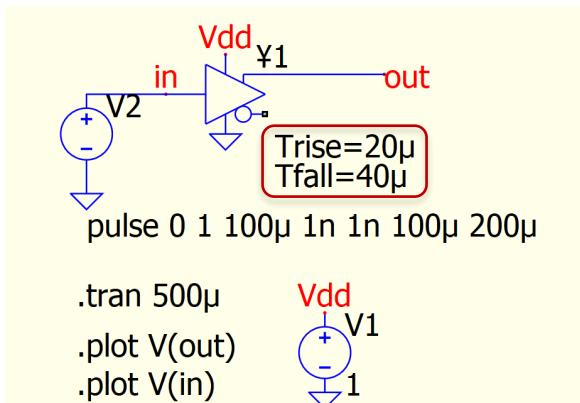
- TD2 (Asymmetrical delay)
 - TD2 : Asymmetrical delay
 - **Default TD2=TD**
 - If different delay times for rising and falling edge, set TD2 for falling edge delay time
(i.e. TD only control rising edge delay time)



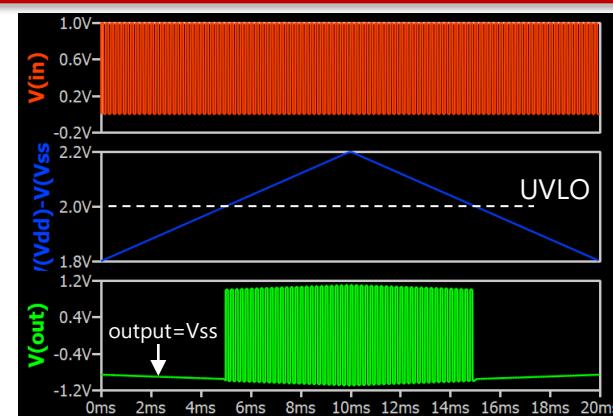
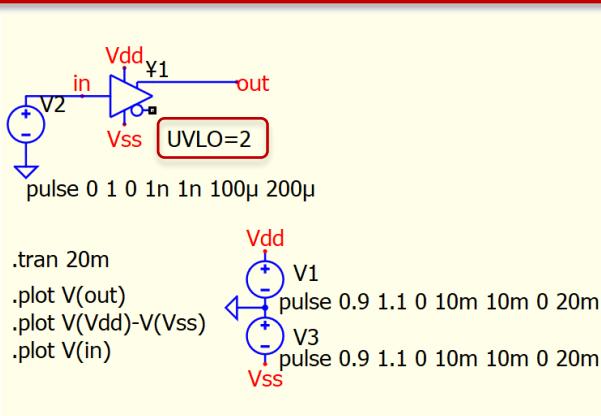
Instance Params : Trise (Rise time), Tfall (Fall time) and UVLO

Qspice : Logic - Trise Tfall.qsch | Logic - UVLO.qsch

- TRISE and TFALL
 - Trise : Rise time
 - Tfall : Fall time
 - **Default TRISE=0s**
 - **Default TFALL=0s**



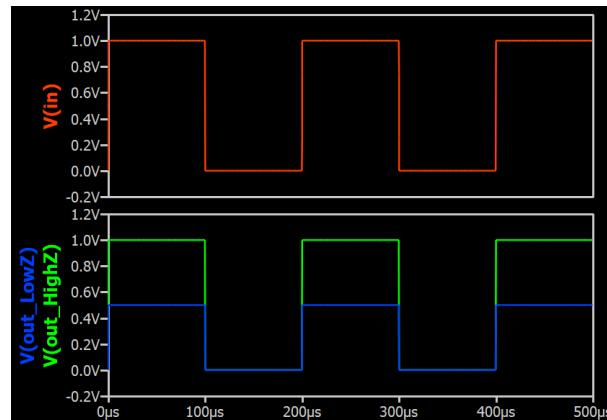
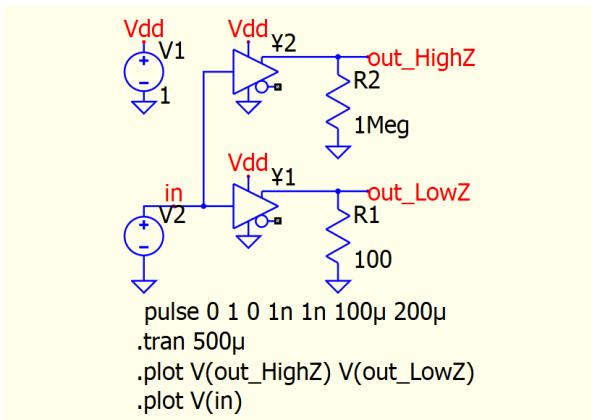
- UVLO
 - UVLO : Under Voltage Lock Out
 - **Default UVLO=0V**
 - UVLO : Minimum $Vdd-Vss$ voltage to operate
 - Output only enabled when $Vdd-Vss > UVLO$
 - Output equals Vss when gate disable



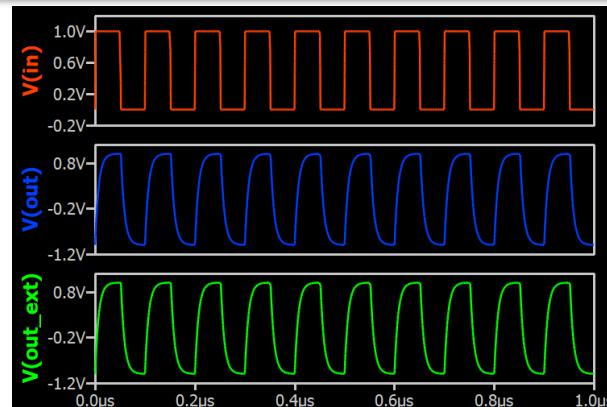
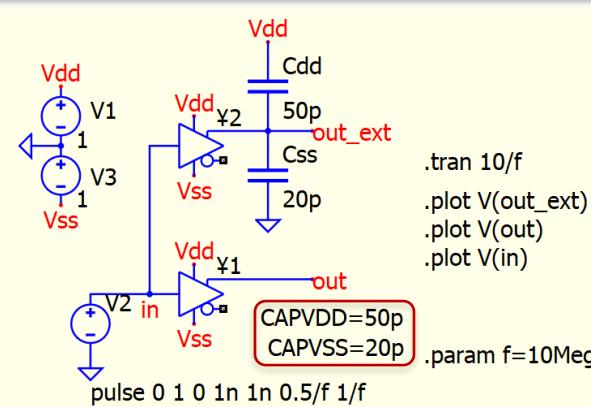
Instance Params : Output R and C (Rsink, Rsrc, Capvdd, CapVss)

Qspice : Logic - RSINK RSRC.qsch ; Logic - Capvdd Capvss.qsch

- RSINK and RSRC
 - RSINK : Res to Vss when o/p high
 - RSRC : Res to Vdd when o/p low
 - **Default RSINK=100Ω**
 - **Default RSRC=100Ω**
- Example
 - This simulation shows loading effect when output to a 100 ohms, where o/p level is reduced to half of Vdd



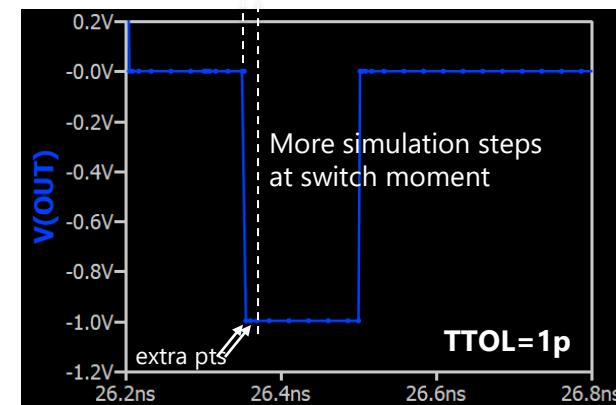
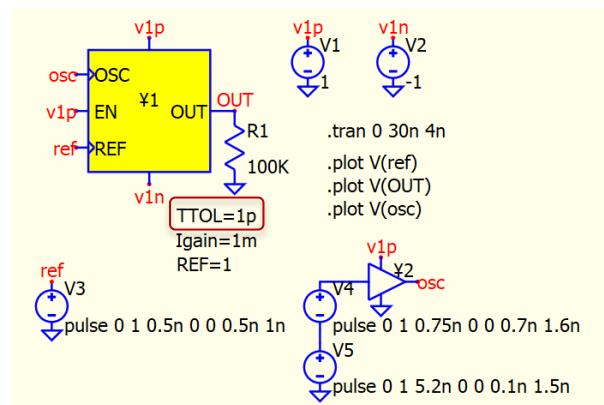
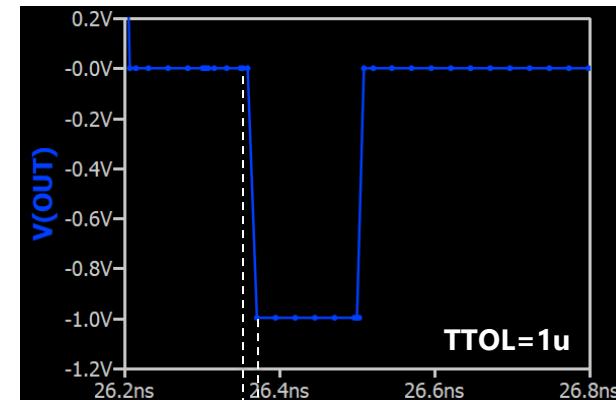
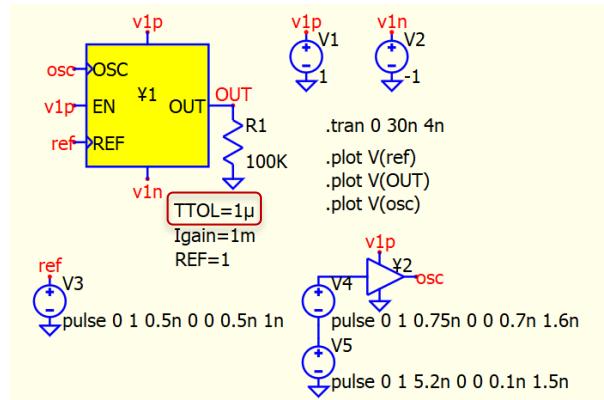
- CAPVDD, CAPVSS
 - Capvdd : Capacitance from an output to Vdd
 - Capvss : Capacitance from an output to Vss
- Explanation
 - Capacitance Capvdd/Capvss equivalent Cdd/Css this example
 - This demo can have frequency response because Rsink=Rsrc=100 internally



Instance Params : TTOL (Temporal Tolerance)

Qspice : Logic - TTOL.qsch

- TTOL
 - TTOL : Temporal tolerance
 - **Default TTOL=1u**
 - TTOL allows one to determine how accurately the switch time should be found



¥ Truth Table : AND, OR, XOR

Qspice : Truth Table of AND OR XOR.qsch

- AND

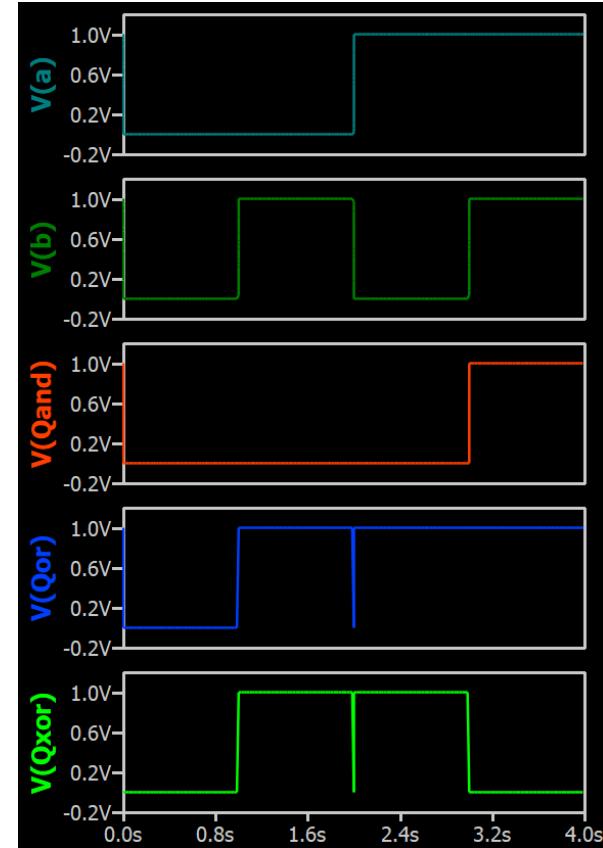
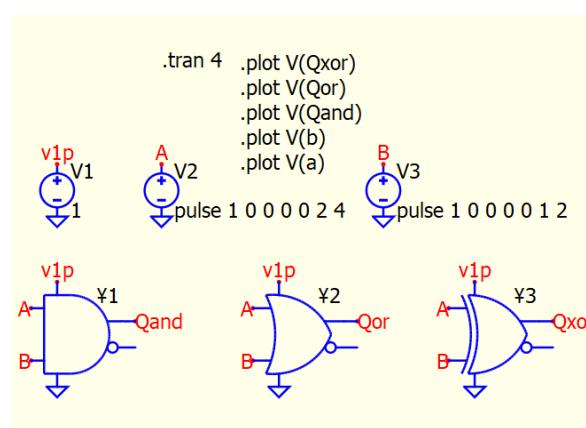
¥-Device AND			
A	B	Q	_Q
0	0	0	1
0	1	0	1
1	0	0	1
1	1	1	0

- OR

¥-Device OR			
A	B	Q	_Q
0	0	0	1
0	1	1	0
1	0	1	0
1	1	1	0

- XOR

¥-Device XOR			
A	B	Q	_Q
0	0	0	1
0	1	1	0
1	0	1	0
1	1	0	1



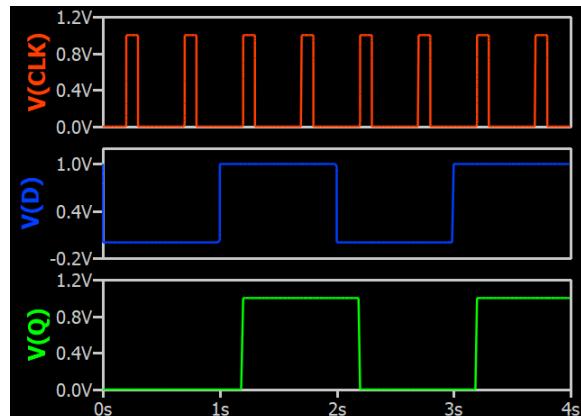
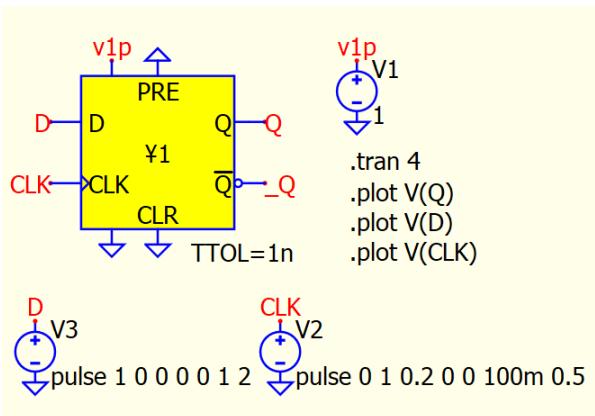
¥ Truth Table : D-FLOP and T-FLOP

Qspice : Truth Table of D-FLOP.qsch ; Truth Table of T-FLOP.qsch

- D-FLOP

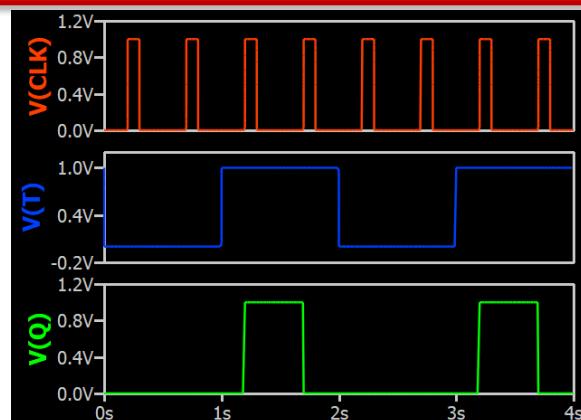
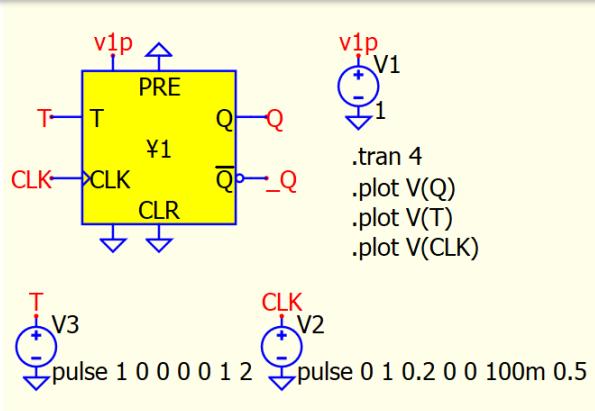
- PRE : Active High (=SET)
- CLR : Active High (=RESET)

¥-Device D-flop					
CLK	D	PRE	CLR	Q	\bar{Q}
↑	0	0	0	0	1
↑	1	0	0	1	0
x	x	0	0	Q	\bar{Q}
x	x	1	0	1	0
x	x	x	1	0	1



- T-FLOP

¥-Device T-flop				
CLK	T	PRE	CLR	Q_{n+1}
↑	0	0	0	0
↑	1	0	0	\bar{Q}_n
x	x	0	0	Q
x	x	1	0	1
x	x	x	1	0

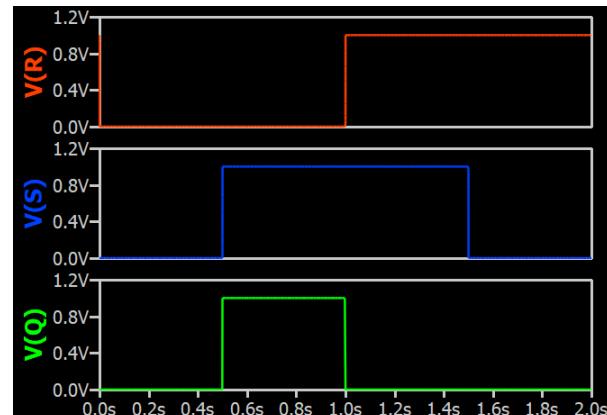
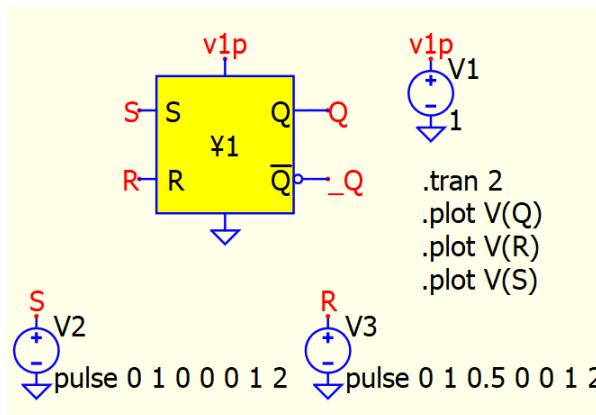


¥ Truth Table : SR-FLOP and JK-FLOP

Qspice : Truth Table of SR-FLOP.qsch ; Truth Table of JK-FLOP.qsch

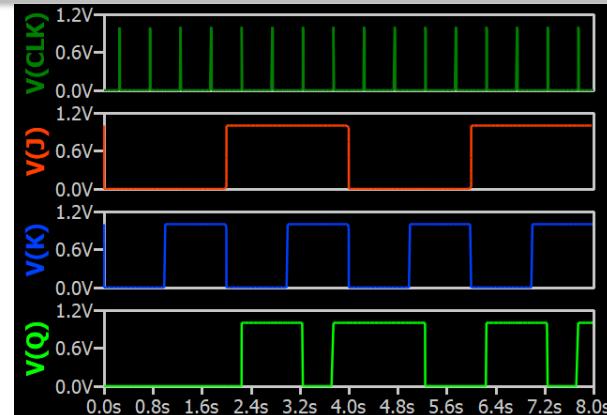
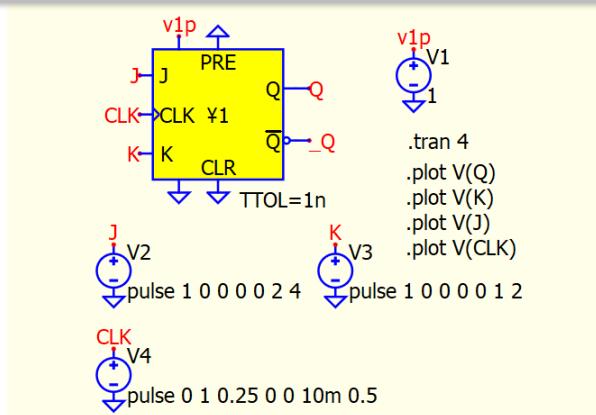
- SR-FLOP

R	S	Q	\bar{Q}
0	0	0	1
0	1	1	0
1	x	0	1



- JK-FLOP

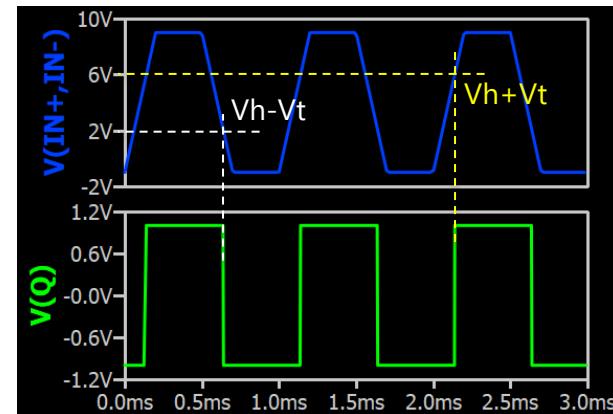
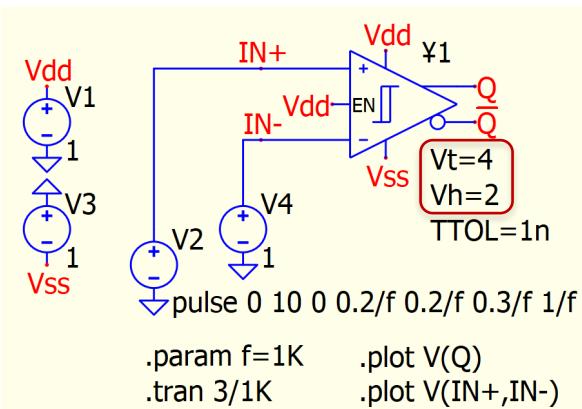
CLK	J	K	PRE	CLR	Q_{n+1}
\uparrow	0	0	0	0	Q_n
\uparrow	0	1	0	0	0
\uparrow	1	0	0	0	1
\uparrow	1	1	0	0	\bar{Q}_n
x	x	x	0	0	Q
x	x	x	1	0	1
x	x	x	x	1	0



¥-Device : Schmitt Trigger (HMITT) and Instance Parameters VT VH

Qspice : HMITT - Vt Vh.qsch

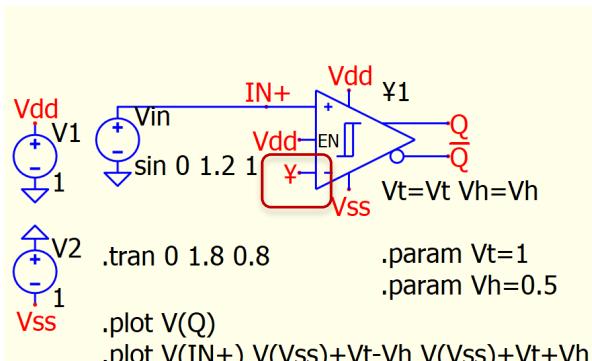
- Schmitt Trigger
 - HMITT is schmitt trigger logic input
- VT and VH
 - Vt : Threshold voltage
 - Vh : Half hysteresis voltage
 - Hysteresis for differential
 $V(IN+,IN-) = V(IN+) - V(IN-)$
 - True : $V(IN+,IN-) > VT + VH$
 - False : $V(IN+,IN-) < VT - VH$
 - Supply voltage Vdd and Vss only affect HMITT output but not input comparison



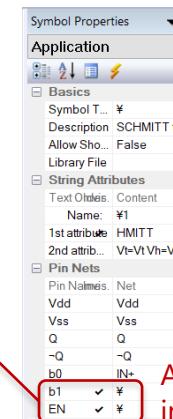
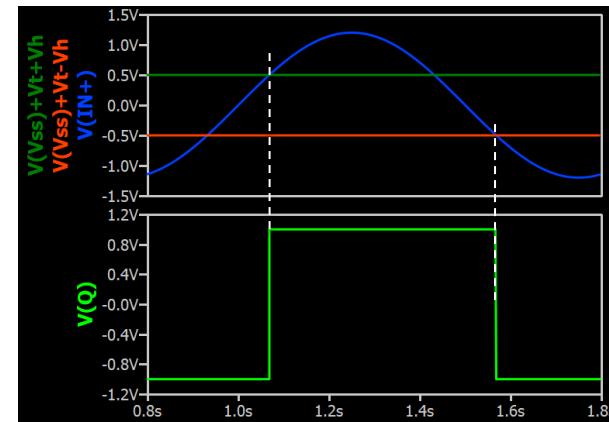
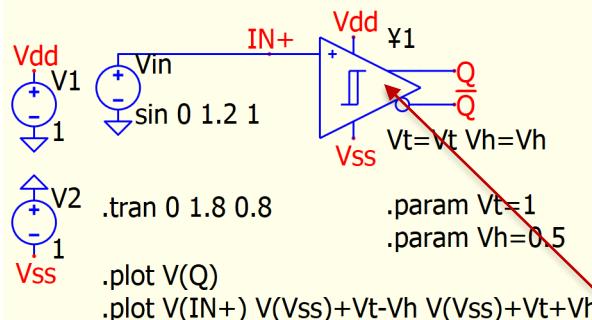
¥-Device : Schmitt Trigger - IN- to ¥ node, EN to ¥ node

Qspice : HMITT - IN- to ¥.qsch | HMITT - EN to ¥.qsch

- IN- connect to ¥
 - Schmitt trigger comparator allows IN- connect to ¥
 - This is equivalent IN- connect to Vss
 - Schmitt trigger output
TRUE : $V(IN+) > V(VSS) + VT + VH$
FALSE : $V(IN+) < V(VSS) + VT - VH$



Identical Setup

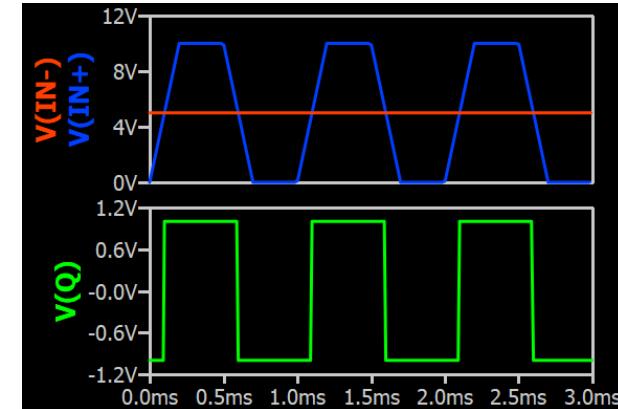
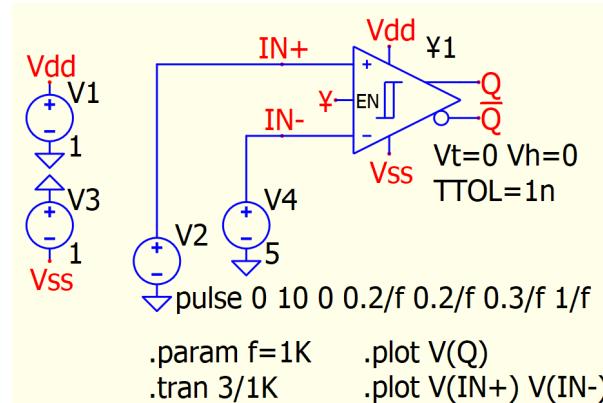


Assign ¥ in Pin Nets in Symbol Properties

¥-Device : Schmitt Trigger – Simple Comparator

Qspice : HMITT - Simple Comparator.qsch

- Simple comparator
 - A simple comparator can be built with $V_t=0$ and $V_h=0$, which are the default values for V_t and V_h
 - It will only compare the output based on the relationship between $V(\text{IN}+)$ and $V(\text{IN}-)$

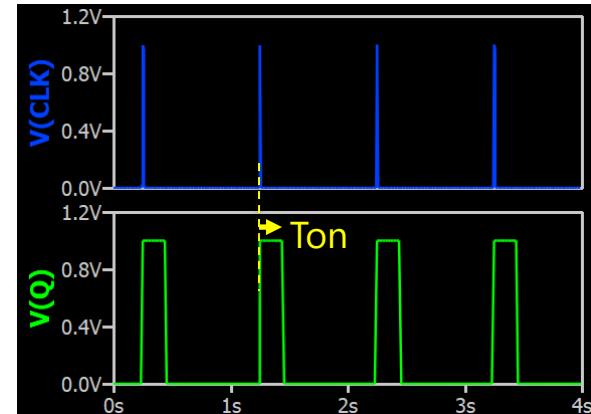
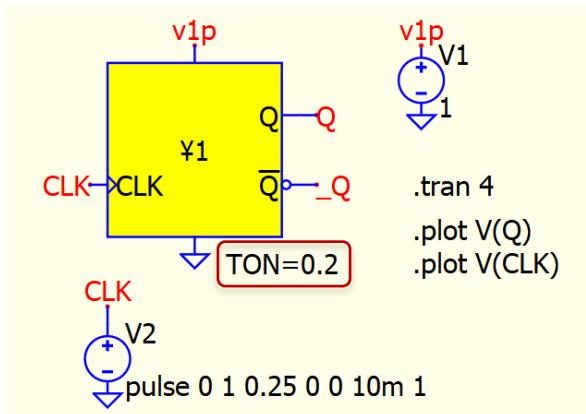


¥-Device : Monostable and Latch (Sample and Hold S&H)

Qspice : Usage - Monostable.qsch | Usage - Latch Sample and Hold.qsch

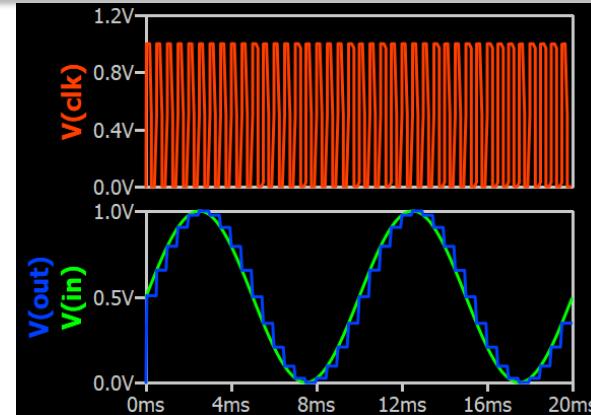
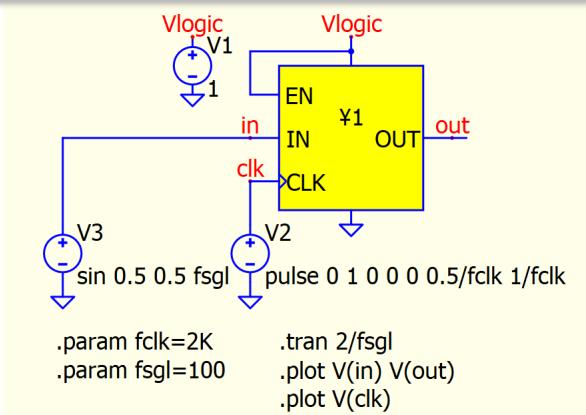
• Monostable

- TON : Monostable on time
- **Default TON=0s**
- Need to add this attribute when Monostable Symbol is called to use in Qspice
- TON must be specified to use Monostable
- CLK trigger a minimum on-time pulse



• Latch

- Edge-sensitive Sample and Hold



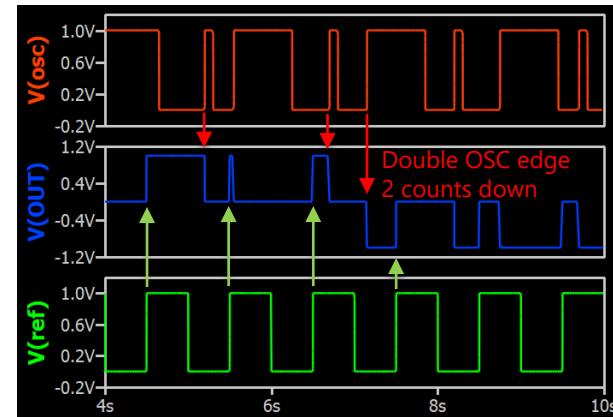
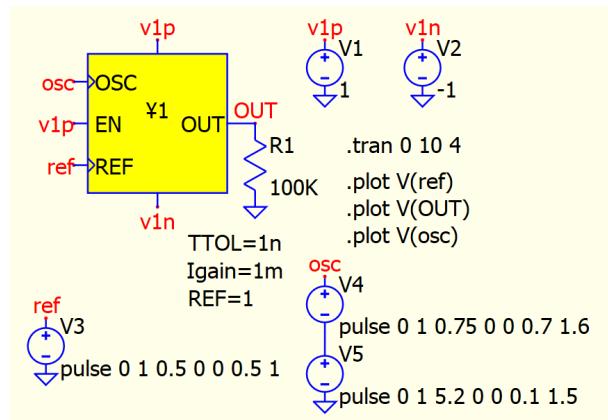
¥ Truth Table : Φ -DET (Phi-Det) [Symbol : PhaseDetector in analog]

Qspice : Truth Table of Phi-Det.qsch

- Φ -DET (Phi-Det)
 - Phase/Frequency Detector

¥-Device Phi-Det		
REF	OSC	OUT
↑	x	Up
x	↑	Down
↑	↑	Unchange

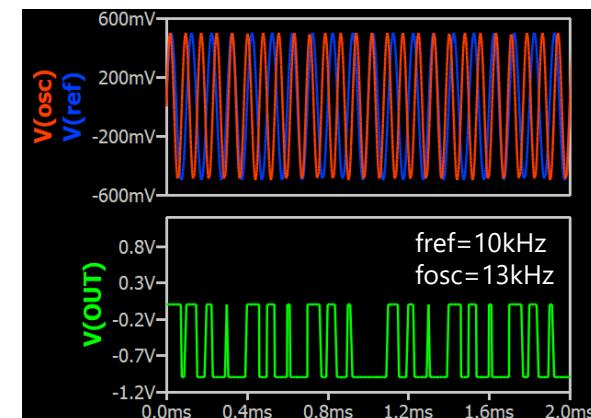
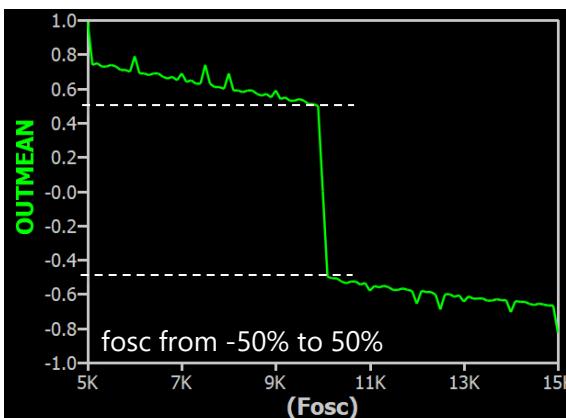
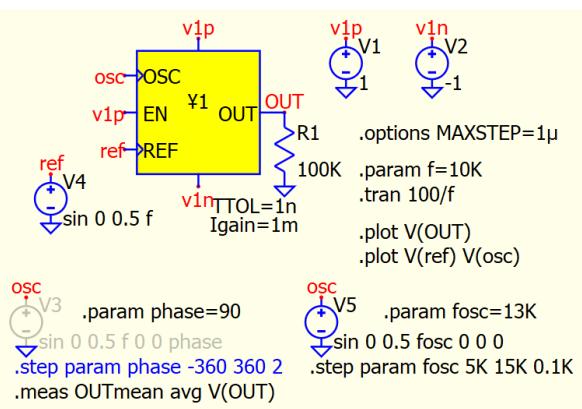
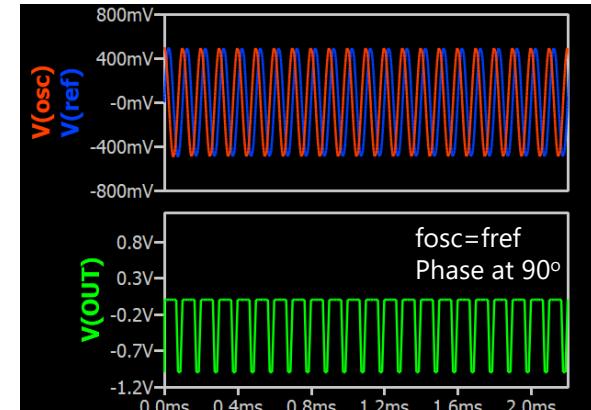
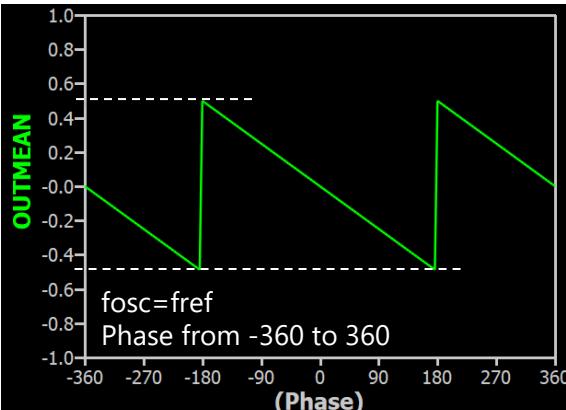
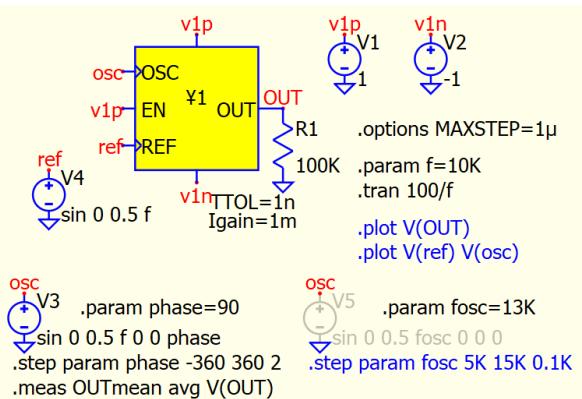
- Important
 - Output is current, not voltage
 - Suggest to set a higher Igain for OUT can reach Vdd/Vss with load (Default Igain only 10µA)
 - This device is a [Vdd, 0, Vss] 3-state counter, therefore, must operate with dual supply
 - REF edge counts up
 - OSC edge counts down



- Phase/Frequency Detection
 - Next slide is simulation results in phase change and frequency change
 - Mean of PWM output pattern can differentiate it is OSC signal phase or frequency deviate from REF signal
 - This is a key component in Phase Lock Loop (PLL)

¥-Device Φ -DET (Phi-Det) : OSC and REF Relationship with OUT

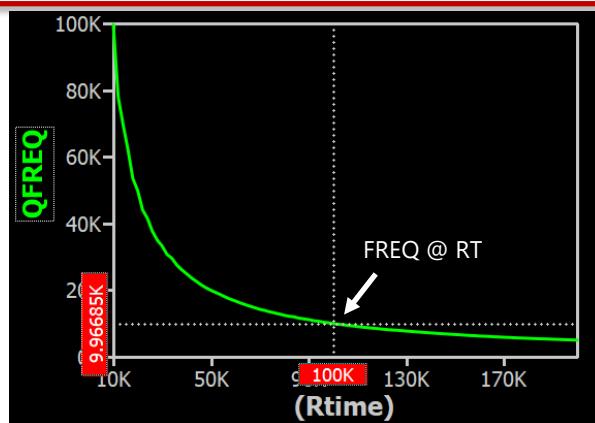
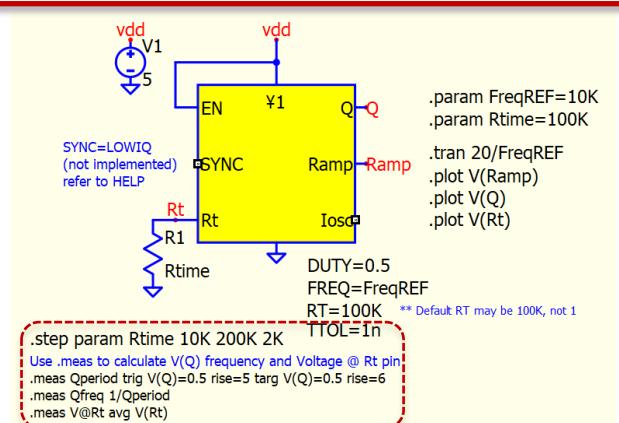
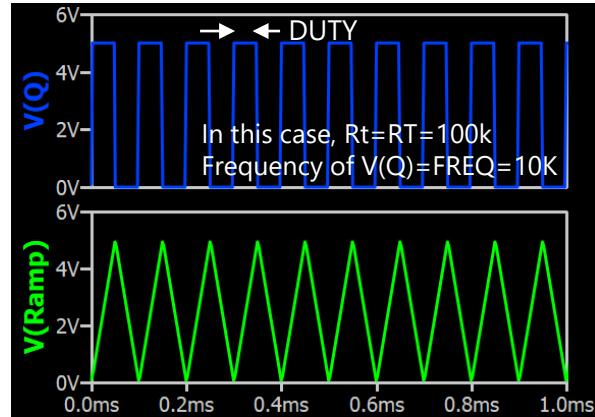
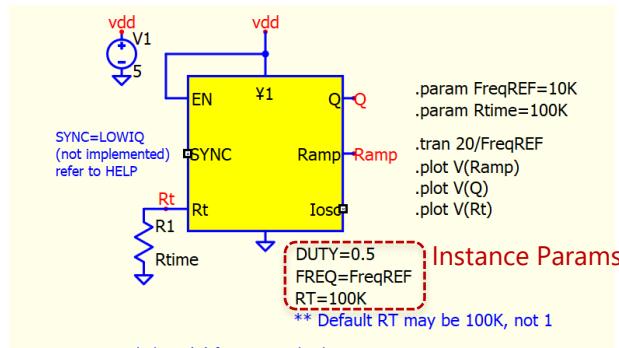
Qspice : Usage - Phi-Det (Freq and Phase).qsch



¥-Device EXTOSC : Oscillator programmed with an external resistor

Qspice : Usage - Extosc - Rtime .tran.qsch | Usage - Extosc - Rtime .step.qsch

- EXTOSC
 - Oscillator programmed with an external resistor
 - Instance Parameters
 - DUTY : Oscillated V(Q) duty [Default DUTY = 0.9]
 - FREQ : Oscillated Frequency @ RT [Default FREQ=100kHz]
 - RT : Timing Resistance (Rtime) value at FREQ [Default RT=100kohms]
 - Symbol : **ExtOsc4** in analog
 - Oscillator frequency is controlled by external resistor with this symbol as no Vres1 and Vres2 pins
- V(Q) frequency vs Rtime
 - This simulation uses .step param Rtime and .meas to plot frequency of V(Q) vs Rtime relationship
 - It can observe that V(Q) frequency has inverse relationship with Rt
 - $\text{Freq of } V(Q) = \frac{RT}{Rtime} \times \text{FREQ}$

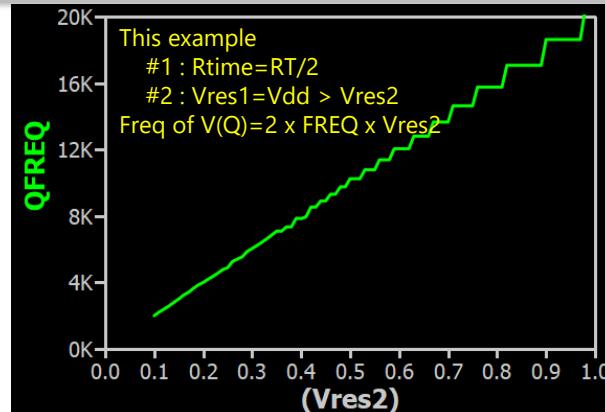
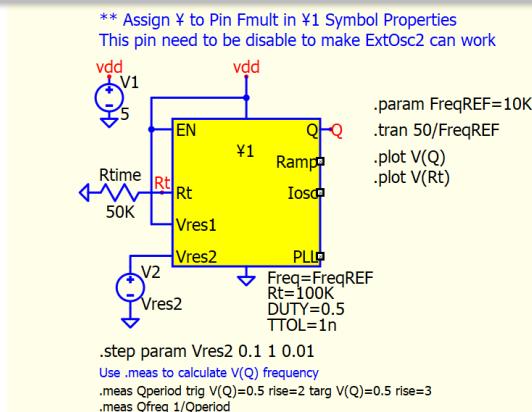
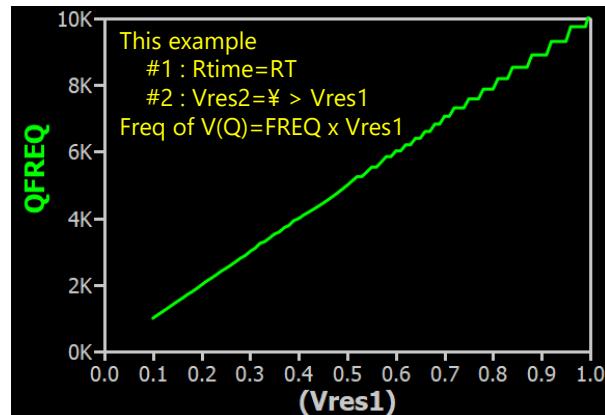
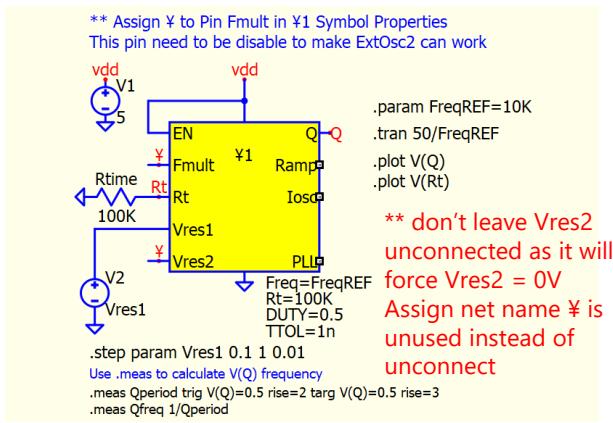


¥-Device EXTOSC : Oscillator programmed with an external resistor

Qspice : Usage - Extosc - VRES1.step.qsch | Usage - Extosc - VRES2.step.qsch

- V(Q) frequency vs Vres1/2
 - Symbol : **ExtOsc2** in analog
 - Oscillator frequency is controlled by voltage at Vres1 or Vres2 pins
 - This model with Vres1 and Vres2
 - Vres2 is not mentioned in Qspice HELP, but indeed there
 - Oscillator uses minimum value of Vres1 and Vres2 to determine output frequency
 - Instance Parameter VRT (voltage on timing resistor) can affect Frequency
 - **Freq of V(Q)**

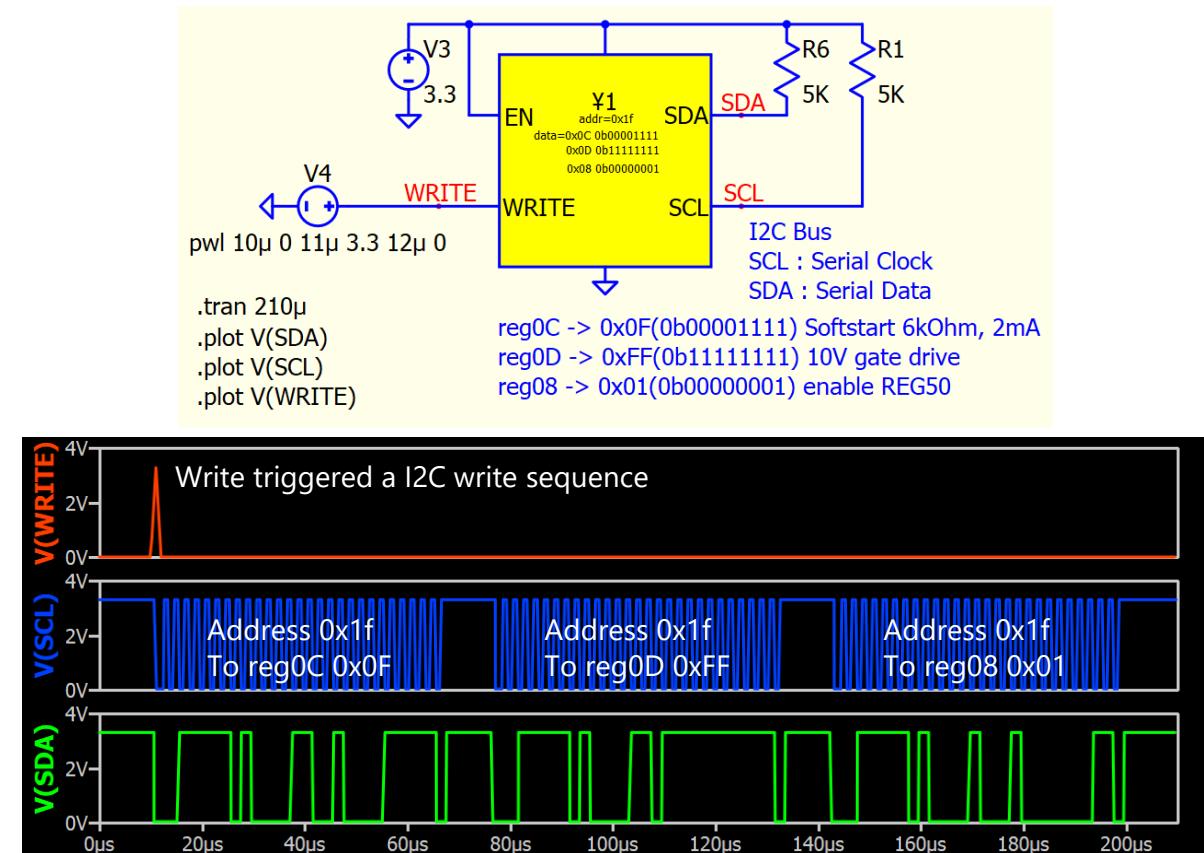
$$= \frac{RT}{Rtime} \times FREQ \times \frac{\min(Vres1, Vres2)}{VRT}$$
- Typically, the spare one would be used for frequency foldback when the output is shorted to ground
- ** Fmult should connect to ¥ in using ExtOsc2 symbol
 - Method #1 : Connect to a Net ¥
 - Method #2 : Right Click symbol, System Properties, find Pin Name Fmult and assign Net as ¥, Fmult will be invisible and connect to ¥



¥-Device I2C

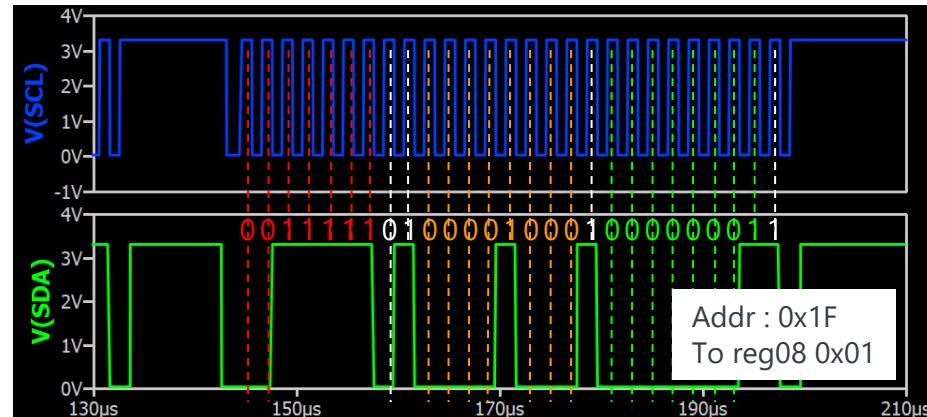
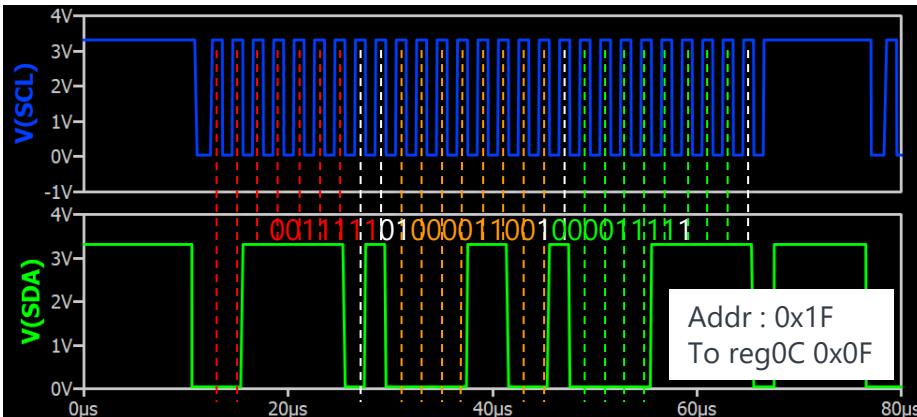
Qspice : Usage – I2C.qsch

- I2C
 - Master I²C
 - Not in Qspice HELP
 - Write information into slave registers to instruct its to perform task
 - Rising edge from **WRITE** will trigger I2C ¥-Device to output I2C data which defined in **addr=** and **data=**
 - SCL : Serial Clock
 - SDA : Serial Data
- Syntax
 - ¥nnn VDD VSS SDA SCL EN
WRITE ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥ ¥
 - I2C addr=<addr>
data=<reg> <data> ...



¥-Device I2C

Qspice : Usage – I2C.qsch



¥-Device I2C Timing Diagram

- I2C Timing
 - [Address 7-bits][Read/Write][ACK][REG][ACK][DATA][ACT]
- To Register 0C , Data 0x0F (0b00001111)
 - 001111101000011001000011111
 - In HEX : [0x1f]01[0x0C]1[0b00001111]1
- To Register 08, Data 0x01 (0b00000001)
 - 001111101000010001000000011
 - In HEX : [0x1f]01[0x08]1[0b00000001]1

¥1
addr=0x1f
data=0x0C 0b00001111
0x0D 0b11111111
0x08 0b00000001

Address
0x1F=0b0011111 (7bits)

¥-Device I2C : Reference of I2C Timing Diagram

- I2C Bus : Write

- Reference
 - Understanding the I2C Bus
 - Application Report SLVA704
 - <https://www.ti.com/lit/an/slva704/slva704.pdf>

Writing to a Slave On The I^C Bus

To write on the I^C bus, the master will send a start condition on the bus with the slave's address, as well as the last bit (the R/W bit) set to 0, which signifies a write. After the slave sends the acknowledge bit, the master will then send the register address of the register it wishes to write to. The slave will acknowledge again, letting the master know it is ready. After this, the master will start sending the register data to the slave, until the master has sent all the data it needs to (sometimes this is only a single byte), and the master will terminate the transmission with a STOP condition.

Figure 8 shows an example of writing a single byte to a slave register.

- Master Controls SDA Line
- Slave Controls SDA Line

Write to One Register in a Device

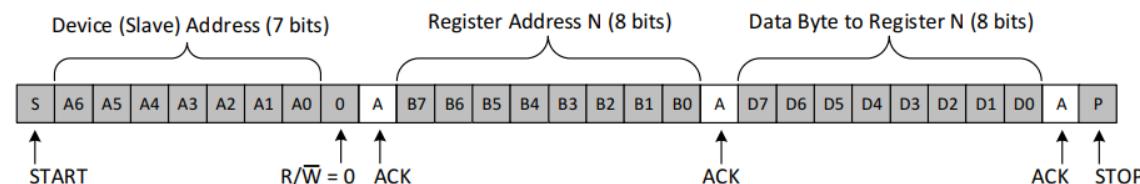


Figure 8. Example I^C Write to Slave Device's Register

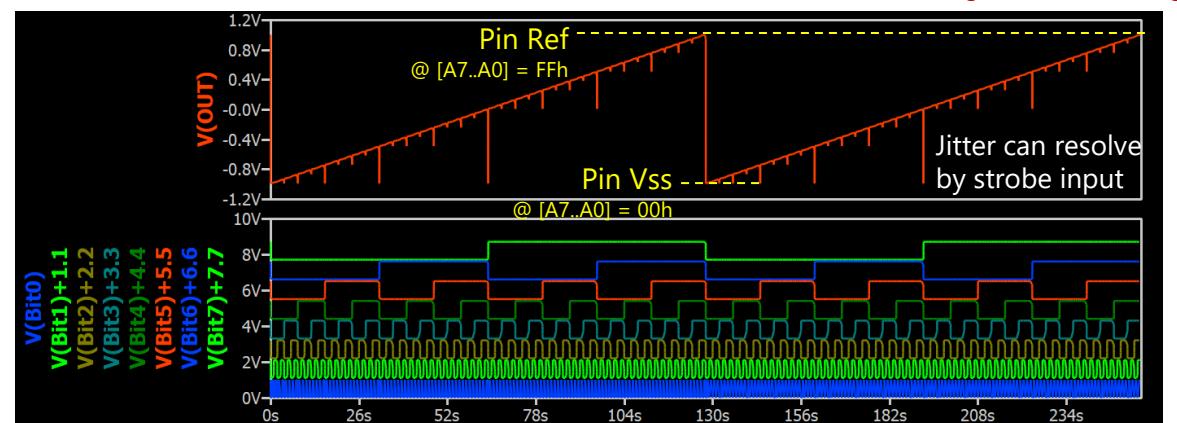
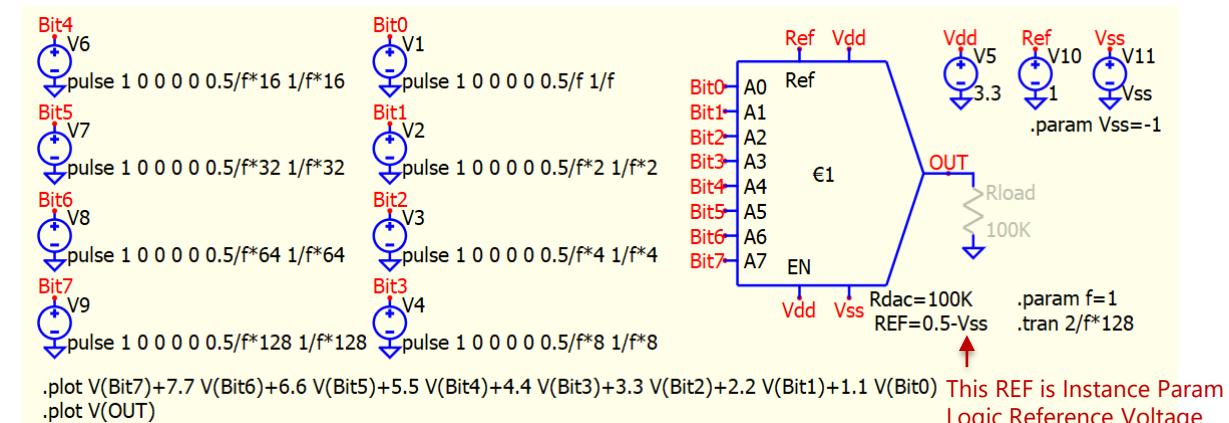
Read=1
Write=0

ϵ -Device

€-Device DAC : Build-in Symbol DAC8.qsym

Qspice : DAC - Basic.qsch

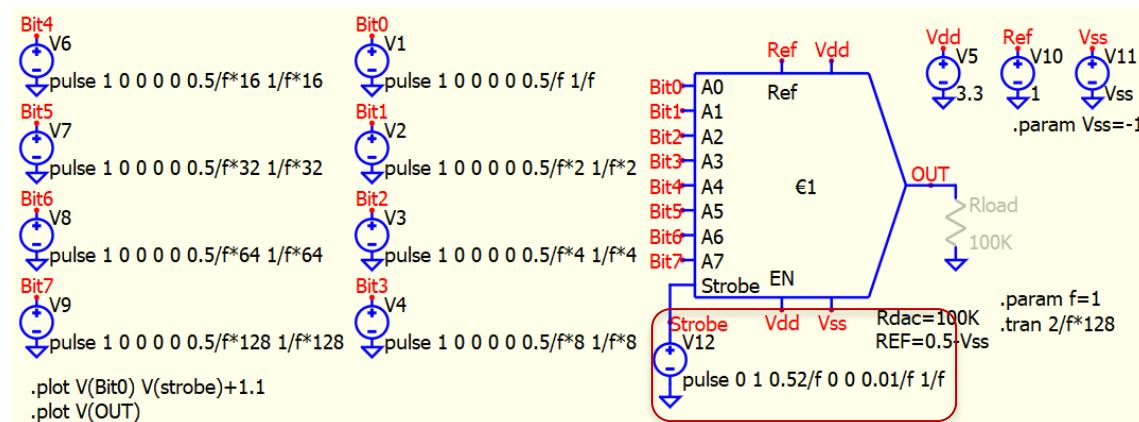
- DAC
 - DAC : Digital to Analog Converter
- Important Pins
 - Ref : the maximum voltage value that the DAC can reach
 - A7 : MSB of input word A
 - A0 : LSB of input word A
 - EN : Enable
- Instance Params
 - Common instance params can refer to €-Device section (e.g. REF)



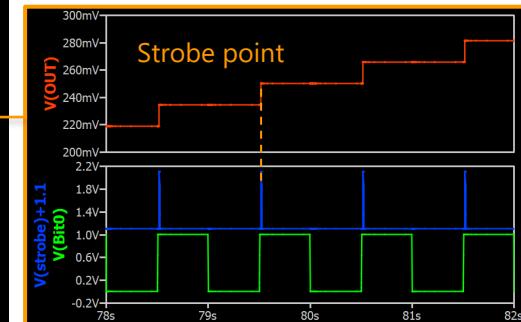
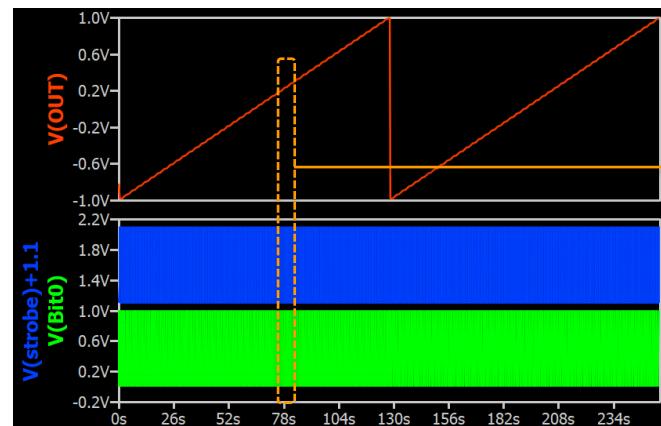
€-Device DAC : Build-in Symbol DAC8strobe.qsym

Qspice : DAC - Strobe.qsch

- Strobe
 - In practice, it named as load DAC strobe (LDAC)
 - This pin transfers all input register data to the DAC registers
 - It resolve jitter in V(out) in previous slide



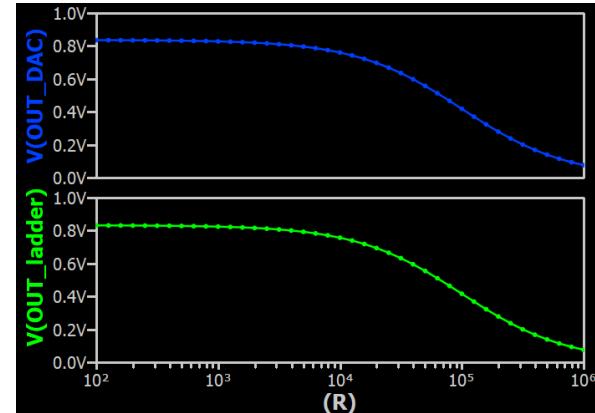
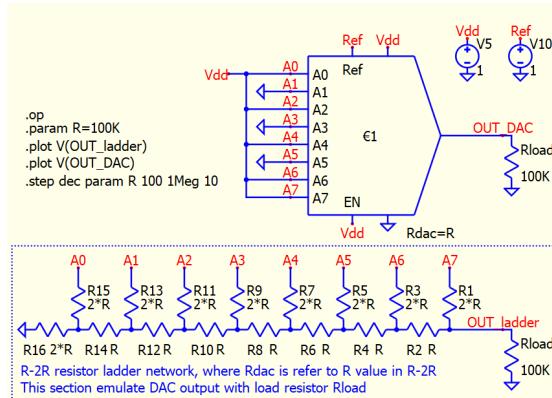
- Symbol
 - Build-in symbol with strobe is
 - DAC8strobe.qsym



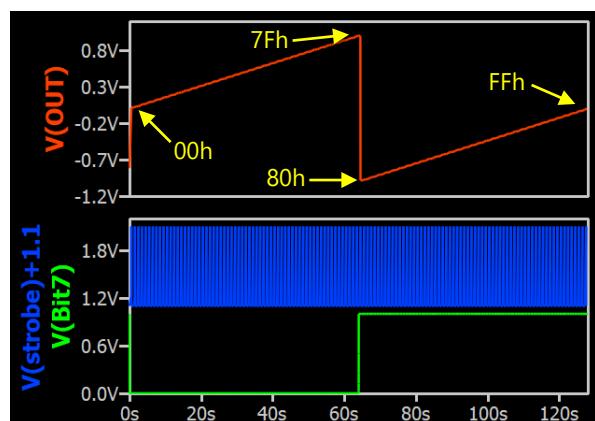
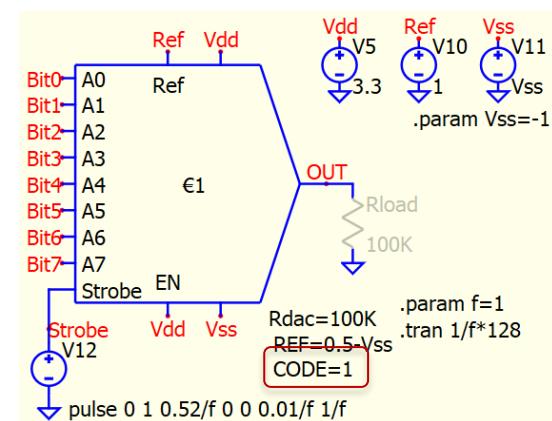
€-Device DAC Instance Params : RDAC

Qspice : DAC - RDAC.qsch ; DAC - CODE.qsch

- RDAC
 - Rdac : R of R-2R DAC
 - R-2R resistor ladder network is inexpensive solution for digital to analog conversion
 - Reference
 - https://en.wikipedia.org/wiki/Resist_ladder
 - Therefore, to prevent loading effect, a voltage buffer should be used in DAC output



- CODE
 - Code : Non-zero maps from -n to n-1 to 0 to 2n-1
 - Default CODE=0**
 - CODE=0 : Unsigned
 - CODE=1 : Signed - two's complement

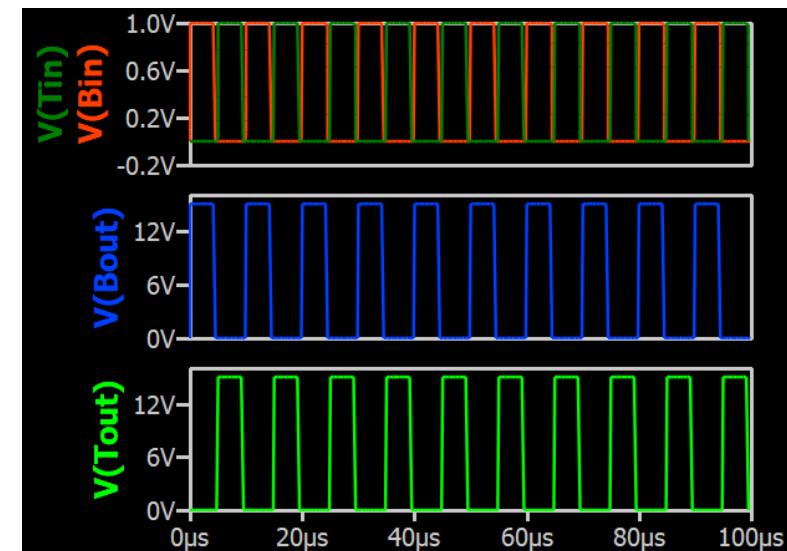
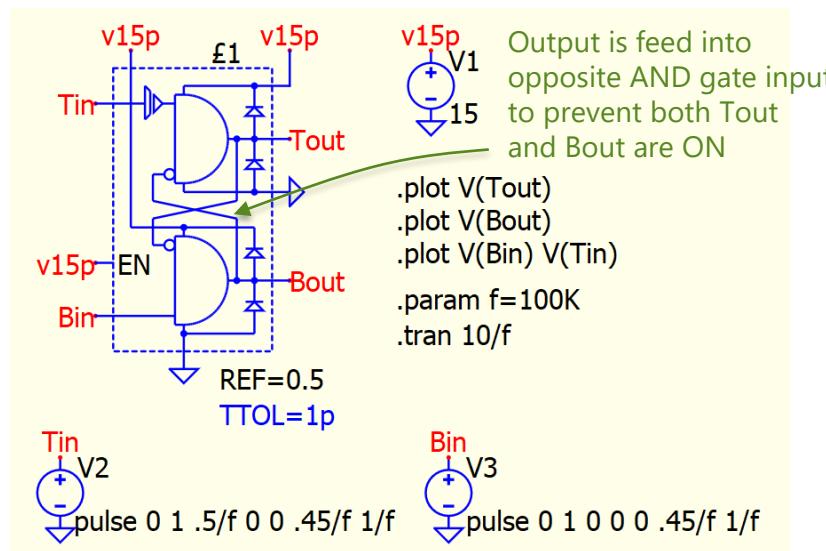


f -Device

f-Device : Dual Gate Driver

Qspice : Dual Gate Driver.qsch

- f-Device Dual Gate Driver
 - Syntax: fnnn Vdd Vss BOOST TOPGATE SW BOTGATE TCTRL BCTRL EN ¥ ¥ ¥ ... GATEDRIVER [INSTANCE PARAMETERS]
 - This behavioral device expects Top Input and Bottom Input has deadtime in between



£ [Dual Gate Driver] Instance Params

Gate Driver Instance Parameters

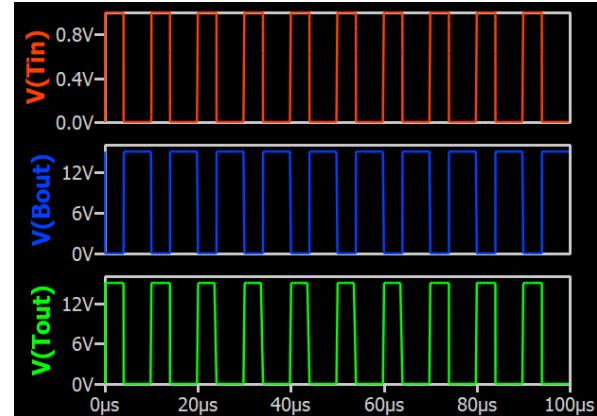
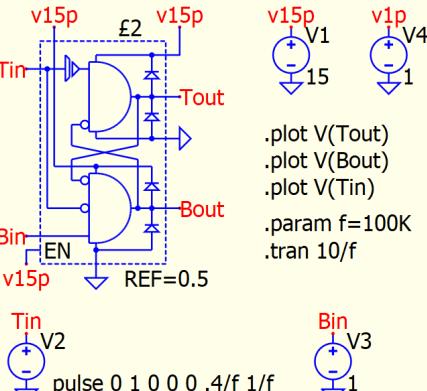
Name	Description	Units	Default
BOOST	Add logic such that the top FET is off if the bottom is controlled to be on		(not set)
BUCK	Add logic such that the bottom FET is off if the top is controlled to be on		(not set)
CAPVDD	Capacitance from a logic output to Vdd(or BOOST)	F	0.
CAPVSS	Capacitance from a logic output to Vss(or SW)	F	0.
M	Number of parallel devices		1.
REF	Logic reference for enable input	V	$(Vdd + Vss) \div 2$
ROFF1	Resistance used to pull bottom FET to VSS	Ω	RON1
RON1	Resistance used to pull bottom FET to VDD	Ω	1.
ROFF2	Resistance used to pull top FET to SW	Ω	ROFF
RON2	Resistance used to pull top FET to BOOST	Ω	RON1
RPASSIVE	Resistance used to pull both FETs' gates low when the driver is not enabled	Ω	1Meg
TEMP	Instance temperature	$^{\circ}C$	27.
TTOL	Temporal tolerance	s	
UVLO	Minimum Vdd-Vss voltage to operate	V	2.

£ [Dual Gate Driver] Instance Params - Buck and Boost

Qspice : Dual Gate Driver (Buck).qsch; Dual Gate Driver (Boost).qsch

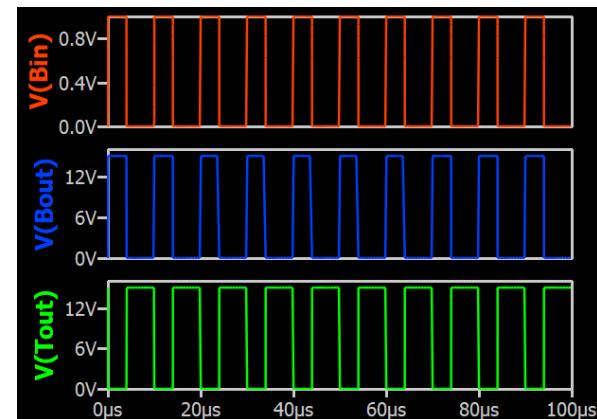
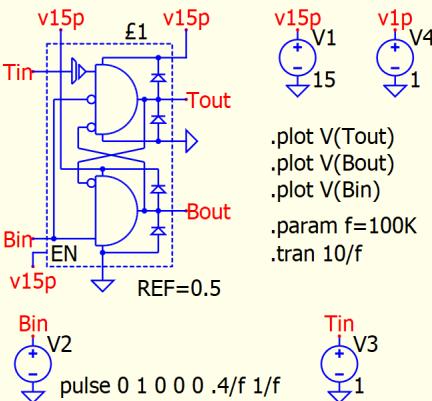
• BUCK

- Add logic such that the bottom FET is off if the top is controlled to on
- **Tin** is inverted to drive Bottom AND gate
 - Bin connects to LOW
- Switch of buck converter is generally at High Side



• BOOST

- Add logic such that the top FET is off if the bottom is controlled to be on
- **Bin** is inverted to drive Top AND gate
 - Tin connects to HIGH
- Switch of boost converter is generally at Low Side

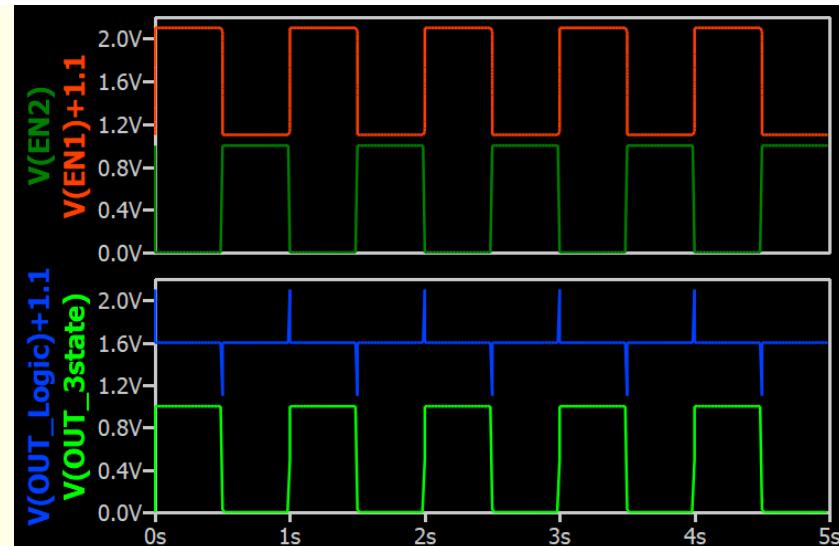
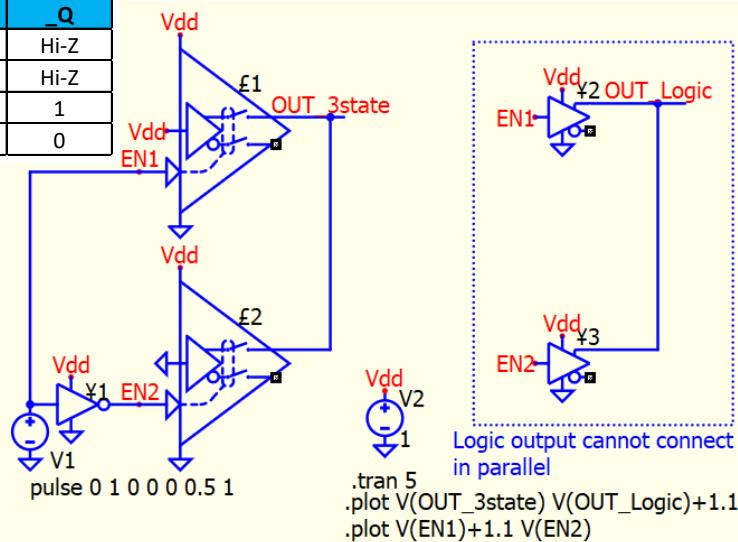


f-Device : Tri-state Buffer

- Tri-state Buffer

- Syntax: fnnn Vdd Vss Q Q̄ IN EN ¥ ¥ ¥ ... 3STATE [INSTANCE PARAMETERS]
- A tri-state output allows multiple circuits to share the same output line(s)
- Output into High-Z when disable

f-Device Tri-state Buffer			
EN	IN	Q	_Q
0	0	Hi-Z	Hi-Z
0	1	Hi-Z	Hi-Z
1	0	0	1
1	1	1	0

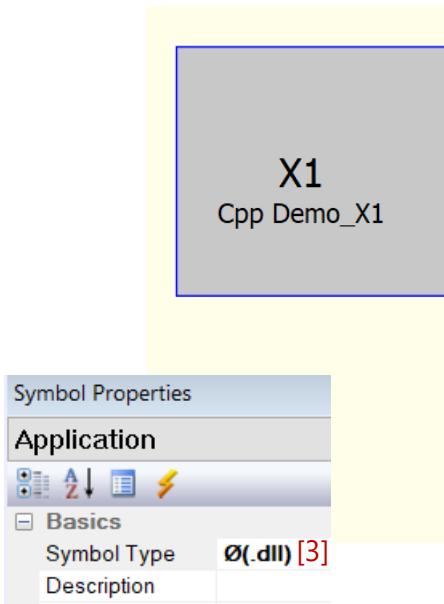


\emptyset -Device
.DLL

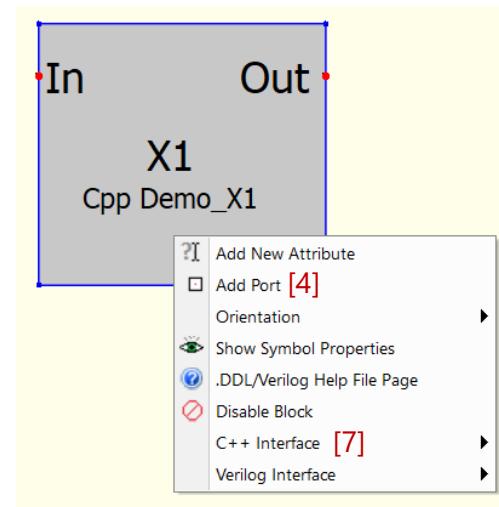
Workflow to Create .DLL C++ (\emptyset -Device)

Qspice : Cpp_Demo.qsch

- [1] In schematic, Right click > Draw Hierarchical Entry
- [2] Right click hierarchical block and Show Symbol Properties
- [3] In Symbol Type, change to \emptyset (.dll)



- [4] Right click hierarchical block > Add Port
- [5] Right click each port, select corresponding Port Type
 - For In, Port Type : Input
 - For Out, Port Type : Output
- [6] Right click each port, select corresponding Data Type
 - For In, Data Type : float (64 bit double)
 - For Out, Data Type : float (64 bit double)
- [7] Right click hierarchical block > C++ Interface
 - Create C++ Template > OK



Workflow to Create .DLL C++ (Ø-Device)

Qspice : Cpp_Demo.qsch

The screenshot shows the QSPICE interface with a code editor window titled "QSPICE™ - cpp_demo_x1.cpp". The code is an automatically generated C++ file. Handwritten annotations include:

- "#include <cmath>" with a red arrow pointing to it, labeled [8].
- "Out = pow(In,5);" with a red arrow pointing to it, labeled [9].
- "\"Cpp_Demo_X1\" created successfully" at the bottom with a red arrow pointing to it, labeled [10].

A context menu is open over the code, with "Compile DLL [10] F5" highlighted.

```
// Automatically generated C++ file on Tue Sep 12 23:27:26 2023
//
// To build with Digital Mars C++ Compiler:
//
// dmc -mn -WD cpp_demo_x1.cpp kernel32.lib

union uData
{
    bool b;
    char c;
    unsigned char uc;
    short s;
    unsigned short us;
    int i;
    unsigned int ui;
    float f;
    double d;
    long long int i64;
    unsigned long long int ui64;
    char *str;
    unsigned char *bytes;
};

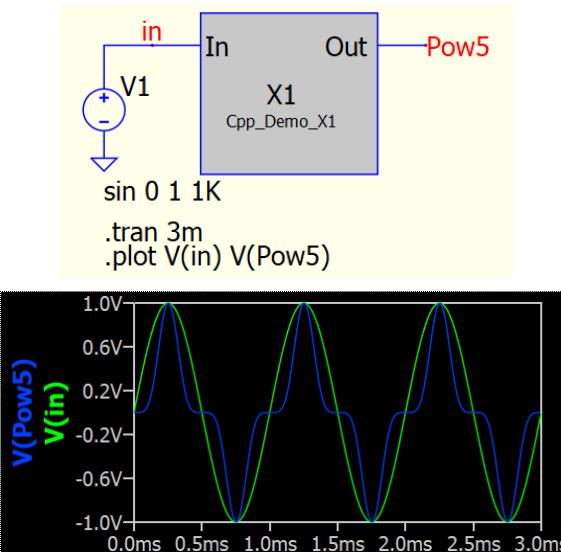
// int DllMain() must exist and return 1 for a process to load the
// See https://docs.microsoft.com/en-us/windows/win32/dlls/dllmain
int __stdcall DllMain(void *module, unsigned int reason, void *res

// #undef pin names lest they collide with names in any header file
#undef In
#undef Out
#include <cmath> [8]
extern "C" __declspec(dllexport) void cpp_demo_x1(void **opaque, d
{
    double In = data[0].d; // input
    double &Out = data[1].d; // output

    // Implement module evaluation code here:
    Out = pow(In,5); [9]
}

"Cpp_Demo_X1" created successfully [10]
```

- [8] add `#include<cmath>` if math function is needed
- [9] Implement the function of the device below the comment
`// Implement module evaluation code here`
- [10] Right click > Compile DLL
 - If success, a successful statement in status bar
- [11] Run SPICE simulation that call the C++ device



Ø-Device Instance Parameters

Ø-Device Instance Parameters

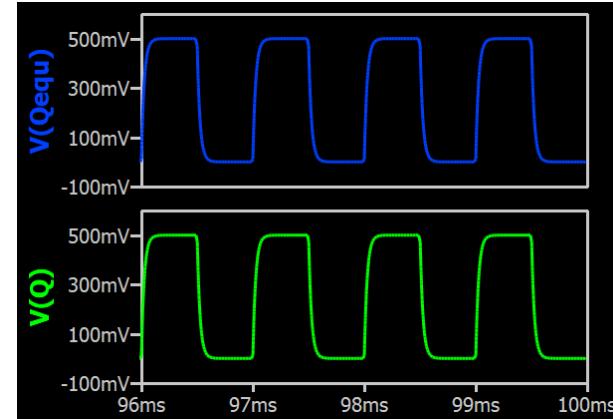
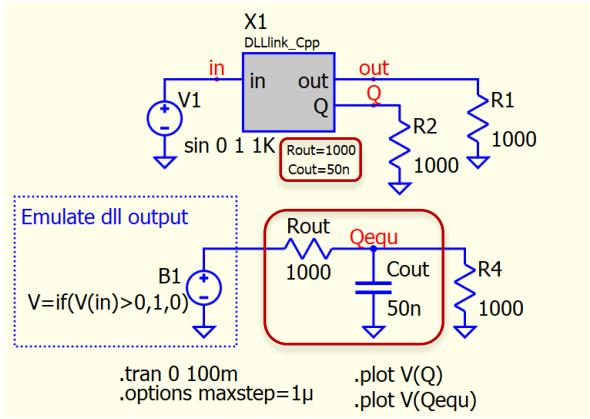
Name	Description	Units	Default
COUT	Output capacitance	C	0.
MAXTIMESTEP	Maximum time between evaluations	s	Infinite
REF	Logic threshold for inputs declared as boolean	V	.5
ROUT	Output impedance	Ω	1000.
VHIGH	Logic high level for outputs declared as boolean	V	1.
VLSB	ADC and DAC incremental voltage for an LSB change for multi-bit binary data types	V	1.

\emptyset -Device Instance Params : Rout / Cout and Vhigh

Qspice : DLLlink - Rout Cout.qsch / DLLlink - VHIGH.qsch

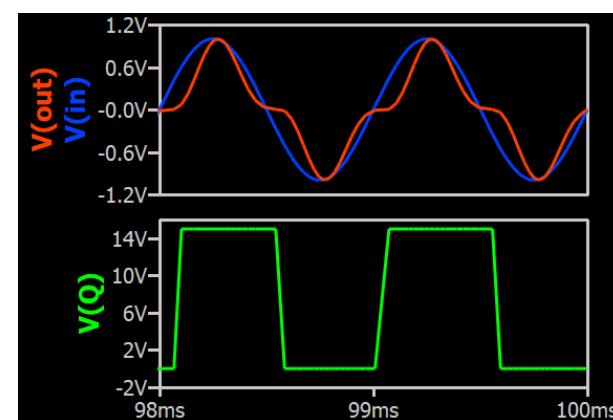
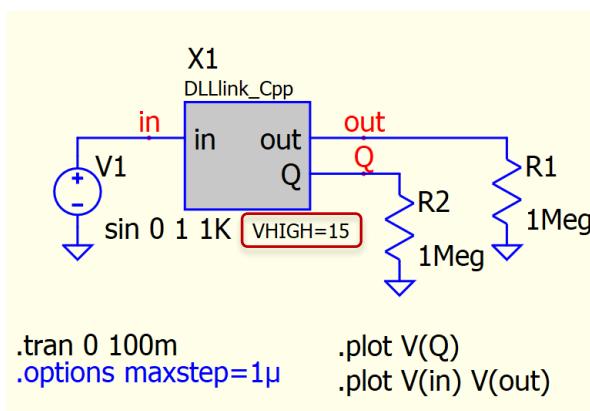
ROUT and COUT

- Rout : Output Impedance
- Cout : Output capacitance
- **Default ROUT=1000Ω**
- **Default COUT=0F**
- Example
 - In this example, it shown circuit arrangement of Rout and Cout in .dll device output



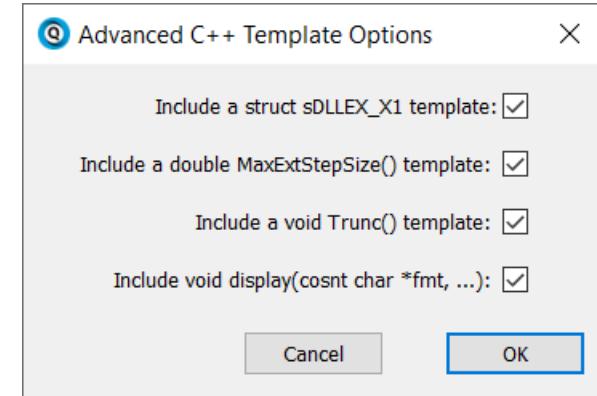
VHIGH

- Vhigh : Logic high level for outputs declared as Boolean
- **Default VHIGH=1V**



Ø-Device (Template)

- Ø-Device Advanced C++ Template Options
 - [1] Struct template
 - Declare the structure variable which can be used between functions
 - Pointer variable, e.g. inst->[variable]
 - [2] MaxExtStepSize()
 - Decide maximum time step in simulation (maxstep)
 - Special usage : Can return -1e308 to abort simulation and goes to the next step (if any)
 - [3] Trunc()
 - Limit Temporal TOLerance timestep (TTOL)
 - [4] Display()
 - For diagnostic print statements
 - To display a string in output windows during simulation



Ø-Device (Template)

Qspice : DLLex.qsch

```
// Automatically generated C++ file on Mon Nov 13 22:18:25 2023
// To build with Digital Mars C++ Compiler:
//   dmc -mn -WD dllex_x1.cpp kernel32.lib

#include <stdio.h>
#include <malloc.h>
#include <stdarg.h>
#include <time.h>

union uData
{
    bool b;
    char c;
    unsigned char uc;
    short s;
    unsigned short us;
    int i;
    unsigned int ui;
    float f;
    double d;
    long long int i64;
    unsigned long long int ui64;
    char *str;
    unsigned char *bytes;
};

// int DllMain() must exist and return 1 for a process to load the .DLL
// See https://docs.microsoft.com/en-us/windows/win32/dlls/dllmain for more information.
int __stdcall DllMain(void *module, unsigned int reason, void *reserved) { return 1; }

void display(const char *fmt, ...)
// for diagnostic print statements
{
    msleep(30);
    fflush(stdout);
    va_list args = { 0 };
    va_start(args, fmt);
    vprintf(fmt, args);
    va_end(args);
    fflush(stdout);
    msleep(30);
}

void bzero(void *ptr, unsigned int count)
{
    unsigned char *first = (unsigned char *) ptr;
    unsigned char *last = first + count;
    while(first < last)
        *first++ = '\0';
}

//
```

union uData
Define all data types

display()
To print in console
As msleep(30), can slow down simulation each time display() is called

bzero()
Reset all value in struct to zero

MaxExtStepSize() [2]
To determine maximum time step

Trunc() [3]
To determine if any next timestep

```
// #undef pin names lest they collide with names in any header file(s) you might include.
#ifndef _INCL_DLIB_CXX_ALGORITHMS
#define _INCL_DLIB_CXX_ALGORITHMS
#endif
// declare the structure here
struct sDLLEX_X1
{
    // input
    double in = data[0].d;
    // parameter
    double K = data[1].d;
    // output
    double &out = data[2].d;
};

// if(!*opaque) only run at beginning
if(!*opaque)
{
    *opaque = (struct sDLLEX_X1 *) malloc(sizeof(struct sDLLEX_X1));
    bzero(*opaque, sizeof(struct sDLLEX_X1));
}
struct sDLLEX_X1 *inst = *opaque;

// Implement module evaluation code here:
// main code

extern "C" __declspec(dllexport) void dllex_x1(struct sDLLEX_X1 **opaque, double t, union uData *data)
{
    double in = data[0].d; // input
    double K = data[1].d; // input parameter
    double &out = data[2].d; // output

    if(!*opaque)
    {
        *opaque = (struct sDLLEX_X1 *) malloc(sizeof(struct sDLLEX_X1));
        bzero(*opaque, sizeof(struct sDLLEX_X1));
    }
    struct sDLLEX_X1 *inst = *opaque;

    // Implement module evaluation code here:
}

extern "C" __declspec(dllexport) double MaxExtStepSize(struct sDLLEX_X1 *inst)
{
    return 1e308; // implement a good choice of max timestep size that depends on struct sDLLEX_X1
}

extern "C" __declspec(dllexport) void Trunc(struct sDLLEX_X1 *inst, double t, union uData *data, double *timestep)
// limit the timestep to a tolerance if the circuit causes a change in struct sDLLEX_X1
{
    const double ttol = 1e-9;
    if(*timestep > ttol)
    {
        double &out = data[2].d; // output

        // Save output vector
        const double _out = out;

        struct sDLLEX_X1 tmp = *inst;
        dllex_x1(&(tmp), t, data);
        // if(tmp != *inst) // implement a meaningful way to detect if the state has changed
        // *timestep = ttol;

        // Restore output vector
        out = _out;
    }
}

extern "C" __declspec(dllexport) void Destroy(struct sDLLEX_X1 *inst)
{
    free(inst);
}
```

[1] Struct template

Define pointer data used throughout the code

Main

main code

destroy()

Call this function upon termination of the simulation

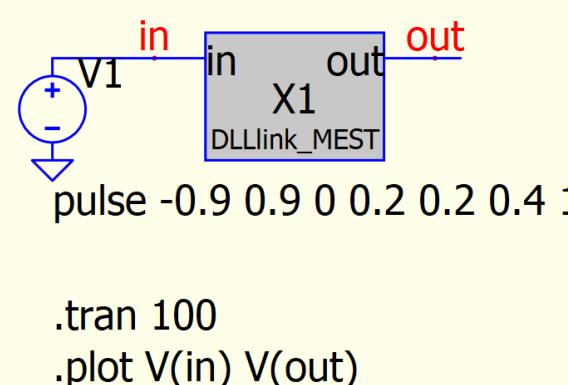
Another good reference from @physicboy

https://github.com/physicboy/QSPICE/blob/main/PWM_example_SRbuck/Three%20Complexity%20Levels%20of%20PWM%20Implementation%20for%20Digital%20Controller%20Simulation.pdf

Ø-Device (Template) : [2] MaxExtStepSize()

Qspice : DLLlink_MaxExtStepSize_Abort.qsch | dlllink_mest.cpp

- **MaxExtStepSize()**
 - Return value in `MaxExtStepSize()` determines maxstep
 - Return `1e308` equivalent maxstep is infinite (default)
 - This example demonstrates change of maxstep from infinite to 0.02 during simulation



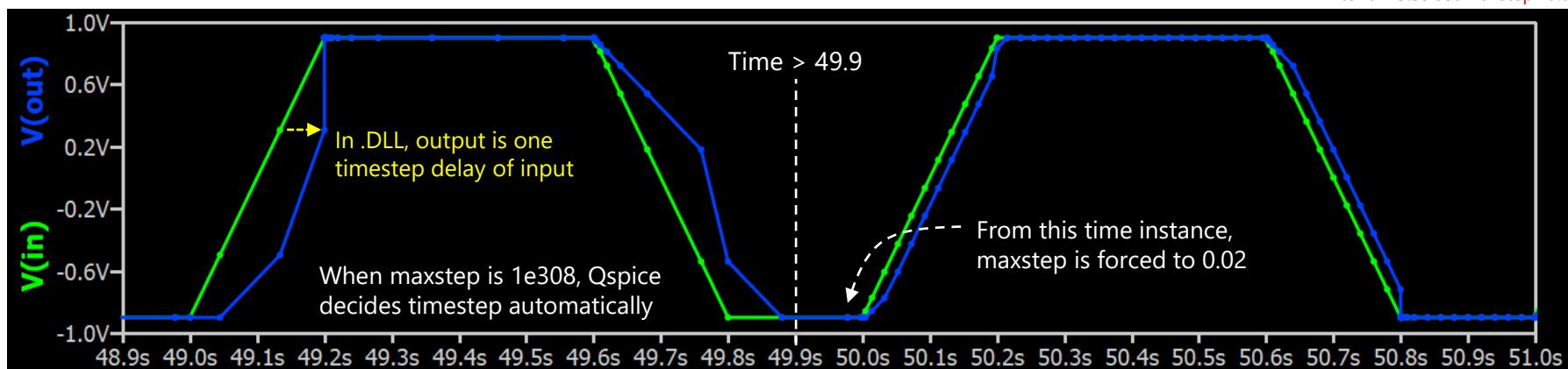
```
struct sDLLLINK_MEST
{
    // declare the structure here
    float t; ← assign an inst->t
};

extern "C" __declspec(dllexport) void dlllink_mest(struct
{
    double in = data[0].d; // input
    double out = data[1].d; // output

    if(!*opaque)
    {
        *opaque = (struct sDLLLINK_MEST *) malloc(sizeof(
            bzero(*opaque, sizeof(struct sDLLLINK_MEST));
    }
    struct sDLLLINK_MEST *inst = *opaque;

    // Implement module evaluation code here:
    out = in; ← inst->t = t as MaxExtStepSize() will
    inst->t = t; ← not accept t but only inst->t
} extern "C" __declspec(dllexport) double MaxExtStepSize(
{
    //return 1e308; // implement a good choice of max t
    if (inst->t > 49.9)
        return 0.2e-1;
    else
        return 1e308; ← If condition
}
```

- Before $t < 49.9s$, maxstep set to max
- After $t > 49.9s$ set maxstep=0.02

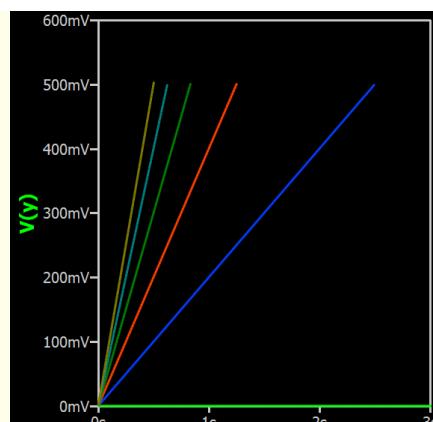
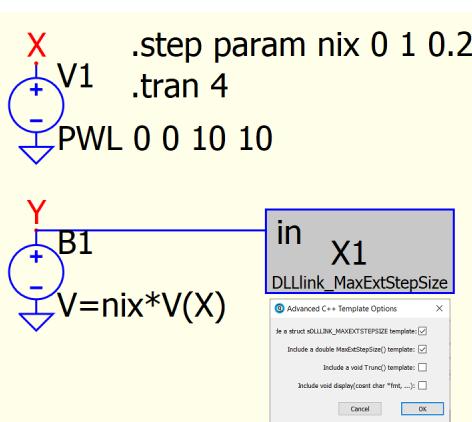


Ø-Device (Template) : [2] MaxExtStepSize()

Qspice : DLLlink_MaxExtStepSize_Abort.qsch | dlllink_maxextstepsize.cpp

- MaxExtStepSize()

- A special usage (abort simulation)
 - Have MaxExtStepSize() to return -1e308 can abort simulation and goes to the next step (if any)
 - ** Specifically -1e308, no other number



```
struct sDLLLINK_MAXEXTSTEPSIZE
{
    // declare the structure here
    double x; Declare pointer inst->x
};

extern "C" __declspec(dllexport) void dlllink_maxextste
{
    double in = data[0].d; // input

    if(!*opaque)
    {
        *opaque = (struct sDLLLINK_MAXEXTSTEPSIZE *) mal
        bzero(*opaque, sizeof(struct sDLLLINK_MAXEXTSTEP
    }
    struct sDLLLINK_MAXEXTSTEPSIZE *inst = *opaque;

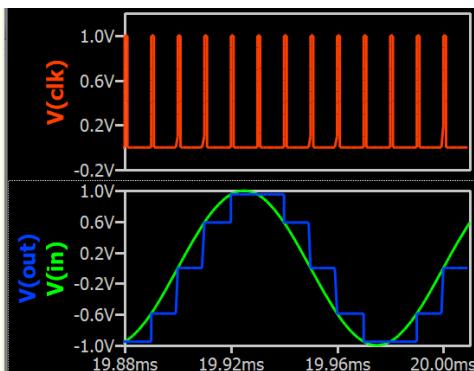
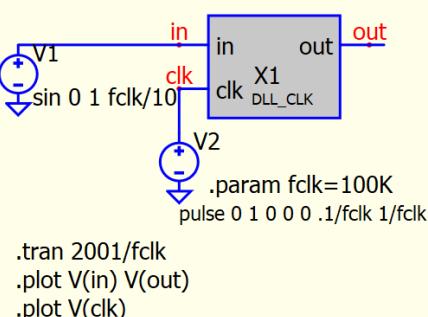
// Implement module evaluation code here:
    inst->x = in; Pointer is required to pass value of "in" to other
} function, in this case, to EaxExtStepSize()
}

extern "C" __declspec(dllexport) double MaxExtStepSize(
{
    if (inst->x > 0.5) {return -1e308;}
    return 1e308; // implement a good choice of max time
}
```

Ø-Device (Template) : [3] Trunc(), Example#1 - Rising Edge Detection

Qspice : DLL_CLK.qsch | dll_clk.dll

- Advanced C++ Template Options
 - Include a void **Trunc() template**
 - Include a **struct** template
- Purpose of this example
 - Limit timestep with Trunc() if the circuit causes a change
 - Struct to store instance variable which only used within C++ code (pointer to pass variable between functions)
 - Demonstrate how to implement rising edge detection and sampling time calculation



```
struct sDLL_CLK
{
    // declare the structure here
    bool last_clk;
    double lastT;
};

extern "C" __declspec(dllexport) void dll_clk(struct sDLL_CLK
{
    bool clk = data[0].b; // input
    double in = data[1].d; // input
    double &out = data[2].d; // output

    if(!*opaque)
    {
        *opaque = (struct sDLL_CLK *) malloc(sizeof(struct sDLL_CLK));
        bzero(*opaque, sizeof(struct sDLL_CLK));
    }
    struct sDLL_CLK *inst = *opaque;

    // Implement module evaluation code here:
    if (clk & !inst->last_clk){
        double T = t - inst->lastT; // T : sampling period ca
        inst->lastT = t;
        out = in;
    }
    inst->last_clk = clk;
}

extern "C" __declspec(dllexport) void Trunc(struct sDLL_CLK
{ // limit the timestep to a tolerance if the circuit ca
const double ttol = 1e-9; // Line#74, next slide
if(*timestep > ttol)
{
    double &out = data[2].d; // output

    // Save output vector
    const double _out = out;

    struct sDLL_CLK tmp = *inst;
    dll_clk(&(tmp), t, data);
    // if(tmp != *inst) // implement a meaningful way to detect
    // *timestep = ttol;
    if((tmp.last_clk != inst->last_clk) & !inst->last_clk)
        *timestep = ttol;

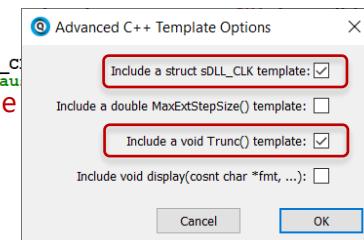
    // Restore output vector
    out = _out;
}
```

[1] Declare structure variable
inst->last_clk : to store last clock
inst->last : to store last rising edge time

User code

[2] detect rising edge (last_clk=0, clk=1)

[3] Calculate time between two rising edge (T)

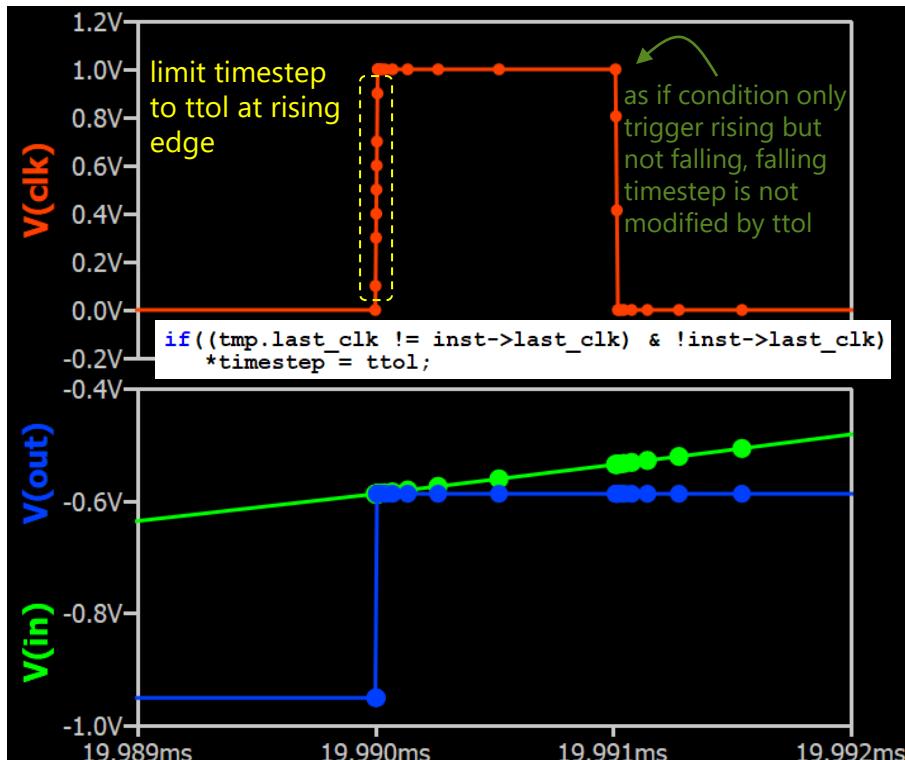


[4] if the circuit causes a change, limit the timestep to *timestep=ttol
User needs to define what the change (if condition) to force *timestep=ttol

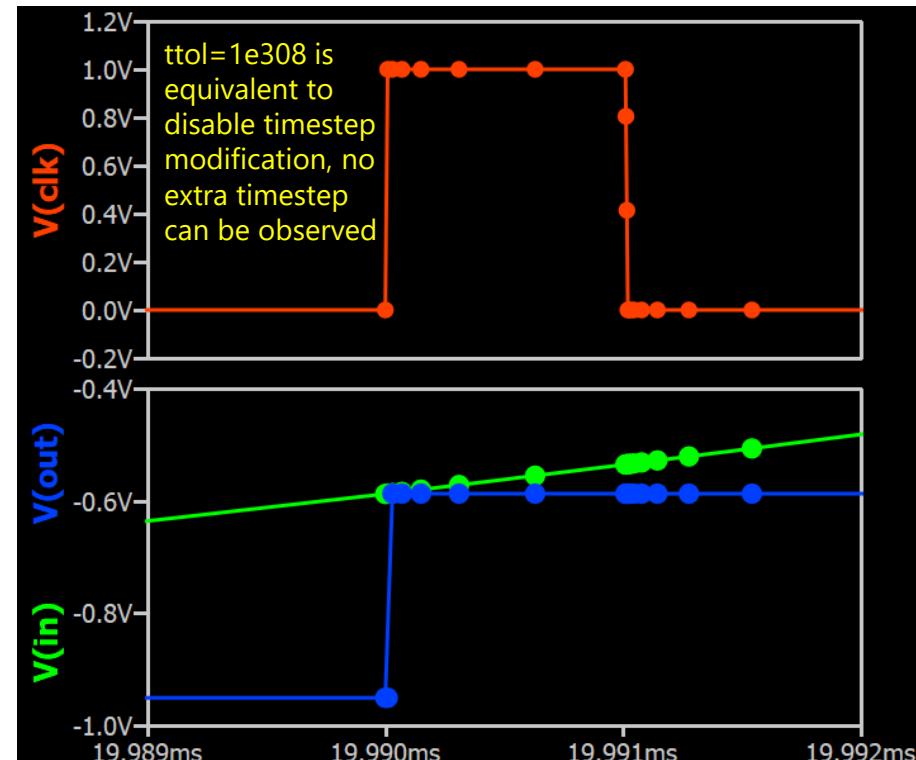
Ø-Device (Template) : [3] Trunc() and ttol

Qspice : DLL CLK.qsch | dll clk.dll

Line#74 : const double ttol=1e-9;



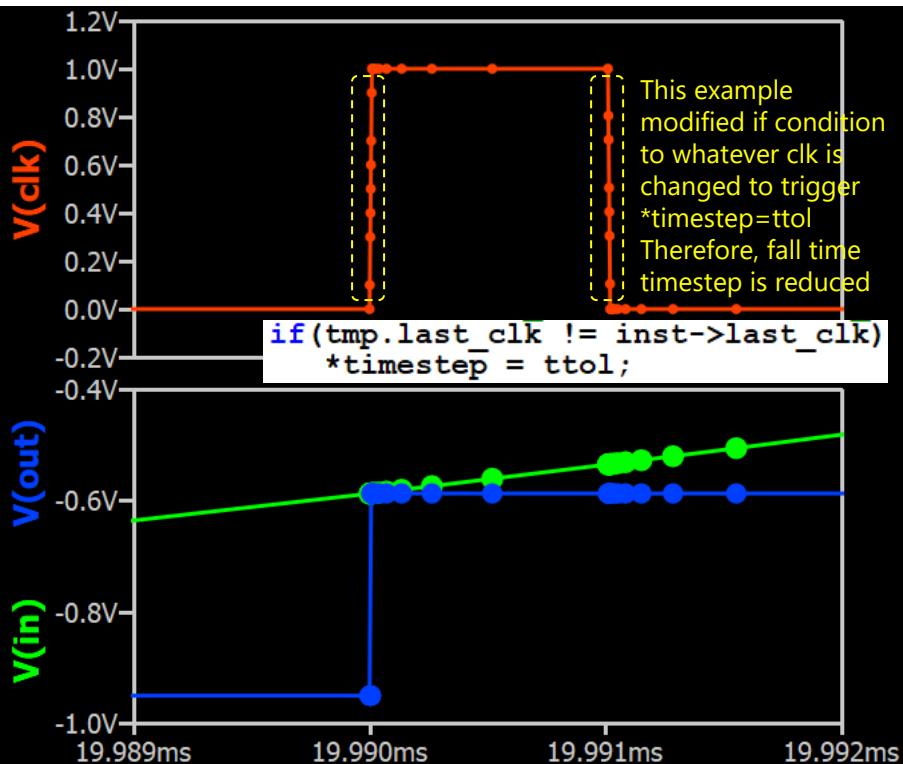
Line#74 : const double ttol=1e308;



Ø-Device (Template) : [3] Trunc() and ttol

Qspice : DLL CLK.qsch | dll clk.dll

Line#74 : const double ttol=1e-9;



Comment of Trunc() template

- Most critical in Trunc() for user to modify are these 2 lines

```
const double ttol = 1e-9;  
// if(tmp != *inst) // implement a meaningful way to detect if the state has changed  
// *timestep = ttol;
```

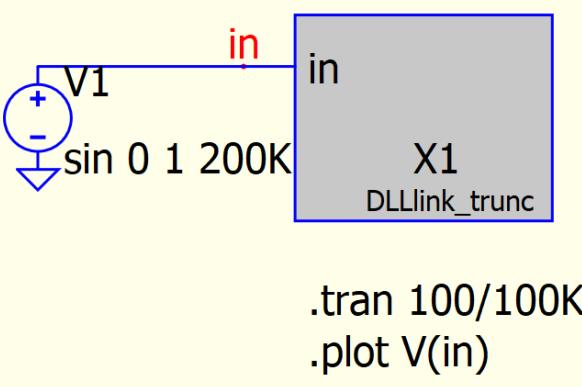
- ttol : limit Temporal tolerance timestep
- if (condition) : condition where timestep temporary force to ttol
 - In Trunc(), struct tmp is created for the purpose to compare *inst
 - User has to utilize tmp and *inst to detect if the state has changed

Ø-Device (Template) : [3] Trunc() and ttol – Example#2 Zero-crossing

Qspice : DLLlink_trunc.qsch | dlllink_trunc.cpp

- Trunc() example

- This example is to reduce simulation timestep at signal zero-crossing
- Code keynote
 - Use `inst->x = in` to pass data to `Trunc()`
 - In `Trunc()`, use if condition to force `ttol` when `tmp.x` within ± 0.1



```
struct sDLLLINK_TRUNC
{
    // declare the structure here
    double x;
};

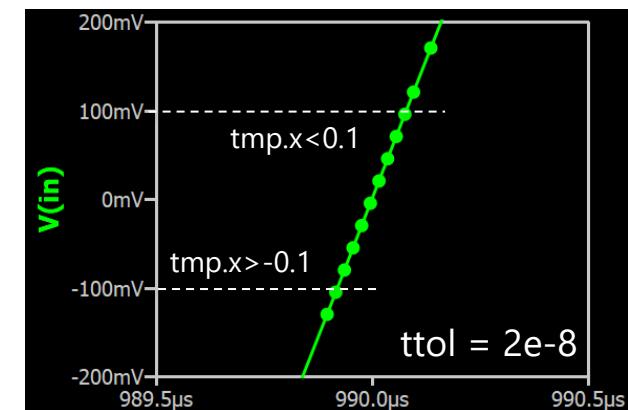
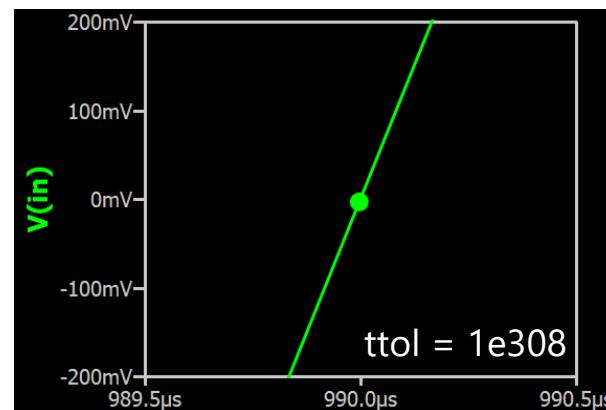
extern "C" __declspec(dllexport) void dll
{
    double in = data[0].d; // input

    if(!*opaque)
    {
        *opaque = (struct sDLLLINK_TRUNC *) bzero(*opaque, sizeof(struct sDLLLINK_TRUNC));
        struct sDLLLINK_TRUNC *inst = *opaque;
    }

    // Implement module evaluation code here:
    inst->x = in;
}
```

```
const double ttol = 2e-8;
if(*timestep > ttol)
{
    // Save output vector
    struct sDLLLINK_TRUNC tmp = *inst;
    dlllink_trunc(&tmp, t, data);
    // if(tmp != *inst) // implement a measure
    // *timestep = ttol;
    if (tmp.x < 0.1 & tmp.x > -0.1)
        *timestep = ttol;
}
```

** If use `inst->x` to replace `tmp.x`, couldn't achieve this pattern

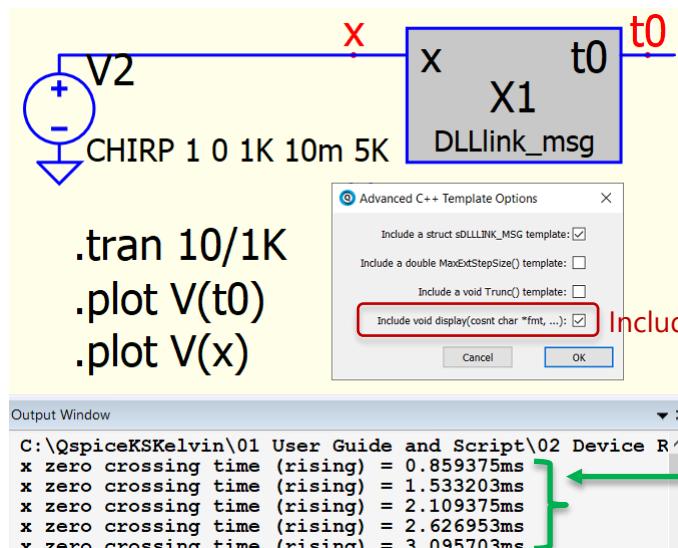


Ø-Device (Template) : [4] Display()

Qspice : DLLlink_msg.qsch | dlllink_msg.cpp

- Display() example

- Include display() can return a string in output window during simulation
- This example detect zero crossing of input x and output its time (simulation time)
- Display() is used to return this zero crossing time with a string



```
struct sDLLLINK_MSG
{
    // declare the structure here
    double last_x;
};

extern "C" __declspec(dllexport) void dlllink_msg(struct sDLLLINK
{
    double x = data[0].d; // input
    double &t0 = data[1].d; // output

    if (!*opaque)
    {
        *opaque = (struct sDLLLINK_MSG *) malloc(sizeof(struct sDLL
            bzero(*opaque, sizeof(struct sDLLLINK_MSG));
    }
    struct sDLLLINK_MSG *inst = *opaque;

    // Implement module evaluation code here:
    if (x>=0 & inst->last_x<0)
    {
        t0 = t;
        display("x zero crossing time (rising) = %fms\n",t0/1e-3);
    }
    inst->last_x = x;
}
```

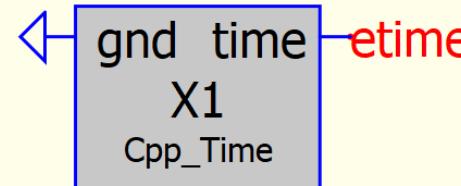
A red bracket on the right side of the code is labeled "Display a string".

**Ø-Device (.DLL)
Supplementary**

Ø-Device : Simulation time and call from directory

Qspice : cpp_time.cpp

- Time
 - **t** is simulation time in C++ code



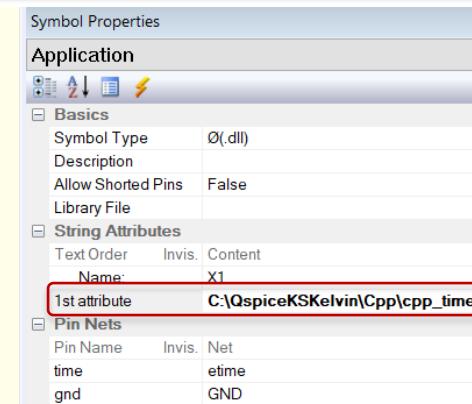
.tran 1
.plot V(etime)

```
// #undef pin names lest they collide with  
// #undef time  
  
extern "C" __declspec(dllexport) void cpp_  
{  
    double &time = data[0].d; // output  
  
    // Implement module evaluation code here:  
    time = t;  
}
```

- Dll from other directory
 - 1st attribute can accept absolute or relative path name
 - If space in directory path, add "" for string format
 - e.g. "C:\Qspice KSKelvin\Cpp\cpp_time"
 - To call for example `cpp_time.dll`, not to include .dll
 - Don't attempt to modify .cpp when path included



.tran 1
.plot V(etime)



Ø-Device : Simulation time – Analog and DLL Time

Qspice : Analog and DLL Time.qsch

- Analog and DLL Time
 - Exact time "Time" is analog Newton-Raphson iteration which can be called from Behavioral source $V=Time$
 - .DLL "t" is dll time from very last timestep
- In this example
 - out0 output .DLL time "t", which is a different by a timestep to analog time "Tnewton" : Timestep = $V(Tnewton)-V(Tc++)$
 - In the same way, for out1=in1, .DLL output is last timestep data sample and therefore, out1 not exactly equal in1 at same time!

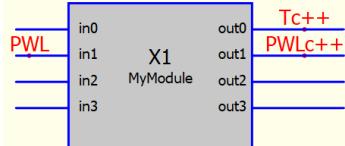
```
extern "C" __declspec(dllexport) void mym
{
    double in0 = data[0].d; // input
    double in1 = data[1].d; // input
    double in2 = data[2].d; // input
    double in3 = data[3].d; // input
    double out0 = data[4].d; // output
    double out1 = data[5].d; // output
    double out2 = data[6].d; // output
    double out3 = data[7].d; // output
}
```

// Implement module evaluation code here:

```
    out0=t;
    out1=in1;
```

out0 = t;

out1 = in1;



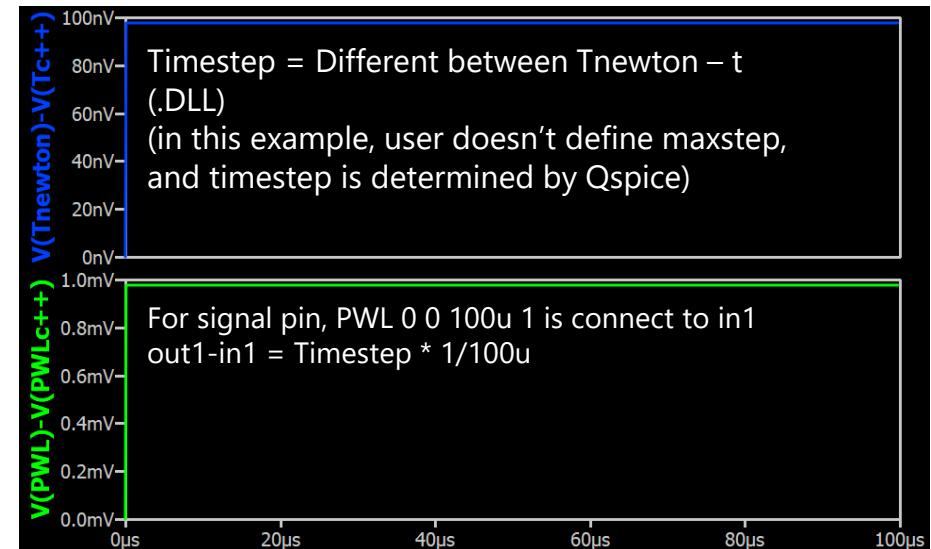
```
.tran 100u
.plot V(PWL)-V(PWLc++)
.plot V(Tnewton)-V(Tc++)
.plot V(x)
```

For verification

```
x
V1
.option maxstep=10n
pulse 0 1 0 5μ 5μ 10μ 20μ
```

According to Mike Engelhardt

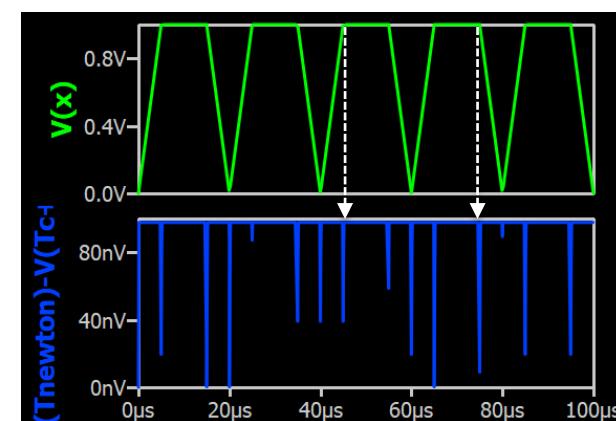
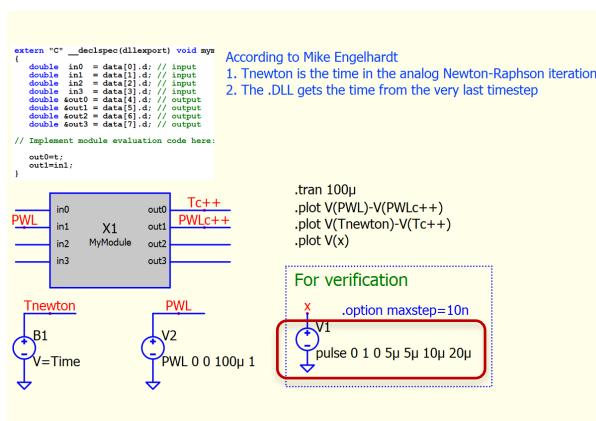
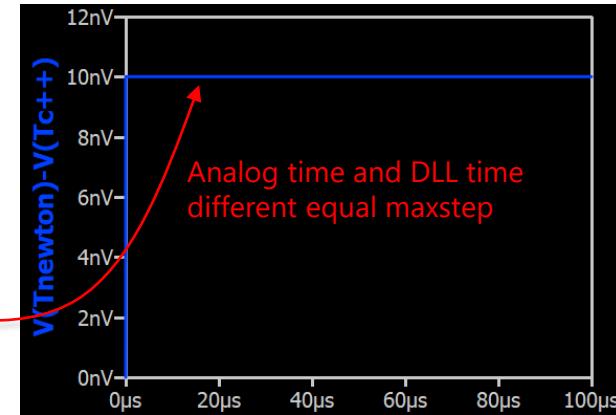
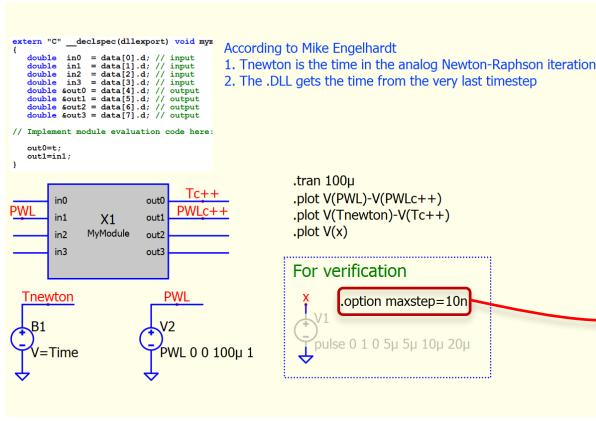
1. Tnewton is the time in the analog Newton-Raphson iteration
2. The .DLL gets the time from the very last timestep



Ø-Device : Simulation time – Analog and DLL Time

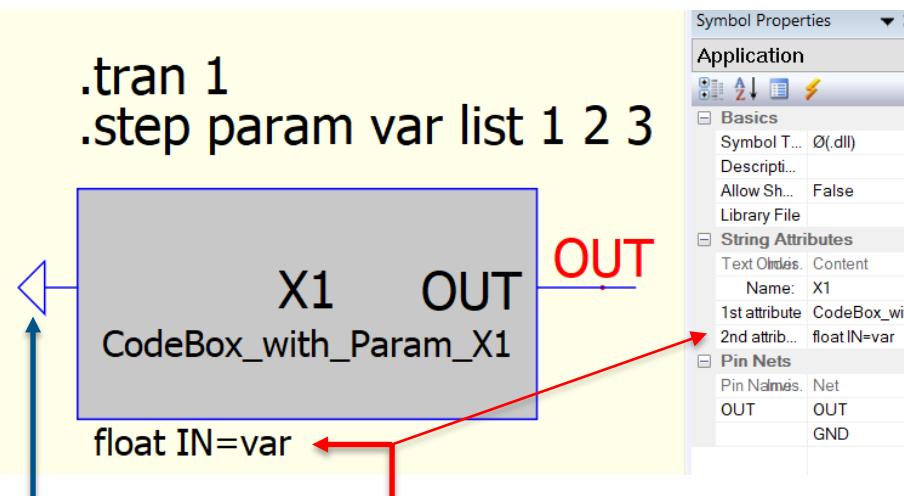
Qspice : Analog and DLL Time.qsch

- Change of Timestep #1
 - Different between DLL t and analog time can be affected by assigning max time step with .option maxstep
 - In this example, time different is clamped to equal maxstep setting



Ø-Device with Input Parameter

Qspice : CodeBox_with_Param.qsch



[1] For Input parameter, in creating hierarchical block

1. Right click the block > select Add attribute
2. [data type] [Input Port name] = [parameter] or <val>

As GND is needed if hierarchical doesn't have input port

- Add Port
- Right click Port > Data Type > DLL's GND

```
// #undef pin names lest they collide with names in ^  
#undef OUT  
  
extern "C" __declspec(dllexport) void codebox_with_param_x1(  
{  
    double IN = data[0].d; // input parameter  
    double &OUT = data[1].d; // output  
  
    // Implement module evaluation code here:  
    OUT = IN;  
}
```

** Important note!! Whenever you change input port, parameter or output port, you should recreate and copy code to a new C++ template, as Qspice requires particular order for index in data[]

- Right click the block > C++ Interface > Create C++ Template
- In this example, float IN=var will auto generate as input parameter
double IN = data[0].d;

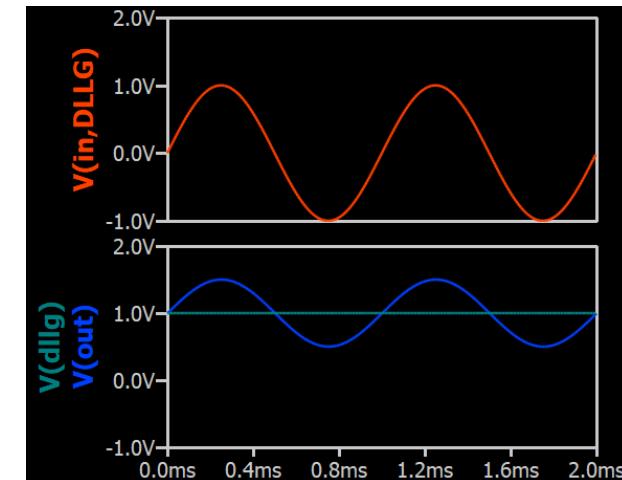
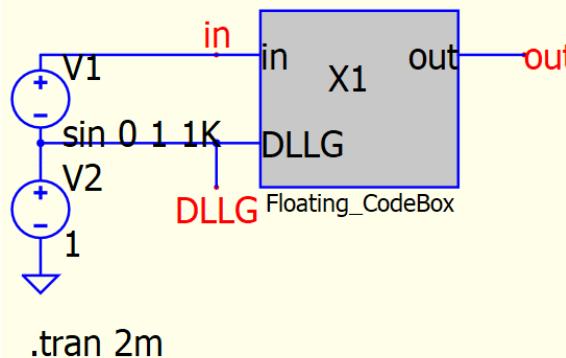
DLL's GND in Ø-Device

Qspice : Floating_CodeBox.qsch

- Two Purposes of DLL's Gnd
 - Floating operation where Ø-Device reference is not 0
 - Only output but no input port is defined (previous slide)

Example of floating ground operation

```
// Implement module evaluation code here:  
out = in * 0.5;
```



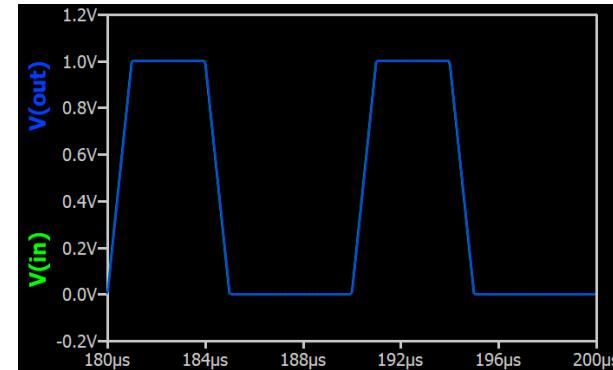
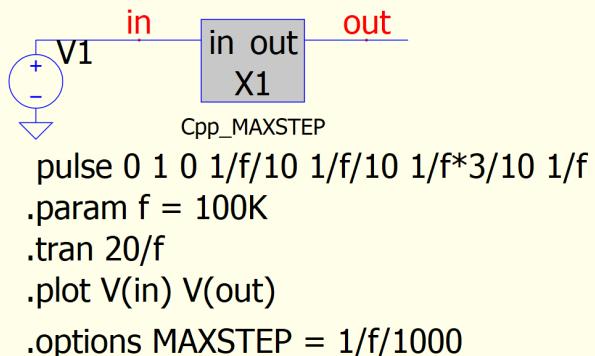
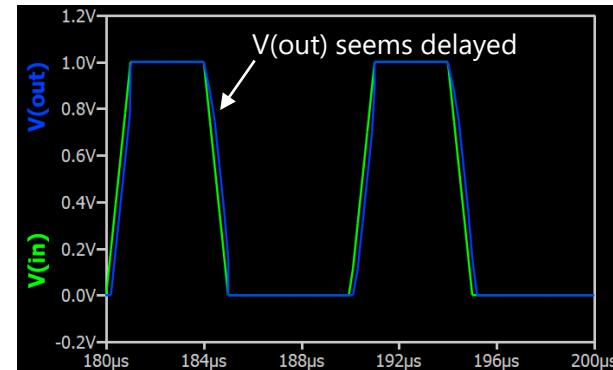
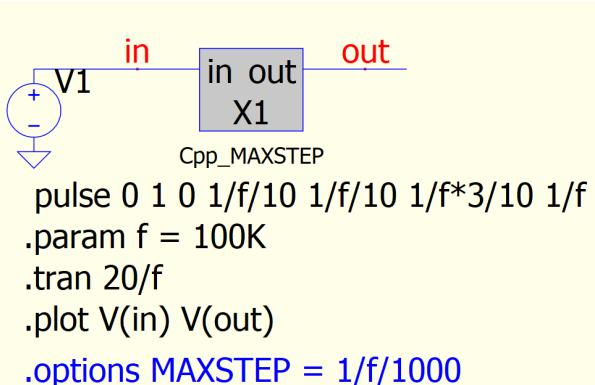
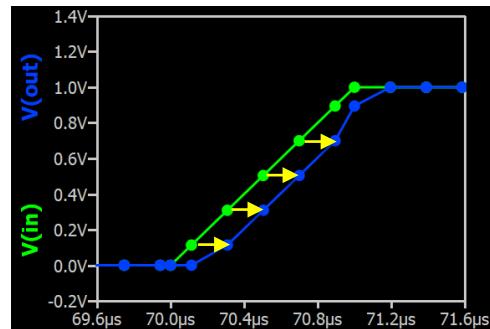
Engelhardt

The inputs and outputs of a .DLL go through a converter. If there's no DLL GND specified, the converters operate ground referenced. If you give a .DLL a GND, then inputs and output are referred to that .DLL GND port. It lets you run your logic hot decked as one might in an offline converter.

Use of MAXSTEP in C++ block (\emptyset -Device)

Qspice : Cpp_MAXSTEP.qsch

- If delay in response is observed when C++ block is used, consider to limit maximum time step by adding
 - .options MAXSTEP=<value>
 - The reason V(out) looks delayed is because output of .DLL is always one time step delay



Global and Instance/Member Variables

Qspice : Variable-OneDLLBlock.qsch | dllvar.cpp

- Global and Instance/Member Variables
 - The C++ code in this example increments variables **a** and **b** by 1 every second
 - The instance/member variable **a** is output to **y1**, while the global variable **b** is output to **y2**
 - If the schematic consists of only one DLL block, **y1** and **y2** will be identical
 - However, when multiple DLL blocks are used, the global variables will update each other, leading to unexpected results in the output

```
float b; ← Global variable

struct sDLLVAR
{
    // declare the structure here
    float a; ← Member variable
    float lastT;
};

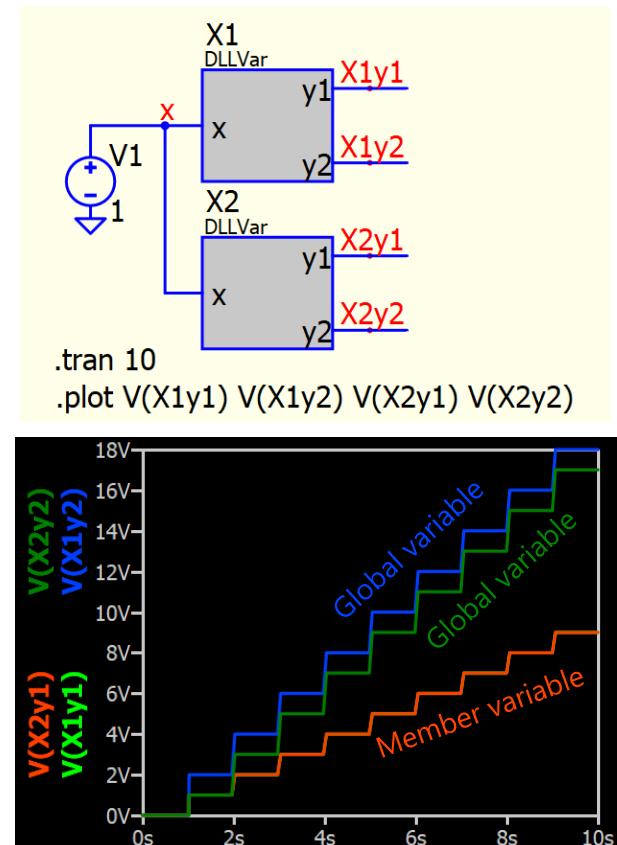
extern "C" __declspec(dllexport) void
{
    double x = data[0].d; // input
    double &y1 = data[1].d; // output
    double &y2 = data[2].d; // output

    if(!*opaque)
    {
        *opaque = (struct sDLLVAR *) malloc(sizeof(struct sDLLVAR));
        bzero(*opaque, sizeof(struct sDLLVAR));
    }
    struct sDLLVAR *inst = *opaque;

    // Implement module evaluation code here
    if (t - inst->lastT > 1)
    {
        inst->a = inst->a + 1;
        y1 = inst->a;

        b = b + 1;
        y2 = b;

        inst->lastT = t; Increase a and b
    }
}
```



Global and Instance/Member Variables – Initialization

Qspice : Variable-Initialization.qsch | dllvar.cpp

- Global Variable Initialization

- Initial value can be assigned directly in declaration

- Member Variable Initialization

- Choose method 1 or 2
- Method 1
 - `(*opaque)->[var] = [initial];`
 - Put this within `if(!*opaque)`
- Method 2
 - Set an initial status variable (e.g. `float init`) and use if condition to check this initial status
 - If initial status is true, enter the if condition and setup all instances with their respective initial values

```
float b=3; ← Global variable Initialization

struct sDLLVAR
{
    // declare the structure here
    float a;
    float init; ← Instance variable Initialization
    float lastT; with a status variable (method 2)
};

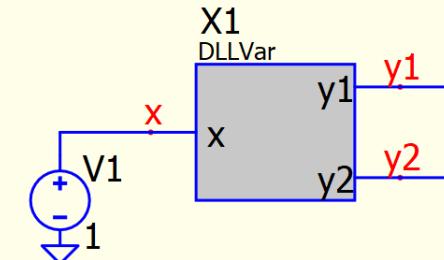
extern "C" __declspec(dllexport) void dllvar(s
{
    double x = data[0].d; // input
    double &y1 = data[1].d; // output
    double &y2 = data[2].d; // output

    if(!*opaque)
    {
        *opaque = (struct sDLLVAR *) malloc(sizeof(struct sDLLVAR));
        bzero(*opaque, sizeof(struct sDLLVAR));

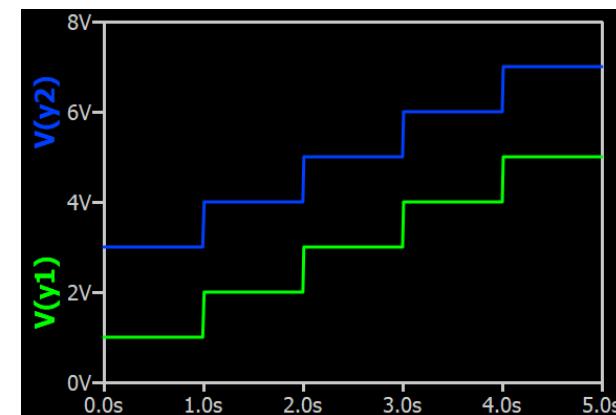
        // assign initial value (method 1)
        (*opaque)->a = 1; Initialize (method 1)
    }
    struct sDLLVAR *inst = *opaque;

    // Implement module evaluation code here:
    // assign initial value (method 2)
    if (inst->init == 0){
        inst->a = 1;
        inst->init = 1;
    }

    y1 = inst->a;
    y2 = b; If condition for inst->init to
            help initialize (method 2)
}
```



.tran 5
.plot V(y1) V(y2)



Local Variable

Qspice : Local-Variable.qsch | freq2voltage.cpp

- Local Variable

- Local variables are only accessible within the scope of that function, which can't be accessed or modified outside of it
- It is useful in Qspice for variable which is not required to store between each timestep of simulation

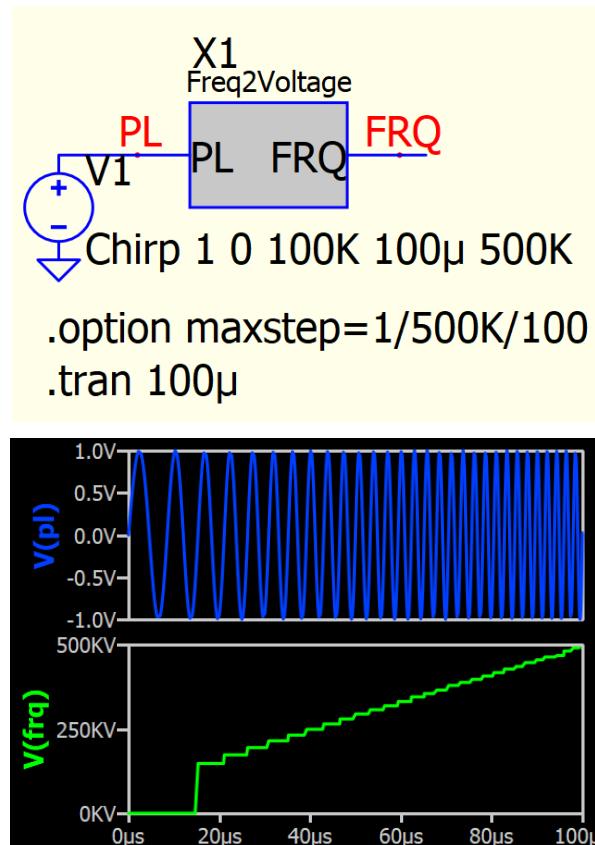
```
struct sFREQ2VOLTAGE
{
    // declare the structure here
    float lastT;
    float lastPL;
};

extern "C" __declspec(dllexport) void freq2voltage(
{
    double PL = data[0].d; // input
    double &FRQ = data[1].d; // output

    if(!*opaque)
    {
        *opaque = (struct sFREQ2VOLTAGE *) malloc(sizeof(struct sFREQ2VOLTAGE));
        bzero(*opaque, sizeof(struct sFREQ2VOLTAGE));
    }
    struct sFREQ2VOLTAGE *inst = *opaque;

    // Implement module evaluation code here:

    // rising edge at 0V
    if (inst->lastPL < 0 & PL > 0) {
        if (inst->lastT != 0){
            float T = t - inst->lastT;
            FRQ = 1/T;
        }
        inst->lastT = t;
    }
    inst->lastPL = PL;
}
```

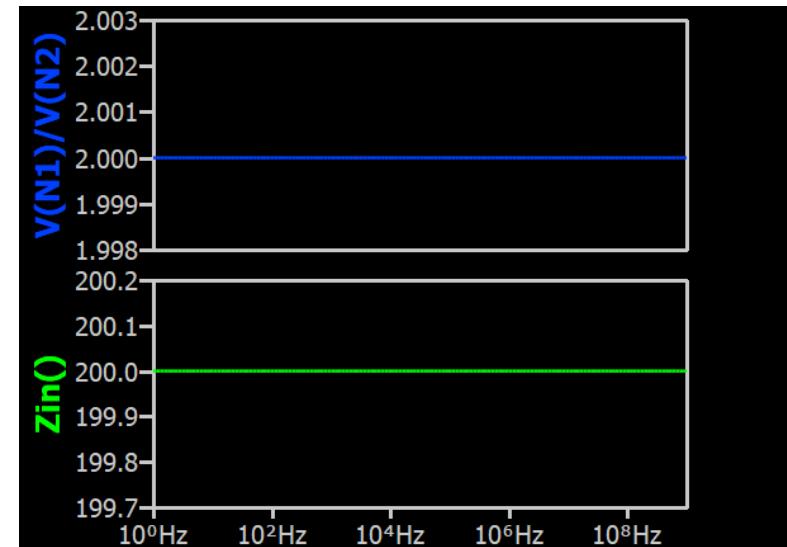
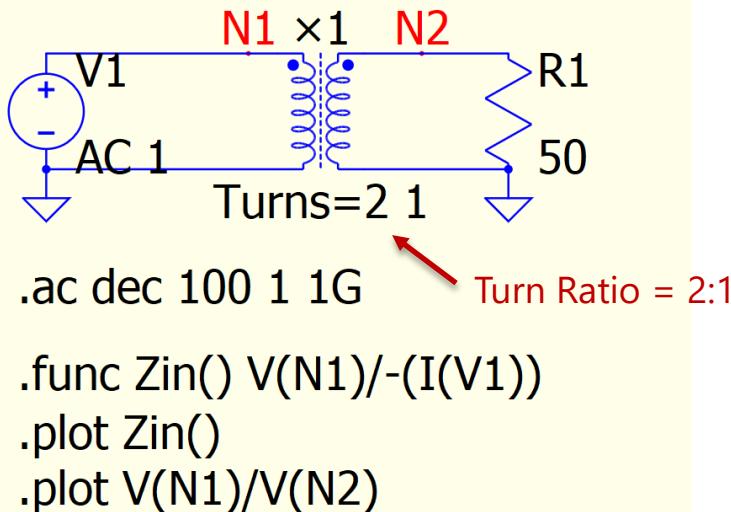


**x-Device
Transformer**

✗-Device : Transformer

Qspice : Transformer - Basic.qsch

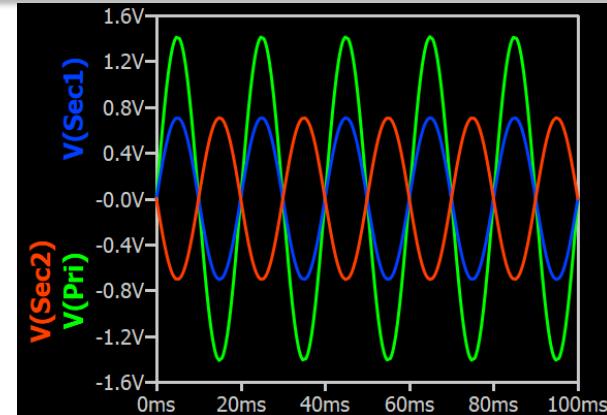
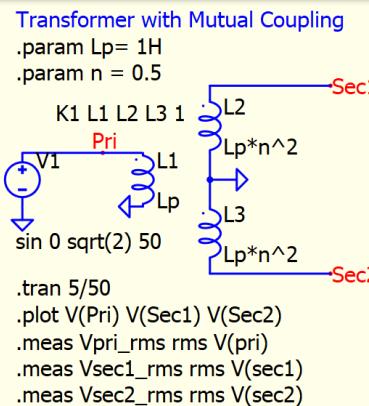
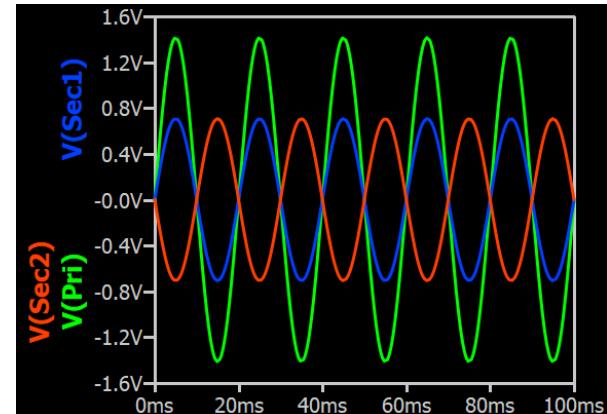
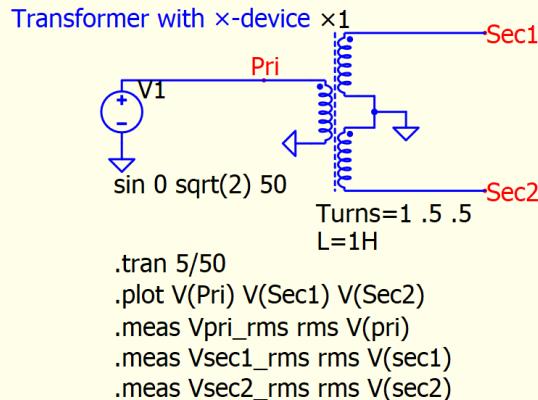
- ✗-Device: Transformer
 - Syntax: $\times nnn \text{ «PRI+ PRI- SEC1+ SEC1- SEC2+ SEC2 [...]» } <\text{TURN}=N1 N2 N3 ...>$ [Additional Instance Parameters]
 - Ideal Transformer Equation (Inductance $\rightarrow \infty$)
 - $n = \frac{N_1}{N_2} = \frac{v_1}{v_2}$ and $Z_{N1} = n^2 Z_{N2}$



\times -Device : Transformer

Qspice : Transformer - Multiple Windings.qsch | Mutual - Multiple Windings.qsch

- Multiple Windings
 - \times -Device supports multiple winding by defining turns ratio
 - Example demonstrate using \times -Device or mutual inductance for one primary and two secondary windings transformer



x-Device : Transformer Instance Params

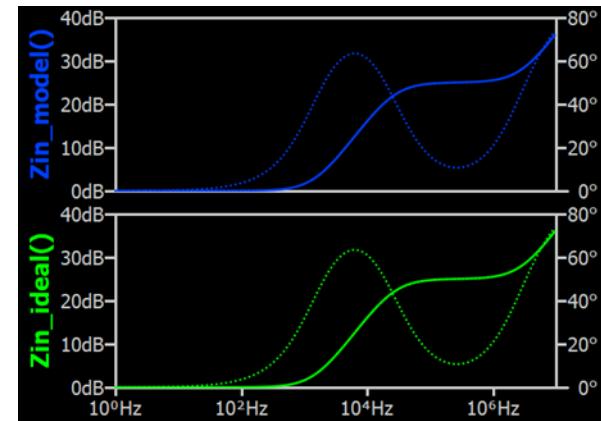
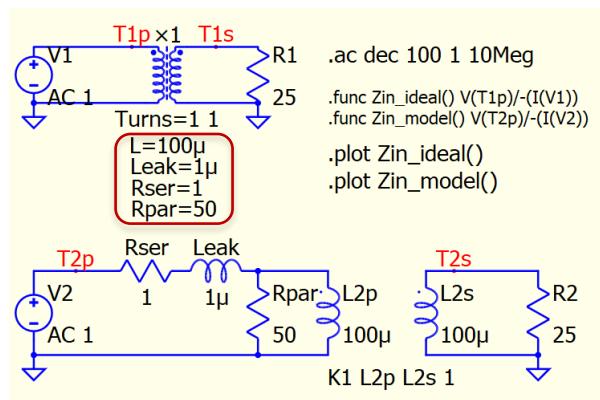
Transformer Instance Parameters

Name	Description	Units	Default
ISAT ¹	Current that drops inductance to SATFRAC of zero-current value	A	Infinite
K ¹	Alternate means of specifying LEAK		1
L	Primary zero-current inductance	H	Infinite
LEAK	Leakage inductance	H	0
LSAT ¹	Inductance asymptotically approached in saturation	H	10% of L
RPAR ¹	Primary parallel resistance	Ω	Infinite
RSER ¹	Primary series resistance	Ω	0.0
SATFRAC ¹	Fractional drop in L at ISAT		0.7
TURNS	List of relative number of turns		

Instance Params : L, Leak, Rser, Rpar, Isat, Lsat, Satfrac

Qspice : Transformer - L Leak Rser Rpar.qsch ; Transformer - Isat Lsat Satfrac.qsch

- L, Leak, Rser, Rpar
 - L : Primary Inductance
 - Leak : Leakage Inductance
 - Rser : Series Resistance
 - Rpar : Parallel Resistance
 - Equivalent model is shown in this simulation



- ISAT, LSAT, SATFRAC
 - Isat : Current that drops inductance to SATFRAC*L
 - Satfrac : Fractional drop in L at Isat
 - Lsat : Inductance asymptotically approached in saturation
 - These parameters are ignored unless L is given

